

EUROPEAN PATENT OFFICE
U.S. PATENT AND TRADEMARK OFFICE

CPC NOTICE OF CHANGES 1860

DATE: JANUARY 1, 2026

PROJECT RP12800

The following classification changes will be effected by this Notice of Changes:

<u>Action</u>	<u>Subclass</u>	<u>Group(s)</u>
SCHEME:		
Symbols Deleted:	H01L	SUBCLASS
	H01L	21/00, 21/02, 21/02002, 21/02005, 21/02008, 21/0201, 21/02013, 21/02016, 21/02019, 21/02021, 21/02024, 21/02027, 21/0203, 21/02032, 21/02035, 21/02041, 21/02043, 21/02046, 21/02049, 21/02052, 21/02054, 21/02057, 21/0206, 21/02063, 21/02065, 21/02068, 21/02071, 21/02074, 21/02076, 21/02079, 21/02082, 21/02085, 21/02087, 21/0209, 21/02093, 21/02096, 21/02098, 21/02101, 21/02104, 21/02107, 21/02109, 21/02112, 21/02115, 21/02118, 21/0212, 21/02123, 21/02126, 21/02129, 21/02131, 21/02134, 21/02137, 21/0214, 21/02142, 21/02145, 21/02148, 21/0215, 21/02153, 21/02156, 21/02159, 21/02161, 21/02164, 21/02167, 21/0217, 21/02172, 21/02175, 21/02178, 21/02181, 21/02183, 21/02186, 21/02189, 21/02192, 21/02194, 21/02197, 21/022, 21/02203, 21/02205, 21/02208, 21/02211, 21/02214, 21/02216, 21/02219, 21/02222, 21/02225, 21/02227, 21/0223, 21/02233, 21/02236, 21/02238, 21/02241, 21/02244, 21/02247, 21/02249, 21/02252, 21/02255, 21/02258, 21/0226, 21/02263, 21/02266, 21/02269, 21/02271, 21/02274, 21/02277, 21/0228, 21/02282, 21/02285, 21/02288, 21/0229, 21/02293, 21/02296, 21/02299, 21/02301, 21/02304, 21/02307, 21/0231, 21/02312, 21/02315, 21/02318, 21/02321, 21/02323, 21/02326, 21/02329, 21/02332, 21/02334, 21/02337, 21/0234, 21/02343, 21/02345, 21/02348, 21/02351, 21/02354, 21/02356, 21/02359, 21/02362, 21/02365, 21/02367, 21/0237, 21/02373, 21/02376, 21/02378, 21/02381, 21/02384, 21/02387, 21/02389, 21/02392, 21/02395, 21/02398, 21/024, 21/02403, 21/02406, 21/02409, 21/02411, 21/02414, 21/02417, 21/0242, 21/02422, 21/02425, 21/02428, 21/0243, 21/02433, 21/02436, 21/02439, 21/02441, 21/02444, 21/02447, 21/0245, 21/02452, 21/02455, 21/02458,

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		21/02461, 21/02463, 21/02466, 21/02469, 21/02472, 21/02474, 21/02477, 21/0248, 21/02483, 21/02485, 21/02488, 21/02491, 21/02494, 21/02496, 21/02499, 21/02502, 21/02505, 21/02507, 21/0251, 21/02513, 21/02516, 21/02518, 21/02521, 21/02524, 21/02527, 21/02529, 21/02532, 21/02535, 21/02538, 21/0254, 21/02543, 21/02546, 21/02549, 21/02551, 21/02554, 21/02557, 21/0256, 21/02562, 21/02565, 21/02568, 21/0257, 21/02573, 21/02576, 21/02579, 21/02581, 21/02584, 21/02587, 21/0259, 21/02592, 21/02595, 21/02598, 21/02601, 21/02603, 21/02606, 21/02609, 21/02612, 21/02614, 21/02617, 21/0262, 21/02623, 21/02625, 21/02628, 21/02631, 21/02634, 21/02636, 21/02639, 21/02642, 21/02645, 21/02647, 21/0265, 21/02653, 21/02656, 21/02658, 21/02661, 21/02664, 21/02667, 21/02669, 21/02672, 21/02675, 21/02678, 21/0268, 21/02683, 21/02686, 21/02689, 21/02691, 21/02694, 21/02697, 21/027, 21/0271, 21/0272, 21/0273, 21/0274, 21/0275, 21/0276, 21/0277, 21/0278, 21/0279, 21/033, 21/0331, 21/0332, 21/0334, 21/0335, 21/0337, 21/0338, 21/04, 21/0405, 21/041, 21/0415, 21/042, 21/0425, 21/043, 21/0435, 21/044, 21/0445, 21/045, 21/0455, 21/046, 21/0465, 21/047, 21/0475, 21/048, 21/0485, 21/049, 21/0495, 21/18, 21/182, 21/185, 21/187, 21/20, 21/2003, 21/2007, 21/2011, 21/2015, 21/22, 21/2205, 21/221, 21/2215, 21/222, 21/2225, 21/223, 21/2233, 21/2236, 21/225, 21/2251, 21/2252, 21/2253, 21/2254, 21/2255, 21/2256, 21/2257, 21/2258, 21/228, 21/24, 21/242, 21/244, 21/246, 21/248, 21/26, 21/2605, 21/261, 21/263, 21/2633, 21/2636, 21/265, 21/26506, 21/26513, 21/2652, 21/26526, 21/26533, 21/2654, 21/26546, 21/26553, 21/2656, 21/26566, 2021/26573, 21/2658, 21/26586, 21/26593, 21/266, 21/268, 21/2683, 21/2686, 21/28, 21/28008, 21/28017, 21/28026, 21/28035, 21/28044, 21/28052, 21/28061, 21/2807, 21/28079, 21/28088, 21/28097, 21/28105, 21/28114, 21/28123, 21/28132, 21/28141, 21/2815, 21/28158, 21/28167, 21/28176, 21/28185, 21/28194, 21/28202, 21/28211, 21/2822, 21/28229, 21/28238, 21/28247, 21/28255, 21/28264, 21/283, 21/285, 21/28506,

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		21/28512, 21/28518, 21/28525, 21/28531, 21/28537, 21/2855, 21/28556, 21/28562, 21/28568, 21/28575, 21/28581, 21/28587, 21/28593, 21/288, 21/2885, 21/30, 21/3003, 21/3006, 21/302, 21/304, 21/3043, 21/3046, 21/306, 21/30604, 21/30608, 21/30612, 21/30617, 21/30621, 21/30625, 21/3063, 21/30635, 21/3065, 21/30655, 21/308, 21/3081, 21/3083, 21/3085, 21/3086, 21/3088, 21/31, 21/3105, 21/31051, 21/31053, 21/31055, 21/31056, 21/31058, 21/311, 21/31105, 21/31111, 21/31116, 21/31122, 21/31127, 21/31133, 21/31138, 21/31144, 21/3115, 21/31155, 21/32, 21/3205, 21/32051, 21/32053, 21/32055, 21/32056, 21/32058, 21/321, 21/32105, 21/3211, 21/32115, 21/3212, 21/32125, 21/3213, 21/32131, 21/32132, 21/32133, 21/32134, 21/32135, 21/32136, 21/32137, 21/32138, 21/32139, 21/3215, 21/32155, 21/322, 21/3221, 21/3223, 21/3225, 21/3226, 21/3228, 21/324, 21/3242, 21/3245, 21/3247, 21/326, 21/34, 21/38, 21/383, 21/385, 21/388, 21/40, 21/42, 21/423, 21/425, 21/426, 21/428, 21/44, 21/441, 21/443, 21/445, 21/447, 21/449, 21/46, 21/461, 21/463, 21/465, 21/467, 21/469, 21/47, 21/471, 21/473, 21/475, 21/4757, 21/47573, 21/47576, 21/4763, 21/47635, 21/477, 21/479, 21/62, 21/64, 21/67, 21/67005, 21/67011, 21/67017, 21/67023, 21/67028, 21/67034, 21/6704, 21/67046, 21/67051, 21/67057, 21/67063, 21/67069, 21/67075, 21/6708, 21/67086, 21/67092, 21/67098, 21/67103, 21/67109, 21/67115, 21/67121, 21/67126, 21/67132, 21/67138, 21/67144, 21/6715, 21/67155, 21/67161, 21/67167, 21/67173, 21/67178, 21/67184, 21/6719, 21/67196, 21/67201, 21/67207, 21/67213, 21/67219, 21/67225, 21/6723, 21/67236, 21/67242, 21/67248, 21/67253, 21/67259, 21/67265, 21/67271, 21/67276, 21/67282, 21/67288, 21/67294, 21/673, 21/67303, 21/67306, 21/67309, 21/67313, 21/67316, 21/6732, 21/67323, 21/67326, 21/6733, 21/67333, 21/67336, 21/6734, 21/67343, 21/67346, 21/6735, 21/67353, 21/67356, 21/67359, 21/67363, 21/67366, 21/67369, 21/67373, 21/67376, 21/67379, 21/67383, 21/67386, 21/67389, 21/67393, 21/67396, 21/677, 21/67703,

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		21/67706, 21/67709, 21/67712, 21/67715, 21/67718, 21/67721, 21/67724, 21/67727, 21/6773, 21/67733, 21/67736, 21/67739, 21/67742, 21/67745, 21/67748, 21/67751, 21/67754, 21/67757, 21/6776, 21/67763, 21/67766, 21/67769, 21/67772, 21/67775, 21/67778, 21/67781, 21/67784, 21/67787, 21/6779, 21/67793, 21/67796, 21/68, 21/681, 21/682, 21/683, 21/6831, 21/6833, 21/6835, 21/6836, 21/6838, 21/687, 21/68707, 21/68714, 21/68721, 21/68728, 21/68735, 21/68742, 21/6875, 21/68757, 21/68764, 21/68771, 21/68778, 21/68785, 21/68792, 21/70, 21/702, 21/705, 21/707, 21/7624, 21/76243, 21/76245, 21/76248, 21/76251, 21/76254, 21/76256, 21/76259, 21/76262, 21/77, 21/78, 21/7806, 21/7813
	H01L	22/00, 22/10, 22/12, 22/14, 22/20, 22/22, 22/24, 22/26, 22/30, 22/32, 22/34
	H01L	2221/00, 2221/67, 2221/683, 2221/68304, 2221/68309, 2221/68313, 2221/68318, 2221/68322, 2221/68327, 2221/68331, 2221/68336, 2221/6834, 2221/68345, 2221/6835, 2221/68354, 2221/68359, 2221/68363, 2221/68368, 2221/68372, 2221/68377, 2221/68381, 2221/68386, 2221/6839, 2221/68395
	H10D	89/011, 89/013, 89/015
Symbols New:	H10D	64/011, 64/0111, 64/0112, 64/01125, 64/0113, 64/0114, 64/0115, 64/0116, 64/0117, 64/0118, 64/012, 64/0121, 64/0122, 64/0123, 64/0124, 64/0125, 64/0126, 64/013, 64/01302, 64/01304, 64/01306, 64/01308, 64/0131, 64/01312, 64/01314, 64/01316, 64/01318, 64/0132, 64/01322, 64/01324, 64/01326, 64/01328, 64/0133, 64/01332, 64/01334, 64/01336, 64/01338, 64/0134, 64/01342, 64/01344, 64/01346, 64/01348, 64/0135, 64/01352, 64/01354, 64/01356, 64/01358, 64/0136, 64/01362, 64/01364, 64/01366
	H10P	SUBCLASS
	H10P	10/00, 10/12, 10/126, 10/128, 10/1285, 10/14
	H10P	14/00, 14/20, 14/203, 14/22, 14/24, 14/26, 14/263, 14/265, 14/27, 14/271, 14/272, 14/274, 14/276, 14/278, 14/279, 14/29,

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		14/2901, 14/2902, 14/2903, 14/2904, 14/2905, 14/2906, 14/2907, 14/2908, 14/2909, 14/2911, 14/2912, 14/2913, 14/2914, 14/2915, 14/2916, 14/2917, 14/2918, 14/2919, 14/2921, 14/2922, 14/2923, 14/2924, 14/2925, 14/2926, 14/32, 14/3202, 14/3204, 14/3206, 14/3208, 14/3211, 14/3212, 14/3214, 14/3216, 14/3218, 14/3221, 14/3222, 14/3224, 14/3226, 14/3228, 14/3231, 14/3232, 14/3234, 14/3236, 14/3238, 14/3241, 14/3242, 14/3244, 14/3246, 14/3248, 14/3251, 14/3252, 14/3254, 14/3256, 14/3258, 14/34, 14/3402, 14/3404, 14/3406, 14/3408, 14/3411, 14/3412, 14/3414, 14/3416, 14/3418, 14/3421, 14/3422, 14/3424, 14/3426, 14/3428, 14/3431, 14/3432, 14/3434, 14/3436, 14/3438, 14/3441, 14/3442, 14/3444, 14/3446, 14/3448, 14/3451, 14/3452, 14/3454, 14/3456, 14/3458, 14/3461, 14/3462, 14/3464, 14/3466, 14/36, 14/3602, 14/38, 14/3802, 14/3804, 14/3806, 14/3808, 14/381, 14/3812, 14/3814, 14/3816, 14/3818, 14/382, 14/3822, 14/3824, 14/40, 14/412, 14/414, 14/416, 14/418, 14/42, 14/43, 14/432, 14/44, 14/45, 14/46, 14/47, 14/48, 14/60, 14/61, 14/63, 14/6302, 14/6304, 14/6306, 14/6308, 14/6309, 14/6312, 14/6314, 14/6316, 14/6318, 14/6319, 14/6322, 14/6324, 14/6326, 14/6328, 14/6329, 14/6332, 14/6334, 14/6336, 14/6338, 14/6339, 14/6342, 14/6344, 14/6346, 14/6348, 14/6349, 14/65, 14/6502, 14/6504, 14/6506, 14/6508, 14/6509, 14/6512, 14/6514, 14/6516, 14/6518, 14/6519, 14/6522, 14/6524, 14/6526, 14/6528, 14/6529, 14/6532, 14/6534, 14/6536, 14/6538, 14/6539, 14/6542, 14/6544, 14/6546, 14/6548, 14/66, 14/662, 14/665, 14/668, 14/6681, 14/6682, 14/6684, 14/6686, 14/6687, 14/6689, 14/68, 14/683, 14/687, 14/69, 14/6902, 14/6903, 14/6905, 14/6906, 14/6907, 14/6908, 14/6909, 14/691, 14/6911, 14/6912, 14/6913, 14/6914, 14/692, 14/6921, 14/69215, 14/6922, 14/6923, 14/6924, 14/6925, 14/6926, 14/6927, 14/6928, 14/6929, 14/693, 14/6931, 14/6932, 14/6933, 14/6934, 14/6936, 14/6938, 14/6939, 14/69391, 14/69392, 14/69393,

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<u>Action</u>	<u>Subclass</u>	<u>Group(s)</u>
		14/69394, 14/69395, 14/69396, 14/69397, 14/69398, 14/694, 14/6943, 14/69433, 14/6947, 14/69471, 14/69472, 14/69473, 14/69474, 14/69475, 14/69476, 14/69477, 14/69478
	H10P	30/00, 30/20, 30/202, 30/204, 30/2042, 30/2044, 30/206, 30/208, 30/209, 30/21, 30/212, 30/214, 30/218, 30/22, 30/221, 30/222, 30/224, 30/225, 30/226, 30/28, 30/40
	H10P	32/00, 32/10, 32/12, 32/1204, 32/14, 32/1404, 32/1406, 32/1408, 32/141, 32/1412, 32/1414, 32/15, 32/16, 32/17, 32/171, 32/172, 32/173, 32/174, 32/18, 32/185, 32/19, 32/20, 32/30, 32/302
	H10P	34/00, 34/10, 34/20, 34/40, 34/42, 34/422
	H10P	36/00, 36/03, 36/07, 36/20
	H10P	50/00, 50/20, 50/24, 50/242, 50/244, 50/246, 50/26, 50/262, 50/263, 50/264, 50/266, 50/267, 50/268, 50/269, 50/28, 50/282, 50/283, 50/285, 50/286, 50/287, 50/60, 50/61, 50/613, 50/617, 50/64, 50/642, 50/644, 50/646, 50/648, 50/66, 50/663, 50/667, 50/68, 50/683, 50/69, 50/691, 50/692, 50/693, 50/694, 50/695, 50/696, 50/71, 50/73
	H10P	52/00, 52/20, 52/202, 52/203, 52/207, 52/209, 52/40, 52/402, 52/403, 52/407, 52/409
	H10P	54/00, 54/20, 54/30, 54/40, 54/50, 54/52, 54/90, 54/92, 54/922, 54/924, 54/94
	H10P	56/00
	H10P	58/00, 58/20, 58/22
	H10P	70/00, 70/10, 70/12, 70/125, 70/15, 70/18, 70/20, 70/23, 70/234, 70/237, 70/27, 70/273, 70/277, 70/30, 70/40, 70/50, 70/52, 70/54, 70/56, 70/58, 70/60, 70/70, 70/80
	H10P	72/00, 72/04, 72/0402, 72/0404, 72/0406, 72/0408, 72/0411, 72/0412, 72/0414, 72/0416, 72/0418, 72/0421, 72/0422, 72/0424, 72/0426, 72/0428, 72/0431, 72/0432, 72/0434, 72/0436, 72/0438, 72/0441, 72/0442, 72/0444, 72/0446, 72/0448, 72/0451, 72/0452, 72/0454, 72/0456, 72/0458, 72/0461, 72/0462, 72/0464, 72/0466, 72/0468, 72/0471, 72/0472, 72/0474, 72/0476, 72/0478, 72/06, 72/0602, 72/0604, 72/0606, 72/0608, 72/0611, 72/0612, 72/0614, 72/0616, 72/0618, 72/10, 72/12, 72/123, 72/127,

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		72/13, 72/135, 72/14, 72/145, 72/15, 72/155, 72/16, 72/165, 72/17, 72/175, 72/18, 72/19, 72/1902, 72/1904, 72/1906, 72/1908, 72/1911, 72/1912, 72/1914, 72/1916, 72/1918, 72/1921, 72/1922, 72/1924, 72/1926, 72/1928, 72/30, 72/32, 72/3202, 72/3204, 72/3206, 72/3208, 72/3211, 72/3212, 72/3214, 72/3216, 72/3218, 72/3221, 72/3222, 72/33, 72/3302, 72/3304, 72/3306, 72/3308, 72/3311, 72/3312, 72/3314, 72/34, 72/3402, 72/3404, 72/3406, 72/3408, 72/3411, 72/3412, 72/36, 72/3602, 72/3604, 72/37, 72/38, 72/50, 72/53, 72/57, 72/70, 72/72, 72/722, 72/74, 72/7402, 72/7404, 72/7406, 72/7408, 72/741, 72/7412, 72/7414, 72/7416, 72/7418, 72/742, 72/7422, 72/7424, 72/7426, 72/7428, 72/743, 72/7432, 72/7434, 72/7436, 72/7438, 72/744, 72/7442, 72/7444, 72/7446, 72/7448, 72/745, 72/76, 72/7602, 72/7604, 72/7606, 72/7608, 72/7611, 72/7612, 72/7614, 72/7616, 72/7618, 72/7621, 72/7622, 72/7624, 72/7626, 72/78
	H10P	74/00, 74/20, 74/203, 74/207, 74/23, 74/232, 74/235, 74/238, 74/27, 74/273, 74/277
	H10P	76/00, 76/20, 76/202, 76/204, 76/2041, 76/2042, 76/2043, 76/2045, 76/2047, 76/2049, 76/40, 76/403, 76/405, 76/408, 76/4083, 76/4085, 76/4088
	H10P	90/00, 90/12, 90/123, 90/124, 90/126, 90/128, 90/129, 90/14, 90/15, 90/16, 90/18, 90/19, 90/1902, 90/1904, 90/1906, 90/1908, 90/191, 90/1912, 90/1914, 90/1916, 90/1918, 90/192, 90/1922, 90/1924, 90/21, 90/212, 90/22, 90/24
	H10P	95/00, 95/02, 95/04, 95/06, 95/062, 95/064, 95/066, 95/08, 95/11, 95/112, 95/40, 95/402, 95/405, 95/408, 95/50, 95/60, 95/70, 95/80, 95/90, 95/902, 95/904, 95/906, 95/92, 95/94
Warnings Deleted:	H01L	SUBCLASS
	H01L	21/3247
Warnings New:	H10D	64/011, 64/0111, 64/0112, 64/01125, 64/0114, 64/0115, 64/0116, 64/0117, 64/0118, 64/012, 64/0121, 64/0122, 64/0123, 64/0124, 64/0125, 64/0126,

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		64/013, 64/01302, 64/01356, 64/01358, 64/0136, 64/01362, 64/01364, 64/01366
	H10D	84/0102
	H10D	86/01
	H10D	87/00
	H10D	88/101
	H10D	89/60
	H10P	10/00, 10/12, 10/126, 10/128, 10/14
	H10P	14/00, 14/29, 14/2924, 14/2926, 14/42, 14/43, 14/44, 14/45, 14/46, 14/47, 14/48, 14/60, 14/6308, 14/6309, 14/6316, 14/6318, 14/6319, 14/6322, 14/6324, 14/68, 14/683, 14/687, 14/69, 14/6903, 14/6906, 14/6907, 14/6908, 14/6909, 14/691, 14/6911, 14/6912, 14/6913, 14/6914, 14/6921, 14/6938, 14/6939, 14/69391, 14/69392, 14/69393, 14/69394, 14/69395, 14/69396, 14/69397, 14/694, 14/6943, 14/6947, 14/69471, 14/69472, 14/69473, 14/69474, 14/69475, 14/69476, 14/69477, 14/69478
	H10P	30/00, 30/20, 30/202, 30/2042, 30/2044, 30/208, 30/21, 30/212, 30/214, 30/218, 30/22, 30/221, 30/222, 30/28, 30/40
	H10P	32/00, 32/10, 32/173, 32/20
	H10P	34/00, 34/10, 34/20, 34/40
	H10P	36/00, 36/03, 36/20
	H10P	50/00, 50/20, 50/24, 50/26, 50/264, 50/28, 50/282, 50/283, 50/286, 50/287, 50/60, 50/663, 50/68, 50/683
	H10P	52/00, 52/20, 52/202, 52/207, 52/209, 52/40, 52/402, 52/407, 52/409
	H10P	54/00, 54/52, 54/92
	H10P	56/00
	H10P	58/00, 58/20
	H10P	72/70, 72/72, 72/74, 72/7402, 72/7404
	H10P	90/00, 90/19, 90/1914, 90/1916, 90/1918, 90/21, 90/22, 90/24
	H10P	95/00, 95/02, 95/04, 95/06, 95/062, 95/08, 95/11, 95/40, 95/402, 95/405, 95/408, 95/50, 95/60, 95/70, 95/80, 95/90, 95/904, 95/92
Warnings Modified:	H10D	84/01, 84/0107, 84/0112, 84/0123, 84/0198, 84/02
	H10D	88/01
Notes Deleted:	H01L	SUBCLASS

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<u>Action</u>	<u>Subclass</u>	<u>Group(s)</u>
Notes New:	H10D	64/01
	H10P	SUBCLASS
	H10P	10/00
	H10P	30/20
	H10P	32/1408
	H10P	54/00
	H10P	56/00
	H10P	58/00
	H10P	70/00
	H10P	90/00
Notes Modified:	B81B	SUBCLASS
	B81C	SUBCLASS
	C04B	2235/96
	G09G	SUBCLASS
	H02M	SUBCLASS
	H02N	SUBCLASS
Guidance Headings New:	H10P	10/00
	H10P	30/00
	H10P	50/00
	H10P	70/00
DEFINITIONS:		
Definitions Deleted: (no frozen (F) symbol definitions should be deleted)	H01L	SUBCLASS
	H01L	21/00, 21/02002, 21/02005, 21/0201, 21/02013, 21/02016, 21/02019, 21/02021, 21/02024, 21/02027, 21/0203, 21/02032, 21/02035, 21/02041, 21/02043, 21/02046, 21/02052, 21/02054, 21/02057, 21/0206, 21/02079, 21/02082, 21/02087, 21/0209, 21/02096, 21/02098, 21/02101, 21/02104, 21/02107, 21/02112, 21/02115, 21/02118, 21/02129, 21/02164, 21/02167, 21/0217, 21/02172, 21/02175, 21/02197, 21/022, 21/02214, 21/02219, 21/02227, 21/02252, 21/02255, 21/02263, 21/02266, 21/02269, 21/02271, 21/0228, 21/02288, 21/02293, 21/02296, 21/02299, 21/02301, 21/02318, 21/02321, 21/02326, 21/02332, 21/02334, 21/02365, 21/02606, 21/02658, 21/02664, 21/02697, 21/027, 21/0271, 21/0273, 21/0276, 21/0277, 21/0278, 21/033, 21/0331, 21/0335, 21/0337, 21/0338, 21/04, 21/0405, 21/0445, 21/046, 21/18, 21/185,

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<u>Action</u>	<u>Subclass</u>	<u>Group(s)</u>
		21/187, 21/22, 21/223, 21/225, 21/2254, 21/228, 21/24, 21/26, 21/263, 21/265, 21/266, 21/28, 21/28008, 21/28017, 21/28026, 21/28035, 21/28052, 21/28061, 21/28114, 21/28123, 21/28158, 21/28185, 21/28211, 21/28229, 21/283, 21/285, 21/28525, 21/28531, 21/288, 21/30, 21/304, 21/3043, 21/306, 21/30608, 21/30621, 21/30625, 21/3063, 21/3065, 21/308, 21/3085, 21/3086, 21/3088, 21/31, 21/3105, 21/31051, 21/31053, 21/31055, 21/31056, 21/31105, 21/31111, 21/31116, 21/31127, 21/31133, 21/31144, 21/3115, 21/3205, 21/321, 21/32105, 21/3211, 21/32115, 21/3212, 21/3213, 21/32131, 21/32132, 21/32133, 21/32134, 21/32136, 21/32137, 21/32138, 21/32139, 21/3215, 21/322, 21/3221, 21/3225, 21/34, 21/38, 21/42, 21/425, 21/426, 21/44, 21/441, 21/445, 21/447, 21/449, 21/46, 21/465, 21/467, 21/469, 21/47, 21/4763, 21/67, 21/67017, 21/67028, 21/67092, 21/67103, 21/67109, 21/67115, 21/67121, 21/67126, 21/67132, 21/67138, 21/67144, 21/6715, 21/67213, 21/67219, 21/67225, 21/6723, 21/67242, 21/67276, 21/673, 21/67333, 21/6734, 21/67363, 21/67366, 21/67706, 21/67721, 21/67742, 21/67763, 21/67766, 21/67784, 21/67796, 21/68, 21/682, 21/683, 21/6835, 21/6836, 21/687, 21/70, 21/7624, 21/78, 21/7806, 21/7813
	H01L	22/00, 22/10, 22/12, 22/20, 22/24, 22/26, 22/34
	H01L	2221/68372

The following subclasses/groups are also impacted by this Notice of Changes (indicate subclasses/groups outside of the project scope, such as those listed in the CRL):

A47G, A61B, A61N, B01B, B01J, B05B, B05D, B08B, B21F, B23K, B23Q, B24B, B24C, B25B, B25J, B26D, B28D, B29C, B32B, B33Y, B41M, B65B, B65G, B65H, B81B, B81C, C04B, C07F, C09D, C09G, C09K, C22C, C23C, C23F, C23G, C25D, C25F, C30B, F04C, F16B, F16C, F24F, F25B, F27B, G01K, G01L, G01M, G01N, G01R, G01S, G01T, G02F, G03F, G05B, G06F, G06K, G06V, G09G, G11B, G11C, H01B, H01J, H01M, H01R, H01S, H02M, H02N, H02S, H03B, H03F, H03H, H03K, H04N, H04R, H05B, H05F, H05K, H10F, H10K, H10N

This Notice of Changes includes the following [Check the ones included]:

1. CLASSIFICATION SCHEME CHANGES

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- ☒ A. New, Modified or Deleted Group(s)
- ☒ B. New, Modified or Deleted Warning(s)
- ☒ C. New, Modified or Deleted Note(s)
- ☒ D. New, Modified or Deleted Guidance Heading(s)

2. DEFINITIONS

- ☐ A. New or Modified Definitions (Full definition template)
- ☒ B. Modified or Deleted Definitions (Definitions Quick Fix)

- 3. ☒ REVISION CONCORDANCE LIST (RCL)
- 4. ☒ CHANGES TO THE CPC-TO-IPC CONCORDANCE LIST (CICL)
- 5. ☒ CHANGES TO THE CROSS-REFERENCE LIST (CRL)

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1. CLASSIFICATION SCHEME CHANGES

A. New, Modified or Deleted Group(s)**SUBCLASS H01L - SEMICONDUCTOR DEVICES NOT COVERED BY CLASS H10**

<u>Type*</u>	<u>Symbol</u>	<u>Indent Level</u> <u>Number of dots</u> <u>(e.g. 0, 1, 2)</u>	<u>Title</u> "CPC only" text should normally be enclosed in {curly brackets}**	<u>Transferred to*</u>
D	H01L	Subclass	SEMICONDUCTOR DEVICES NOT COVERED BY CLASS H10 (use of semiconductor devices for measuring G01; resistors in general H01C; magnets, inductors or transformers H01F; capacitors in general H01G; electrolytic devices H01G9/00; batteries or accumulators H01M; waveguides, resonators or lines of the waveguide type H01P; line connectors or current collectors H01R; stimulated-emission devices H01S; electromechanical resonators H03H; loudspeakers, microphones, gramophone pick-ups or like acoustic electromechanical transducers H04R; electric light sources in general H05B; printed circuits, hybrid circuits, casings or constructional details of electrical apparatus, manufacture of assemblages of electrical components H05K; use of semiconductor devices in circuits having a particular application, see the subclass for the application)	
D	H01L21/00	0	Processes or apparatus adapted for the manufacture or treatment of semiconductor or solid state devices or of parts thereof	<administrative transfer to H10P95/00>
D	H01L21/02	1	Manufacture or treatment of semiconductor devices or of parts thereof	<administrative transfer to H10P95/00>
D	H01L21/02002	2	{Preparing wafers}	<administrative transfer to H10P90/00>
D	H01L21/02005	3	{Preparing bulk and homogeneous wafers}	<administrative transfer to H10P90/12>
D	H01L21/02008	4	{Multistep processes}	<administrative transfer to H10P90/12>

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D	H01L21/0201	5	{Specific process step}	<administrative transfer to H10P90/12>
D	H01L21/02013	6	{Grinding, lapping}	<administrative transfer to H10P90/123>
D	H01L21/02016	6	{Backside treatment}	<administrative transfer to H10P90/124>
D	H01L21/02019	6	{Chemical etching}	<administrative transfer to H10P90/126>
D	H01L21/02021	6	{Edge treatment, chamfering}	<administrative transfer to H10P90/128>
D	H01L21/02024	6	{Mirror polishing}	<administrative transfer to H10P90/129>
D	H01L21/02027	4	{Setting crystal orientation}	<administrative transfer to H10P90/14>
D	H01L21/0203	4	{Making porous regions on the surface}	<administrative transfer to H10P90/15>
D	H01L21/02032	4	{by reclaiming or re-processing}	<administrative transfer to H10P90/16>
D	H01L21/02035	4	{Shaping}	<administrative transfer to H10P90/18>
D	H01L21/02041	2	{Cleaning}	<administrative transfer to H10P70/00>
D	H01L21/02043	3	{Cleaning before device manufacture, i.e. Begin-Of-Line process}	<administrative transfer to H10P70/10>
D	H01L21/02046	4	{Dry cleaning only (H01L21/02085 takes precedence)}	<administrative transfer to H10P70/12>
D	H01L21/02049	5	{with gaseous HF}	<administrative transfer to H10P70/125>
D	H01L21/02052	4	{Wet cleaning only (H01L21/02085 takes precedence)}	<administrative transfer to H10P70/15>
D	H01L21/02054	4	{combining dry and wet cleaning steps (H01L21/02085 takes precedence)}	<administrative transfer to H10P70/18>
D	H01L21/02057	3	{Cleaning during device manufacture}	<administrative transfer to H10P70/20>
D	H01L21/0206	4	{during, before or after processing of insulating layers}	<administrative transfer to H10P70/23>
D	H01L21/02063	5	{the processing being the formation of vias or contact holes}	<administrative transfer to H10P70/234>
D	H01L21/02065	5	{the processing being a planarization of insulating layers}	<administrative transfer to H10P70/237>
D	H01L21/02068	4	{during, before or after processing of conductive layers, e.g. polysilicon or amorphous silicon layers}	<administrative transfer to H10P70/27>
D	H01L21/02071	5	{the processing being a delineation, e.g. RIE, of conductive layers}	<administrative transfer to H10P70/273>

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D	H01L21/02074	5	{the processing being a planarization of conductive layers}	<administrative transfer to H10P 70/277>
D	H01L21/02076	3	{Cleaning after the substrates have been singulated}	<administrative transfer to H10P 70/30>
D	H01L21/02079	3	{Cleaning for reclaiming}	<administrative transfer to H10P 70/40>
D	H01L21/02082	3	{product to be cleaned}	<administrative transfer to H10P 70/50>
D	H01L21/02085	4	{Cleaning of diamond}	<administrative transfer to H10P 70/52>
D	H01L21/02087	4	{Cleaning of wafer edges}	<administrative transfer to H10P 70/54>
D	H01L21/0209	4	{Cleaning of wafer backside}	<administrative transfer to H10P 70/56>
D	H01L21/02093	4	{Cleaning of porous materials}	<administrative transfer to H10P 70/58>
D	H01L21/02096	3	{only mechanical cleaning}	<administrative transfer to H10P 70/60>
D	H01L21/02098	3	{only involving lasers, e.g. laser ablation}	<administrative transfer to H10P 70/70>
D	H01L21/02101	3	{only involving supercritical fluids}	<administrative transfer to H10P 70/80>
D	H01L21/02104	2	{Forming layers (deposition in general C23C; crystal growth in general C30B)}	<administrative transfer to H10P 14/00>
D	H01L21/02107	3	{Forming insulating materials on a substrate}	<administrative transfer to H10P 14/60>
D	H01L21/02109	4	{characterised by the type of layer, e.g. type of material, porous/non-porous, pre-cursors, mixtures or laminates}	<administrative transfer to H10P 14/66>
D	H01L21/02112	5	{characterised by the material of the layer}	<administrative transfer to H10P 14/68>
D	H01L21/02115	6	{the material being carbon, e.g. alpha-C, diamond or hydrogen doped carbon}	<administrative transfer to H10P 14/6902>
D	H01L21/02118	6	{carbon based polymeric organic or inorganic material, e.g. polyimides, poly cyclobutene or PVC (polymers <u>per se</u> C08G, photoresist <u>per se</u> G03F)}	<administrative transfer to H10P 14/683 >
D	H01L21/0212	7	{the material being fluoro carbon compounds, e.g. (CF _x) _n , (CH _x F _y) _n or polytetrafluoroethylene}	<administrative transfer to H10P 14/687 >
D	H01L21/02123	6	{the material containing silicon}	<administrative transfer to H10P 14/6903>
D	H01L21/02126	7	{the material containing Si, O, and at least one of H, N, C, F, or other}	<administrative transfer to H10P 14/6922>

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			non-metal elements, e.g. SiOC, SiOC:H or SiONC }	
D	H01L21/02129	8	{the material being boron or phosphorus doped silicon oxides, e.g. BPSG, BSG or PSG}	<administrative transfer to H10P14/6923>
D	H01L21/02131	8	{the material being halogen doped silicon oxides, e.g. FSG}	<administrative transfer to H10P14/6924>
D	H01L21/02134	8	{the material comprising hydrogen silsesquioxane, e.g. HSQ}	<administrative transfer to H10P14/6925>
D	H01L21/02137	8	{the material comprising alkyl silsesquioxane, e.g. MSQ}	<administrative transfer to H10P14/6926>
D	H01L21/0214	8	{the material being a silicon oxynitride, e.g. SiON or SiON:H}	<administrative transfer to H10P14/6927>
D	H01L21/02142	7	{the material containing silicon and at least one metal element, e.g. metal silicate based insulators or metal silicon oxynitrides}	<administrative transfer to H10P14/6928>
D	H01L21/02145	8	{the material containing aluminium, e.g. AlSiOx }	<administrative transfer to H10P14/6929>
D	H01L21/02148	8	{the material containing hafnium, e.g. HfSiOx or HfSiON}	<administrative transfer to H10P14/693>
D	H01L21/0215	8	{the material containing tantalum, e.g. TaSiOx }	<administrative transfer to H10P14/6931>
D	H01L21/02153	8	{the material containing titanium, e.g. TiSiOx }	<administrative transfer to H10P14/6932>
D	H01L21/02156	8	{the material containing at least one rare earth element, e.g. silicate of lanthanides, scandium or yttrium }	<administrative transfer to H10P14/6933>
D	H01L21/02159	8	{the material containing zirconium, e.g. ZrSiOx }	<administrative transfer to H10P14/6934>
D	H01L21/02161	8	{the material containing more than one metal element }	<administrative transfer to H10P14/6936>
D	H01L21/02164	7	{the material being a silicon oxide, e.g. SiO ₂ }	<administrative transfer to H10P14/69215>
D	H01L21/02167	7	{the material being a silicon carbide not containing oxygen, e.g. SiC, SiC:H or silicon carbonitrides (H01L 21/02126 and H01L 21/0214 take precedence)}	<administrative transfer to H10P14/6905>
D	H01L21/0217	7	{the material being a silicon nitride not containing oxygen, e.g. SixNy or SixByNz (H01L21/02126 and H01L21/0214 take precedence)}	<administrative transfer to H10P14/69433>
D	H01L21/02172	6	{the material containing at least one metal element, e.g. metal oxides, metal nitrides, metal oxynitrides or metal carbides (materials containing silicon H01L21/02123; metal silicates H01L21/02142)}	<administrative transfer to H10P14/6938>

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D	H01L21/02175	7	{characterised by the metal (H01L21/02197 takes precedence)}	<administrative transfer to H10P14/6939>
D	H01L21/02178	8	{the material containing aluminium, e.g. Al ₂ O ₃ }	<administrative transfer to H10P14/69391>
D	H01L21/02181	8	{the material containing hafnium, e.g. HfO ₂ }	<administrative transfer to H10P14/69392>
D	H01L21/02183	8	{the material containing tantalum, e.g. Ta ₂ O ₅ }	<administrative transfer to H10P14/69393>
D	H01L21/02186	8	{the material containing titanium, e.g. TiO ₂ }	<administrative transfer to H10P14/69394>
D	H01L21/02189	8	{the material containing zirconium, e.g. ZrO ₂ }	<administrative transfer to H10P14/69395>
D	H01L21/02192	8	{the material containing at least one rare earth metal element, e.g. oxides of lanthanides, scandium or yttrium}	<administrative transfer to H10P14/69396>
D	H01L21/02194	8	{the material containing more than one metal element}	<administrative transfer to H10P14/69397>
D	H01L21/02197	7	{the material having a perovskite structure, e.g. BaTiO ₃ }	<administrative transfer to H10P14/69398>
D	H01L21/022	5	{the layer being a laminate, i.e. composed of sublayers, e.g. stacks of alternating high-k metal oxides (adhesion layers or buffer layers H01L21/02304, H01L21/02362)}	<administrative transfer to H10P14/662>
D	H01L21/02203	5	{the layer being porous}	<administrative transfer to H10P14/665>
D	H01L21/02205	5	{the layer being characterised by the precursor material for deposition}	<administrative transfer to H10P14/668>
D	H01L21/02208	6	{the precursor containing a compound comprising Si}	<administrative transfer to H10P14/6681>
D	H01L21/02211	7	{the compound being a silane, e.g. disilane, methylsilane or chlorosilane}	<administrative transfer to H10P14/6682>
D	H01L21/02214	7	{the compound comprising silicon and oxygen}	<administrative transfer to H10P14/6684>
D	H01L21/02216	8	{the compound being a molecule comprising at least one silicon-oxygen bond and the compound having hydrogen or an organic group attached to the silicon or oxygen, e.g. a siloxane}	<administrative transfer to H10P14/6686>
D	H01L21/02219	7	{the compound comprising silicon and nitrogen}	<administrative transfer to H10P14/6687>
D	H01L21/02222	8	{the compound being a silazane}	<administrative transfer to H10P14/6689>
D	H01L21/02225	4	{characterised by the process for the formation of the insulating layer}	<administrative transfer to H10P14/63>
D	H01L21/02227	5	{formation by a process other than a deposition process}	<administrative transfer to H10P14/6302>

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D	H01L21/0223	6	{formation by oxidation, e.g. oxidation of the substrate}	<administrative transfer to H10P14/6304>
D	H01L21/02233	7	{of the semiconductor substrate or a semiconductor layer}	<administrative transfer to H10P14/6306>
D	H01L21/02236	8	{group IV semiconductor}	<administrative transfer to H10P14/6308>
D	H01L21/02238	9	{silicon in uncombined form, i.e. pure silicon}	<administrative transfer to H10P14/6309>
D	H01L21/02241	8	{III-V semiconductor}	<administrative transfer to H10P14/6312>
D	H01L21/02244	7	{of a metallic layer}	<administrative transfer to H10P14/6314>
D	H01L21/02247	6	{formation by nitridation, e.g. nitridation of the substrate}	<administrative transfer to H10P14/6316>
D	H01L21/02249	6	{formation by combined oxidation and nitridation performed simultaneously}	<administrative transfer to H10P14/6318>
D	H01L21/02252	6	{formation by plasma treatment, e.g. plasma oxidation of the substrate (after treatment of an insulating film by plasma H01L21/3105 and subgroups)}	<administrative transfer to H10P14/6319>
D	H01L21/02255	6	{formation by thermal treatment (H01L21/02252 takes precedence; after treatment of an insulating film H01L21/3105 and subgroups)}	<administrative transfer to H10P14/6322>
D	H01L21/02258	6	{formation by anodic treatment, e.g. anodic oxidation}	<administrative transfer to H10P14/6324>
D	H01L21/0226	5	{formation by a deposition process (<u>per se</u> C23C)}	<administrative transfer to H10P14/6326>
D	H01L21/02263	6	{deposition from the gas or vapour phase}	<administrative transfer to H10P14/6328>
D	H01L21/02266	7	{deposition by physical ablation of a target, e.g. sputtering, reactive sputtering, physical vapour deposition or pulsed laser deposition}	<administrative transfer to H10P14/6329>
D	H01L21/02269	7	{deposition by thermal evaporation (H01L21/02293 takes precedence)}	<administrative transfer to H10P14/6332>
D	H01L21/02271	7	{deposition by decomposition or reaction of gaseous or vapour phase compounds, i.e. chemical vapour deposition (H01L21/02266 takes precedence)}	<administrative transfer to H10P14/6334>
D	H01L21/02274	8	{in the presence of a plasma [PECVD]}	<administrative transfer to H10P14/6336>
D	H01L21/02277	8	{the reactions being activated by other means than plasma or thermal, e.g. photo-CVD}	<administrative transfer to H10P14/6338>

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D	H01L21/0228	8	{deposition by cyclic CVD, e.g. ALD, ALE, pulsed CVD}	<administrative transfer to H10P14/6339>
D	H01L21/02282	6	{liquid deposition, e.g. spin-coating, sol-gel techniques, spray coating}	<administrative transfer to H10P14/6342>
D	H01L21/02285	7	{Langmuir-Blodgett techniques}	<administrative transfer to H10P14/6344>
D	H01L21/02288	7	{printing, e.g. ink-jet printing (<u>per se</u> B41J)}	<administrative transfer to H10P14/6346>
D	H01L21/0229	7	{liquid atomic layer deposition}	<administrative transfer to H10P14/6348>
D	H01L21/02293	6	{formation of epitaxial layers by a deposition process (epitaxial growth <u>per se</u> C30B)}	<administrative transfer to H10P14/6349>
D	H01L21/02296	4	{characterised by the treatment performed before or after the formation of the layer (H01L21/02227 and subgroups take precedence)}	<administrative transfer to H10P14/65>
D	H01L21/02299	5	{pre-treatment}	<administrative transfer to H10P14/6502>
D	H01L21/02301	6	{in-situ cleaning}	<administrative transfer to H10P14/6504>
D	H01L21/02304	6	{formation of intermediate layers, e.g. buffer layers, layers to improve adhesion, lattice match or diffusion barriers}	<administrative transfer to H10P14/6506>
D	H01L21/02307	6	{treatment by exposure to a liquid}	<administrative transfer to H10P14/6508>
D	H01L21/0231	6	{treatment by exposure to electromagnetic radiation, e.g. UV light}	<administrative transfer to H10P14/6509>
D	H01L21/02312	6	{treatment by exposure to a gas or vapour}	<administrative transfer to H10P14/6512>
D	H01L21/02315	7	{treatment by exposure to a plasma}	<administrative transfer to H10P14/6514>
D	H01L21/02318	5	{post-treatment}	<administrative transfer to H10P14/6516>
D	H01L21/02321	6	{introduction of substances into an already existing insulating layer (H01L21/02227 and subgroups take precedence)}	<administrative transfer to H10P14/6518>
D	H01L21/02323	7	{introduction of oxygen}	<administrative transfer to H10P14/6519>
D	H01L21/02326	8	{into a nitride layer, e.g. changing SiN to SiON}	<administrative transfer to H10P14/6522>
D	H01L21/02329	7	{introduction of nitrogen}	<administrative transfer to H10P14/6524>
D	H01L21/02332	8	{into an oxide layer, e.g. changing SiO to SiON}	<administrative transfer to H10P14/6526>

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D	H01L21/02334	6	{in-situ cleaning after layer formation, e.g. removing process residues}	<administrative transfer to H10P14/6528>
D	H01L21/02337	6	{treatment by exposure to a gas or vapour}	<administrative transfer to H10P14/6529>
D	H01L21/0234	7	{treatment by exposure to a plasma}	<administrative transfer to H10P14/6532>
D	H01L21/02343	6	{treatment by exposure to a liquid}	<administrative transfer to H10P14/6534>
D	H01L21/02345	6	{treatment by exposure to radiation, e.g. visible light}	<administrative transfer to H10P14/6536>
D	H01L21/02348	7	{treatment by exposure to UV light}	<administrative transfer to H10P14/6538>
D	H01L21/02351	7	{treatment by exposure to corpuscular radiation, e.g. exposure to electrons, alpha-particles, protons or ions}	<administrative transfer to H10P14/6539>
D	H01L21/02354	7	{using a coherent radiation, e.g. a laser}	<administrative transfer to H10P14/6542>
D	H01L21/02356	6	{treatment to change the morphology of the insulating layer, e.g. transformation of an amorphous layer into a crystalline layer}	<administrative transfer to H10P14/6544>
D	H01L21/02359	6	{treatment to change the surface groups of the insulating layer}	<administrative transfer to H10P14/6546>
D	H01L21/02362	6	{formation of intermediate layers, e.g. capping layers or diffusion barriers}	<administrative transfer to H10P14/6548>
D	H01L21/02365	3	{Forming inorganic semiconducting materials on a substrate}	<administrative transfer to H10P14/20>
D	H01L21/02367	4	{Substrates}	<administrative transfer to H10P14/29>
D	H01L21/0237	5	{Materials}	<administrative transfer to H10P14/2901>
D	H01L21/02373	6	{Group 14 semiconducting materials}	<administrative transfer to H10P14/2902>
D	H01L21/02376	7	{Carbon, e.g. diamond-like carbon}	<administrative transfer to H10P14/2903>
D	H01L21/02378	7	{Silicon carbide}	<administrative transfer to H10P14/2904>
D	H01L21/02381	7	{Silicon, silicon germanium, germanium}	<administrative transfer to H10P14/2905>
D	H01L21/02384	7	{including tin}	<administrative transfer to H10P14/2906>
D	H01L21/02387	6	{Group 13/15 materials}	<administrative transfer to H10P14/2907>
D	H01L21/02389	7	{Nitrides}	<administrative transfer to H10P14/2908>

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D	H01L21/02392	7	{Phosphides}	<administrative transfer to H10P14/2909>
D	H01L21/02395	7	{Arsenides}	<administrative transfer to H10P14/2911>
D	H01L21/02398	7	{Antimonides}	<administrative transfer to H10P14/2912>
D	H01L21/024	6	{Group 12/16 materials}	<administrative transfer to H10P14/2913>
D	H01L21/02403	7	{Oxides}	<administrative transfer to H10P14/2914>
D	H01L21/02406	7	{Sulfides}	<administrative transfer to H10P14/2915>
D	H01L21/02409	7	{Selenides}	<administrative transfer to H10P14/2916>
D	H01L21/02411	7	{Tellurides}	<administrative transfer to H10P14/2917>
D	H01L21/02414	6	{Oxide semiconducting materials not being Group 12/16 materials, e.g. ternary compounds}	<administrative transfer to H10P14/2918>
D	H01L21/02417	6	{Chalcogenide semiconducting materials not being oxides, e.g. ternary compounds}	<administrative transfer to H10P14/2919>
D	H01L21/0242	6	{Crystalline insulating materials}	<administrative transfer to H10P14/2921>
D	H01L21/02422	6	{Non-crystalline insulating materials, e.g. glass, polymers}	<administrative transfer to H10P14/2922>
D	H01L21/02425	6	{Conductive materials, e.g. metallic silicides}	<administrative transfer to H10P14/2923>
D	H01L21/02428	5	{Structure}	<administrative transfer to H10P14/2924>
D	H01L21/0243	6	{Surface structure}	<administrative transfer to H10P14/2925>
D	H01L21/02433	5	{Crystal orientation}	<administrative transfer to H10P14/2926>
D	H01L21/02436	4	{Intermediate layers between substrates and deposited layers}	<administrative transfer to H10P14/32>
D	H01L21/02439	5	{Materials}	<administrative transfer to H10P14/3202>
D	H01L21/02441	6	{Group 14 semiconducting materials}	<administrative transfer to H10P14/3204>
D	H01L21/02444	7	{Carbon, e.g. diamond-like carbon}	<administrative transfer to H10P14/3206>
D	H01L21/02447	7	{Silicon carbide}	<administrative transfer to H10P14/3208>
D	H01L21/0245	7	{Silicon, silicon germanium, germanium}	<administrative transfer to H10P14/3211>
D	H01L21/02452	7	{including tin}	<administrative transfer to H10P14/3212>

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D	H01L21/02455	6	{Group 13/15 materials}	<administrative transfer to H10P14/3214>
D	H01L21/02458	7	{Nitrides}	<administrative transfer to H10P14/3216>
D	H01L21/02461	7	{Phosphides}	<administrative transfer to H10P14/3218>
D	H01L21/02463	7	{Arsenides}	<administrative transfer to H10P14/3221>
D	H01L21/02466	7	{Antimonides}	<administrative transfer to H10P14/3222>
D	H01L21/02469	6	{Group 12/16 materials}	<administrative transfer to H10P14/3224>
D	H01L21/02472	7	{Oxides}	<administrative transfer to H10P14/3226>
D	H01L21/02474	7	{Sulfides}	<administrative transfer to H10P14/3228>
D	H01L21/02477	7	{Selenides}	<administrative transfer to H10P14/3231>
D	H01L21/0248	7	{Tellurides}	<administrative transfer to H10P14/3232>
D	H01L21/02483	6	{Oxide semiconducting materials not being Group 12/16 materials, e.g. ternary compounds}	<administrative transfer to H10P14/3234>
D	H01L21/02485	6	{Other chalcogenide semiconducting materials not being oxides, e.g. ternary compounds}	<administrative transfer to H10P14/3236>
D	H01L21/02488	6	{Insulating materials}	<administrative transfer to H10P14/3238>
D	H01L21/02491	6	{Conductive materials}	<administrative transfer to H10P14/3241>
D	H01L21/02494	5	{Structure}	<administrative transfer to H10P14/3242>
D	H01L21/02496	6	{Layer structure}	<administrative transfer to H10P14/3244>
D	H01L21/02499	7	{Monolayers}	<administrative transfer to H10P14/3246>
D	H01L21/02502	7	{consisting of two layers}	<administrative transfer to H10P14/3248>
D	H01L21/02505	7	{consisting of more than two layers}	<administrative transfer to H10P14/3251>
D	H01L21/02507	8	{Alternating layers, e.g. superlattice}	<administrative transfer to H10P14/3252>
D	H01L21/0251	7	{Graded layers}	<administrative transfer to H10P14/3254>
D	H01L21/02513	6	{Microstructure}	<administrative transfer to H10P14/3256>
D	H01L21/02516	5	{Crystal orientation}	<administrative transfer to H10P14/3258>

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D	H01L21/02518	4	{Deposited layers}	<administrative transfer to H10P14/34>
D	H01L21/02521	5	{Materials}	<administrative transfer to H10P14/3402>
D	H01L21/02524	6	{Group 14 semiconducting materials}	<administrative transfer to H10P14/3404>
D	H01L21/02527	7	{Carbon, e.g. diamond-like carbon}	<administrative transfer to H10P14/3406>
D	H01L21/02529	7	{Silicon carbide}	<administrative transfer to H10P14/3408>
D	H01L21/02532	7	{Silicon, silicon germanium, germanium}	<administrative transfer to H10P14/3411>
D	H01L21/02535	7	{including tin}	<administrative transfer to H10P14/3412>
D	H01L21/02538	6	{Group 13/15 materials}	<administrative transfer to H10P14/3414>
D	H01L21/0254	7	{Nitrides}	<administrative transfer to H10P14/3416>
D	H01L21/02543	7	{Phosphides}	<administrative transfer to H10P14/3418>
D	H01L21/02546	7	{Arsenides}	<administrative transfer to H10P14/3421>
D	H01L21/02549	7	{Antimonides}	<administrative transfer to H10P14/3422>
D	H01L21/02551	6	{Group 12/16 materials}	<administrative transfer to H10P14/3424>
D	H01L21/02554	7	{Oxides}	<administrative transfer to H10P14/3426>
D	H01L21/02557	7	{Sulfides}	<administrative transfer to H10P14/3428>
D	H01L21/0256	7	{Selenides}	<administrative transfer to H10P14/3431>
D	H01L21/02562	7	{Tellurides}	<administrative transfer to H10P14/3432>
D	H01L21/02565	6	{Oxide semiconducting materials not being Group 12/16 materials, e.g. ternary compounds}	<administrative transfer to H10P14/3434>
D	H01L21/02568	6	{Chalcogenide semiconducting materials not being oxides, e.g. ternary compounds}	<administrative transfer to H10P14/3436>
D	H01L21/0257	5	{Doping during depositing}	<administrative transfer to H10P14/3438>
D	H01L21/02573	6	{Conductivity type}	<administrative transfer to H10P14/3441>
D	H01L21/02576	7	{N-type}	<administrative transfer to H10P14/3442>
D	H01L21/02579	7	{P-type}	<administrative transfer to H10P14/3444>

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D	H01L21/02581	7	{Transition metal or rare earth elements}	<administrative transfer to H10P14/3446>
D	H01L21/02584	6	{Delta-doping}	<administrative transfer to H10P14/3448>
D	H01L21/02587	5	{Structure}	<administrative transfer to H10P14/3451>
D	H01L21/0259	6	{Microstructure}	<administrative transfer to H10P14/3452>
D	H01L21/02592	7	{amorphous}	<administrative transfer to H10P14/3454>
D	H01L21/02595	7	{polycrystalline}	<administrative transfer to H10P14/3456>
D	H01L21/02598	7	{monocrystalline}	<administrative transfer to H10P14/3458>
D	H01L21/02601	7	{Nanoparticles (fullerenes H10K85/211)}	<administrative transfer to H10P14/3461>
D	H01L21/02603	7	{Nanowires}	<administrative transfer to H10P14/3462>
D	H01L21/02606	7	{Nanotubes (carbon nanotubes H10K85/211)}	<administrative transfer to H10P14/3464>
D	H01L21/02609	5	{Crystal orientation}	<administrative transfer to H10P14/3466>
D	H01L21/02612	4	{Formation types}	<administrative transfer to H10P14/20>
D	H01L21/02614	5	{Transformation of metal, e.g. oxidation, nitridation}	<administrative transfer to H10P14/203>
D	H01L21/02617	5	{Deposition types}	<administrative transfer to H10P14/20>
D	H01L21/0262	6	{Reduction or decomposition of gaseous compounds, e.g. CVD}	<administrative transfer to H10P14/24>
D	H01L21/02623	6	{Liquid deposition}	<administrative transfer to H10P14/26>
D	H01L21/02625	7	{using melted materials}	<administrative transfer to H10P14/263>
D	H01L21/02628	7	{using solutions}	<administrative transfer to H10P14/265>
D	H01L21/02631	6	{Physical deposition at reduced pressure, e.g. MBE, sputtering, evaporation}	<administrative transfer to H10P14/22>
D	H01L21/02634	6	{Homoepitaxy}	<administrative transfer to H10P14/20>
D	H01L21/02636	6	{Selective deposition, e.g. simultaneous growth of mono- and non-monocrystalline semiconductor materials}	<administrative transfer to H10P14/27>
D	H01L21/02639	7	{Preparation of substrate for selective deposition}	<administrative transfer to H10P14/271>

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D	H01L21/02642	8	{Mask materials other than SiO ₂ or SiN}	<administrative transfer to H10P14/272>
D	H01L21/02645	8	{Seed materials}	<administrative transfer to H10P14/274>
D	H01L21/02647	7	{Lateral overgrowth}	<administrative transfer to H10P14/276>
D	H01L21/0265	8	{Pendeoepitaxy}	<administrative transfer to H10P14/278>
D	H01L21/02653	7	{Vapour-liquid-solid growth}	<administrative transfer to H10P14/279>
D	H01L21/02656	4	{Special treatments}	<administrative transfer to H10P14/20>
D	H01L21/02658	5	{Pretreatments (cleaning in general H01L21/02041)}	<administrative transfer to H10P14/36>
D	H01L21/02661	6	{In-situ cleaning}	<administrative transfer to H10P14/3602>
D	H01L21/02664	5	{Aftertreatments (planarisation in general H01L21/304)}	<administrative transfer to H10P14/38>
D	H01L21/02667	6	{Crystallisation or recrystallisation of non-monocrystalline semiconductor materials, e.g. regrowth}	<administrative transfer to H10P14/3802>
D	H01L21/02669	7	{using crystallisation inhibiting elements}	<administrative transfer to H10P14/3804>
D	H01L21/02672	7	{using crystallisation enhancing elements}	<administrative transfer to H10P14/3806>
D	H01L21/02675	7	{using laser beams}	<administrative transfer to H10P14/3808>
D	H01L21/02678	8	{Beam shaping, e.g. using a mask}	<administrative transfer to H10P14/381>
D	H01L21/0268	9	{Shape of mask}	<administrative transfer to H10P14/3812>
D	H01L21/02683	8	{Continuous wave laser beam}	<administrative transfer to H10P14/3814>
D	H01L21/02686	8	{Pulsed laser beam}	<administrative transfer to H10P14/3816>
D	H01L21/02689	7	{using particle beams}	<administrative transfer to H10P14/3818>
D	H01L21/02691	7	{Scanning of a beam}	<administrative transfer to H10P14/382>
D	H01L21/02694	6	{Controlling the interface between substrate and epitaxial layer, e.g. by ion implantation followed by annealing}	<administrative transfer to H10P14/3822>
D	H01L21/02697	3	{Forming conducting materials on a substrate}	<administrative transfer to H10P14/40>
D	H01L21/027	2	Making masks on semiconductor bodies for further photolithographic	<administrative transfer to H10P76/00>

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			processing not provided for in group H01L21/18 or H01L21/34 photographic masks or originals per se G03F1/00; registration or positioning of photographic masks or originals G03F9/00; photographic cameras G03B; control of position G05D3/00	
D	H01L21/0271	3	{comprising organic layers}	<administrative transfer to H10P 76/20>
D	H01L21/0272	4	{for lift-off processes}	<administrative transfer to H10P 76/202>
D	H01L21/0273	4	{characterised by the treatment of photoresist layers}	<administrative transfer to H10P 76/204>
D	H01L21/0274	5	{Photolithographic processes}	<administrative transfer to H10P 76/2041>
D	H01L21/0275	6	{using lasers}	<administrative transfer to H10P 76/2042>
D	H01L21/0276	6	{using an anti-reflective coating (anti-reflective coating for lithography in general G03F7/09)}	<administrative transfer to H10P 76/2043>
D	H01L21/0277	5	{Electrolithographic processes}	<administrative transfer to H10P 76/2045>
D	H01L21/0278	5	{Röntgenlithographic or X-ray lithographic processes}	<administrative transfer to H10P 76/2047>
D	H01L21/0279	5	{Ionlithographic processes}	<administrative transfer to H10P 76/2049>
D	H01L21/033	3	comprising inorganic layers	<administrative transfer to H10P 76/40>
D	H01L21/0331	4	{for lift-off processes}	<administrative transfer to H10P 76/403>
D	H01L21/0332	4	{characterised by their composition, e.g. multilayer masks, materials}	<administrative transfer to H10P 76/405>
D	H01L21/0334	4	{characterised by their size, orientation, disposition, behaviour, shape, in horizontal or vertical plane}	<administrative transfer to H10P 76/408>
D	H01L21/0335	5	{characterised by their behaviour during the process, e.g. soluble masks, redeposited masks}	<administrative transfer to H10P 76/4083>
D	H01L21/0337	5	{characterised by the process involved to create the mask, e.g. lift-off masks, sidewalls, or to modify the mask, e.g. pre-treatment, post-treatment}	<administrative transfer to H10P 76/4085>
D	H01L21/0338	5	{Process specially adapted to improve the resolution of the mask}	<administrative transfer to H10P 76/4088>

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D	H01L21/04	2	the devices having potential barriers, e.g. a PN junction, depletion layer or carrier concentration layer	<administrative transfer to H10P 95/00>
D	H01L21/0405	3	{the devices having semiconductor bodies comprising semiconducting carbon, e.g. diamond, diamond-like carbon}	<administrative transfer to H10D 62/8303>
D	H01L21/041	4	{Making n- or p-doped regions}	<administrative transfer to H10P 95/92>
D	H01L21/0415	5	{using ion implantation}	<administrative transfer to H10P 30/2044>
D	H01L21/042	4	{Changing their shape, e.g. forming recesses (etching of the semiconductor body H01L21/302)}	<administrative transfer to H10P 50/00>
D	H01L21/0425	4	{Making electrodes}	<administrative transfer to H10D 64/0114>
D	H01L21/043	5	{Ohmic electrodes}	<administrative transfer to H10D 64/0114>
D	H01L21/0435	5	{Schottky electrodes}	<administrative transfer to H10D 64/0122>
D	H01L21/044	5	{Conductor-insulator-semiconductor electrodes}	<administrative transfer to H10D 64/01364>
D	H01L21/0445	3	{the devices having semiconductor bodies comprising crystalline silicon carbide}	<administrative transfer to H10D 62/8325>
D	H01L21/045	4	{passivating silicon carbide surfaces}	<administrative transfer to H10D 62/8325>
D	H01L21/0455	4	{Making n or p doped regions or layers, e.g. using diffusion}	<administrative transfer to H10P 32/172>
D	H01L21/046	5	{using ion implantation}	<administrative transfer to H10P 30/2042 and H10P 30/21 simultaneously>
D	H01L21/0465	6	{using masks}	<administrative transfer to H10P 30/22>
D	H01L21/047	6	{characterised by the angle between the ion beam and the crystal planes or the main crystal surface}	<administrative transfer to H10P 30/2042 and H10P 30/222 simultaneously>
D	H01L21/0475	4	{Changing the shape of the semiconductor body, e.g. forming recesses, (etching of the semiconductor body H01L21/302)}	<administrative transfer to H10P 50/00>
D	H01L21/048	4	{Making electrodes}	<administrative transfer to H10D 64/0115>
D	H01L21/0485	5	{Ohmic electrodes}	<administrative transfer to H10D 64/0115>
D	H01L21/049	5	{Conductor-insulator-semiconductor electrodes, e.g. MIS contacts}	<administrative transfer to H10D 64/01366>
D	H01L21/0495	5	{Schottky electrodes}	<administrative transfer to H10D 64/0123>

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D	H01L21/18	3	the devices having semiconductor bodies comprising elements of Group IV of the Periodic Table or IIIIBV compounds with or without impurities, e.g. doping materials {(H01L21/041 - H01L21/0425, H01L21/045 - H01L21/048 take precedence)}	<administrative transfer to H10P 10/00>
D	H01L21/182	4	{Intermixing or interdiffusion or disordering of III-V heterostructures, e.g. IILD}	<administrative transfer to H10P 14/3824>
D	H01L21/185	4	{Joining of semiconductor bodies for junction formation}	<administrative transfer to H10P 10/12>
D	H01L21/187	5	{by direct bonding}	<administrative transfer to H10P 10/128>
D	H01L21/20	4	Deposition of semiconductor materials on a substrate, e.g. epitaxial growth {solid phase epitaxy}	<administrative transfer to H10P 14/20>
D	H01L21/2003	5	{characterised by the substrate}	<administrative transfer to H10P 14/29>
D	H01L21/2007	6	{Bonding of semiconductor wafers to insulating substrates or to semiconducting substrates using an intermediate insulating layer (H01L21/2011 takes precedence; bonding of semiconductor wafers to semiconductor wafers for junction formation H01L21/187)}	<administrative transfer to H10P 90/1914>
D	H01L21/2011	6	{the substrate being of crystalline insulating material, e.g. sapphire}	<administrative transfer to H10P 10/14>
D	H01L21/2015	6	{the substrate being of crystalline semiconductor material, e.g. lattice adaptation, heteroepitaxy}	<administrative transfer to H10P 14/29>
D	H01L21/22	4	Diffusion of impurity materials, e.g. doping materials, electrode materials, into or out of a semiconductor body, or between semiconductor regions; {Interactions between two or more impurities; Redistribution of impurities}	<administrative transfer to H10P 32/00>
D	H01L21/2205	5	{from the substrate during epitaxy, e.g. autodoping; Preventing or using autodoping}	<administrative transfer to H10P 32/15>
D	H01L21/221	5	{of killers}	<administrative transfer to H10P 32/18 and H10P 32/171 simultaneously>
D	H01L21/2215	6	{in IIIIBV compounds}	<administrative transfer to H10P 32/18 and H10P 32/174 simultaneously>

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D	H01L21/222	5	{Lithium-drift}	<administrative transfer to H10P 32/185>
D	H01L21/2225	5	{Diffusion sources}	<administrative transfer to H10P 32/19>
D	H01L21/223	5	using diffusion into or out of a solid from or into a gaseous phase {(H01L21/221 - H01L21/222 take precedence; diffusion through an applied layer H01L21/225)}	<administrative transfer to H10P 32/12 and H10P 32/171 simultaneously >
D	H01L21/2233	6	{Diffusion into or out of AIIIBV compounds}	<administrative transfer to H10P 32/12 and H10P 32/174 simultaneously>
D	H01L21/2236	6	{from or into a plasma phase}	<administrative transfer to H10P 32/1204>
D	H01L21/225	5	using diffusion into or out of a solid from or into a solid phase, e.g. a doped oxide layer {(H01L21/221 - H01L21/222 take precedence)}	<administrative transfer to H10P 32/14>
D	H01L21/2251	6	{Diffusion into or out of group IV semiconductors}	<administrative transfer to H10P 32/14 and H10P 32/171 simultaneously>
D	H01L21/2252	7	{using predeposition of impurities into the semiconductor surface, e.g. from a gaseous phase}	<administrative transfer to H10P 32/1404 and H10P 32/171 simultaneously>
D	H01L21/2253	8	{by ion implantation}	<administrative transfer to H10P 32/1406 and H10P 32/171 simultaneously >
D	H01L21/2254	7	{from or through or into an applied layer, e.g. photoresist, nitrides}	<administrative transfer to H10P 32/1408 and H10P 32/171 simultaneously >
D	H01L21/2255	8	{the applied layer comprising oxides only, e.g. P2O5, PSG, H3BO3, doped oxides}	<administrative transfer to H10P 32/141 and H10P 32/171 simultaneously >
D	H01L21/2256	9	{through the applied layer}	<administrative transfer to H10P 32/1412 and H10P 32/171 simultaneously >
D	H01L21/2257	8	{the applied layer being silicon or silicide or SIPOS, e.g. polysilicon, porous silicon}	<administrative transfer to H10P 32/1414 and H10P 32/171 simultaneously >
D	H01L21/2258	6	{Diffusion into or out of AIIIBV compounds}	<administrative transfer to H10P 32/14 and H10P 32/174 simultaneously>
D	H01L21/228	5	using diffusion into or out of a solid from or into a liquid phase, e.g. alloy diffusion processes {(H01L21/221 - H01L21/222 take precedence)}	<administrative transfer to H10P 32/16>
D	H01L21/24	4	Alloying of impurity materials, e.g. doping materials, electrode	<administrative transfer to H10P 95/50>

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			materials, with a semiconductor body {(H01L21/182 takes precedence)}	
D	H01L21/242	5	{Alloying of doping materials with AIIIBV compounds}	<administrative transfer to H10P 95/50>
D	H01L21/244	5	{Alloying of electrode materials}	<administrative transfer to H10P 95/50>
D	H01L21/246	6	{with AIIIBV compounds}	<administrative transfer to H10P 95/50>
D	H01L21/248	5	{Apparatus specially adapted for the alloying}	<administrative transfer to H10P 95/50>
D	H01L21/26	4	Bombardment with radiation {(H01L21/3105 takes precedence)}	<administrative transfer to H10P 34/00>
D	H01L21/2605	5	{using natural radiation, e.g. alpha, beta or gamma radiation}	<administrative transfer to H10P 34/10>
D	H01L21/261	5	to produce a nuclear reaction transmuting chemical elements	<administrative transfer to H10P 34/20>
D	H01L21/263	5	with high-energy radiation (H01L21/261 takes precedence)	<administrative transfer to H10P 34/40>
D	H01L21/2633	6	{for etching, e.g. sputteretching}	<administrative transfer to H10P 50/20>
D	H01L21/2636	6	{for heating, e.g. electron beam heating}	<administrative transfer to H10P 95/90>
D	H01L21/265	6	producing ion implantation	<administrative transfer to H10P 30/20>
D	H01L21/26506	7	{in group IV semiconductors}	<administrative transfer to H10P 30/204 and H10P 30/208 simultaneously>
D	H01L21/26513	8	{of electrically active species}	<administrative transfer to H10P 30/204 and H10P 30/21 simultaneously>
D	H01L21/2652	9	{Through-implantation}	<administrative transfer to H10P 30/204 and H10P 30/212 simultaneously>
D	H01L21/26526	8	{Recoil-implantation}	<administrative transfer to H10P 30/204 and H10P 30/214 simultaneously>
D	H01L21/26533	8	{of electrically inactive species in silicon to make buried insulating layers}	<administrative transfer to H10P 30/209>
D	H01L21/2654	7	{in AIIIBV compounds}	<administrative transfer to H10P 30/206 and H10P 30/208 simultaneously>
D	H01L21/26546	8	{of electrically active species}	<administrative transfer to H10P 30/206 and H10P 30/21 simultaneously>
D	H01L21/26553	9	{Through-implantation}	<administrative transfer to H10P 30/206 and H10P 30/212 simultaneously>

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D	H01L21/2656	8	{characterised by the implantation of both electrically active and inactive species in the same semiconductor region to be doped}	<administrative transfer to H10P 30/206 and H10P 30/218 simultaneously>
D	H01L21/26566	7	{of a cluster, e.g. using a gas cluster ion beam}	<administrative transfer to H10P 30/224>
D	H01L2021/26573	7	{in diamond}	<administrative transfer to H10P 30/2044>
D	H01L21/2658	7	{of a molecular ion, e.g. decaborane}	<administrative transfer to H10P 30/225>
D	H01L21/26586	7	{characterised by the angle between the ion beam and the crystal planes or the main crystal surface}	<administrative transfer to H10P 30/222>
D	H01L21/26593	7	{at a temperature lower than room temperature}	<administrative transfer to H10P 30/226>
D	H01L21/266	7	using masks {(H01L21/26586 takes precedence)}	<administrative transfer to H10P 30/22>
D	H01L21/268	6	using electromagnetic radiation, e.g. laser radiation	<administrative transfer to H10P 34/42>
D	H01L21/2683	7	{using X-ray lasers}	<administrative transfer to H10P 34/42>
D	H01L21/2686	7	{using incoherent radiation}	<administrative transfer to H10P 34/422>
D	H01L21/28	4	Manufacture of electrodes on semiconductor bodies using processes or apparatus not provided for in groups H01L21/20 - H01L21/268	<administrative transfer to H10D 64/011>
D	H01L21/28008	5	{Making conductor-insulator-semiconductor electrodes}	<administrative transfer to H10D 64/013>
D	H01L21/28017	6	{the insulator being formed after the semiconductor body, the semiconductor being silicon}	<administrative transfer to H10D 64/01302>
D	H01L21/28026	7	{characterised by the conductor (H01L21/28176 takes precedence)}	<administrative transfer to H10D 64/01304>
D	H01L21/28035	8	{the final conductor layer next to the insulator being silicon, e.g. polysilicon, with or without impurities (H01L21/28105 takes precedence)}	<administrative transfer to H10D 64/01306>
D	H01L21/28044	9	{the conductor comprising at least another non-silicon conductive layer}	<administrative transfer to H10D 64/01308>
D	H01L21/28052	10	{the conductor comprising a silicide layer formed by the silicidation reaction of silicon with a metal layer (formed by metal ion implantation H01L21/28044)}	<administrative transfer to H10D 64/0131>

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D	H01L21/28061	10	{the conductor comprising a metal or metal silicide formed by deposition, e.g. sputter deposition, i.e. without a silicidation reaction (H01L21/28052 takes precedence)}	<administrative transfer to H10D 64/01312>
D	H01L21/2807	8	{the final conductor layer next to the insulator being Si or Ge or C and their alloys except Si}	<administrative transfer to H10D 64/01314>
D	H01L21/28079	8	{the final conductor layer next to the insulator being a single metal, e.g. Ta, W, Mo, Al}	<administrative transfer to H10D 64/01316>
D	H01L21/28088	8	{the final conductor layer next to the insulator being a composite, e.g. TiN}	<administrative transfer to H10D 64/01318>
D	H01L21/28097	8	{the final conductor layer next to the insulator being a metallic silicide}	<administrative transfer to H10D 64/0132>
D	H01L21/28105	8	{the final conductor next to the insulator having a lateral composition or doping variation, or being formed laterally by more than one deposition step}	<administrative transfer to H10D 64/01322>
D	H01L21/28114	8	{characterised by the sectional shape, e.g. T, inverted-T}	<administrative transfer to H10D 64/01324>
D	H01L21/28123	8	{Lithography-related aspects, e.g. sub-lithography lengths; Isolation-related aspects, e.g. to solve problems arising at the crossing with the side of the device isolation; Planarisation aspects}	<administrative transfer to H10D 64/01326>
D	H01L21/28132	9	{conducting part of electrode is defined by a sidewall spacer or a similar technique, e.g. oxidation under mask, plating}	<administrative transfer to H10D 64/01328>
D	H01L21/28141	9	{insulating part of the electrode is defined by a sidewall spacer, e.g. dummy spacer, or a similar technique, e.g. oxidation under mask, plating}	<administrative transfer to H10D 64/01334>
D	H01L21/2815	9	{part or whole of the electrode is a sidewall spacer or made by a similar technique, e.g. transformation under mask, plating}	<administrative transfer to H10D 64/0133>
D	H01L21/28158	7	{Making the insulator}	<administrative transfer to H10D 64/01332>
D	H01L21/28167	8	{on single crystalline silicon, e.g. using a liquid, i.e. chemical oxidation}	<administrative transfer to H10D 64/01336>
D	H01L21/28176	9	{with a treatment, e.g. annealing, after the formation of the definitive gate conductor}	<administrative transfer to H10D 64/01338>

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D	H01L21/28185	9	{with a treatment, e.g. annealing, after the formation of the gate insulator and before the formation of the definitive gate conductor}	<administrative transfer to H10D 64/0134>
D	H01L21/28194	9	{by deposition, e.g. evaporation, ALD, CVD, sputtering, laser deposition (H01L21/28202 takes precedence)}	<administrative transfer to H10D 64/01342>
D	H01L21/28202	9	{in a nitrogen-containing ambient, e.g. nitride deposition, growth, oxynitridation, NH ₃ nitridation, N ₂ O oxidation, thermal nitridation, RTN, plasma nitridation, RPN}	<administrative transfer to H10D 64/01344>
D	H01L21/28211	9	{in a gaseous ambient using an oxygen or a water vapour, e.g. RTO, possibly through a layer (H01L21/28194 and H01L21/28202 take precedence)}	<administrative transfer to H10D 64/01346>
D	H01L21/2822	8	{with substrate doping, e.g. N, Ge, C implantation, before formation of the insulator}	<administrative transfer to H10D 64/01348>
D	H01L21/28229	8	{by deposition of a layer, e.g. metal, metal compound or polysilicon, followed by transformation thereof into an insulating layer}	<administrative transfer to H10D 64/0135>
D	H01L21/28238	8	{with sacrificial oxide}	<administrative transfer to H10D 64/01352>
D	H01L21/28247	7	{passivation or protection of the electrode, e.g. using re-oxidation}	<administrative transfer to H10D 64/01354>
D	H01L21/28255	6	{the insulator being formed after the semiconductor body, the semiconductor belonging to Group IV and not being elemental silicon, e.g. Ge, SiGe, SiGeC}	<administrative transfer to H10D 64/01356>
D	H01L21/28264	6	{the insulator being formed after the semiconductor body, the semiconductor being a III-V compound}	<administrative transfer to H10D 64/01358>
D	H01L21/283	5	Deposition of conductive or insulating materials for electrodes {conducting electric current}	<administrative transfer to H10P 14/40>
D	H01L21/285	6	from a gas or vapour, e.g. condensation	<administrative transfer to H10P 14/42>
D	H01L21/28506	7	{of conductive layers}	<administrative transfer to H10P 14/40>
D	H01L21/28512	8	{on semiconductor bodies comprising elements of Group IV of the Periodic Table}	<administrative transfer to H10D 64/0111>

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D	H01L21/28518	9	{the conductive layers comprising silicides (H01L21/28537 takes precedence)}	<administrative transfer to H10D 64/0112>
D	H01L21/28525	9	{the conductive layers comprising semiconducting material (H01L21/28518, H01L21/28537 take precedence)}	<administrative transfer to H10D 64/0113>
D	H01L21/28531	10	{Making of side-wall contacts}	<administrative transfer to H10D 64/0113>
D	H01L21/28537	9	{Deposition of Schottky electrodes}	<administrative transfer to H10D 64/0121>
D	H01L21/2855	9	{by physical means, e.g. sputtering, evaporation (H01L21/28518 - H01L21/28537 and H01L21/28568 take precedence)}	<administrative transfer to H10P 14/44>
D	H01L21/28556	9	{by chemical means, e.g. CVD, LPCVD, PECVD, laser CVD (H01L21/28518 - H01L21/28537 and H01L21/28568 take precedence)}	<administrative transfer to H10P 14/43>
D	H01L21/28562	10	{Selective deposition}	<administrative transfer to H10P 14/432>
D	H01L21/28568	9	{the conductive layers comprising transition metals (H01L21/28518 takes precedence)}	<administrative transfer to H10P 14/418>
D	H01L21/28575	8	{on semiconductor bodies comprising IIIIBV compounds}	<administrative transfer to H10D 64/0116>
D	H01L21/28581	9	{Deposition of Schottky electrodes}	<administrative transfer to H10D 64/0124>
D	H01L21/28587	9	{characterised by the sectional shape, e.g. T, inverted T}	<administrative transfer to H10D 64/0125>
D	H01L21/28593	10	{asymmetrical sectional shape}	<administrative transfer to H10D 64/0126>
D	H01L21/288	6	from a liquid, e.g. electrolytic deposition	<administrative transfer to H10P 14/46>
D	H01L21/2885	7	{using an external electrical current, i.e. electro-deposition}	<administrative transfer to H10P 14/47>
D	H01L21/30	4	Treatment of semiconductor bodies using processes or apparatus not provided for in groups H01L21/20 - H01L21/26 (manufacture of electrodes thereon H01L21/28)	<administrative transfer to H10P 95/00>
D	H01L21/3003	5	{Hydrogenation or deuterisation, e.g. using atomic hydrogen from a plasma}	<administrative transfer to H10P 95/94>
D	H01L21/3006	6	{of IIIIBV compounds}	<administrative transfer to H10P 95/94>

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D	H01L21/302	5	to change their surface-physical characteristics or shape, e.g. etching, polishing, cutting	<administrative transfer to H10P50/00>
D	H01L21/304	6	Mechanical treatment, e.g. grinding, polishing, cutting {(H01L21/30625 takes precedence)}	<administrative transfer to H10P52/00>
D	H01L21/3043	7	{Making grooves, e.g. cutting}	<administrative transfer to H10P52/00>
D	H01L21/3046	7	{using blasting, e.g. sand-blasting (H01L21/2633 takes precedence)}	<administrative transfer to H10P52/00>
D	H01L21/306	6	Chemical or electrical treatment, e.g. electrolytic etching (to form insulating layers H01L21/31)	<administrative transfer to H10P50/00>
D	H01L21/30604	7	{Chemical etching}	<administrative transfer to H10P50/642>
D	H01L21/30608	8	{Anisotropic liquid etching (H01L21/3063 takes precedence)}	<administrative transfer to H10P50/644>
D	H01L21/30612	8	{Etching of AIIBV compounds}	<administrative transfer to H10P50/646>
D	H01L21/30617	9	{Anisotropic liquid etching}	<administrative transfer to H10P50/648>
D	H01L21/30621	9	{Vapour phase etching}	<administrative transfer to H10P50/246>
D	H01L21/30625	7	{With simultaneous mechanical treatment, e.g. mechanico-chemical polishing}	<administrative transfer to H10P52/402>
D	H01L21/3063	7	Electrolytic etching	<administrative transfer to H10P50/613>
D	H01L21/30635	8	{of AIIBV compounds}	<administrative transfer to H10P50/617>
D	H01L21/3065	7	Plasma etching; Reactive-ion etching	<administrative transfer to H10P50/242>
D	H01L21/30655	8	{comprising alternated and repeated etching and passivation steps, e.g. Bosch process}	<administrative transfer to H10P50/244>
D	H01L21/308	7	using masks (H01L21/3063, H01L21/3065 take precedence)	<administrative transfer to H10P50/691>
D	H01L21/3081	8	{characterised by their composition, e.g. multilayer masks, materials}	<administrative transfer to H10P50/692>
D	H01L21/3083	8	{characterised by their size, orientation, disposition, behaviour, shape, in horizontal or vertical plane}	<administrative transfer to H10P50/693>
D	H01L21/3085	9	{characterised by their behaviour during the process, e.g. soluble masks, redeposited masks}	<administrative transfer to H10P50/694>
D	H01L21/3086	9	{characterised by the process involved to create the mask, e.g. lift-off masks, sidewalls, or to modify	<administrative transfer to H10P50/695>

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			the mask, e.g. pre-treatment, post-treatment}	
D	H01L21/3088	9	{Process specially adapted to improve the resolution of the mask}	<administrative transfer to H10P50/696>
D	H01L21/31	5	to form insulating layers thereon, e.g. for masking or by using photolithographic techniques (encapsulating layers H01L21/56); After treatment of these layers; Selection of materials for these layers	<administrative transfer to H10P14/60>
D	H01L21/3105	6	After-treatment	<administrative transfer to H10P95/00>
D	H01L21/31051	7	{Planarisation of the insulating layers (H01L21/31058 takes precedence)}	<administrative transfer to H10P95/06>
D	H01L21/31053	8	{involving a dielectric removal step}	<administrative transfer to H10P95/062>
D	H01L21/31055	9	{the removal being a chemical etching step, e.g. dry etching etching per se H01L21/311}	<administrative transfer to H10P95/064>
D	H01L21/31056	10	{the removal being a selective chemical etching step, e.g. selective dry etching through a mask}	<administrative transfer to H10P95/066>
D	H01L21/31058	7	{of organic layers}	<administrative transfer to H10P95/08>
D	H01L21/311	7	Etching the insulating layers {by chemical or physical means (H01L21/31058 takes precedence)}	<administrative transfer to H10P50/28>
D	H01L21/31105	8	{Etching inorganic layers}	<administrative transfer to H10P50/282>
D	H01L21/31111	9	{by chemical means}	<administrative transfer to H10P50/283>
D	H01L21/31116	10	{by dry-etching}	<administrative transfer to H10P50/283>
D	H01L21/31122	11	{of layers not containing Si, e.g. PZT, Al ₂ O ₃ }	<administrative transfer to H10P50/285>
D	H01L21/31127	8	{Etching organic layers}	<administrative transfer to H10P50/286>
D	H01L21/31133	9	{by chemical means}	<administrative transfer to H10P50/287>
D	H01L21/31138	10	{by dry-etching}	<administrative transfer to H10P50/287>
D	H01L21/31144	8	{using masks}	<administrative transfer to H10P50/73>
D	H01L21/3115	7	Doping the insulating layers	<administrative transfer to H10P32/20>
D	H01L21/31155	8	{by ion implantation}	<administrative transfer to H10P30/40>

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D	H01L21/32	6	using masks	<administrative transfer to H10P14/61>
D	H01L21/3205	6	Deposition of non-insulating-, e.g. conductive- or resistive-, layers on insulating layers; After-treatment of these layers (manufacture of electrodes H01L21/28)	<administrative transfer to H10P14/40>
D	H01L21/32051	7	{Deposition of metallic or metal-silicide layers}	<administrative transfer to H10P14/412>
D	H01L21/32053	8	{of metal-silicide layers}	<administrative transfer to H10P14/414>
D	H01L21/32055	7	{Deposition of semiconductive layers, e.g. poly - or amorphous silicon layers}	<administrative transfer to H10P14/416>
D	H01L21/32056	7	{Deposition of conductive or semi-conductive organic layers (H01L21/32058 takes precedence)}	<administrative transfer to H10P14/40>
D	H01L21/32058	7	{Deposition of superconductive layers}	<administrative transfer to H10P14/40>
D	H01L21/321	7	After treatment	<administrative transfer to H10P95/00>
D	H01L21/32105	8	{Oxidation of silicon-containing layers}	<administrative transfer to H10P14/6308>
D	H01L21/3211	8	{Nitridation of silicon-containing layers}	<administrative transfer to H10P14/6316>
D	H01L21/32115	8	{Planarisation}	<administrative transfer to H10P95/04>
D	H01L21/3212	9	{by chemical mechanical polishing [CMP]}	<administrative transfer to H10P52/403>
D	H01L21/32125	10	{by simultaneously passing an electrical current, i.e. electrochemical mechanical polishing, e.g. ECMP}	<administrative transfer to H10P52/203>
D	H01L21/3213	8	Physical or chemical etching of the layers, e.g. to produce a patterned layer from a pre-deposited extensive layer	<administrative transfer to H10P50/00>
D	H01L21/32131	9	{by physical means only}	<administrative transfer to H10P50/262>
D	H01L21/32132	10	{of silicon-containing layers}	<administrative transfer to H10P50/263>
D	H01L21/32133	9		<administrative transfer to H10P50/264>
D	H01L21/32134	10	{by liquid etching only}	<administrative transfer to H10P50/667>
D	H01L21/32135	10	{by vapour etching only}	<administrative transfer to H10P50/266>

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D	H01L21/32136	11	{using plasmas}	<administrative transfer to H10P50/267>
D	H01L21/32137	12	{of silicon-containing layers}	<administrative transfer to H10P50/268>
D	H01L21/32138	11	{pre- or post-treatments, e.g. anti-corrosion processes}	<administrative transfer to H10P50/269>
D	H01L21/32139	9	{using masks}	<administrative transfer to H10P50/71>
D	H01L21/3215	8	Doping the layers	<administrative transfer to H10P32/30>
D	H01L21/32155	9	{Doping polycrystalline - or amorphous silicon layers}	<administrative transfer to H10P32/302>
D	H01L21/322	5	to modify their internal properties, e.g. to produce internal imperfections	<administrative transfer to H10P36/00>
D	H01L21/3221	6	{of silicon bodies, e.g. for gettering}	<administrative transfer to H10P36/03>
D	H01L21/3223	7	{using cavities formed by hydrogen or noble gas ion implantation}	<administrative transfer to H10P95/405>
D	H01L21/3225	7	{Thermally inducing defects using oxygen present in the silicon body for intrinsic gettering (H01L21/3226 takes precedence)}	<administrative transfer to H10P36/20>
D	H01L21/3226	7	{of silicon on insulator}	<administrative transfer to H10P36/07>
D	H01L21/3228	6	{of IIIIV compounds, e.g. to make them semi-insulating}	<administrative transfer to H10P95/408>
D	H01L21/324	5	Thermal treatment for modifying the properties of semiconductor bodies, e.g. annealing, sintering (H01L21/20 - H01L21/288 and H01L21/302 - H01L21/322 take precedence)	<administrative transfer to H10P95/90>
D	H01L21/3242	6	{for the formation of PN junctions without addition of impurities (H01L21/22 takes precedence)}	<administrative transfer to H10P95/902>
D	H01L21/3245	6	{of IIIIV compounds}	<administrative transfer to H10P95/904>
D	H01L21/3247	6	{for altering the shape, e.g. smoothing the surface}	<administrative transfer to H10P95/906>
D	H01L21/326	5	Application of electric currents or fields, e.g. for electroforming (H01L21/20 - H01L21/288 and H01L21/302 - H01L21/324 take precedence)	<administrative transfer to H10P95/80>
D	H01L21/34	3	the devices having semiconductor bodies not provided for in groups H01L21/18, H10D48/04 and	<administrative transfer to H10P10/00>

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			H10D48/07, with or without impurities, e.g. doping materials	
D	H01L21/38	4	Diffusion of impurity materials, e.g. doping materials, electrode materials, into or out of a semiconductor body, or between semiconductor regions	<administrative transfer to H10P 32/00>
D	H01L21/383	5	using diffusion into or out of a solid from or into a gaseous phase	<administrative transfer to H10P 32/12 and H10P 32/17 simultaneously>
D	H01L21/385	5	using diffusion into or out of a solid from or into a solid phase, e.g. a doped oxide layer	<administrative transfer to H10P 32/14 and H10P 32/17 simultaneously >
D	H01L21/388	5	using diffusion into or out of a solid from or into a liquid phase, e.g. alloy diffusion processes	<administrative transfer to H10P 32/16 and H10P 32/17 simultaneously >
D	H01L21/40	4	Alloying of impurity materials, e.g. doping materials, electrode materials, with a semiconductor body	<administrative transfer to H10P 95/50>
D	H01L21/42	4	Bombardment with radiation	<administrative transfer to H10P 34/00>
D	H01L21/423	5	with high-energy radiation	<administrative transfer to H10P 34/40>
D	H01L21/425	6	producing ion implantation	<administrative transfer to H10P 30/202>
D	H01L21/426	7	using masks	<administrative transfer to H10P 30/22>
D	H01L21/428	6	using electromagnetic radiation, e.g. laser radiation	<administrative transfer to H10P 34/42>
D	H01L21/44	4	Manufacture of electrodes on semiconductor bodies using processes or apparatus not provided for in groups H01L21/38 - H01L21/428	<administrative transfer to H10D 64/011>
D	H01L21/441	5	Deposition of conductive or insulating materials for electrodes	<administrative transfer to H10D 64/011>
D	H01L21/443	6	from a gas or vapour, e.g. condensation	<administrative transfer to H10D 64/011>
D	H01L21/445	6	from a liquid, e.g. electrolytic deposition	<administrative transfer to H10P 14/47>
D	H01L21/447	5	involving the application of pressure, e.g. thermo-compression bonding	<administrative transfer to H10P 14/40 >
D	H01L21/449	5	involving the application of mechanical vibrations, e.g. ultrasonic vibrations	<administrative transfer to H10P 14/40>
D	H01L21/46	4	Treatment of semiconductor bodies using processes or apparatus not	<administrative transfer to H10P 95/00>

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			provided for in groups H01L21/428 (manufacture of electrodes thereon H01L21/44)	
D	H01L21/461	5	to change their surface-physical characteristics or shape, e.g. etching, polishing, cutting	<administrative transfer to H10P 50/00>
D	H01L21/463	6	Mechanical treatment, e.g. grinding, ultrasonic treatment	<administrative transfer to H10P 52/00, H10P 54/00 and H10P 95/60 simultaneously>
D	H01L21/465	6	Chemical or electrical treatment, e.g. electrolytic etching (to form insulating layers H01L21/469)	<administrative transfer to H10P 50/20, H10P 52/00 and H10P 95/70 simultaneously>
D	H01L21/467	7	using masks	<administrative transfer to H10P 50/69>
D	H01L21/469	6	to form insulating layers thereon, e.g. for masking or by using photolithographic techniques (encapsulating layers H01L21/56); After-treatment of these layers	<administrative transfer to H10P 14/60>
D	H01L21/47	7	Organic layers, e.g. photoresist (H01L21/475, H01L21/4757 take precedence)	<administrative transfer to H10P 14/68>
D	H01L21/471	7	Inorganic layers (H01L21/475, H01L21/4757 take precedence)	<administrative transfer to H10P 14/69>
D	H01L21/473	8	composed of oxides or glassy oxides or oxide based glass	<administrative transfer to H10P 14/692 >
D	H01L21/475	7	using masks	<administrative transfer to H10P 14/61>
D	H01L21/4757	7	After-treatment	<administrative transfer to H10P 50/28>
D	H01L21/47573	8	{Etching the layer}	<administrative transfer to H10P 50/282>
D	H01L21/47576	8	{Doping the layer}	<administrative transfer to H10P 30/40>
D	H01L21/4763	6	Deposition of non-insulating, e.g. conductive -, resistive -, layers on insulating layers; After-treatment of these layers (manufacture of electrodes H01L21/28, {H01L21/44})	<administrative transfer to H10P 14/40>
D	H01L21/47635	7	{After-treatment of these layers}	<administrative transfer to H10P 95/00>
D	H01L21/477	5	Thermal treatment for modifying the properties of semiconductor bodies, e.g. annealing, sintering (H01L21/38 - H01L21/449 and	<administrative transfer to H10P 95/90>

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			H01L21/461 - H01L21/475 take precedence)	
D	H01L21/479	5	Application of electric currents or fields, e.g. for electroforming (H01L21/38 - H01L21/449 and H01L21/461 - H01L21/475 take precedence)	<administrative transfer to H10P95/80>
D	H01L21/62	2	the devices having no potential barriers	<administrative transfer to H10P95/00>
D	H01L21/64	1	Manufacture or treatment of solid state devices other than semiconductor devices, or of parts thereof, not peculiar to a single device provided for in subclasses H10F, H10H, H10K or H10N	<administrative transfer to H10P95/00>
D	H01L21/67	1	Apparatus specially adapted for handling semiconductor or electric solid state devices during manufacture or treatment thereof; Apparatus specially adapted for handling wafers during manufacture or treatment of semiconductor or electric solid state devices or components {; Apparatus not specifically provided for elsewhere (processes per se H01L21/30, H01L21/46, H01L23/00; simple temporary support means, e.g. using adhesives, electric or magnetic means H01L21/68, H01L21/302; apparatus for manufacturing arrangements for connecting or disconnecting semiconductor or solid-state bodies and for methods related thereto H01L24/74;)}	<administrative transfer to H10P72/00>
D	H01L21/67005	2	{ Apparatus not specifically provided for elsewhere (processes per se H01L21/30, H01L21/46, H01L23/00; simple temporary support means, e.g. using adhesives, electric or magnetic means H01L21/68, H01L21/302)}	<administrative transfer to H10P72/00>
D	H01L21/67011	3	{ Apparatus for manufacture or treatment (processes H01L21/30, H01L21/46; for production or after-treatment of single crystals or homogeneous polycrystalline material C30B35/00)}	<administrative transfer to H10P72/04>
D	H01L21/67017	4	{ Apparatus for fluid treatment (H01L21/67126, H01L21/6715 take precedence)}	<administrative transfer to H10P72/0402>

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D	H01L21/67023	5	{for general liquid treatment, e.g. etching followed by cleaning}	<administrative transfer to H10P72/0404>
D	H01L21/67028	5	{for cleaning followed by drying, rinsing, stripping, blasting or the like}	<administrative transfer to H10P72/0406>
D	H01L21/67034	6	{for drying}	<administrative transfer to H10P72/0408>
D	H01L21/6704	6	{for wet cleaning or washing}	<administrative transfer to H10P72/0411>
D	H01L21/67046	7	{using mainly scrubbing means, e.g. brushes}	<administrative transfer to H10P72/0412>
D	H01L21/67051	7	{using mainly spraying means, e.g. nozzles}	<administrative transfer to H10P72/0414>
D	H01L21/67057	7	{with the semiconductor substrates being dipped in baths or vessels}	<administrative transfer to H10P72/0416>
D	H01L21/67063	5	{for etching}	<administrative transfer to H10P72/0418>
D	H01L21/67069	6	{for drying etching}	<administrative transfer to H10P72/0421>
D	H01L21/67075	6	{for wet etching}	<administrative transfer to H10P72/0422>
D	H01L21/6708	7	{using mainly spraying means, e.g. nozzles}	<administrative transfer to H10P72/0424>
D	H01L21/67086	7	{with the semiconductor substrates being dipped in baths or vessels}	<administrative transfer to H10P72/0426>
D	H01L21/67092	4	{Apparatus for mechanical treatment or grinding or cutting, see the relevant groups in subclasses B24B or B28D}	<administrative transfer to H10P72/0428>
D	H01L21/67098	4	{Apparatus for thermal treatment}	<administrative transfer to H10P72/0431>
D	H01L21/67103	5	{mainly by conduction}	<administrative transfer to H10P72/0432>
D	H01L21/67109	5	{mainly by convection}	<administrative transfer to H10P72/0434>
D	H01L21/67115	5	{mainly by radiation}	<administrative transfer to H10P72/0436>
D	H01L21/67121	4	{Apparatus for making assemblies not otherwise provided for, e.g. package constructions}	<administrative transfer to H10P72/0438>
D	H01L21/67126	4	{Apparatus for sealing, encapsulating, glassing, decapsulating or the like (processes H01L23/02, H01L23/28)}	<administrative transfer to H10P72/0441>
D	H01L21/67132	4	{Apparatus for placing on an insulating substrate, e.g. tape}	<administrative transfer to H10P72/0442>
D	H01L21/67138	4	{Apparatus for wiring semiconductor or solid state device}	<administrative transfer to H10P72/0444>

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D	H01L21/67144	4	{Apparatus for mounting on conductive members, e.g. leadframes or conductors on insulating substrates}	<administrative transfer to H10P72/0446>
D	H01L21/6715	4	{Apparatus for applying a liquid, a resin, an ink or the like (H01L21/67126 takes precedence)}	<administrative transfer to H10P72/0448>
D	H01L21/67155	4	{Apparatus for manufacturing or treating in a plurality of work-stations}	<administrative transfer to H10P72/0451>
D	H01L21/67161	5	{characterized by the layout of the process chambers}	<administrative transfer to H10P72/0452>
D	H01L21/67167	6	{surrounding a central transfer chamber}	<administrative transfer to H10P72/0454>
D	H01L21/67173	6	{in-line arrangement}	<administrative transfer to H10P72/0456>
D	H01L21/67178	6	{vertical arrangement}	<administrative transfer to H10P72/0458>
D	H01L21/67184	5	{characterized by the presence of more than one transfer chamber}	<administrative transfer to H10P72/0461>
D	H01L21/6719	5	{characterized by the construction of the processing chambers, e.g. modular processing chambers}	<administrative transfer to H10P72/0462>
D	H01L21/67196	5	{characterized by the construction of the transfer chamber}	<administrative transfer to H10P72/0464>
D	H01L21/67201	5	{characterized by the construction of the load-lock chamber}	<administrative transfer to H10P72/0466>
D	H01L21/67207	5	{comprising a chamber adapted to a particular process}	<administrative transfer to H10P72/0468>
D	H01L21/67213	6	{comprising at least one ion or electron beam chamber (coating by ion implantation C23C; ion or electron beam tubes H01J37/00)}	<administrative transfer to H10P72/0471>
D	H01L21/67219	6	{comprising at least one polishing chamber (polishing apparatuses B24B)}	<administrative transfer to H10P72/0472>
D	H01L21/67225	6	{comprising at least one lithography chamber (lithographic apparatuses G03F7/00)}	<administrative transfer to H10P72/0474>
D	H01L21/6723	6	{comprising at least one plating chamber (electroless plating apparatuses C23C, electroplating apparatuses C25D)}	<administrative transfer to H10P72/0476>
D	H01L21/67236	5	{the substrates being processed being not semiconductor wafers, e.g. leadframes or chips}	<administrative transfer to H10P72/0478>
D	H01L21/67242	3	{Apparatus for monitoring, sorting or marking testing or measuring during manufacture H01L22/00,	<administrative transfer to H10P72/06>

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			marks per se H01L23/544; testing individual semiconductor devices G01R31/26}	
D	H01L21/67248	4	{Temperature monitoring}	<administrative transfer to H10P72/0602>
D	H01L21/67253	4	{Process monitoring, e.g. flow or thickness monitoring}	<administrative transfer to H10P72/0604>
D	H01L21/67259	4	{Position monitoring, e.g. misposition detection or presence detection}	<administrative transfer to H10P72/0606>
D	H01L21/67265	5	{of substrates stored in a container, a magazine, a carrier, a boat or the like}	<administrative transfer to H10P72/0608>
D	H01L21/67271	4	{Sorting devices}	<administrative transfer to H10P72/0611>
D	H01L21/67276	4	{Production flow monitoring, e.g. for increasing throughput program-control systems per se G05B19/00, e.g. total factory control G05B19/418}	<administrative transfer to H10P72/0612>
D	H01L21/67282	4	{Marking devices}	<administrative transfer to H10P72/0614>
D	H01L21/67288	4	{Monitoring of warpage, curvature, damage, defects or the like}	<administrative transfer to H10P72/0616>
D	H01L21/67294	4	{using identification means, e.g. labels on substrates or labels on containers}	<administrative transfer to H10P72/0618>
D	H01L21/673	2	using specially adapted carriers {or holders; Fixing the workpieces on such carriers or holders (holders for supporting a complete device in operation H01L23/32)}	<administrative transfer to H10P72/10>
D	H01L21/67303	3	{Vertical boat type carrier whereby the substrates are horizontally supported, e.g. comprising rod-shaped elements}	<administrative transfer to H10P72/12 >
D	H01L21/67306	4	{characterized by a material, a roughness, a coating or the like}	<administrative transfer to H10P72/123>
D	H01L21/67309	4	{characterized by the substrate support}	<administrative transfer to H10P72/127>
D	H01L21/67313	3	{Horizontal boat type carrier whereby the substrates are vertically supported, e.g. comprising rod-shaped elements}	<administrative transfer to H10P72/13>
D	H01L21/67316	4	{characterized by a material, a roughness, a coating or the like}	<administrative transfer to H10P72/135>
D	H01L21/6732	3	{Vertical carrier comprising wall type elements whereby the substrates are horizontally	<administrative transfer to H10P72/14>

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			supported, e.g. comprising sidewalls}	
D	H01L21/67323	4	{characterized by a material, a roughness, a coating or the like}	<administrative transfer to H10P72/145>
D	H01L21/67326	3	{Horizontal carrier comprising wall type elements whereby the substrates are vertically supported, e.g. comprising sidewalls}	<administrative transfer to H10P72/15>
D	H01L21/6733	4	{characterized by a material, a roughness, a coating or the like}	<administrative transfer to H10P72/155>
D	H01L21/67333	3	{Trays for chips (magazine for components H05K13/0084)}	<administrative transfer to H10P72/16>
D	H01L21/67336	4	{characterized by a material, a roughness, a coating or the like}	<administrative transfer to H10P72/165>
D	H01L21/6734	3	{specially adapted for supporting large square shaped substrates (containers and packaging elements for glass sheets B65D85/48, transporting of glass products during their manufacture C03B35/00)}	<administrative transfer to H10P72/17>
D	H01L21/67343	4	{characterized by a material, a roughness, a coating or the like}	<administrative transfer to H10P72/175>
D	H01L21/67346	3	{characterized by being specially adapted for supporting a single substrate or by comprising a stack of such individual supports}	<administrative transfer to H10P72/18>
D	H01L21/6735	3	{Closed carriers}	<administrative transfer to H10P72/19>
D	H01L21/67353	4	{specially adapted for a single substrate}	<administrative transfer to H10P72/1902>
D	H01L21/67356	4	{specially adapted for containing chips, dies or ICs}	<administrative transfer to H10P72/1904>
D	H01L21/67359	4	{specially adapted for containing masks, reticles or pellicles}	<administrative transfer to H10P72/1906>
D	H01L21/67363	4	{specially adapted for containing substrates other than wafers (H01L21/67356, H01L21/67359 take precedence)}	<administrative transfer to H10P72/1908>
D	H01L21/67366	4	{characterised by materials, roughness, coatings or the like (materials relating to an injection moulding process B29C45/00; chemical composition of materials C08L51/00)}	<administrative transfer to H10P72/1911>
D	H01L21/67369	4	{characterised by shock absorbing elements, e.g. retainers or cushions}	<administrative transfer to H10P72/1912>
D	H01L21/67373	4	{characterised by locking systems}	<administrative transfer to H10P72/1914>

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D	H01L21/67376	4	{characterised by sealing arrangements}	<administrative transfer to H10P 72/1916>
D	H01L21/67379	4	{characterised by coupling elements, kinematic members, handles or elements to be externally gripped}	<administrative transfer to H10P 72/1918>
D	H01L21/67383	4	{characterised by substrate supports}	<administrative transfer to H10P 72/1921>
D	H01L21/67386	4	{characterised by the construction of the closed carrier}	<administrative transfer to H10P 72/1922>
D	H01L21/67389	4	{characterised by atmosphere control}	<administrative transfer to H10P 72/1924>
D	H01L21/67393	5	{characterised by the presence of atmosphere modifying elements inside or attached to the closed carrier}	<administrative transfer to H10P 72/1926>
D	H01L21/67396	4	{characterised by the presence of antistatic elements}	<administrative transfer to H10P 72/1928>
D	H01L21/677	2	for conveying, e.g. between different workstations	<administrative transfer to H10P 72/30>
D	H01L21/67703	3	{between different workstations}	<administrative transfer to H10P 72/32>
D	H01L21/67706	4	{Mechanical details, e.g. roller, belt (H01L21/67709 takes precedence)}	<administrative transfer to H10P 72/3202>
D	H01L21/67709	4	{using magnetic elements}	<administrative transfer to H10P 72/3204>
D	H01L21/67712	4	{the substrate being handled substantially vertically}	<administrative transfer to H10P 72/3206>
D	H01L21/67715	4	{Changing the direction of the conveying path}	<administrative transfer to H10P 72/3208>
D	H01L21/67718	4	{Changing orientation of the substrate, e.g. from a horizontal position to a vertical position}	<administrative transfer to H10P 72/3211>
D	H01L21/67721	4	{the substrates to be conveyed not being semiconductor wafers or large planar substrates, e.g. chips, lead frames (H01L21/6773 takes precedence)}	<administrative transfer to H10P 72/3212>
D	H01L21/67724	4	{by means of a cart or a vehicle}	<administrative transfer to H10P 72/3214>
D	H01L21/67727	4	{using a general scheme of a conveying path within a factory}	<administrative transfer to H10P 72/3216>
D	H01L21/6773	4	{Conveying cassettes, containers or carriers}	<administrative transfer to H10P 72/3218>
D	H01L21/67733	4	{Overhead conveying}	<administrative transfer to H10P 72/3221>
D	H01L21/67736	4	{Loading to or unloading from a conveyor}	<administrative transfer to H10P 72/3222>

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D	H01L21/67739	3	{into and out of processing chamber}	<administrative transfer to H10P 72/33>
D	H01L21/67742	4	{Mechanical parts of transfer devices (robots in general in B25J)}	<administrative transfer to H10P 72/3302>
D	H01L21/67745	4	{characterized by movements or sequence of movements of transfer devices}	<administrative transfer to H10P 72/3304>
D	H01L21/67748	4	{horizontal transfer of a single workpiece}	<administrative transfer to H10P 72/3306>
D	H01L21/67751	4	{vertical transfer of a single workpiece}	<administrative transfer to H10P 72/3308>
D	H01L21/67754	4	{horizontal transfer of a batch of workpieces}	<administrative transfer to H10P 72/3311>
D	H01L21/67757	4	{vertical transfer of a batch of workpieces}	<administrative transfer to H10P 72/3312>
D	H01L21/6776	4	{Continuous loading and unloading into and out of a processing chamber, e.g. transporting belts within processing chambers}	<administrative transfer to H10P 72/3314>
D	H01L21/67763	3	{the wafers being stored in a carrier, involving loading and unloading (H01L21/6779 takes precedence)}	<administrative transfer to H10P 72/34>
D	H01L21/67766	4	{Mechanical parts of transfer devices (robots in general in B25J)}	<administrative transfer to H10P 72/3402>
D	H01L21/67769	4	{Storage means}	<administrative transfer to H10P 72/3404>
D	H01L21/67772	4	{involving removal of lid, door, cover}	<administrative transfer to H10P 72/3406>
D	H01L21/67775	4	{Docking arrangements}	<administrative transfer to H10P 72/3408>
D	H01L21/67778	4	{involving loading and unloading of wafers}	<administrative transfer to H10P 72/3411>
D	H01L21/67781	5	{Batch transfer of wafers}	<administrative transfer to H10P 72/3412>
D	H01L21/67784	3	{using air tracks}	<administrative transfer to H10P 72/36>
D	H01L21/67787	4	{with angular orientation of the workpieces}	<administrative transfer to H10P 72/3602>
D	H01L21/6779	4	{the workpieces being stored in a carrier, involving loading and unloading}	<administrative transfer to H10P 72/3604>
D	H01L21/67793	3	{with orientating and positioning by means of a vibratory bowl or track}	<administrative transfer to H10P 72/37>
D	H01L21/67796	3	{with angular orientation of workpieces (H01L21/67787 and H01L21/67793 take precedence)}	<administrative transfer to H10P 72/38>
D	H01L21/68	2	for positioning, orientation or alignment	<administrative transfer to H10P 72/50>

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D	H01L21/681	3	{using optical controlling means}	<administrative transfer to H10P72/53>
D	H01L21/682	3	{Mask-wafer alignment (in general G03F7/70, G03F9/70)}	<administrative transfer to H10P72/57>
D	H01L21/683	2	for supporting or gripping (for conveying H01L21/677, for positioning, orientation or alignment H01L21/68)	<administrative transfer to H10P72/70>
D	H01L21/6831	3	{using electrostatic chucks}	<administrative transfer to H10P72/72>
D	H01L21/6833	4	{Details of electrostatic chucks}	<administrative transfer to H10P72/722>
D	H01L21/6835	3	{using temporarily an auxiliary support}	<administrative transfer to H10P72/74>
D	H01L21/6836	4	{Wafer tapes, e.g. grinding or dicing support tapes (adhesive tapes in general C09J7/20)}	<administrative transfer to H10P72/7402>
D	H01L21/6838	3	{with gripping and holding devices using a vacuum; Bernoulli devices}	<administrative transfer to H10P72/78>
D	H01L21/687	3	using mechanical means, e.g. chucks, clamps or pinches {(using electrostatic chucks H01L21/6831)}	<administrative transfer to H10P72/76 >
D	H01L21/68707	4	{the wafers being placed on a robot blade, or gripped by a gripper for conveyance}	<administrative transfer to H10P72/7602>
D	H01L21/68714	4	{the wafers being placed on a susceptor, stage or support}	<administrative transfer to H10P72/7604>
D	H01L21/68721	5	{characterised by edge clamping, e.g. clamping ring}	<administrative transfer to H10P72/7606>
D	H01L21/68728	5	{characterised by a plurality of separate clamping members, e.g. clamping fingers}	<administrative transfer to H10P72/7608>
D	H01L21/68735	5	{characterised by edge profile or support profile}	<administrative transfer to H10P72/7611>
D	H01L21/68742	5	{characterised by a lifting arrangement, e.g. lift pins}	<administrative transfer to H10P72/7612>
D	H01L21/6875	5	{characterised by a plurality of individual support members, e.g. support posts or protrusions}	<administrative transfer to H10P72/7614>
D	H01L21/68757	5	{characterised by a coating or a hardness or a material}	<administrative transfer to H10P72/7616>
D	H01L21/68764	5	{characterised by a movable susceptor, stage or support, others than those only rotating on their own vertical axis, e.g. susceptors on a rotating carroussel}	<administrative transfer to H10P72/7618>
D	H01L21/68771	5	{characterised by supporting more than one semiconductor substrate}	<administrative transfer to H10P72/7621>

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D	H01L21/68778	5	{characterised by supporting substrates others than wafers, e.g. chips}	<administrative transfer to H10P 72/7622>
D	H01L21/68785	5	{characterised by the mechanical construction of the susceptor, stage or support}	<administrative transfer to H10P 72/7624>
D	H01L21/68792	5	{characterised by the construction of the shaft}	<administrative transfer to H10P 72/7626>
D	H01L21/70	1	Manufacture or treatment of devices consisting of a plurality of solid state components formed in or on a common substrate or of parts thereof; Manufacture of integrated circuit devices or of parts thereof ({multistep manufacturing processes of assemblies consisting of a plurality of individual semiconductor or other solid state devices H01L25/00; } manufacture of assemblies consisting of preformed electrical components H05K3/00, H05K13/00)	<administrative transfer to H10D 84/01>
D	H01L21/702	2	{of thick-or thin-film circuits or parts thereof}	<administrative transfer to H10D 84/01>
D	H01L21/705	3	{of thick-film circuits or parts thereof}	<administrative transfer to H10D 84/01>
D	H01L21/707	3	{of thin-film circuits or parts thereof}	<administrative transfer to H10D 84/01>
D	H01L21/7624	5	{using semiconductor on insulator [SOI] technology}	<administrative transfer to H10P 90/1906 and H10W 10/181 simultaneously>
D	H01L21/76243	6	{using silicon implanted buried insulating layers, e.g. oxide layers, i.e. SIMOX techniques}	<administrative transfer to H10P 90/1908 and H10W 10/181 simultaneously >
D	H01L21/76245	6	{using full isolation by porous oxide silicon, i.e. FIPOS techniques}	<administrative transfer to H10P 90/191 and H10W 10/181 simultaneously >
D	H01L21/76248	6	{using lateral overgrowth techniques, i.e. ELO techniques}	<administrative transfer to H10P 90/1912 and H10W 10/181 simultaneously >
D	H01L21/76251	6	{using bonding techniques}	<administrative transfer to H10P 90/1914 and H10W 10/181 simultaneously >
D	H01L21/76254	7	{with separation/delamination along an ion implanted layer, e.g. Smart-cut, Unibond}	<administrative transfer to H10P 90/1916 and H10W 10/181 simultaneously >
D	H01L21/76256	7	{using silicon etch back techniques, e.g. BESOI, ELTRAN}	<administrative transfer to H10P 90/1922 and H10W 10/181 simultaneously >

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D	H01L21/76259	7	{with separation/delamination along a porous layer}	<administrative transfer to H10P 90/1924 and H10W 10/181 simultaneously >
D	H01L21/76262	6	{using selective deposition of single crystal silicon, i.e. SEG techniques}	<administrative transfer to H10P 90/1912 and H10W 10/181 simultaneously >
D	H01L21/77	2	Manufacture or treatment of devices consisting of a plurality of solid state components or integrated circuits formed in, or on, a common substrate (manufacture or treatment of electronic memory devices H10B)	<administrative transfer to H10D 84/01>
D	H01L21/78	3	with subsequent division of the substrate into plural individual devices (cutting to change the surface-physical characteristics or shape of semiconductor bodies H01L21/304)	<administrative transfer to H10P 54/00>
D	H01L21/7806	4	{involving the separation of the active layers from a substrate}	<administrative transfer to H10P 95/11>
D	H01L21/7813	5	{leaving a reusable substrate, e.g. epitaxial lift off}	<administrative transfer to H10P 95/112>
D	H01L 22/00	0	{Testing or measuring during manufacture or treatment; Reliability measurements, i.e. testing of parts without further processing to modify the parts as such; Structural arrangements therefor}	<administrative transfer to H10P 74/00>
D	H01L22/10	1	{Measuring as part of the manufacturing process (burn-in G01R31/2855)}	<administrative transfer to H10P 74/20>
D	H01L22/12	2	{for structural parameters, e.g. thickness, line width, refractive index, temperature, warp, bond strength, defects, optical inspection, electrical measurement of structural dimensions, metallurgic measurement of diffusions (electrical measurement of diffusions H01L22/14)}	<administrative transfer to H10P 74/203>
D	H01L22/14	2	{for electrical parameters, e.g. resistance, deep-levels, CV, diffusions by electrical means}	<administrative transfer to H10P 74/207>
D	H01L22/20	1	{Sequence of activities consisting of a plurality of measurements, corrections, marking or sorting steps}	<administrative transfer to H10P 74/23>

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D	H01L22/22	2	{Connection or disconnection of sub-entities or redundant parts of a device in response to a measurement (testing and repair of stores after manufacture including at wafer scale G11C29/00; fuses per se H01L23/525)}	<administrative transfer to H10P74/232>
D	H01L22/24	2	{Optical enhancement of defects or not directly visible states, e.g. selective electrolytic deposition, bubbles in liquids, light emission, colour change (voltage contrast G01R31/311)}	<administrative transfer to H10P74/235>
D	H01L22/26	2	{Acting in response to an ongoing measurement without interruption of processing, e.g. endpoint detection, in-situ thickness measurement (endpoint detection arrangements in CMP apparatus B24B37/013, in discharge apparatus H01J37/32)}	<administrative transfer to H10P74/238>
D	H01L22/30	1	{Structural arrangements specially adapted for testing or measuring during manufacture or treatment, or specially adapted for reliability measurements}	<administrative transfer to H10P74/27>
D	H01L22/32	2	{Additional lead-in metallisation on a device or substrate, e.g. additional pads or pad portions, lines in the scribe line, sacrificed conductors (arrangements for conducting electric current to or from the solid state body in operation H01L23/48)}	<administrative transfer to H10P74/273>
D	H01L22/34	2	{Circuits for electrically characterising or monitoring manufacturing processes, e.g. whole test die, wafers filled with test structures, on-board-devices incorporated on each die, process control monitors or pad structures thereof, devices in scribe line (switching, multiplexing, gating devices G01R19/25; process control with lithography, e.g. dose control, G03F7/20; structures for alignment control by optical means G03F7/70633)}	<administrative transfer to H10P74/277>
D	H01L 2221/00	0	Processes or apparatus adapted for the manufacture or treatment of semiconductor or solid state	<No transfer>

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			devices or of parts thereof covered by H01L 21/00	
D	H01L 2221/67	1	Apparatus for handling semiconductor or electric solid state devices during manufacture or treatment thereof; Apparatus for handling wafers during manufacture or treatment of semiconductor or electric solid state devices or components; Apparatus not specifically provided for elsewhere	<administrative transfer to H10P 72/00>
D	H01L 2221/683	2	for supporting or gripping	<administrative transfer to H10P 72/70>
D	H01L 2221/68304	3	using temporarily an auxiliary support	<administrative transfer to H10P 72/74>
D	H01L 2221/68309	4	Auxiliary support including alignment aids	<administrative transfer to H10P 72/7408>
D	H01L 2221/68313	4	Auxiliary support including a cavity for storing a finished device, e.g. IC package, or a partly finished device, e.g. die, during manufacturing or mounting	<administrative transfer to H10P 72/741>
D	H01L 2221/68318	4	Auxiliary support including means facilitating the separation of a device or wafer from the auxiliary support	<administrative transfer to H10P 72/7412>
D	H01L 2221/68322	5	Auxiliary support including means facilitating the selective separation of some of a plurality of devices from the auxiliary support	<administrative transfer to H10P 72/7414>
D	H01L 2221/68327	4	used during dicing or grinding	<administrative transfer to H10P 72/7416>
D	H01L 2221/68331	5	of passive members, e.g. die mounting substrate	<administrative transfer to H10P 72/7418>
D	H01L 2221/68336	5	involving stretching of the auxiliary support post dicing	<administrative transfer to H10P 72/742>
D	H01L 2221/6834	4	used to protect an active side of a device or wafer	<administrative transfer to H10P 72/7422>
D	H01L 2221/68345	4	used as a support during the manufacture of self supporting substrates	<administrative transfer to H10P 72/7424>
D	H01L 2221/6835	4	used as a support during build up manufacturing of active devices	<administrative transfer to H10P 72/7426>
D	H01L 2221/68354	4	used to support diced chips prior to mounting	<administrative transfer to H10P 72/7428>
D	H01L 2221/68359	4	used as a support during manufacture of interconnect decals or build up layers	<administrative transfer to H10P 72/743>

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D	H01L 2221/68363	4	used in a transfer process involving transfer directly from an origin substrate to a target substrate without use of an intermediate handle substrate	<administrative transfer to H10P 72/7432>
D	H01L 2221/68368	4	used in a transfer process involving at least two transfer steps, i.e. including an intermediate handle substrate	<administrative transfer to H10P 72/7434>
D	H01L 2221/68372	4	used to support a device or wafer when forming electrical connections thereto	<administrative transfer to H10P 72/7436>
D	H01L 2221/68377	4	with parts of the auxiliary support remaining in the finished device	<administrative transfer to H10P 72/7438>
D	H01L 2221/68381	4	Details of chemical or physical process used for separating the auxiliary support from a device or wafer	<administrative transfer to H10P 72/744>
D	H01L 2221/68386	5	Separation by peeling	<administrative transfer to H10P 72/7442>
D	H01L 2221/6839	6	using peeling wedge or knife or bar	<administrative transfer to H10P 72/7444>
D	H01L 2221/68395	6	using peeling wheel	<administrative transfer to H10P 72/7446>

SUBCLASS H10D – INORGANIC ELECTRIC SEMICONDUCTOR DEVICES

<u>Type*</u>	<u>Symbol</u>	<u>Indent Level</u> <u>Number of</u> <u>dots (e.g. 0,</u> <u>1, 2)</u>	<u>Title</u> <u>“CPC only” text should</u> <u>normally be enclosed in</u> <u>{curly brackets}**</u>	<u>Transferred to#</u>
U	H10D 64/01	1	Manufacture or treatment	
Q	H10D 64/011	2	{of electrodes ohmically coupled to a semiconductor}	H10D 64/011, H10D 64/0111, H10D 64/0112, H10D 64/01125, H10D 64/0113, H10D 64/0114, H10D 64/0115, H10D 64/0116, H10D 64/0117, H10D 64/0118, H10D 64/012, H10D 64/0121, H10D 64/0122, H10D 64/0123, H10D 64/0124, H10D 64/0125, H10D 64/0126, H10D 64/013, H10D 64/01302, H10D 64/01304, H10D 64/01306, H10D 64/01308, H10D 64/0131, H10D 64/01312, H10D 64/01314, H10D 64/01316, H10D 64/01318, H10D 64/0132, H10D 64/01322, H10D 64/01324, H10D 64/01326, H10D 64/01328, H10D 64/0133, H10D 64/01332,

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<u>Type*</u>	<u>Symbol</u>	<u>Indent Level</u> <u>Number of</u> <u>dots (e.g. 0,</u> <u>1, 2)</u>	<u>Title</u> <u>“CPC only” text should</u> <u>normally be enclosed in</u> <u>{curly brackets}**</u>	<u>Transferred to#</u>
				H10D 64/01334, H10D 64/01336, H10D 64/01338, H10D 64/0134, H10D 64/01342, H10D 64/01344, H10D 64/01346, H10D 64/01348, H10D 64/0135, H10D 64/01352, H10D 64/01354, H10D 64/01356, H10D 64/01358, H10D 64/0136, H10D 64/01362, H10D 64/01364, H10D 64/01366
N	H10D 64/0111	3	{to Group IV semiconductors}	
Q	H10D 64/0112	4	{using conductive layers comprising silicides}	H10D 64/0112, H10D 64/01125
N	H10D 64/01125	5	{the silicides being formed by chemical reaction with the semiconductor after the contact hole formation}	
N	H10D 64/0113	4	{the conductive layers comprising highly doped semiconductor materials, e.g. polysilicon layers or amorphous silicon layers}	
Q	H10D 64/0114	4	{to diamond, semiconducting diamond-like carbon or graphene}	H10D 64/0114, H10D 64/0122, H10D 64/01364
Q	H10D 64/0115	4	{to silicon carbide}	H10D 64/0115, H10D 64/0123, H10D 64/01366
N	H10D 64/0116	3	{to Group III-V semiconductors}	
N	H10D 64/0117	4	{characterised by the sectional shape, e.g. T or inverted T}	
N	H10D 64/0118	5	{asymmetrical sectional shape}	
N	H10D 64/012	2	{of electrodes comprising a Schottky barrier to a semiconductor}	
N	H10D 64/0121	3	{to Group IV semiconductors}	
N	H10D 64/0122	4	{to diamond, semiconducting diamond-like carbon or graphene}	
N	H10D 64/0123	4	{to silicon carbide}	
N	H10D 64/0124	3	{to Group III-V semiconductors}	
Q	H10D 64/0125	4	{characterised by the sectional shape, e.g. T or inverted T}	H10D 64/0125, H10D 64/0117, H10D 64/0136
Q	H10D 64/0126	5	{the sectional shape being asymmetrical}	H10D 64/0126, H10D 64/0118, H10D 64/01362
N	H10D 64/013	2	{of electrodes having a conductor capacitively	

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<u>Type*</u>	<u>Symbol</u>	<u>Indent Level</u> <u>Number of</u> <u>dots (e.g. 0,</u> <u>1, 2)</u>	<u>Title</u> <u>“CPC only” text should</u> <u>normally be enclosed in</u> <u>{curly brackets}**</u>	<u>Transferred to#</u>
			coupled to a semiconductor by an insulator}	
N	H10D 64/01302	3	{the insulator being formed after the semiconductor body, the semiconductor being silicon }	
N	H10D 64/01304	4	{characterised by the conductor}	
N	H10D 64/01306	5	{the conductor comprising a layer of silicon contacting the insulator, e.g. polysilicon }	
N	H10D 64/01308	6	{the conductor further comprising a non-elemental silicon additional conductive layer, e.g. a metal silicide layer formed by the reaction of silicon with an implanted metal}	
N	H10D 64/0131	7	{the additional conductive layer comprising a silicide layer formed by the silicidation reaction between the layer of silicon with a metal layer which is not formed by metal implantation}	
N	H10D 64/01312	7	{the additional layer comprising a metal or metal silicide formed by deposition, i.e. without a silicidation reaction, e.g. sputter deposition }	
N	H10D 64/01314	5	{the conductor comprising a layer of Ge, C or of compounds of Si, Ge or C contacting the insulator}	
N	H10D 64/01316	5	{the conductor comprising a layer of elemental metal contacting the insulator, e.g. Ta, W, Mo or Al}	
N	H10D 64/01318	5	{the conductor comprising a layer of alloy material, compound material or organic material contacting the insulator, e.g. TiN (comprising a layer of alloys of Si, Ge or C H10D 64/01314)}	
N	H10D 64/0132	6	{the conductor being a metallic silicide }	

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<u>Type*</u>	<u>Symbol</u>	<u>Indent Level</u> <u>Number of</u> <u>dots (e.g. 0,</u> <u>1, 2)</u>	<u>Title</u> <u>“CPC only” text should</u> <u>normally be enclosed in</u> <u>{curly brackets}**</u>	<u>Transferred to#</u>
N	H10D 64/01322	5	{the conductor contacting the insulator having a lateral variation in doping, composition or deposition steps}	
N	H10D 64/01324	5	{characterised by the sectional shape, e.g. T or inverted-T}	
N	H10D 64/01326	5	{Aspects related to lithography, isolation or planarisation of the conductor}	
N	H10D 64/01328	6	{by defining the conductor using a sidewall spacer mask, a transformation under a mask or a plating at a sidewall}	
N	H10D 64/0133	6	{at least part of the entire electrode being a sidewall spacer, being formed by transformation under a mask or being formed by plating at a sidewall}	
N	H10D 64/01332	4	{Making the insulator}	
N	H10D 64/01334	5	{by defining the insulator using a sidewall spacer mask, a transformation under a mask or a plating at a sidewall}	
N	H10D 64/01336	5	{on single crystalline silicon, e.g. chemical oxidation using a liquid}	
N	H10D 64/01338	6	{with a treatment, e.g. annealing, after the formation of the conductor}	
N	H10D 64/0134	6	{with a treatment, e.g. annealing, after the formation of the insulator and before the formation of the conductor}	
N	H10D 64/01342	6	{by deposition, e.g. evaporation, ALD or laser deposition (H10D 64/01344 takes precedence)}	
N	H10D 64/01344	6	{in a nitrogen-containing ambient, e.g. N ₂ O oxidation}	
N	H10D 64/01346	6	{in a gaseous ambient using an oxygen or a water vapour, e.g. oxidation through a layer (H10D 64/01344 takes precedence)}	

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<u>Type*</u>	<u>Symbol</u>	<u>Indent Level</u> <u>Number of</u> <u>dots (e.g. 0,</u> <u>1, 2)</u>	<u>Title</u> <u>“CPC only” text should</u> <u>normally be enclosed in</u> <u>{curly brackets}**</u>	<u>Transferred to#</u>
N	H10D 64/01348	5	{with substrate doping, e.g. N, Ge or C implantation, before formation of the insulator}	
N	H10D 64/0135	5	{by deposition of a layer, e.g. metal, metal compound or polysilicon, followed by transformation thereof into the insulator}	
N	H10D 64/01352	5	{with sacrificial oxide}	
N	H10D 64/01354	4	{passivation or protection of the electrode, e.g. using re-oxidation}	
N	H10D 64/01356	3	{the insulator being formed after the semiconductor body, the semiconductor being a Group IV material and not being silicon, e.g. Ge, SiGe or SiGeC (H10D 64/01364, H10D 64/01366 take precedence)}	
N	H10D 64/01358	3	{the insulator being formed after the semiconductor body, the semiconductor being a Group III-V material}	
N	H10D 64/0136	4	{characterised by the sectional shape, e.g. T or inverted-T}	
N	H10D 64/01362	5	{asymmetrical sectional shape}	
N	H10D 64/01364	3	{the semiconductor being diamond, semiconducting diamond-like carbon or graphene}	
N	H10D 64/01366	3	{the semiconductor being silicon carbide}	
C	H10D 84/01	1	Manufacture or treatment	H10D 84/01, H10D 84/0102, H10D 84/0105, H10D 84/0107, H10D 84/0109, H10D 84/0112, H10D 84/0114, H10D 84/0116, H10D 84/0119, H10D 84/0121, H10D 84/0123, H10D 84/0126, H10D 84/0128, H10D 84/013, H10D 84/0133, H10D 84/0135, H10D 84/0137, H10D 84/014, H10D 84/0142, H10D 84/0144, H10D 84/0147, H10D 84/0149, H10D 84/0151, H10D 84/0153, H10D 84/0156, H10D 84/0158, H10D 84/016, H10D 84/0163,

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<u>Type*</u>	<u>Symbol</u>	<u>Indent Level</u> <u>Number of</u> <u>dots (e.g. 0,</u> <u>1, 2)</u>	<u>Title</u> <u>“CPC only” text should</u> <u>normally be enclosed in</u> <u>{curly brackets}**</u>	<u>Transferred to#</u>
				H10D 84/0165, H10D 84/0167, H10D 84/017, H10D 84/0172, H10D 84/0174, H10D 84/0177, H10D 84/0179, H10D 84/0181, H10D 84/0184, H10D 84/0186, H10D 84/0188, H10D 84/0191, H10D 84/0193, H10D 84/0195, H10D 84/0198, H10D 84/02, H10D 84/03, H10D 84/032, H10D 84/035, H10D 84/038, H10D 84/05, H10D 84/07, H10D 84/08, H10D 86/01, H10D 86/011, H10D 86/021, H10D 86/0212, H10D 86/0214, H10D 86/0221, H10D 86/0223, H10D 86/0225, H10D 86/0227, H10D 86/0229, H10D 86/0231, H10D 86/0241, H10D 86/0251, H10D 86/03, H10D 87/00, H10D 88/01, H10D 88/101, H10D 89/60, H10D 89/601, H10D 89/611, H10D 89/711, H10D 89/713, H10D 89/811, H10D 89/813, H10D 89/814, H10D 89/815, H10D 89/817, H10D 89/819, H10D 89/911, H10D 89/921, H10D 89/931
D	H10D 89/011	1	{Division of wafers or substrates to produce devices, each consisting of a single electric circuit element}	<administrative transfer to H10P 58/00>
D	H10D 89/013	2	{the wafers or substrates being semiconductor bodies}	<administrative transfer to H10P 58/00>
D	H10D 89/015	2	{the wafers or substrates being other than semiconductor bodies, e.g. insulating bodies}	<administrative transfer to H10P 58/00>

SUBCLASS H10P - GENERIC PROCESSES OR APPARATUS FOR THE MANUFACTURE OR TREATMENT OF DEVICES COVERED BY CLASS H10

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<u>Type*</u>	<u>Symbol</u>	<u>Indent Level Number of dots (e.g. 0, 1, 2)</u>	<u>Title</u> <u>“CPC only” text should normally be enclosed in {curly brackets}**</u>	<u>Transferred to#</u>
N	H10P	Subclass	GENERIC PROCESSES OR APPARATUS FOR THE MANUFACTURE OR TREATMENT OF DEVICES COVERED BY CLASS H10	
Q	H10P 10/00	0	Bonding of wafers, substrates or parts of devices	H10P 10/00, H10P 14/00, H10P 95/00
Q	H10P 10/12	1	{Bonding of semiconductor wafers or semiconductor substrates to semiconductor wafers or semiconductor substrates (preparing SOI wafers using bonding H10P 90/1914)}	H10P 10/12, H10P 10/126, H10P 10/128, H10P 10/1285, H10P 54/52, H10P 56/00, H10P 90/1914, H10P 90/1916
N	H10P 10/126	2	{characterised by the composition of the bonding layer, e.g. dopant concentration or stoichiometry}	
N	H10P 10/128	2	{by direct semiconductor to semiconductor bonding}	
N	H10P 10/1285	3	{by bonding laterally separated doped regions to each other}	
N	H10P 10/14	1	{Bonding of semiconductor wafers to insulating substrates}	
N	H10P 14/00	0	Formation of materials, e.g. in the shape of layers or pillars	
N	H10P 14/20	1	of semiconductor materials	
N	H10P 14/203	2	{using transformation of metal, e.g. oxidation or nitridation}	
N	H10P 14/22	2	using physical deposition, e.g. vacuum deposition or sputtering	
N	H10P 14/24	2	using chemical vapour deposition [CVD]	
N	H10P 14/26	2	using liquid deposition	
N	H10P 14/263	3	{using melted materials}	
N	H10P 14/265	3	{using solutions}	
N	H10P 14/27	2	{using selective deposition, e.g. simultaneous growth of monocrystalline and non-monocrystalline semiconductor materials}	
N	H10P 14/271	3	{characterised by the preparation of substrate for selective deposition}	
N	H10P 14/272	4	{using mask materials other than SiO ₂ or SiN}	
N	H10P 14/274	4	{using seed materials}	
N	H10P 14/276	3	{Lateral overgrowth}	
N	H10P 14/278	4	{Pendeoepitaxy}	
N	H10P 14/279	3	{Vapour-liquid-solid growth}	

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Type*	Symbol	Indent Level Number of dots (e.g. 0, 1, 2)	Title <u>“CPC only” text should normally be enclosed in {curly brackets}**</u>	Transferred to[#]
Q	H10P 14/29	2	{characterised by the substrates}	H10P 14/29, H10P 14/2924, H10P 14/2925, H10P 14/2926
N	H10P 14/2901	3	{Materials}	
N	H10P 14/2902	4	{being Group IVA materials}	
N	H10P 14/2903	5	{Carbon, e.g. diamond-like carbon}	
N	H10P 14/2904	5	{Silicon carbide}	
N	H10P 14/2905	5	{Silicon, silicon germanium or germanium}	
N	H10P 14/2906	5	{including tin}	
N	H10P 14/2907	4	{being Group IIIA-VA materials}	
N	H10P 14/2908	5	{Nitrides}	
N	H10P 14/2909	5	{Phosphides}	
N	H10P 14/2911	5	{Arsenides}	
N	H10P 14/2912	5	{Antimonides}	
N	H10P 14/2913	4	{being Group IIB-VIA materials}	
N	H10P 14/2914	5	{Oxides}	
N	H10P 14/2915	5	{Sulfides}	
N	H10P 14/2916	5	{Selenides}	
N	H10P 14/2917	5	{Tellurides}	
N	H10P 14/2918	4	{being semiconductor metal oxides (Group IIB-VIA materials H10P 14/2913)}	
N	H10P 14/2919	4	{being chalcogenide semiconducting materials not being oxides, e.g. ternary compounds}	
N	H10P 14/2921	4	{being crystalline insulating materials}	
N	H10P 14/2922	4	{being non-crystalline insulating materials, e.g. glass or polymers}	
N	H10P 14/2923	4	{being conductive materials, e.g. metallic silicides}	
N	H10P 14/2924	3	{Structures}	
N	H10P 14/2925	4	{Surface structures}	
N	H10P 14/2926	3	{Crystal orientations}	
N	H10P 14/32	2	{characterised by intermediate layers between substrates and deposited layers}	
N	H10P 14/3202	3	{Materials thereof}	
N	H10P 14/3204	4	{being Group IVA semiconducting materials}	
N	H10P 14/3206	5	{Carbon, e.g. diamond-like carbon}	
N	H10P 14/3208	5	{Silicon carbide}	
N	H10P 14/3211	5	{Silicon, silicon germanium or germanium}	
N	H10P 14/3212	5	{including tin}	
N	H10P 14/3214	4	{being Group IIIA-VA semiconductors}	
N	H10P 14/3216	5	{Nitrides}	

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Type*	Symbol	Indent Level Number of dots (e.g. 0, 1, 2)	Title “CPC only” text should normally be enclosed in {curly brackets}**	Transferred to#
N	H10P 14/3218	5	{Phosphides}	
N	H10P 14/3221	5	{Arsenides}	
N	H10P 14/3222	5	{Antimonides}	
N	H10P 14/3224	4	{being Group IIB-VIA semiconductors}	
N	H10P 14/3226	5	{Oxides}	
N	H10P 14/3228	5	{Sulfides}	
N	H10P 14/3231	5	{Selenides}	
N	H10P 14/3232	5	{Tellurides}	
N	H10P 14/3234	4	{being oxide semiconducting materials (Group IIB-VIA semiconductors H10P 14/3224)}	
N	H10P 14/3236	4	{being chalcogenide semiconducting materials not being oxides, e.g. ternary compounds}	
N	H10P 14/3238	4	{being insulating materials}	
N	H10P 14/3241	4	{being conductive materials}	
N	H10P 14/3242	3	{Structure}	
N	H10P 14/3244	4	{Layer structure}	
N	H10P 14/3246	5	{Monolayers}	
N	H10P 14/3248	5	{consisting of two layers}	
N	H10P 14/3251	5	{consisting of three or more layers}	
N	H10P 14/3252	6	{Alternating layers, e.g. superlattice}	
N	H10P 14/3254	5	{Graded layers}	
N	H10P 14/3256	4	{Microstructure}	
N	H10P 14/3258	3	{Crystal orientation}	
N	H10P 14/34	2	{Deposited materials, e.g. layers}	
N	H10P 14/3402	3	{characterised by the chemical composition}	
N	H10P 14/3404	4	{being Group IVA materials}	
N	H10P 14/3406	5	{Carbon, e.g. diamond-like carbon}	
N	H10P 14/3408	5	{Silicon carbide}	
N	H10P 14/3411	5	{Silicon, silicon germanium or germanium}	
N	H10P 14/3412	5	{including tin}	
N	H10P 14/3414	4	{being group IIIA-VIA materials}	
N	H10P 14/3416	5	{Nitrides}	
N	H10P 14/3418	5	{Phosphides}	
N	H10P 14/3421	5	{Arsenides}	
N	H10P 14/3422	5	{Antimonides}	
N	H10P 14/3424	4	{being Group IIB-VIA materials}	
N	H10P 14/3426	5	{Oxides}	
N	H10P 14/3428	5	{Sulfides}	
N	H10P 14/3431	5	{Selenides}	
N	H10P 14/3432	5	{Tellurides}	

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Type*	Symbol	Indent Level Number of dots (e.g. 0, 1, 2)	Title “CPC only” text should normally be enclosed in {curly brackets}**	Transferred to#
N	H10P 14/3434	4	{being oxide semiconductor materials (Group IIB-VIA semiconductor materials H10P 14/3424)}	
N	H10P 14/3436	4	{being chalcogenide semiconductor materials not being oxides, e.g. ternary compounds}	
N	H10P 14/3438	3	{Doping during depositing}	
N	H10P 14/3441	4	{Conductivity type}	
N	H10P 14/3442	5	{N-type}	
N	H10P 14/3444	5	{P-type}	
N	H10P 14/3446	5	{Transition metal elements; Rare earth elements}	
N	H10P 14/3448	4	{Delta-doping}	
N	H10P 14/3451	3	{Structure}	
N	H10P 14/3452	4	{Microstructure}	
N	H10P 14/3454	5	{Amorphous}	
N	H10P 14/3456	5	{Polycrystalline}	
N	H10P 14/3458	5	{Monocrystalline}	
N	H10P 14/3461	5	{Nanoparticles}	
N	H10P 14/3462	5	{Nanowires}	
N	H10P 14/3464	5	{Nanotubes}	
N	H10P 14/3466	3	{Crystal orientation}	
N	H10P 14/36	2	{characterised by treatments done before the formation of the materials}	
N	H10P 14/3602	3	{In-situ cleaning}	
N	H10P 14/38	2	{characterised by treatments done after the formation of the materials}	
N	H10P 14/3802	3	{Crystallisation or recrystallisation of non-monocrystalline semiconductor materials, e.g. regrowth}	
N	H10P 14/3804	4	{using crystallisation-inhibiting elements}	
N	H10P 14/3806	4	{using crystallisation-enhancing elements}	
N	H10P 14/3808	4	{using laser beams}	
N	H10P 14/381	5	{Beam shaping, e.g. using a mask}	
N	H10P 14/3812	6	{Shape of mask}	
N	H10P 14/3814	5	{Continuous wave laser beam}	
N	H10P 14/3816	5	{Pulsed laser beam}	
N	H10P 14/3818	4	{using particle beams}	
N	H10P 14/382	4	{Scanning of a beam}	
N	H10P 14/3822	3	{Controlling the interface between substrate and epitaxial layer, e.g. by ion implantation followed by annealing}	

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N	H10P 14/3824	3	{Intermixing, interdiffusion or disordering of III-V heterostructures, e.g. IILD}	
N	H10P 14/40	1	of conductive or resistive materials	
N	H10P 14/412	2	{Deposition of metallic or metal-silicide materials}	
N	H10P 14/414	3	{of metal-silicide materials}	
N	H10P 14/416	2	{of highly doped semiconductor materials, e.g. polysilicon layers or amorphous silicon layers}	
N	H10P 14/418	2	{the conductive layers comprising transition metals}	
Q	H10P 14/42	2	using a gas or vapour	H10P 14/42, H10P 14/43
N	H10P 14/43	3	Chemical deposition, e.g. chemical vapour deposition [CVD]	
N	H10P 14/432	4	{using selective deposition}	
Q	H10P 14/44	3	Physical vapour deposition [PVD]	H10P 14/44, H10P 14/45
N	H10P 14/45	4	Sputtering	
Q	H10P 14/46	2	using a liquid	H10P 14/46, H10P 14/48
Q	H10P 14/47	3	Electrolytic deposition, i.e. electroplating; Electroless plating	H10P 14/46, H10P 14/47, H10P 14/48, H10D 64/011, H10D 64/012, H10D 64/013,
N	H10P 14/48	4	{Electroless plating}	
Q	H10P 14/60	1	of insulating materials	H10P 14/60, H10P 95/70, H10P 95/80
N	H10P 14/61	2	using masks	
N	H10P 14/63	2	{characterised by the formation processes}	
N	H10P 14/6302	3	{Non-deposition formation processes}	
N	H10P 14/6304	4	{Formation by oxidation, e.g. oxidation of the substrate}	
N	H10P 14/6306	5	{of the semiconductor materials}	
Q	H10P 14/6308	6	{of Group IV semiconductors}	H10P 14/6308, H10P 14/6309, H10P 14/6318, H10P 14/6319, H10P 14/6322, H10P 14/6324
N	H10P 14/6309	7	{of silicon in uncombined form, i.e. pure silicon}	
N	H10P 14/6312	6	{of Group III-V semiconductors}	
N	H10P 14/6314	5	{of a metallic layer}	
Q	H10P 14/6316	4	{Formation by nitridation, e.g. nitridation of the substrate}	H10P 14/6316, H10P 14/6318, H10P 14/6319,

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				H10P 14/6322, H10P 14/6324
N	H10P 14/6318	4	{Formation by simultaneous oxidation and nitridation}	
N	H10P 14/6319	4	{Formation by plasma treatments, e.g. plasma oxidation of the substrate}	
N	H10P 14/6322	4	{Formation by thermal treatments (formation by plasma treatment H10P 14/6319)}	
N	H10P 14/6324	4	{Formation by anodic treatments, e.g. anodic oxidation}	
N	H10P 14/6326	3	{Deposition processes}	
N	H10P 14/6328	4	{Deposition from the gas or vapour phase}	
N	H10P 14/6329	5	{using physical ablation of a target, e.g. physical vapour deposition or pulsed laser deposition}	
N	H10P 14/6332	5	{using thermal evaporation (formation of epitaxial layers by a deposition process H10P 14/6349)}	
N	H10P 14/6334	5	{using decomposition or reaction of gaseous or vapour phase compounds, i.e. chemical vapour deposition (deposition by physical ablation of a target H10P 14/6329)}	
N	H10P 14/6336	6	{in the presence of a plasma [PECVD]}	
N	H10P 14/6338	6	{the reactions being activated by other means than plasma or thermal, e.g. photo-CVD}	
N	H10P 14/6339	6	{deposition by cyclic CVD, e.g. ALD, ALE or pulsed CVD}	
N	H10P 14/6342	4	{Liquid deposition, e.g. spin-coating, sol-gel techniques or spray coating}	
N	H10P 14/6344	5	{using Langmuir-Blodgett techniques}	
N	H10P 14/6346	5	{using printing, e.g. ink-jet printing}	
N	H10P 14/6348	5	{Liquid ALD}	
N	H10P 14/6349	4	{Deposition of epitaxial materials}	
N	H10P 14/65	2	{characterised by treatments performed before or after the formation of the materials}	
N	H10P 14/6502	3	{of treatments performed before formation of the materials}	
N	H10P 14/6504	4	{In-situ cleaning}	
N	H10P 14/6506	4	{Formation of intermediate materials}	
N	H10P 14/6508	4	{by exposure to a liquid}	

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N	H10P 14/6509	4	{by exposure to electromagnetic radiation, e.g. UV light}	
N	H10P 14/6512	4	{by exposure to a gas or vapour}	
N	H10P 14/6514	5	{by exposure to a plasma }	
N	H10P 14/6516	3	{of treatments performed after formation of the materials}	
N	H10P 14/6518	4	{by introduction of substances into an already-existing insulating layer}	
N	H10P 14/6519	5	{the substance being oxygen }	
N	H10P 14/6522	6	{introduced into a nitride material, e.g. changing SiN to SiON}	
N	H10P 14/6524	5	{the substance being nitrogen }	
N	H10P 14/6526	6	{introduced into an oxide material, e.g. changing SiO to SiON}	
N	H10P 14/6528	4	{In-situ cleaning after layer formation, e.g. removing process residues}	
N	H10P 14/6529	4	{by exposure to a gas or vapour}	
N	H10P 14/6532	5	{by exposure to a plasma }	
N	H10P 14/6534	4	{by exposure to a liquid }	
N	H10P 14/6536	4	{by exposure to radiation, e.g. visible light }	
N	H10P 14/6538	5	{by exposure to UV light }	
N	H10P 14/6539	5	{by exposure to corpuscular radiation, e.g. exposure to electrons, alpha - particles, protons or ions}	
N	H10P 14/6542	5	{by using coherent radiation, e.g. using a laser}	
N	H10P 14/6544	4	{to change the morphology of the insulating materials, e.g. transformation of an amorphous layer into a crystalline layer}	
N	H10P 14/6546	4	{to change the surface groups of the insulating materials}	
N	H10P 14/6548	4	{by forming intermediate materials, e.g. capping layers or diffusion barriers}	
N	H10P 14/66	2	{characterised by the type of materials}	
N	H10P 14/662	3	{Laminate layers, e.g. stacks of alternating high-k metal oxides (adhesion layers or buffer layers H10P14/6508, H10P14/6548)}	
N	H10P 14/665	3	{Porous materials}	
N	H10P 14/668	3	{the materials being characterised by the deposition precursor materials}	
N	H10P 14/6681	4	{the precursor containing a compound comprising Si}	

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N	H10P 14/6682	5	{the compound being a silane, e.g. disilane, methylsilane or chlorosilane}	
N	H10P 14/6684	5	{the compound comprising silicon and oxygen}	
N	H10P 14/6686	6	{the compound being a molecule comprising at least one silicon-oxygen bond and the compound having hydrogen or an organic group attached to the silicon or oxygen, e.g. a siloxane}	
N	H10P 14/6687	5	{the compound comprising silicon and nitrogen}	
N	H10P 14/6689	6	{the compound being a silazane}	
Q	H10P 14/68	2	Organic materials, e.g. photoresists	H10P 14/68, H10P 14/69
Q	H10P 14/683	3	{carbon-based polymeric organic materials, e.g. polyimides, poly cyclobutene or PVC}	H10P 14/683, H10P 14/69
Q	H10P 14/687	4	{the materials being fluorocarbon compounds, e.g. (CH _x F _y) _n or polytetrafluoroethylene}	H10P 14/687, H10P 14/69
Q	H10P 14/69	2	Inorganic materials	H10P 14/69, H10P 14/694
N	H10P 14/6902	3	{composed of carbon, e.g. alpha-C, diamond or hydrogen doped carbon}	
Q	H10P 14/6903	3	{containing silicon}	H10P 14/6903, H10P 14/6921, H10P 14/6943
N	H10P 14/6905	4	{being a silicon carbide or silicon carbonitride and not containing oxygen, e.g. SiC or SiC:H}	
N	H10P 14/6906	3	{containing at least one metal element and not containing oxygen, e.g. metal carbides or metal carbonitrides (metal nitrides H10P 14/6947)}	
N	H10P 14/6907	4	{characterised by the metal}	
N	H10P 14/6908	5	{the material containing aluminium}	
N	H10P 14/6909	5	{the material containing hafnium}	
N	H10P 14/691	5	{the material containing tantalum}	
N	H10P 14/6911	5	{the material containing titanium}	
N	H10P 14/6912	5	{the material containing zirconium}	
N	H10P 14/6913	5	{the material containing at least one rare earth metal element}	
N	H10P 14/6914	5	{the material containing two or more metal elements}	
N	H10P 14/692	3	composed of oxides, glassy oxides or oxide-based glasses	
N	H10P 14/6921	4	{containing silicon}	

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N	H10P 14/69215	5	{the material being a silicon oxide, e.g. SiO ₂ }	
N	H10P 14/6922	5	{the material containing Si, O and at least one of H, N, C, F or other non-metal elements, e.g. SiOC, SiOC:H or SiONC}	
N	H10P 14/6923	6	{the material being boron or phosphorus doped silicon oxides, e.g. BPSG, BSG or PSG}	
N	H10P 14/6924	6	{the material being halogen doped silicon oxides, e.g. FSG}	
N	H10P 14/6925	6	{the material comprising hydrogen silsesquioxane, e.g. HSQ}	
N	H10P 14/6926	6	{the material comprising alkyl silsesquioxane, e.g. MSQ}	
N	H10P 14/6927	6	{the material being a silicon oxynitride, e.g. SiON or SiON:H}	
N	H10P 14/6928	5	{the material containing silicon and at least one metal element, e.g. metal silicate based insulators or metal silicon oxynitrides}	
N	H10P 14/6929	6	{the material containing aluminium, e.g. AlSiO _x }	
N	H10P 14/693	6	{the material containing hafnium, e.g. HfSiO _x or HfSiON}	
N	H10P 14/6931	6	{the material containing tantalum, e.g. TaSiO _x }	
N	H10P 14/6932	6	{the material containing titanium, e.g. TiSiO _x }	
N	H10P 14/6933	6	{the material containing at least one rare earth element, e.g. silicate of scandium or silicate of yttrium}	
N	H10P 14/6934	6	{the material containing zirconium, e.g. ZrSiO _x }	
N	H10P 14/6936	6	{the material containing two or more metal elements}	
Q	H10P 14/6938	4	{the material containing at least one metal element, e.g. metal oxides, metal oxynitrides or metal oxycarbides}	H10P 14/6938, H10P 14/6906, H10P 14/6947
Q	H10P 14/6939	5	{characterised by the metal}	H10P 14/6939, H10P 14/6907, H10P 14/69471
Q	H10P 14/69391	6	{the material containing aluminium, e.g. Al ₂ O ₃ }	H10P 14/69391, H10P 14/6908, H10P 14/69472

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Q	H10P 14/69392	6	{the material containing hafnium, e.g. HfO ₂ }	H10P 14/69392, H10P 14/6909, H10P 14/69473
Q	H10P 14/69393	6	{the material containing tantalum, e.g. Ta ₂ O ₅ }	H10P 14/69393, H10P 14/691, H10P 14/69474
Q	H10P 14/69394	6	{the material containing titanium, e.g. TiO ₂ }	H10P 14/69394, H10P 14/6911, H10P 14/69475
Q	H10P 14/69395	6	{the material containing zirconium, e.g. ZrO ₂ }	H10P 14/69395, H10P 14/6912, H10P 14/69476
Q	H10P 14/69396	6	{the material containing at least one rare earth metal element, e.g. oxides of lanthanides, scandium or yttrium }	H10P 14/69396, H10P 14/6913, H10P 14/69477
Q	H10P 14/69397	6	{the material containing two or more metal elements }	H10P 14/69397, H10P 14/6914, H10P 14/69478
N	H10P 14/69398	5	{the material having a perovskite structure, e.g. Ba TiO ₃ }	
N	H10P 14/694	3	composed of nitrides	
N	H10P 14/6943	4	{containing silicon (silicon oxynitrides H10P 14/6927)}	
N	H10P 14/69433	5	{the material being a silicon nitride not containing oxygen, e.g. SixNy or SixByNz }	
N	H10P 14/6947	4	{the material containing at least one metal element and not containing oxygen, e.g. metal nitrides }	
N	H10P 14/69471	5	{characterised by the metal }	
N	H10P 14/69472	6	{the material containing aluminium }	
N	H10P 14/69473	6	{the material containing hafnium }	
N	H10P 14/69474	6	{the material containing tantalum }	
N	H10P 14/69475	6	{the material containing titanium }	
N	H10P 14/69476	6	{the material containing zirconium }	
N	H10P 14/69477	6	{the material containing at least one rare earth metal element }	
N	H10P 14/69478	6	{the material containing two or more metal elements }	
N	H10P 30/00	0	Ion implantation into wafers, substrates or parts of devices	
Q	H10P 30/20	1	into semiconductor materials, e.g. for doping	H10P 30/20, H10P 30/00
Q	H10P 30/202	2	{characterised by the semiconductor materials }	H10P 30/202, H10P 30/208, H10P 30/21, H10P 30/212, H10P 30/22, H10P 30/221,

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				H10P 30/222, H10P 30/28
N	H10P 30/204	3	{into Group IV semiconductors}	
Q	H10P 30/2042	4	{into crystalline silicon carbide}	H10P 30/2042, H10P 30/21, H10P 30/218, H10P 30/28
Q	H10P 30/2044	4	{into semiconducting carbon, e.g. diamond or semiconducting diamond-like carbon}	H10P 30/2044, H10P 30/208, H10P 30/21, H10P 30/212, H10P 30/22, H10P 30/221, H10P 30/222, H10P 30/28
N	H10P 30/206	3	{into Group III-V semiconductors}	
N	H10P 30/208	2	{of electrically inactive species}	
N	H10P 30/209	3	{in silicon to make buried insulating layers}	
Q	H10P 30/21	2	{of electrically active species}	H10P 30/21, H10P 30/214, H10P 30/28
Q	H10P 30/212	3	{Through-implantation}	H10P 30/212, H10P 30/214, H10P 30/28
N	H10P 30/214	2	{Recoil-implantation}	
N	H10P 30/218	2	{characterised by the implantation in a compound semiconductor of both electrically active and inactive species in the same semiconductor region to be doped n-type or p-type}	
N	H10P 30/22	2	using masks	
N	H10P 30/221	3	{characterised by the angle between the ion beam and the mask}	
Q	H10P 30/222	2	{characterised by the angle between the ion beam and the crystal planes or the main crystal surface (characterised by the angle between the ion beam and the mask H10P 30/221)}	H10P 30/222, H10P 30/221
N	H10P 30/224	2	{of a cluster, e.g. using a gas cluster ion beam}	
N	H10P 30/225	2	{of a molecular ion, e.g. decaborane}	
N	H10P 30/226	2	{at a temperature lower than room temperature}	
N	H10P 30/28	2	characterised by an annealing step, e.g. for activation of dopants	
Q	H10P 30/40	1	into insulating materials	H10P 30/40, H10P 32/20
Q	H10P 32/00	0	Diffusion of dopants within, into or out of wafers, substrates or parts of devices	H10P 32/00, H10P 32/10

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			(during formation of materials H10P 14/00)	
N	H10P 32/10	1	Diffusion of dopants within, into or out of semiconductor bodies or layers	
N	H10P 32/12	2	between a solid phase and a gaseous phase	
N	H10P 32/1204	3	{from a plasma phase}	
N	H10P 32/14	2	within a single semiconductor body or layer in a solid phase; between different semiconductor bodies or layers, both in a solid phase	
N	H10P 32/1404	3	{using predeposition followed by drive-in of impurities into the semiconductor surface, e.g. predeposition from a gaseous phase}	
N	H10P 32/1406	4	{by ion implantation}	
N	H10P 32/1408	3	{from or through or into an external applied layer, e.g. photoresist or nitride layers}	
N	H10P 32/141	4	{the applied layer comprising oxides only}	
N	H10P 32/1412	5	{through the applied layer}	
N	H10P 32/1414	4	{the applied layer being silicon, silicide or SIPOS, e.g. polysilicon or porous silicon}	
N	H10P 32/15	2	{from the substrate during epitaxy, e.g. autodoping; Preventing or using autodoping}	
N	H10P 32/16	2	between a solid phase and a liquid phase	
N	H10P 32/17	2	{characterised by the semiconductor material}	
N	H10P 32/171	3	{being group IV material}	
N	H10P 32/172	4	{being crystalline silicon carbide}	
N	H10P 32/173	4	{being semiconducting carbon, e.g. diamond or semiconducting diamond-like carbon}	
N	H10P 32/174	3	{being Group III-V material}	
N	H10P 32/18	2	{Diffusion lifetime killers}	
N	H10P 32/185	2	{Lithium-drift diffusion}	
N	H10P 32/19	2	{Diffusion sources}	
N	H10P 32/20	1	Diffusion for doping of insulating layers	
N	H10P 32/30	1	Diffusion for doping of conductive or resistive layers	
N	H10P 32/302	2	{Doping polycrystalline silicon or amorphous silicon layers}	

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Q	H10P 34/00	0	Irradiation with electromagnetic or particle radiation of wafers, substrates or parts of devices	H10P 34/00, H10P 34/10, H10P 34/20, H10P 34/40
N	H10P 34/10	1	{with corpuscular radiation}	
N	H10P 34/20	1	for inducing a nuclear reaction transmuting chemical elements	
N	H10P 34/40	1	with high-energy radiation	
N	H10P 34/42	2	with electromagnetic radiation, e.g. laser annealing (laser cutting H10P 54/20)	
N	H10P 34/422	3	{using incoherent radiation}	
Q	H10P 36/00	0	Gettering within semiconductor bodies	H10P 36/00, H10P 36/20, H10P 95/40
Q	H10P 36/03	1	{within silicon bodies}	H10P 36/03, H10P 95/402
N	H10P 36/07	2	{of silicon-on-insulator structures}	
N	H10P 36/20	1	Intrinsic gettering, i.e. thermally inducing defects by using oxygen present in the silicon body	
Q	H10P 50/00	0	Etching of wafers, substrates or parts of devices	H10P 50/00, H10P 50/20, H10P 50/24, H10P 50/26, H10P 50/60, H10P 50/61, H10P 50/64, H10P 50/66, H10P 52/00, H10P 95/00, H10P 95/02, H10P 95/70
Q	H10P 50/20	1	Dry etching; Plasma etching; Reactive-ion etching	H10P 50/20, H10P 50/24, H10P 50/26, H10P 50/60, H10P 50/61, H10P 50/64, H10P 50/66
N	H10P 50/24	2	of semiconductor materials	
N	H10P 50/242	3	{of Group IV materials}	
N	H10P 50/244	4	{comprising alternated and repeated etching and passivation steps}	
N	H10P 50/246	3	{of Group III-V materials}	
N	H10P 50/26	2	of conductive or resistive materials	
N	H10P 50/262	3	{by physical means only}	
N	H10P 50/263	4	{of silicon-containing layers}	
Q	H10P 50/264	3	{by chemical means}	H10P 50/264, H10P 50/663
N	H10P 50/266	4	{by vapour etching only}	
N	H10P 50/267	5	{using plasmas}	
N	H10P 50/268	6	{of silicon-containing layers}	

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Type*	Symbol	Indent Level Number of dots (e.g. 0, 1, 2)	Title “CPC only” text should normally be enclosed in {curly brackets}**	Transferred to[#]
N	H10P 50/269	5	{pre- or post-treatments, e.g. anti-corrosion processes}	
Q	H10P 50/28	2	of insulating materials	H10P 50/28, H10P 50/68
Q	H10P 50/282	3	{of inorganic materials}	H10P 50/282, H10P 50/683
Q	H10P 50/283	4	{by chemical means}	H10P 50/283, H10P 50/683
N	H10P 50/285	5	{of materials not containing Si, e.g. PZT or Al ₂ O ₃ }	
Q	H10P 50/286	3	{of organic materials}	H10P 50/286, H10P 50/68
Q	H10P 50/287	4	{by chemical means}	H10P 50/287, H10P 50/68
N	H10P 50/60	1	Wet etching	
N	H10P 50/61	2	Electrolytic etching	
N	H10P 50/613	3	{of Group IV materials}	
N	H10P 50/617	3	{of Group III-V materials}	
N	H10P 50/64	2	of semiconductor materials	
N	H10P 50/642	3	{Chemical etching}	
N	H10P 50/644	4	{Anisotropic liquid etching (H10P 50/61 takes precedence)}	
N	H10P 50/646	4	{of Group III-V materials}	
N	H10P 50/648	5	{Anisotropic liquid etching}	
N	H10P 50/66	2	of conductive or resistive materials	
N	H10P 50/663	3	{by chemical means only}	
N	H10P 50/667	4	{by liquid etching only}	
N	H10P 50/68	2	of insulating materials	
N	H10P 50/683	3	{of inorganic materials}	
N	H10P 50/69	1	{using masks for semiconductor materials}	
N	H10P 50/691	2	{for Group V materials or Group III-V materials}	
N	H10P 50/692	3	{characterised by their composition, e.g. multilayer masks or materials}	
N	H10P 50/693	3	{characterised by their size, orientation, disposition, behaviour or shape, in horizontal or vertical plane}	
N	H10P 50/694	4	{characterised by their behaviour during the process, e.g. soluble masks or redeposited masks}	
N	H10P 50/695	4	{characterised by the process involved to create the mask, e.g. lift-off masks or sidewalls or to modify the mask}	
N	H10P 50/696	4	{Process specially adapted to improve the resolution of the mask}	

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N	H10P 50/71	1	{using masks for conductive or resistive materials}	
N	H10P 50/73	1	{using masks for insulating materials}	
Q	H10P 52/00	0	Grinding, lapping or polishing of wafers, substrates or parts of devices	H10P 52/00, H10P 52/20, H10P 52/40, H10P 54/00, H10P 54/20, H10P 54/30, H10P 54/40, H10P 54/50, H10P 54/52, H10P 54/90, H10P 54/92, H10P 54/922, H10P 54/924, H10P 54/94, H10P 95/60
N	H10P 52/20	1	Electromechanical polishing [EMP]; Electrochemical mechanical polishing [ECMP]	
N	H10P 52/202	2	{of semiconductor materials}	
N	H10P 52/203	2	{of conductive or resistive materials}	
N	H10P 52/207	2	{of inorganic insulating materials}	
N	H10P 52/209	2	{of organic insulating materials}	
N	H10P 52/40	1	Chemomechanical polishing [CMP] (electrochemical mechanical polishing H10P 52/20)	
Q	H10P 52/402	2	{of semiconductor materials}	H10P 52/402, H10P 52/202
N	H10P 52/403	2	{of conductive or resistive materials}	
N	H10P 52/407	3	{of inorganic insulating materials}	
N	H10P 52/409	3	{of organic insulating materials}	
N	H10P 54/00	0	Cutting or separating of wafers, substrates or parts of devices	
N	H10P 54/20	1	by laser cutting	
N	H10P 54/30	1	by forming weakened zones for subsequent cutting or separating, e.g. by laser treatment or by ion implantation	
N	H10P 54/40	1	by sawing, e.g. using revolving or reciprocating blades	
N	H10P 54/50	1	by scoring, breaking or cleaving	
N	H10P 54/52	2	{by cleaving}	
N	H10P 54/90	1	Auxiliary processes or arrangements	
N	H10P 54/92	2	for protecting or reinforcing the surface of wafers or substrates during cutting or separating, e.g. using adhesive tapes	
N	H10P 54/922	3	{Arrangements for stress mitigation, e.g. crack stops}	
N	H10P 54/924	3	{using expanding wafer tapes}	

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N	H10P 54/94	2	After-treatments, e.g. removal of adhesive tapes or supports	
N	H10P 56/00	0	Debonding of wafers, substrates or parts of devices	
Q	H10P 58/00	0	Singulating wafers or substrates into multiple chips, i.e. dicing	H10P 58/00, H10P 58/20, H10P 58/22, H10P 54/00, H10P 54/20, H10P 54/30, H10P 54/40, H10P 54/50, H10P 54/52, H10P 54/90, H10P 54/922, H10P 54/924, H10P 54/94
N	H10P 58/20	1	{comprising two or more processes, e.g. etching and cutting}	
N	H10P 58/22	2	{characterised by the singulation processes being performed on multiple sides of the wafer or substrate}	
N	H10P 70/00	0	Cleaning of wafers, substrates or parts of devices	
N	H10P 70/10	1	{Cleaning before device manufacture, i.e. Begin-Of-Line process}	
N	H10P 70/12	2	{by dry cleaning only (H10P 70/52 takes precedence)}	
N	H10P 70/125	3	{with gaseous HF}	
N	H10P 70/15	2	{by wet cleaning only (H10P 70/52 takes precedence)}	
N	H10P 70/18	2	{by combined dry cleaning and wet cleaning (H10P 70/52 takes precedence)}	
N	H10P 70/20	1	{Cleaning during device manufacture}	
N	H10P 70/23	2	{during, before or after processing of insulating materials}	
N	H10P 70/234	3	{the processing being the formation of vias or contact holes}	
N	H10P 70/237	3	{the processing being a planarisation of insulating layers}	
N	H10P 70/27	2	{during, before or after processing of conductive materials, e.g. polysilicon or amorphous silicon layers}	
N	H10P 70/273	3	{the processing being a delineation of conductive layers, e.g. by RIE}	
N	H10P 70/277	3	{the processing being a planarisation of conductive layers}	
N	H10P 70/30	1	{Cleaning after the substrates have been singulated}	

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N	H10P 70/40	1	{Cleaning for reclaiming}	
N	H10P 70/50	1	{characterised by the part to be cleaned}	
N	H10P 70/52	2	{Cleaning of diamond}	
N	H10P 70/54	2	{Cleaning of wafer edges}	
N	H10P 70/56	2	{Cleaning of wafer backside}	
N	H10P 70/58	2	{Cleaning of porous materials}	
N	H10P 70/60	1	{Cleaning only by mechanical processes}	
N	H10P 70/70	1	{Cleaning only by lasers processes, e.g. laser ablation}	
N	H10P 70/80	1	{Cleaning only by supercritical fluids}	
N	H10P 72/00	0	Handling or holding of wafers, substrates or devices during manufacture or treatment thereof	
N	H10P 72/04	1	{Apparatus for manufacture or treatment}	
N	H10P 72/0402	2	{Apparatus for fluid treatment (H10P 72/0441, H10P 72/0448 take precedence)}	
N	H10P 72/0404	3	{for general liquid treatment, e.g. etching followed by cleaning}	
N	H10P 72/0406	3	{for cleaning followed by drying, rinsing, stripping, blasting or the like}	
N	H10P 72/0408	4	{for drying}	
N	H10P 72/0411	4	{for wet cleaning or washing}	
N	H10P 72/0412	5	{using mainly scrubbing means, e.g. brushes}	
N	H10P 72/0414	5	{using mainly spraying means, e.g. nozzles}	
N	H10P 72/0416	5	{with the semiconductor substrates being dipped in baths or vessels}	
N	H10P 72/0418	3	{for etching}	
N	H10P 72/0421	4	{for drying etching}	
N	H10P 72/0422	4	{for wet etching}	
N	H10P 72/0424	5	{using mainly spraying means, e.g. nozzles}	
N	H10P 72/0426	5	{with the semiconductor substrates being dipped in baths or vessels}	
N	H10P 72/0428	2	{Apparatus for mechanical treatment or grinding or cutting}	
N	H10P 72/0431	2	{Apparatus for thermal treatment}	
N	H10P 72/0432	3	{mainly by conduction}	
N	H10P 72/0434	3	{mainly by convection}	
N	H10P 72/0436	3	{mainly by radiation}	

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N	H10P 72/0438	2	{Apparatus for making assemblies not otherwise provided for, e.g. package constructions}	
N	H10P 72/0441	2	{Apparatus for sealing, encapsulating, glassing, decapsulating or the like}	
N	H10P 72/0442	2	{Apparatus for placing on an insulating substrate, e.g. tape}	
N	H10P 72/0444	2	{Apparatus for wiring semiconductor or solid-state device}	
N	H10P 72/0446	2	{Apparatus for mounting on conductive members, e.g. leadframes or conductors on insulating substrates}	
N	H10P 72/0448	2	{Apparatus for applying a liquid, a resin, an ink or the like}	
N	H10P 72/0451	2	{Apparatus for manufacturing or treating in a plurality of work-stations}	
N	H10P 72/0452	3	{characterised by the layout of the process chambers}	
N	H10P 72/0454	4	{surrounding a central transfer chamber}	
N	H10P 72/0456	4	{in-line arrangement}	
N	H10P 72/0458	4	{vertical arrangement}	
N	H10P 72/0461	3	{characterised by the presence of two or more transfer chambers}	
N	H10P 72/0462	3	{characterised by the construction of the processing chambers, e.g. modular processing chambers}	
N	H10P 72/0464	3	{characterised by the construction of the transfer chamber}	
N	H10P 72/0466	3	{characterised by the construction of the load-lock chamber}	
N	H10P 72/0468	3	{comprising a chamber adapted to a particular process}	
N	H10P 72/0471	4	{comprising at least one ion or electron beam chamber}	
N	H10P 72/0472	4	{comprising at least one polishing chamber}	
N	H10P 72/0474	4	{comprising at least one lithography chamber}	
N	H10P 72/0476	4	{comprising at least one plating chamber}	
N	H10P 72/0478	2	{the substrates being processed being not semiconductor wafers, e.g. leadframes or chips}	
N	H10P 72/06	1	{Apparatus for monitoring, sorting, marking, testing or measuring}	
N	H10P 72/0602	2	{Temperature monitoring}	

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N	H10P 72/0604	2	{Process monitoring, e.g. flow or thickness monitoring}	
N	H10P 72/0606	2	{Position monitoring, e.g. misposition detection or presence detection}	
N	H10P 72/0608	3	{of substrates stored in a container, a magazine, a carrier, a boat or the like}	
N	H10P 72/0611	2	{Sorting devices}	
N	H10P 72/0612	2	{Production flow monitoring, e.g. for increasing throughput}	
N	H10P 72/0614	2	{Marking devices}	
N	H10P 72/0616	2	{Monitoring of warpages, curvatures, damages, defects or the like}	
N	H10P 72/0618	2	{using identification means, e.g. labels on substrates or labels on containers}	
N	H10P 72/10	1	using carriers specially adapted therefor, e.g. front opening unified pods [FOUP]	
N	H10P 72/12	2	{Vertical boat type carrier whereby the substrates are horizontally supported, e.g. comprising rod-shaped elements}	
N	H10P 72/123	3	{characterised by a material, a roughness, a coating or the like}	
N	H10P 72/127	3	{characterised by the substrate support}	
N	H10P 72/13	2	{Horizontal boat type carrier whereby the substrates are vertically supported, e.g. comprising rod-shaped elements}	
N	H10P 72/135	3	{characterised by a material, a roughness, a coating or the like}	
N	H10P 72/14	2	{Vertical carrier comprising wall type elements whereby the substrates are horizontally supported, e.g. comprising sidewalls}	
N	H10P 72/145	3	{characterised by a material, a roughness, a coating or the like}	
N	H10P 72/15	2	{Horizontal carrier comprising wall type elements whereby the substrates are vertically supported, e.g. comprising sidewalls}	
N	H10P 72/155	3	{characterised by a material, a roughness, a coating or the like}	
N	H10P 72/16	2	{Trays for chips}	
N	H10P 72/165	3	{characterised by a material, a roughness, a coating or the like}	
N	H10P 72/17	2	{specially adapted for supporting large square shaped substrates}	
N	H10P 72/175	3	{characterised by a material, a roughness, a coating or the like}	

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N	H10P 72/18	2	{characterised by being specially adapted for supporting a single substrate or by comprising a stack of such individual supports}	
N	H10P 72/19	2	{closed carriers}	
N	H10P 72/1902	3	{specially adapted for a single substrate}	
N	H10P 72/1904	3	{specially adapted for containing chips, dies or ICs}	
N	H10P 72/1906	3	{specially adapted for containing masks, reticles or pellicles}	
N	H10P 72/1908	3	{specially adapted for containing substrates other than wafers}	
N	H10P 72/1911	3	{characterised by materials, roughness, coatings or the like}	
N	H10P 72/1912	4	{characterised by shock absorbing elements, e.g. retainers or cushions}	
N	H10P 72/1914	3	{characterised by locking systems}	
N	H10P 72/1916	3	{characterised by sealing arrangements}	
N	H10P 72/1918	3	{characterised by coupling elements, kinematic members, handles or elements to be externally gripped}	
N	H10P 72/1921	3	{characterised by substrate supports}	
N	H10P 72/1922	3	{characterised by the construction of the closed carrier}	
N	H10P 72/1924	3	{characterised by atmosphere control}	
N	H10P 72/1926	4	{characterised by the presence of atmosphere modifying elements inside or attached to the closed carrier}	
N	H10P 72/1928	5	{characterised by the presence of antistatic elements}	
N	H10P 72/30	1	for conveying, e.g. between different workstations	
N	H10P 72/32	2	{between different workstations}	
N	H10P 72/3202	3	{Mechanical details, e.g. rollers or belts}	
N	H10P 72/3204	3	{using magnetic elements}	
N	H10P 72/3206	3	{the substrate being handled substantially vertically}	
N	H10P 72/3208	3	{Changing the direction of the conveying path}	
N	H10P 72/3211	3	{Changing orientation of the substrate, e.g. from a horizontal position to a vertical position}	
N	H10P 72/3212	3	{the substrates to be conveyed not being semiconductor wafers or large planar substrates, e.g. chips or lead frames}	
N	H10P 72/3214	3	{by means of a cart or a vehicle}	

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N	H10P 72/3216	3	{using a general scheme of a conveying path within a factory}	
N	H10P 72/3218	3	{Conveying cassettes, containers or carriers}	
N	H10P 72/3221	3	{Overhead conveying}	
N	H10P 72/3222	3	{Loading to or unloading from a conveyor}	
N	H10P 72/33	2	{into and out of processing chamber}	
N	H10P 72/3302	3	{Mechanical parts of transfer devices}	
N	H10P 72/3304	3	{characterised by movements or sequence of movements of transfer devices}	
N	H10P 72/3306	3	{Horizontal transfer of a single workpiece}	
N	H10P 72/3308	3	{Vertical transfer of a single workpiece}	
N	H10P 72/3311	3	{Horizontal transfer of a batch of workpieces}	
N	H10P 72/3312	3	{Vertical transfer of a batch of workpieces}	
N	H10P 72/3314	3	{Continuous loading and unloading into and out of a processing chamber, e.g. transporting belts within processing chambers}	
N	H10P 72/34	2	{the wafers being stored in a carrier, involving loading and unloading}	
N	H10P 72/3402	3	{Mechanical parts of transfer devices}	
N	H10P 72/3404	3	{Storage means}	
N	H10P 72/3406	3	{involving removal of lid, door or cover}	
N	H10P 72/3408	3	{Docking arrangements}	
N	H10P 72/3411	3	{involving loading and unloading of wafers}	
N	H10P 72/3412	4	{Batch transfer of wafers}	
N	H10P 72/36	2	{using air tracks}	
N	H10P 72/3602	3	{with angular orientation of the workpieces}	
N	H10P 72/3604	3	{the workpieces being stored in a carrier, involving loading and unloading}	
N	H10P 72/37	2	{with orientating and positioning by means of a vibratory bowl or track}	
N	H10P 72/38	2	{with angular orientation of workpieces}	
N	H10P 72/50	1	for positioning, orientation or alignment	
N	H10P 72/53	2	{using optical controlling means}	
N	H10P 72/57	2	{Mask-wafer alignment}	
Q	H10P 72/70	1	for supporting or gripping	H10P 72/70, H10P 72/72, H10P 72/74,

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				H10P 72/7448, H10P 72/745
N	H10P 72/72	2	using electrostatic chucks	
N	H10P 72/722	3	{Details of electrostatic chucks}	
N	H10P 72/74	2	{using temporarily an auxiliary support}	
Q	H10P 72/7402	3	{Wafer tapes, e.g. grinding or dicing support tapes}	H10P 72/7402, H10P 72/7404, H10P 72/7406
N	H10P 72/7404	4	{the wafer tape being a laminate of three or more layers, e.g. including additional layers beyond a base layer and an uppermost adhesive layer}	
N	H10P 72/7406	5	{the wafer tape being a laminate of four or more layers, e.g. including two or more additional layers beyond a base layer and an uppermost adhesive layer}	
N	H10P 72/7408	3	{the auxiliary support including alignment aids}	
N	H10P 72/741	3	{the auxiliary support including a cavity for storing a finished or partly finished device during manufacturing or mounting, e.g. for an IC package or for a chip}	
N	H10P 72/7412	3	{the auxiliary support including means facilitating the separation of a device or wafer from the auxiliary support}	
N	H10P 72/7414	4	{the auxiliary support including means facilitating the selective separation of some of a plurality of devices from the auxiliary support}	
N	H10P 72/7416	3	{used during dicing or grinding}	
N	H10P 72/7418	4	{of passive members, e.g. a chip mounting substrate}	
N	H10P 72/742	4	{involving stretching of the auxiliary support post dicing}	
N	H10P 72/7422	3	{used to protect an active side of a device or wafer}	
N	H10P 72/7424	3	{used as a support during the manufacture of self-supporting substrates}	
N	H10P 72/7426	3	{used as a support during build up manufacturing of active devices}	
N	H10P 72/7428	3	{used to support diced chips prior to mounting}	
N	H10P 72/743	3	{used as a support during manufacture of interconnect decals or build up layers}	

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N	H10P 72/7432	3	{used in a transfer process involving transfer directly from an origin substrate to a target substrate without use of an intermediate handle substrate}	
N	H10P 72/7434	3	{used in a transfer process involving at least two transfer steps, i.e. including an intermediate handle substrate}	
N	H10P 72/7436	3	{used to support a device or a wafer when forming electrical connections thereto}	
N	H10P 72/7438	3	{with parts of the auxiliary support remaining in the finished device}	
N	H10P 72/744	3	{Details of chemical or physical process used for separating the auxiliary support from a device or a wafer}	
N	H10P 72/7442	4	{Separation by peeling}	
N	H10P 72/7444	5	{using a peeling wedge, a knife or a bar}	
N	H10P 72/7446	5	{using a peeling wheel}	
N	H10P 72/7448	3	{the bond interface between the auxiliary support and the wafer comprising two or more, e.g. multilayer adhesive or adhesive and release layer}	
N	H10P 72/745	4	{the bond interface between the auxiliary support and the wafer comprises three or more layers}	
N	H10P 72/76	2	using mechanical means, e.g. clamps or pinches	
N	H10P 72/7602	3	{the wafers being placed on a robot blade or gripped by a gripper for conveyance}	
N	H10P 72/7604	3	{the wafers being placed on a susceptor, stage or support}	
N	H10P 72/7606	4	{characterised by edge clamping, e.g. clamping ring}	
N	H10P 72/7608	4	{characterised by a plurality of separate clamping members, e.g. clamping fingers}	
N	H10P 72/7611	4	{characterised by edge profile or support profile}	
N	H10P 72/7612	4	{characterised by lifting arrangements, e.g. lift pins}	
N	H10P 72/7614	4	{characterised by a plurality of individual support members, e.g. support posts or protrusions}	
N	H10P 72/7616	4	{characterised by a coating, a hardness or a material}	

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N	H10P 72/7618	4	{characterised by a movable susceptor, stage or support, others than those only rotating on their own vertical axis, e.g. susceptors on a rotating carousel}	
N	H10P 72/7621	4	{characterised by supporting two or more semiconductor substrates}	
N	H10P 72/7622	4	{characterised by supporting substrates others than wafers, e.g. chips}	
N	H10P 72/7624	4	{characterised by the mechanical construction of the susceptor, stage or support}	
N	H10P 72/7626	4	{characterised by the construction of the shaft}	
N	H10P 72/78	2	using vacuum or suction, e.g. Bernoulli chucks	
N	H10P 74/00	0	Testing or measuring during manufacture or treatment of wafers, substrates or devices	
N	H10P 74/20	1	characterised by the properties tested or measured, e.g. structural or electrical properties	
N	H10P 74/203	2	{Structural properties, e.g. testing or measuring thicknesses, line widths, warpage, bond strengths or physical defects}	
N	H10P 74/207	2	{Electrical properties, e.g. testing or measuring of resistance, deep levels or capacitance-voltage characteristics}	
N	H10P 74/23	1	{characterised by multiple measurements, corrections, marking or sorting processes}	
N	H10P 74/232	2	{comprising connection or disconnection of parts of a device in response to a measurement}	
N	H10P 74/235	2	{comprising optical enhancement of defects or not-directly-visible states}	
N	H10P 74/238	2	{comprising acting in response to an ongoing measurement without interruption of processing, e.g. endpoint detection or in-situ thickness measurement}	
N	H10P 74/27	1	{Structural arrangements therefor}	
N	H10P 74/273	2	{Interconnections for measuring or testing, e.g. probe pads}	
N	H10P 74/277	2	{Circuits for electrically characterising or monitoring manufacturing processes,	

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<u>Type*</u>	<u>Symbol</u>	<u>Indent Level Number of dots (e.g. 0, 1, 2)</u>	<u>Title</u> “CPC only” text should normally be enclosed in {curly brackets}**	<u>Transferred to#</u>
			e.g. circuits in tested chips or circuits in testing wafers}	
N	H10P 76/00	0	Manufacture or treatment of masks on semiconductor bodies, e.g. by lithography or photolithography	
N	H10P 76/20	1	of masks comprising organic materials	
N	H10P 76/202	2	{for lift-off processes}	
N	H10P 76/204	2	{of organic photoresist masks}	
N	H10P 76/2041	3	{Photolithographic processes}	
N	H10P 76/2042	4	{using lasers}	
N	H10P 76/2043	4	{using an anti-reflective coating}	
N	H10P 76/2045	3	{Electron beam lithography processes}	
N	H10P 76/2047	3	{X-ray beam lithography processes}	
N	H10P 76/2049	3	{Ion beam lithography processes}	
N	H10P 76/40	1	of masks comprising inorganic materials	
N	H10P 76/403	2	{for lift-off processes}	
N	H10P 76/405	2	{characterised by their composition, e.g. multilayer masks}	
N	H10P 76/408	2	{characterised by their sizes, orientations, dispositions, behaviours or shapes}	
N	H10P 76/4083	3	{characterised by their behaviours during the lithography processes, e.g. soluble masks or redeposited masks}	
N	H10P 76/4085	3	{characterised by the processes involved to create the masks}	
N	H10P 76/4088	3	{Processes for improving the resolution of the masks}	
Q	H10P 90/00	0	Preparation of wafers not covered by a single main group of this subclass, e.g. wafer reinforcement	H10P 90/00, H10P 90/19, H10P 90/1902, H10P 90/1904, H10P 90/1906, H10P 90/21, H10P 90/212, H10P 90/22, H10P 90/24, H10P 56/00, H10P 10/12
N	H10P 90/12	1	{Preparing bulk and homogeneous wafers}	
N	H10P 90/123	2	{by grinding or lapping}	
N	H10P 90/124	2	{by processing the backside of the wafers}	
N	H10P 90/126	2	{by chemical etching}	
N	H10P 90/128	2	{by edge treatment, e.g. chamfering}	
N	H10P 90/129	2	{by polishing}	
N	H10P 90/14	2	{by setting crystal orientation}	

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<u>Type*</u>	<u>Symbol</u>	<u>Indent Level Number of dots (e.g. 0, 1, 2)</u>	<u>Title</u> <u>“CPC only” text should normally be enclosed in {curly brackets}**</u>	<u>Transferred to#</u>
N	H10P 90/15	2	{by making porous regions on the surface}	
N	H10P 90/16	2	{by reclaiming or re-processing}	
N	H10P 90/18	2	{by shaping}	
N	H10P 90/19	1	{Preparing inhomogeneous wafers}	
N	H10P 90/1902	2	{Preparing horizontally inhomogeneous wafers}	
N	H10P 90/1904	2	{Preparing vertically inhomogeneous wafers}	
N	H10P 90/1906	3	{Preparing SOI wafers}	
N	H10P 90/1908	4	{using silicon implanted buried insulating layers, e.g. oxide layers [SIMOX]}	
N	H10P 90/191	4	{using full isolation by porous oxide silicon [FIPOS]}	
N	H10P 90/1912	4	{using selective deposition, e.g. epitaxial lateral overgrowth [ELO] or selective deposition of single crystal silicon}	
Q	H10P 90/1914	4	{using bonding}	H10P 90/1914, H10P 10/126, H10P 10/128, H10P 10/1285, H10P 10/14, H10P 54/52, H10P 90/1918, H10P 90/192
Q	H10P 90/1916	5	{with separation or delamination along an ion implanted layer, e.g. Smart-cut}	H10P 90/1916, H10P 10/126, H10P 10/128, H10P 10/1285, H10P 10/14, H10P 54/52, H10P 90/1918, H10P 90/192
N	H10P 90/1918	5	{including charge trapping layers, e.g. polycrystalline materials}	
N	H10P 90/192	6	{irregularly shaped charge trapping layers}	
N	H10P 90/1922	4	{using silicon etch back techniques, e.g. BESOI or ELTRAN}	
N	H10P 90/1924	4	{with separation/delamination along a porous layer}	
N	H10P 90/ 21	1	{by transferring two-dimensional materials}	
N	H10P 90/212	2	{by transferring of graphene}	
N	H10P 90/22	1	{by transferring layers from a donor substrate to a final substrate utilising a temporary handle substrate as an intermediary}	

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<u>Type*</u>	<u>Symbol</u>	<u>Indent Level Number of dots (e.g. 0, 1, 2)</u>	<u>Title</u> “CPC only” text should normally be enclosed in {curly brackets}**	<u>Transferred to#</u>
N	H10P 90/24	1	{by concurrent transfer of multiple parts}	
Q	H10P 95/00	0	Generic processes or apparatus for manufacture or treatments not covered by the other groups of this subclass	H10P 95/00, H10P 95/02, H10P 95/04, H10P 95/06, H10P 95/062, H10P 95/064, H10P 95/066, H10P 95/08, H10P 95/11, H10P 95/112, H10P 95/40, H10P 95/402, H10P 95/405, H10P 95/408, H10P 95/50, H10P 95/60, H10P 95/70, H10P 95/80, H10P 95/90
N	H10P 95/02	1	{Planarisation of semiconductor materials}	
N	H10P 95/04	1	{Planarisation of conductive or resistive materials}	
N	H10P 95/06	1	{Planarisation of inorganic insulating materials}	
Q	H10P 95/062	2	{involving a dielectric removal step}	H10P 52/407, H10P 52/207, H10P 95/062
N	H10P 95/064	3	{the removal being chemical etching}	
N	H10P 95/066	4	{the removal being a selective chemical etching step, e.g. selective dry etching through a mask}	
Q	H10P 95/08	1	{Planarisation of organic insulating materials}	H10P 52/209, H10P 52/409, H10P 95/08
N	H10P 95/11	1	{Separation of active layers from substrates}	
N	H10P 95/112	2	{leaving a reusable substrate, e.g. epitaxial lift off}	
N	H10P 95/40	1	Treatments of semiconductor bodies to modify their internal properties, e.g. to produce internal imperfections	
N	H10P 95/402	2	{of silicon bodies}	
N	H10P 95/405	3	{using cavities formed by hydrogen or noble gas ion implantation}	
N	H10P 95/408	2	{of Group III-V semiconductors, e.g. to render them semi-insulating}	
N	H10P 95/50	1	{Alloying conductive materials with semiconductor bodies}	
Q	H10P 95/60	1	Mechanical treatments, e.g. by ultrasounds	H10P 95/60, H10P 95/02

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Type*	Symbol	Indent Level Number of dots (e.g. 0, 1, 2)	Title “CPC only” text should normally be enclosed in {curly brackets}**	Transferred to[#]
Q	H10P 95/70	1	Chemical treatments	H10P 95/70, H10P 95/80, H10P 95/02
N	H10P 95/80	1	Electrical treatments, e.g. for electroforming	
Q	H10P 95/90	1	Thermal treatments, e.g. annealing or sintering	H10P 95/90, H10P 30/28
N	H10P 95/902	2	{for the formation of PN junctions without addition of impurities}	
Q	H10P 95/904	2	{of Group III-V semiconductors}	H10P 95/904, H10P 30/28
N	H10P 95/906	2	{for altering the shape of semiconductors, e.g. smoothing the surface}	
Q	H10P 95/92	1	{Formation of n- or p-type semiconductors, e.g. doping of graphene}	H10P 95/92, H10P 32/173
N	H10P 95/94	1	{Hydrogenation or deuterisation, e.g. using atomic hydrogen from a plasma}	

*N = new entries where reclassification into entries is involved; C = entries with modified file scope where reclassification of documents from the entries is involved; Q = new entries which are firstly populated with documents via administrative transfers from deleted (D) entries. Afterwards, the transferred documents into the Q entry will either stay or be moved to more appropriate entries, as determined by intellectual reclassification; T = existing entries with enlarged file scope, which receive documents from C or D entries, e.g. when a limiting reference is removed from the entry title; M = entries with no change to the file scope (no reclassification); D = deleted entries; F = frozen entries will be deleted once reclassification of documents from the entries is completed; U = entries that are unchanged.

NOTES:

- **No {curly brackets} are used for titles in CPC only subclasses, e.g. C12Y, A23Y; 2000 series symbol titles of groups found at the end of schemes (orthogonal codes); or the Y section titles. The {curly brackets} are used for 2000 series symbol titles found interspersed throughout the main trunk schemes (breakdown codes).
- U groups: it is obligatory to display the required “anchor” symbol (U group), i.e. the entry immediately preceding a new group or an array of new groups to be created (in case new groups are not clearly subgroups of C-type groups). Always include the symbol, indent level and title of the U group in the table above.
- All entry types should be included in the scheme changes table above for better understanding of the overall scheme change picture. Symbol, indent level, and title are required for all types.
- “Transferred to” column must be completed for all C, D, F, and Q type entries. F groups will be deleted once reclassification is completed.

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- When multiple symbols are included in the “Transferred to” column, avoid using ranges of symbols in order to be as precise as possible.
- For administrative transfer of documents, the following text should be used: “<administrative transfer to XX>”, “<administrative transfer to XX and YY simultaneously>”, or “<administrative transfer to XX, YY, ...and ZZ simultaneously>” when administrative transfer of the same documents is to more than one place.
- Administrative transfer to main trunk groups is assumed to be the source allocation type, unless otherwise indicated.
- Administrative transfer to 2000/Y series groups is assumed to be “additional information”.
- If needed, instructions for allocation type should be indicated within the angle brackets using the abbreviations “ADD” or “INV”: <administrative transfer to XX ADD>, <administrative transfer to XX INV>, or <administrative transfer to XX ADD, YY INV, ... and ZZ ADD simultaneously>.
- In certain situations, the “D” entries of 2000-series or Y-series groups may not require a destination (“Transferred to”) symbol, however it is required to specify “<no transfer>” in the “Transferred to” column for such cases.
- For finalization projects, the deleted “F” symbols should have <no transfer> in the “Transferred to” column.
- For more details about the types of scheme change, see CPC Guide.

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B. New, Modified or Deleted Warning notice(s)**SUBCLASS H01L - SEMICONDUCTOR DEVICES NOT COVERED BY CLASS H10**

<u>Type*</u>	<u>Location</u>	<u>Old Warning</u>	<u>New/Modified Warning</u>
D	H01L	<p>1. The following IPC groups are not in the CPC scheme. The subject matter for these IPC groups is classified in the following CPC groups:</p> <p>H01L21/203 covered by H01L21/02631</p> <p>H01L21/205 covered by H01L21/0262</p> <p>H01L21/208 covered by H01L21/02623</p> <p>H01L21/301 covered by H01L21/30</p> <p>H01L21/36 - H01L21/368 covered by H01L21/02107</p> <p>H01L21/58 covered by H01L24/80</p> <p>H01L21/66 covered by H01L22/00</p> <p>H01L21/98 covered by H01L25/50</p> <p>2. In this subclass non-limiting references (in the sense of paragraph 39 of the Guide to the IPC) may still be displayed in the scheme.</p> <p>3. Due to the ongoing developments in class H10 and related subclasses, the information displayed in notes, references and definitions of this subclass may not be entirely accurate. For each specific subject matter referred to in this subclass, users are invited to consult the relevant place in class H10 and to consider the class H10 information as correct, in case of conflict.</p>	<u>Delete</u> entire warning
D	H01L 21/3247	<p>Group H01L 21/3247 is incomplete pending reclassification of documents from group H01L 21/324.</p> <p>Groups H01L 21/324 and H01L 21/3247 should be considered in order to perform a complete search.</p>	<u>Delete</u> entire warning

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SUBCLASS H10D – INORGANIC ELECTRIC SEMICONDUCTOR DEVICES

<u>Type*</u>	<u>Location</u>	<u>Old Warning</u>	<u>New/Modified Warning</u>
N	H10D 64/011		Group H10D 64/011 is incomplete pending reclassification of documents from group H10P 14/47. Group H10D 64/011 is also impacted by reclassification into groups H10D 64/0111 - H10D 64/0115, H10D 64/0116 - H10D 64/0118, H10D 64/012 - H10D 64/0126 and H10D 64/013 - H10D 64/01366. All groups listed in this Warning should be considered in order to perform a complete search.
N	H10D 64/0111		Groups H10D 64/0111 and H10D 64/0113 are incomplete pending reclassification of documents from group H10D 64/011. Groups H10D 64/011, H10D 64/0111 and H10D 64/0113 should be considered in order to perform a complete search.
N	H10D 64/0112		Group H10D 64/0112 is incomplete pending reclassification of documents from group H10D 64/011. Group H10D 64/0112 is also impacted by reclassification into group H10D 64/01125. Groups H10D 64/011, H10D 64/0112 and H10D 64/01125 should be considered in order to perform a complete search.
N	H10D 64/01125		Group H10D 64/01125 is incomplete pending reclassification of documents from groups H10D 64/011 and H10D 64/0112. Groups H10D 64/011, H10D 64/0112 and H10D 64/01125 should be considered in order to perform a complete search.
N	H10D 64/0114		Group H10D 64/0114 is incomplete pending reclassification of documents from group H10D 64/011. Group H10D 64/0114 is also impacted by reclassification into groups H10D 64/0122 and H10D 64/01364. All groups listed in this Warning should be considered in order to perform a complete search.
N	H10D 64/0115		Group H10D 64/0115 is incomplete pending reclassification of documents from group H10D 64/011. Group H10D 64/0115 is also impacted by reclassification into groups

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<u>Type*</u>	<u>Location</u>	<u>Old Warning</u>	<u>New/Modified Warning</u>
			H10D 64/0123 and H10D 64/01366. All groups listed in this Warning should be considered in order to perform a complete search.
N	H10D 64/0116		Group H10D 64/0116 is incomplete pending reclassification of documents from group H10D 64/011. Groups H10D 64/011 and H10D 64/0116 should be considered in order to perform a complete search.
N	H10D 64/0117		Group H10D 64/0117 is incomplete pending reclassification of documents from groups H10D 64/011 and H10D 64/0125. Groups H10D 64/011, H10D 64/0125 and H10D 64/0117 should be considered in order to perform a complete search.
N	H10D 64/0118		Group H10D 64/0118 is incomplete pending reclassification of documents from groups H10D 64/011 and H10D 64/0126. Groups H10D 64/011, H10D 64/0126 and H10D 64/0118 should be considered in order to perform a complete search.
N	H10D 64/012		Group H10D 64/012 is incomplete pending reclassification of documents from groups H10D 64/011 and H10P 14/47. Groups H10D 64/011, H10P 14/47 and H10D 64/012 should be considered in order to perform a complete search.
N	H10D 64/0121		Group H10D 64/0121 is incomplete pending reclassification of documents from group H10D 64/011. Groups H10D 64/011 and H10D 64/0121 should be considered in order to perform a complete search.
N	H10D 64/0122		Group H10D 64/0122 is incomplete pending reclassification of documents from groups H10D 64/011 and H10D 64/0114. Groups H10D 64/011, H10D 64/0114 and H10D 64/0122 should be considered in order to perform a complete search.
N	H10D 64/0123		Group H10D 64/0123 is incomplete pending reclassification of documents from groups H10D 64/011 and H10D 64/0115. Groups H10D 64/011, H10D 64/0115 and H10D 64/0123 should be considered in order to perform a complete search.

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<u>Type*</u>	<u>Location</u>	<u>Old Warning</u>	<u>New/Modified Warning</u>
N	H10D 64/0124		Group H10D 64/0124 is incomplete pending reclassification of documents from group H10D 64/011. Groups H10D 64/011 and H10D 64/0124 should be considered in order to perform a complete search.
N	H10D 64/0125		Group H10D 64/0125 is incomplete pending reclassification of documents from group H10D 64/011. Group H10D 64/0125 is also impacted by reclassification into groups H10D 64/0117 and H10D 64/0136. All groups listed in this Warning should be considered in order to perform a complete search.
N	H10D 64/0126		Group H10D 64/0126 is incomplete pending reclassification of documents from group H10D 64/011. Group H10D 64/0126 is also impacted by reclassification into groups H10D 64/0118 and H10D 64/01362. All groups listed in this Warning should be considered in order to perform a complete search.
N	H10D 64/013		Group H10D 64/013 is incomplete pending reclassification of documents from groups H10D 64/011 and H10P 14/47. Groups H10D 64/011, H10P 14/47 and H10D 64/013 should be considered in order to perform a complete search.
N	H10D 64/01302		Groups H10D 64/01302 - H10D 64/01354 are incomplete pending reclassification of documents from group H10D 64/011. All groups listed in this Warning should be considered in order to perform a complete search.
N	H10D 64/01356		Group H10D 64/01356 is incomplete pending reclassification of documents from group H10D 64/011. Groups H10D 64/011 and H10D 64/01356 should be considered in order to perform a complete search.
N	H10D 64/01358		Group H10D 64/01358 is incomplete pending reclassification of documents from group H10D 64/011. Groups H10D 64/011 and H10D 64/01358 should be considered in order to perform a complete search.

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<u>Type*</u>	<u>Location</u>	<u>Old Warning</u>	<u>New/Modified Warning</u>
N	H10D 64/0136		Group H10D 64/0136 is incomplete pending reclassification of documents from groups H10D 64/011 and H10D 64/0125. Groups H10D 64/011, H10D 64/0125 and H10D 64/0136 should be considered in order to perform a complete search.
N	H10D 64/01362		Group H10D 64/01362 is incomplete pending reclassification of documents from groups H10D 64/011 and H10D 64/0126. Groups H10D 64/011, H10D 64/0126 and H10D 64/01362 should be considered in order to perform a complete search.
N	H10D 64/01364		Group H10D 64/01364 is incomplete pending reclassification of documents from groups H10D 64/011 and H10D 64/0114. Groups H10D 64/011, H10D 64/0114 and H10D 64/01364 should be considered in order to perform a complete search.
N	H10D 64/01366		Group H10D 64/01366 is incomplete pending reclassification of documents from groups H10D 64/011 and H10D 64/0115. Groups H10D 64/011, H10D 64/0115 and H10D 64/01366 should be considered in order to perform a complete search.
M	H10D 84/01	Group H10D 84/01 is impacted by reclassification into groups H10D 84/02, H10D 84/03, H10D 84/035, H10D 84/038, H10D 84/05, H10D 84/07 and H10D 84/08. All groups listed in this Warning should be considered in order to perform a complete search.	Group H10D 84/01 is impacted by reclassification into groups H10D 84/0102 - H10D 84/0105, H10D 84/0107 - H10D 84/0109, H10D 84/0112 - H10D 84/0121, H10D 84/0123 - H10D 84/0195, H10D 84/0198, H10D 84/02 - H10D 84/08 and H10D 89/60 - H10D 89/931. All groups listed in this Warning should be considered in order to perform a complete search.
N	H10D 84/0102		Groups H10D 84/0102 and H10D 84/0105 are incomplete pending reclassification of documents from group H10D 84/01. Groups H10D 84/01, H10D 84/0102 and H10D 84/0105 should be considered in order to perform a complete search.
M	H10D 84/0107	Groups H10D 84/0107 and H10D 84/0109 are incomplete pending reclassification of documents from groups H10D 84/02, H10D 84/032, H10D	Groups H10D 84/0107 and H10D 84/0109 are incomplete pending reclassification of documents from groups H10D 84/01, H10D 84/02,

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<u>Type*</u>	<u>Location</u>	<u>Old Warning</u>	<u>New/Modified Warning</u>
		84/035, H10D 84/05, H10D 84/07 and H10D 84/08. All groups listed in this Warning should be considered in order to perform a complete search.	H10D 84/032, H10D 84/035, H10D 84/05, H10D 84/07 and H10D 84/08. All groups listed in this Warning should be considered in order to perform a complete search.
M	H10D 84/0112	Groups H10D 84/0112 - H10D 84/0121 are incomplete pending reclassification of documents from groups H10D 84/02, H10D 84/032, H10D 84/035, H10D 84/05, H10D 84/07 and H10D 84/08. All groups listed in this Warning should be considered in order to perform a complete search.	Groups H10D 84/0112 - H10D 84/0121 are incomplete pending reclassification of documents from groups H10D 84/01, H10D 84/02, H10D 84/032, H10D 84/035, H10D 84/05, H10D 84/07 and H10D 84/08. All groups listed in this Warning should be considered in order to perform a complete search.
M	H10D 84/0123	Groups H10D 84/0123, H10D 84/0126, H10D 84/0128, H10D 84/013, H10D 84/0133, H10D 84/0135, H10D 84/0137, H10D 84/014, H10D 84/0142, H10D 84/0144, H10D 84/0147, H10D 84/0158, H10D 84/016, H10D 84/0163, H10D 84/0165, H10D 84/0167, H10D 84/017, H10D 84/0172, H10D 84/0174, H10D 84/0177, H10D 84/0179, H10D 84/0181, H10D 84/0184, H10D 84/0186, H10D 84/0188, H10D 84/0191, H10D 84/0193 and H10D 84/0195 are incomplete pending reclassification of documents from groups H10D 84/02, H10D 84/032, H10D 84/035, H10D 84/05, H10D 84/07 and H10D 84/08. All groups listed in this Warning should be considered in order to perform a complete search.	Groups H10D 84/0123 - H10D 84/0195 are incomplete pending reclassification of documents from groups H10D 84/01, H10D 84/02, H10D 84/032, H10D 84/035, H10D 84/05, H10D 84/07 and H10D 84/08. All groups listed in this Warning should be considered in order to perform a complete search.
M	H10D 84/0198	Group H10D 84/0198 is incomplete pending reclassification of documents from groups H10D 84/02, H10D 84/032, H10D 84/035, H10D 84/05, H10D 84/07 and H10D 84/08.	Group H10D 84/0198 is incomplete pending reclassification of documents from groups H10D 84/01, H10D 84/02, H10D 84/032, H10D 84/035, H10D 84/05, H10D 84/07 and H10D 84/08.

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<u>Type*</u>	<u>Location</u>	<u>Old Warning</u>	<u>New/Modified Warning</u>
		All groups listed in this Warning should be considered in order to perform a complete search.	All groups listed in this Warning should be considered in order to perform a complete search.
M	H10D 84/02	Group H10D 84/02 is incomplete pending reclassification of documents from group H10D 84/01. Group H10D 84/02 is also impacted by reclassification into groups H10D 84/0107 - H10D 84/0109, H10D 84/0112 - H10D 84/0121, H10D 84/0123, H10D 84/0126, H10D 84/0128, H10D 84/013 - H10D 84/0133, H10D 84/0135 - H10D 84/0142, H10D 84/0144, H10D 84/0147, H10D 84/0151 - H10D 84/0153, H10D 84/0156, H10D 84/0158, H10D 84/016, H10D 84/0163, H10D 84/0165 - H10D 84/0195, H10D 84/0198, H10D 84/03 and H10D 88/01. All groups listed in this Warning should be considered in order to perform a complete search.	Groups H10D 84/02 - H10D 84/08 are incomplete pending reclassification of documents from group H10D 84/01. Group H10D 84/02 is also impacted by reclassification into groups H10D 84/0107 - H10D 84/0109, H10D 84/0112 - H10D 84/0121, H10D 84/0123, H10D 84/0126, H10D 84/0128, H10D 84/013 - H10D 84/0133, H10D 84/0135 - H10D 84/0142, H10D 84/0144, H10D 84/0147, H10D 84/0151 - H10D 84/0153, H10D 84/0156, H10D 84/0158, H10D 84/016, H10D 84/0163, H10D 84/0165 - H10D 84/0195, H10D 84/0198, H10D 84/03 and H10D 88/01. All groups listed in this Warning should be considered in order to perform a complete search.
N	H10D 86/01		Groups H10D 86/01 - H10D 86/03 are incomplete pending reclassification of documents from group H10D 84/01. All groups listed in this Warning should be considered in order to perform a complete search.
N	H10D 87/00		Group H10D 87/00 is incomplete pending reclassification of documents from group H10D 84/01. Groups H10D 84/01 and H10D 87/00 should be considered in order to perform a complete search.
M	H10D 88/01	Group H10D 88/01 is incomplete pending reclassification of documents from groups H10D 84/02, H10D 84/032, H10D 84/035, H10D 84/05, H10D 84/07 and H10D 84/08. All groups listed in this Warning should be considered	Group H10D 88/01 is incomplete pending reclassification of documents from groups H10D 84/01, H10D 84/02, H10D 84/032, H10D 84/035, H10D 84/05, H10D 84/07 and H10D 84/08. All groups listed in this Warning should be considered in order to perform a complete search.

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		in order to perform a complete search.	
N	H10D 88/101		Group H10D 88/101 is incomplete pending reclassification of documents from group H10D 84/01. Groups H10D 84/01 and H10D 88/101 should be considered in order to perform a complete search.
N	H10D 89/60		Groups H10D 89/60 - H10D 89/931 are incomplete pending reclassification of documents from group H10D 84/01. All groups listed in this Warning should be considered in order to perform a complete search.

SUBCLASS H10P - GENERIC PROCESSES OR APPARATUS FOR THE MANUFACTURE OR TREATMENT OF DEVICES COVERED BY CLASS H10

<u>Type*</u>	<u>Location</u>	<u>Old Warning</u>	<u>New/Modified Warning</u>
N	H10P 10/00		Group H10P 10/00 is impacted by reclassification into groups H10P 14/00 and H10P 95/00. Groups H10P 10/00, H10P 14/00 and H10P 95/00 should be considered in order to perform a complete search.
N	H10P 10/12		Group H10P 10/12 is incomplete pending reclassification of documents from group H10P 90/00. Group H10P 10/12 is also impacted by reclassification into groups H10P 10/126, H10P 10/128 - H10P 10/1285, H10P 54/52, H10P 56/00, H10P 90/1914 and H10P 90/1916. All groups listed in this Warning should be considered in order to perform a complete search.
N	H10P 10/126		Group H10P 10/126 is incomplete pending reclassification of documents from groups H10P 10/12, H10P 90/1914 and H10P 90/1916. All groups listed in this Warning should be considered in order to perform a complete search.
N	H10P 10/128		Groups H10P 10/128 and H10P 10/1285 are incomplete pending reclassification of documents from groups H10P 10/12, H10P 90/1914 and H10P 90/1916. All groups listed

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<u>Type*</u>	<u>Location</u>	<u>Old Warning</u>	<u>New/Modified Warning</u>
			in this Warning should be considered in order to perform a complete search.
N	H10P 10/14		Group H10P 10/14 is incomplete pending reclassification of documents from groups H10P 90/1914 and H10P 90/1916. Groups H10P 90/1914, H10P 90/1916 and H10P 10/14 should be considered in order to perform a complete search.
N	H10P 14/00		Group H10P 14/00 is incomplete pending reclassification of documents from group H10P 10/00. Groups H10P 10/00 and H10P 14/00 should be considered in order to perform a complete search.
N	H10P 14/29		Group H10P 14/29 is impacted by reclassification into groups H10P 14/2924 - H10P 14/2925 and H10P 14/2926. Groups H10P 14/29, H10P 14/2924 - H10P 14/2925 and H10P 14/2926 should be considered in order to perform a complete search.
N	H10P 14/2924		Groups H10P 14/2924 and H10P 14/2925 are incomplete pending reclassification of documents from group H10P 14/29. Groups H10P 14/29, H10P 14/2924 and H10P 14/2925 should be considered in order to perform a complete search.
N	H10P 14/2926		Group H10P 14/2926 is incomplete pending reclassification of documents from group H10P 14/29. Groups H10P 14/29 and H10P 14/2926 should be considered in order to perform a complete search.
N	H10P 14/42		Group H10P 14/42 is impacted by reclassification into group H10P 14/43. Groups H10P 14/42 and H10P 14/43 should be considered in order to perform a complete search.
N	H10P 14/43		Group H10P 14/43 is incomplete pending reclassification of documents from group H10P 14/42. Groups H10P 14/42 and H10P 14/43 should be considered in order to perform a complete search.
N	H10P 14/44		Group H10P 14/44 is impacted by reclassification into group H10P 14/45. Groups H10P 14/44 and H10P 14/45 should be considered in order to perform a complete search.

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<u>Type*</u>	<u>Location</u>	<u>Old Warning</u>	<u>New/Modified Warning</u>
N	H10P 14/45		Group H10P 14/45 is incomplete pending reclassification of documents from group H10P 14/44. Groups H10P 14/44 and H10P 14/45 should be considered in order to perform a complete search.
N	H10P 14/46		Group H10P 14/46 is incomplete pending reclassification of documents from group H10P 14/47. Group H10P 14/46 is also impacted by reclassification into group H10P 14/48. Groups H10P 14/47, H10P 14/46 and H10P 14/48 should be considered in order to perform a complete search
N	H10P 14/47		Group H10P 14/47 is impacted by reclassification into groups H10P 14/46, H10P 14/48, H10D 64/011, H10D 64/012 and H10D 64/013. All groups listed in this Warning should be considered in order to perform a complete search.
N	H10P 14/48		Group H10P 14/48 is incomplete pending reclassification of documents from groups H10P 14/46 and H10P 14/47. Groups H10P 14/46, H10P 14/47 and H10P 14/48 should be considered in order to perform a complete search.
N	H10P 14/60		Group H10P 14/60 is impacted by reclassification into groups H10P 95/70 and H10P 95/80. Groups H10P 14/60, H10P 95/70 and H10P 95/80 should be considered in order to perform a complete search.
N	H10P 14/6308		Group H10P 14/6308 is impacted by reclassification into groups H10P 14/6309, H10P 14/6318, H10P 14/6319, H10P 14/6322 and H10P 14/6324. All groups listed in this Warning should be considered in order to perform a complete search.
N	H10P 14/6309		Group H10P 14/6309 is incomplete pending reclassification of documents from group H10P 14/6308. Groups H10P 14/6308 and H10P 14/6309 should be considered in order to perform a complete search.
N	H10P 14/6316		Group H10P 14/6316 is impacted by reclassification into groups H10P 14/6318, H10P 14/6319,

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<u>Type*</u>	<u>Location</u>	<u>Old Warning</u>	<u>New/Modified Warning</u>
			H10P 14/6322 and H10P 14/6324. All groups listed in this Warning should be considered in order to perform a complete search.
N	H10P 14/6318		Group H10P 14/6318 is incomplete pending reclassification of documents from groups H10P 14/6308 and H10P 14/6316. Groups H10P 14/6308, H10P 14/6316 and H10P 14/6318 should be considered in order to perform a complete search.
N	H10P 14/6319		Group H10P 14/6319 is incomplete pending reclassification of documents from groups H10P 14/6308 and H10P 14/6316. Groups H10P 14/6308, H10P 14/6316 and H10P 14/6319 should be considered in order to perform a complete search.
N	H10P 14/6322		Group H10P 14/6322 is incomplete pending reclassification of documents from groups H10P 14/6308 and H10P 14/6316. Groups H10P 14/6308, H10P 14/6316 and H10P 14/6322 should be considered in order to perform a complete search.
N	H10P 14/6324		Group H10P 14/6324 is incomplete pending reclassification of documents from groups H10P 14/6308 and H10P 14/6316. Groups H10P 14/6308, H10P 14/6316 and H10P 14/6324 should be considered in order to perform a complete search.
N	H10P 14/68		Group H10P 14/68 is impacted by reclassification into group H10P 14/69. Groups H10P 14/68 and H10P 14/69 should be considered in order to perform a complete search.
N	H10P 14/683		Group H10P 14/683 is impacted by reclassification into group H10P 14/69. Groups H10P 14/683 and H10P 14/69 should be considered in order to perform a complete search.
N	H10P 14/687		Group H10P 14/687 is impacted by reclassification into group H10P 14/69. Groups H10P 14/687 and H10P 14/69 should be considered in order to perform a complete search.
N	H10P 14/69		Group H10P 14/69 is incomplete pending reclassification of documents from groups H10P 14/68, H10P 14/683 and H10P 14/687.

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			Group H10P 14/69 is also impacted by reclassification into group H10P 14/694. All groups listed in this Warning should be considered in order to perform a complete search.
N	H10P 14/6903		Group H10P 14/6903 is impacted by reclassification into groups H10P 14/6921 and H10P 14/6943. Groups H10P 14/6903, H10P 14/6921 and H10P 14/6943 should be considered in order to perform a complete search.
N	H10P 14/6906		Group H10P 14/6906 is incomplete pending reclassification of documents from group H10P 14/6938. Groups H10P 14/6938 and H10P 14/6906 should be considered in order to perform a complete search.
N	H10P 14/6907		Group H10P 14/6907 is incomplete pending reclassification of documents from group H10P 14/6939. Groups H10P 14/6939 and H10P 14/6907 should be considered in order to perform a complete search.
N	H10P 14/6908		Group H10P 14/6908 is incomplete pending reclassification of documents from group H10P 14/69391. Groups H10P 14/69391 and H10P 14/6908 should be considered in order to perform a complete search.
N	H10P 14/6909		Group H10P 14/6909 is incomplete pending reclassification of documents from group H10P 14/69392. Groups H10P 14/69392 and H10P 14/6909 should be considered in order to perform a complete search.
N	H10P 14/691		Group H10P 14/691 is incomplete pending reclassification of documents from group H10P 14/69393. Groups H10P 14/69393 and H10P 14/691 should be considered in order to perform a complete search.
N	H10P 14/6911		Group H10P 14/6911 is incomplete pending reclassification of documents from group H10P 14/69394. Groups H10P 14/69394 and H10P 14/6911 should be considered in order to perform a complete search.
N	H10P 14/6912		Group H10P 14/6912 is incomplete pending reclassification of documents from group H10P 14/69395. Groups

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<u>Type*</u>	<u>Location</u>	<u>Old Warning</u>	<u>New/Modified Warning</u>
			H10P 14/69395 and H10P 14/6912 should be considered in order to perform a complete search.
N	H10P 14/6913		Group H10P 14/6913 is incomplete pending reclassification of documents from group H10P 14/69396. Groups H10P 14/69396 and H10P 14/6913 should be considered in order to perform a complete search.
N	H10P 14/6914		Group H10P 14/6914 is incomplete pending reclassification of documents from group H10P 14/69397. Groups H10P 14/69397 and H10P 14/6914 should be considered in order to perform a complete search.
N	H10P 14/6921		Group H10P 14/6921 is incomplete pending reclassification of documents from group H10P 14/6903. Groups H10P 14/6903 and H10P 14/6921 should be considered in order to perform a complete search.
N	H10P 14/6938		Group H10P 14/6938 is impacted by reclassification into groups H10P 14/6906 and H10P 14/6947. Groups H10P 14/6938, H10P 14/6906 and H10P 14/6947 should be considered in order to perform a complete search.
N	H10P 14/6939		Group H10P 14/6939 is impacted by reclassification into groups H10P 14/6907 and H10P 14/69471. Groups H10P 14/6939, H10P 14/6907 and H10P 14/69471 should be considered in order to perform a complete search.
N	H10P 14/69391		Group H10P 14/69391 is impacted by reclassification into groups H10P 14/6908 and H10P 14/69472. Groups H10P 14/69391, H10P 14/6908 and H10P 14/69472 should be considered in order to perform a complete search.
N	H10P 14/69392		Group H10P 14/69392 is impacted by reclassification into groups H10P 14/6909 and H10P 14/69473. Groups H10P 14/69392, H10P 14/6909 and H10P 14/69473 should be considered in order to perform a complete search.
N	H10P 14/69393		Group H10P 14/69393 is impacted by reclassification into groups

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<u>Type*</u>	<u>Location</u>	<u>Old Warning</u>	<u>New/Modified Warning</u>
			H10P 14/691 and H10P 14/69474. Groups H10P 14/69393, H10P 14/691 and H10P 14/69474 should be considered in order to perform a complete search.
N	H10P 14/69394		Group H10P 14/69394 is impacted by reclassification into groups H10P 14/6911 and H10P 14/69475. Groups H10P 14/69394, H10P 14/6911 and H10P 14/69475 should be considered in order to perform a complete search.
N	H10P 14/69395		Group H10P 14/69395 is impacted by reclassification into groups H10P 14/6912 and H10P 14/69476. Groups H10P 14/69395, H10P 14/6912 and H10P 14/69476 should be considered in order to perform a complete search.
N	H10P 14/69396		Group H10P 14/69396 is impacted by reclassification into groups H10P 14/6913 and H10P 14/69477. Groups H10P 14/69396, H10P 14/6913 and H10P 14/69477 should be considered in order to perform a complete search.
N	H10P 14/69397		Group H10P 14/69397 is impacted by reclassification into groups H10P 14/6914 and H10P 14/69478. Groups H10P 14/69397, H10P 14/6914 and H10P 14/69478 should be considered in order to perform a complete search.
N	H10P 14/694		Group H10P 14/694 is incomplete pending reclassification of documents from group H10P 14/69. Groups H10P 14/69 and H10P 14/694 should be considered in order to perform a complete search.
N	H10P 14/6943		Group H10P 14/6943 is incomplete pending reclassification of documents from group H10P 14/6903. Groups H10P 14/6903 and H10P 14/6943 should be considered in order to perform a complete search.
N	H10P 14/6947		Group H10P 14/6947 is incomplete pending reclassification of documents from group H10P 14/6938. Groups H10P 14/6938 and H10P 14/6947 should be considered in order to perform a complete search.

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<u>Type*</u>	<u>Location</u>	<u>Old Warning</u>	<u>New/Modified Warning</u>
N	H10P 14/69471		Group H10P 14/69471 is incomplete pending reclassification of documents from group H10P 14/6939. Groups H10P 14/6939 and H10P 14/69471 should be considered in order to perform a complete search.
N	H10P 14/69472		Group H10P 14/69472 is incomplete pending reclassification of documents from group H10P 14/69391. Groups H10P 14/69391 and H10P 14/69472 should be considered in order to perform a complete search.
N	H10P 14/69473		Group H10P 14/69473 is incomplete pending reclassification of documents from group H10P 14/69392. Groups H10P 14/69392 and H10P 14/69473 should be considered in order to perform a complete search.
N	H10P 14/69474		Group H10P 14/69474 is incomplete pending reclassification of documents from group H10P 14/69393. Groups H10P 14/69393 and H10P 14/69474 should be considered in order to perform a complete search.
N	H10P 14/69475		Group H10P 14/69475 is incomplete pending reclassification of documents from group H10P 14/69394. Groups H10P 14/69394 and H10P 14/69475 should be considered in order to perform a complete search.
N	H10P 14/69476		Group H10P 14/69476 is incomplete pending reclassification of documents from group H10P 14/69395. Groups H10P 14/69395 and H10P 14/69476 should be considered in order to perform a complete search.
N	H10P 14/69477		Group H10P 14/69477 is incomplete pending reclassification of documents from group H10P 14/69396. Groups H10P 14/69396 and H10P 14/69477 should be considered in order to perform a complete search.
N	H10P 14/69478		Group H10P 14/69478 is incomplete pending reclassification of documents from group H10P 14/69397. Groups H10P 14/69397 and H10P 14/69478 should be considered in order to perform a complete search.
N	H10P 30/00		Group H10P 30/00 is incomplete pending reclassification of documents from group H10P 30/20. Groups

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<u>Type*</u>	<u>Location</u>	<u>Old Warning</u>	<u>New/Modified Warning</u>
			H10P 30/20 and H10P 30/00 should be considered in order to perform a complete search.
N	H10P 30/20		Group H10P 30/20 is impacted by reclassification into group H10P 30/00. Groups H10P 30/20 and H10P 30/00 should be considered in order to perform a complete search.
N	H10P 30/202		Group H10P 30/202 is impacted by reclassification into groups H10P 30/208, H10P 30/21 - H10P 30/212, H10P 30/22 - H10P 30/221, H10P 30/222 and H10P 30/28. All groups listed in this Warning should be considered in order to perform a complete search.
N	H10P 30/2042		Group H10P 30/2042 is impacted by reclassification into groups H10P 30/21, H10P 30/218 and H10P 30/28. All groups listed in this Warning should be considered in order to perform a complete search.
N	H10P 30/2044		Group H10P 30/2044 is impacted by reclassification into groups H10P 30/208, H10P 30/21 - H10P 30/212, H10P 30/22 - H10P 30/221, H10P 30/222 and H10P 30/28. All groups listed in this Warning should be considered in order to perform a complete search.
N	H10P 30/208		Group H10P 30/208 is incomplete pending reclassification of documents from groups H10P 30/202 and H10P 30/2044. Groups H10P 30/202, H10P 30/2044 and H10P 30/208 should be considered in order to perform a complete search.
N	H10P 30/21		Group H10P 30/21 is incomplete pending reclassification of documents from groups H10P 30/202, H10P 30/2042 and H10P 30/2044. Group H10P 30/21 is also impacted by reclassification into groups H10P 30/214 and H10P 30/28. All groups listed in this Warning should be considered in order to perform a complete search.
N	H10P 30/212		Group H10P 30/212 is incomplete pending reclassification of documents from groups H10P 30/202 and H10P 30/2044. Group H10P 30/212 is

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<u>Type*</u>	<u>Location</u>	<u>Old Warning</u>	<u>New/Modified Warning</u>
			also impacted by reclassification into groups H10P 30/214 and H10P 30/28. All groups listed in this Warning should be considered in order to perform a complete search.
N	H10P 30/214		Group H10P 30/214 is incomplete pending reclassification of documents from groups H10P 30/21 and H10P 30/212. Groups H10P 30/21, H10P 30/212 and H10P 30/214 should be considered in order to perform a complete search.
N	H10P 30/218		Group H10P 30/218 is incomplete pending reclassification of documents from group H10P 30/2042. Groups H10P 30/2042 and H10P 30/218 should be considered in order to perform a complete search.
N	H10P 30/22		Group H10P 30/22 is incomplete pending reclassification of documents from groups H10P 30/202 and H10P 30/2044. Groups H10P 30/202, H10P 30/2044 and H10P 30/22 should be considered in order to perform a complete search.
N	H10P 30/221		Group H10P 30/221 is incomplete pending reclassification of documents from groups H10P 30/202, H10P 30/2044 and H10P 30/222. All groups listed in this Warning should be considered in order to perform a complete search.
N	H10P 30/222		Group H10P 30/222 is incomplete pending reclassification of documents from groups H10P 30/202 and H10P 30/2044. Group H10P 30/222 is also impacted by reclassification into group H10P 30/221. All groups listed in this Warning should be considered in order to perform a complete search.
N	H10P 30/28		Group H10P 30/28 is incomplete pending reclassification of documents from groups H10P 30/202, H10P 30/2042, H10P 30/2044, H10P 30/21, H10P 30/212, H10P 95/90 and H10P 95/904. All groups listed in this Warning should be considered in order to perform a complete search.
N	H10P 30/40		Group H10P 30/40 is impacted by reclassification into group

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<u>Type*</u>	<u>Location</u>	<u>Old Warning</u>	<u>New/Modified Warning</u>
			H10P 32/20. Groups H10P 30/40 and H10P 32/20 should be considered in order to perform a complete search.
N	H10P 32/00		Group H10P 32/00 is impacted by reclassification into group H10P 32/10. Groups H10P 32/00 and H10P 32/10 should be considered in order to perform a complete search.
N	H10P 32/10		Group H10P 32/10 is incomplete pending reclassification of documents from group H10P 32/00. Groups H10P 32/00 and H10P 32/10 should be considered in order to perform a complete search.
N	H10P 32/173		Group H10P 32/173 is incomplete pending reclassification of documents from group H10P 95/92. Groups H10P 95/92 and H10P 32/173 should be considered in order to perform a complete search.
N	H10P 32/20		Group H10P 32/20 is incomplete pending reclassification of documents from group H10P 30/40. Groups H10P 30/40 and H10P 32/20 should be considered in order to perform a complete search.
N	H10P 34/00		Group H10P 34/00 is impacted by reclassification into groups H10P 34/10, H10P 34/20 and H10P 34/40. All groups listed in this Warning should be considered in order to perform a complete search.
N	H10P 34/10		Group H10P 34/10 is incomplete pending reclassification of documents from group H10P 34/00. Groups H10P 34/00 and H10P 34/10 should be considered in order to perform a complete search.
N	H10P 34/20		Group H10P 34/20 is incomplete pending reclassification of documents from group H10P 34/00. Groups H10P 34/00 and H10P 34/20 should be considered in order to perform a complete search.
N	H10P 34/40		Group H10P 34/40 is incomplete pending reclassification of documents from group H10P 34/00. Groups H10P 34/00 and H10P 34/40 should be considered in order to perform a complete search.

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<u>Type*</u>	<u>Location</u>	<u>Old Warning</u>	<u>New/Modified Warning</u>
N	H10P 36/00		Group H10P 36/00 is impacted by reclassification into groups H10P 36/20 and H10P 95/40. Groups H10P 36/00, H10P 36/20 and H10P 95/40 should be considered in order to perform a complete search.
N	H10P 36/03		Group H10P 36/03 is impacted by reclassification into group H10P 95/402. Groups H10P 36/03 and H10P 95/402 should be considered in order to perform a complete search.
N	H10P 36/20		Group H10P 36/20 is incomplete pending reclassification of documents from group H10P 36/00. Groups H10P 36/00 and H10P 36/20 should be considered in order to perform a complete search.
N	H10P 50/00		Group H10P 50/00 is impacted by reclassification into groups H10P 50/20, H10P 50/24, H10P 50/26, H10P 50/60, H10P 50/61, H10P 50/64, H10P 50/66, H10P 52/00, H10P 95/00, H10P 95/02 and H10P 95/70. All groups listed in this Warning should be considered in order to perform a complete search.
N	H10P 50/20		Group H10P 50/20 is incomplete pending reclassification of documents from group H10P 50/00. Group H10P 50/20 is also impacted by reclassification into groups H10P 50/24, H10P 50/26, H10P 50/60, H10P 50/61, H10P 50/64 and H10P 50/66. All groups listed in this Warning should be considered in order to perform a complete search.
N	H10P 50/24		Group H10P 50/24 is incomplete pending reclassification of documents from groups H10P 50/00 and H10P 50/20. Groups H10P 50/00, H10P 50/20 and H10P 50/24 should be considered in order to perform a complete search.
N	H10P 50/26		Group H10P 50/26 is incomplete pending reclassification of documents from groups H10P 50/00 and H10P 50/20. Groups H10P 50/00, H10P 50/20 and H10P 50/26 should be considered in order to perform a complete search.

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<u>Type*</u>	<u>Location</u>	<u>Old Warning</u>	<u>New/Modified Warning</u>
N	H10P 50/264		Group H10P 50/264 is impacted by reclassification into group H10P 50/663. Groups H10P 50/264 and H10P 50/663 should be considered in order to perform a complete search.
N	H10P 50/28		Group H10P 50/28 is impacted by reclassification into group H10P 50/68. Groups H10P 50/28 and H10P 50/68 should be considered in order to perform a complete search.
N	H10P 50/282		Group H10P 50/282 is impacted by reclassification into group H10P 50/683. Groups H10P 50/282 and H10P 50/683 should be considered in order to perform a complete search.
N	H10P 50/283		Group H10P 50/283 is impacted by reclassification into group H10P 50/683. Groups H10P 50/283 and H10P 50/683 should be considered in order to perform a complete search.
N	H10P 50/286		Group H10P 50/286 is impacted by reclassification into group H10P 50/68. Groups H10P 50/286 and H10P 50/68 should be considered in order to perform a complete search.
N	H10P 50/287		Group H10P 50/287 is impacted by reclassification into group H10P 50/68. Groups H10P 50/287 and H10P 50/68 should be considered in order to perform a complete search.
N	H10P 50/60		Groups H10P 50/60, H10P 50/61, H10P 50/64 and H10P 50/66 are incomplete pending reclassification of documents from groups H10P 50/00 and H10P 50/20. All groups listed in this Warning should be considered in order to perform a complete search.
N	H10P 50/663		Group H10P 50/663 is incomplete pending reclassification of documents from group H10P 50/264. Groups H10P 50/264 and H10P 50/663 should be considered in order to perform a complete search.
N	H10P 50/68		Group H10P 50/68 is incomplete pending reclassification of documents from groups H10P 50/28, H10P 50/286 and H10P 50/287. All groups listed in this Warning should

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<u>Type*</u>	<u>Location</u>	<u>Old Warning</u>	<u>New/Modified Warning</u>
			be considered in order to perform a complete search.
N	H10P 50/683		Group H10P 50/683 is incomplete pending reclassification of documents from groups H10P 50/282 and H10P 50/283. Groups H10P 50/282, H10P 50/283 and H10P 50/683 should be considered in order to perform a complete search.
N	H10P 52/00		Group H10P 52/00 is incomplete pending reclassification of documents from group H10P 50/00. Group H10P 52/00 is incomplete pending reclassification of documents from group H10P 50/00. Group H10P 52/00 is also impacted by reclassification into groups H10P 52/20, H10P 52/40, H10P 54/00 - H10P 54/94 and H10P 95/60. All groups listed in this Warning should be considered in order to perform a complete search.
N	H10P 52/20		Group H10P 52/20 is incomplete pending reclassification of documents from group H10P 52/00. Groups H10P 52/00 and H10P 52/20 should be considered in order to perform a complete search.
N	H10P 52/202		Group H10P 52/202 is incomplete pending reclassification of documents from group H10P 52/402. Groups H10P 52/402 and H10P 52/202 should be considered in order to perform a complete search.
N	H10P 52/207		Group H10P 52/207 is incomplete pending reclassification of documents from group H10P 95/062. Groups H10P 95/062 and H10P 52/207 should be considered in order to perform a complete search.
N	H10P 52/209		Group H10P 52/209 is incomplete pending reclassification of documents from group H10P 95/08. Groups H10P 95/08 and H10P 52/209 should be considered in order to perform a complete search.
N	H10P 52/40		Group H10P 52/40 is incomplete pending reclassification of documents from group H10P 52/00. Groups H10P 52/00 and H10P 52/40 should be considered in order to perform a complete search.

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<u>Type*</u>	<u>Location</u>	<u>Old Warning</u>	<u>New/Modified Warning</u>
N	H10P 52/402		Group H10P 52/402 is impacted by reclassification into group H10P 52/202. Groups H10P 52/402 and H10P 52/202 should be considered in order to perform a complete search.
N	H10P 52/407		Group H10P 52/407 is incomplete pending reclassification of documents from group H10P 95/062. Groups H10P 95/062 and H10P 52/407 should be considered in order to perform a complete search.
N	H10P 52/409		Group H10P 52/409 is incomplete pending reclassification of documents from group H10P 95/08. Groups H10P 95/08 and H10P 52/409 should be considered in order to perform a complete search.
N	H10P 54/00		Groups H10P 54/00, H10P 54/20, H10P 54/30, H10P 54/40, H10P 54/50, H10P 54/90, H10P 54/922, H10P 54/924 and H10P 54/94 are incomplete pending reclassification of documents from groups H10P 52/00 and H10P 58/00. All groups listed in this Warning should be considered in order to perform a complete search.
N	H10P 54/52		Group H10P 54/52 is incomplete pending reclassification of documents from groups H10P 10/12, H10P 52/00, H10P 58/00, H10P 90/1914 and H10P 90/1916. All groups listed in this Warning should be considered in order to perform a complete search.
N	H10P 54/92		Group H10P 54/92 is incomplete pending reclassification of documents from group H10P 52/00. Groups H10P 52/00 and H10P 54/92 should be considered in order to perform a complete search.
N	H10P 56/00		Group H10P 56/00 is incomplete pending reclassification of documents from groups H10P 10/12 and H10P 90/00. Groups H10P 10/12, H10P 90/00 and H10P 56/00 should be considered in order to perform a complete search.
N	H10P 58/00		Group H10P 58/00 is impacted by reclassification into groups H10P 58/20 - H10P 58/22,

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<u>Type*</u>	<u>Location</u>	<u>Old Warning</u>	<u>New/Modified Warning</u>
			H10P 54/00, H10P 54/20, H10P 54/30, H10P 54/40, H10P 54/50 - H10P 54/52, H10P 54/90, H10P 54/922, H10P 54/924 and H10P 54/94. All groups listed in this Warning should be considered in order to perform a complete search.
N	H10P 58/20		Groups H10P 58/20 and H10P 58/22 are incomplete pending reclassification of documents from group H10P 58/00. Groups H10P 58/00, H10P 58/20 and H10P 58/22 should be considered in order to perform a complete search.
N	H10P 72/70		Group H10P 72/70 is impacted by reclassification into groups H10P 72/72, H10P 72/74 and H10P 72/7448 - H10P 72/745. All groups listed in this Warning should be considered in order to perform a complete search.
N	H10P 72/72		Group H10P 72/72 is incomplete pending reclassification of documents from group H10P 72/70. Groups H10P 72/70 and H10P 72/72 should be considered in order to perform a complete search.
N	H10P 72/74		Groups H10P 72/74, H10P 72/7448 and H10P 72/745 are incomplete pending reclassification of documents from group H10P 72/70. All groups listed in this Warning should be considered in order to perform a complete search.
N	H10P 72/7402		Group H10P 72/7402 is impacted by reclassification into groups H10P 72/7404 and H10P 72/7406. Groups H10P 72/7402, H10P 72/7404 and H10P 72/7406 should be considered in order to perform a complete search.
N	H10P 72/7404		Groups H10P 72/7404 and H10P 72/7406 are incomplete pending reclassification of documents from group H10P 72/7402. Groups H10P 72/7402, H10P 72/7404 and H10P 72/7406 should be considered in order to perform a complete search.
N	H10P 90/00		Group H10P 90/00 is impacted by reclassification into groups H10P 90/19, H10P 90/1902,

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<u>Type*</u>	<u>Location</u>	<u>Old Warning</u>	<u>New/Modified Warning</u>
			H10P 90/1904, H10P 90/1906, H10P 90/21 - H10P 90/212, H10P 90/22, H10P 90/24, H10P 56/00 and H10P 10/12. All groups listed in this Warning should be considered in order to perform a complete search.
N	H10P 90/19		Groups H10P 90/19, H10P 90/1902, H10P 90/1904 and H10P 90/1906 are incomplete pending reclassification of documents from group H10P 90/00. All groups listed in this Warning should be considered in order to perform a complete search.
N	H10P 90/1914		Group H10P 90/1914 is incomplete pending reclassification of documents from group H10P 10/12. Group H10P 90/1914 is also impacted by reclassification into groups H10P 10/126, H10P 10/128 - H10P 10/1285, H10P 10/14, H10P 54/52 and H10P 90/1918 - H10P 90/192. All groups listed in this Warning should be considered in order to perform a complete search.
N	H10P 90/1916		Group H10P 90/1916 is incomplete pending reclassification of documents from group H10P 10/12. Group H10P 90/1916 is also impacted by reclassification into groups H10P 10/126, H10P 10/128 - H10P 10/1285, H10P 10/14, H10P 54/52 and H10P 90/1918 - H10P 90/192. All groups listed in this Warning should be considered in order to perform a complete search.
N	H10P 90/1918		Groups H10P 90/1918 and H10P 90/192 are incomplete pending reclassification of documents from groups H10P 90/1914 and H10P 90/1916. All groups listed in this Warning should be considered in order to perform a complete search.
N	H10P 90/21		Groups H10P 90/21 and H10P 90/212 are incomplete pending reclassification of documents from group H10P 90/00. Groups H10P 90/00, H10P 90/21 and H10P 90/212 should be considered in order to perform a complete search.
N	H10P 90/22		Group H10P 90/22 is incomplete pending reclassification of documents

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			from group H10P 90/00. Groups H10P 90/00 and H10P 90/22 should be considered in order to perform a complete search.
N	H10P 90/24		Group H10P 90/24 is incomplete pending reclassification of documents from group H10P 90/00. Groups H10P 90/00 and H10P 90/24 should be considered in order to perform a complete search.
N	H10P 95/00		Group H10P 95/00 is incomplete pending reclassification of documents from groups H10P 10/00 and H10P 50/00. Group H10P 95/00 is also impacted by reclassification into groups H10P 95/02, H10P 95/04, H10P 95/06 - H10P 95/066, H10P 95/08, H10P 95/11 - H10P 95/112, H10P 95/40 - H10P 95/408, H10P 95/50, H10P 95/60, H10P 95/70, H10P 95/80 and H10P 95/90. All groups listed in this Warning should be considered in order to perform a complete search.
N	H10P 95/02		Group H10P 95/02 is incomplete pending reclassification of documents from groups H10P 50/00, H10P 95/00, H10P 95/60 and H10P 95/70. All groups listed in this Warning should be considered in order to perform a complete search.
N	H10P 95/04		Group H10P 95/04 is incomplete pending reclassification of documents from group H10P 95/00. Groups H10P 95/00 and H10P 95/04 should be considered in order to perform a complete search.
N	H10P 95/06		Groups H10P 95/06, H10P 95/064 and H10P 95/066 are incomplete pending reclassification of documents from group H10P 95/00. All groups listed in this Warning should be considered in order to perform a complete search.
N	H10P 95/062		Group H10P 95/062 is incomplete pending reclassification of documents from group H10P 95/00. Group H10P 95/062 is also impacted by reclassification into groups H10P 52/407 and H10P 52/207. All groups listed in this Warning should

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<u>Type*</u>	<u>Location</u>	<u>Old Warning</u>	<u>New/Modified Warning</u>
			be considered in order to perform a complete search.
N	H10P 95/08		Group H10P 95/08 is incomplete pending reclassification of documents from group H10P 95/00. Group H10P 95/08 is also impacted by reclassification into groups H10P 52/209 and H10P 52/409. All groups listed in this Warning should be considered in order to perform a complete search.
N	H10P 95/11		Groups H10P 95/11 and H10P 95/112 are incomplete pending reclassification of documents from group H10P 95/00. Groups H10P 95/00, H10P 95/11 and H10P 95/112 should be considered in order to perform a complete search.
N	H10P 95/40		Group H10P 95/40 is incomplete pending reclassification of documents from groups H10P 36/00 and H10P 95/00. Groups H10P 36/00, H10P 95/00 and H10P 95/40 should be considered in order to perform a complete search.
N	H10P 95/402		Group H10P 95/402 is incomplete pending reclassification of documents from groups H10P 36/03 and H10P 95/00. Groups H10P 36/03, H10P 95/00 and H10P 95/402 should be considered in order to perform a complete search.
N	H10P 95/405		Group H10P 95/405 is incomplete pending reclassification of documents from group H10P 95/00. Groups H10P 95/00 and H10P 95/405 should be considered in order to perform a complete search.
N	H10P 95/408		Group H10P 95/408 is incomplete pending reclassification of documents from group H10P 95/00. Groups H10P 95/00 and H10P 95/408 should be considered in order to perform a complete search.
N	H10P 95/50		Group H10P 95/50 is incomplete pending reclassification of documents from group H10P 95/00. Groups H10P 95/00 and H10P 95/50 should be considered in order to perform a complete search.

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<u>Type*</u>	<u>Location</u>	<u>Old Warning</u>	<u>New/Modified Warning</u>
N	H10P 95/60		Group H10P 95/60 is incomplete pending reclassification of documents from groups H10P 52/00 and H10P 95/00. Group H10P 95/60 is also impacted by reclassification into group H10P 95/02. All groups listed in this Warning should be considered in order to perform a complete search.
N	H10P 95/70		Group H10P 95/70 is incomplete pending reclassification of documents from groups H10P 14/60, H10P 50/00 and H10P 95/00. Group H10P 95/70 is also impacted by reclassification into groups H10P 95/80 and H10P 95/02. All groups listed in this Warning should be considered in order to perform a complete search.
N	H10P 95/80		Group H10P 95/80 is incomplete pending reclassification of documents from groups H10P 14/60, H10P 95/00 and H10P 95/70. All groups listed in this Warning should be considered in order to perform a complete search.
N	H10P 95/90		Group H10P 95/90 is incomplete pending reclassification of documents from group H10P 95/00. Group H10P 95/90 is also impacted by reclassification into group H10P 30/28. Groups H10P 95/00, H10P 95/90 and H10P 30/28 should be considered in order to perform a complete search
N	H10P 95/904		Group H10P 95/904 is impacted by reclassification into group H10P 30/28. Groups H10P 95/904 and H10P 30/28 should be considered in order to perform a complete search.
N	H10P 95/92		Group H10P 95/92 is impacted by reclassification into group H10P 32/173. Groups H10P 95/92 and H10P 32/173 should be considered in order to perform a complete search.

*N = new warning, M = modified warning, D = deleted warning

NOTE: The "Location" column only requires the symbol PRIOR to the location of the warning. No further directions such as "before" or "after" are required.

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C. New, Modified or Deleted Note(s)**SUBCLASS B81B – MICROSTRUCTURAL DEVICES OR SYSTEMS, e.g. MICROMECHANICAL DEVICES**

<u>Type*</u>	<u>Location</u>	<u>Old Note</u>	<u>New/Modified Note</u>
M	B81B	<p>1. This subclass does not cover:</p> <ul style="list-style-type: none"> • purely electrical or electronic devices per se which are covered by section H, e.g. subclass H01L or class H10; • purely optical devices per se which are covered by subclasses G02B or G02F; • essentially two-dimensional structures, e.g. layered products which are covered by subclass B32B; • chemical or biological structures per se which are covered by section C; • structures in atomic scale produced by manipulation of single atoms or molecules, which are covered by group B82B 1/00. 	<p>1. This subclass does not cover:</p> <ul style="list-style-type: none"> • purely electrical or electronic devices per se which are covered by section H, e.g. class H10; • purely optical devices per se which are covered by subclasses G02B or G02F; • essentially two-dimensional structures, e.g. layered products which are covered by subclass B32B; • chemical or biological structures per se which are covered by section C; • structures in atomic scale produced by manipulation of single atoms or molecules, which are covered by group B82B 1/00.

SUBCLASS B81C – PROCESSES OR APPARATUS SPECIALLY ADAPTED FOR THE MANUFACTURE OR TREATMENT OF MICROSTRUCTURAL DEVICES OR SYSTEMS

<u>Type*</u>	<u>Location</u>	<u>Old Note</u>	<u>New/Modified Note</u>
M	B81C	<p>1. This subclass does not cover:</p> <ul style="list-style-type: none"> • processes or apparatus for the manufacture or treatment of purely electrical or electronic devices, which are covered by section H, e.g. group H01L 21/00; • processes or apparatus involving the manipulation of single atoms or molecules, 	<p>1. This subclass does not cover:</p> <ul style="list-style-type: none"> • processes or apparatus for the manufacture or treatment of purely electrical or electronic devices, which are covered by section H, e.g. subclass H10P; • processes or apparatus involving the manipulation of single atoms or molecules,

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<u>Type*</u>	<u>Location</u>	<u>Old Note</u>	<u>New/Modified Note</u>
		which are covered by group B82B 3/00.	which are covered by group B82B 3/00.

SUBCLASS C04B – LIME, MAGNESIA; SLAG; CEMENTS; COMPOSITIONS THEREOF, e.g. MORTARS, CONCRETE OR LIKE BUILDING MATERIALS; ARTIFICIAL STONE; CERAMICS; REFRACTORIES; TREATMENT OF NATURAL STONE

<u>Type*</u>	<u>Location</u>	<u>Old Note</u>	<u>New/Modified Note</u>
M	C04B 2235/96	Codes C04B 2235/96 - C04B 2235/9692 are to be used only if the property is not identified already by an "invention information" symbol, e.g. by a symbol out of subclass H01L indicating that the ceramic is dielectric, piezoelectric or magnetic.	Indexing Codes C04B 2235/96 - C04B 2235/9692 are to be used only if the property is not identified already by an "invention information" symbol, e.g. by a symbol out of subclass H10N indicating that the ceramic is dielectric, piezoelectric or magnetic.

SUBCLASS G09G – ARRANGEMENTS OR CIRCUITS FOR CONTROL OF INDICATING DEVICES USING STATIC MEANS TO PRESENT VARIABLE INFORMATION

<u>Type*</u>	<u>Location</u>	<u>Old Note</u>	<u>New/Modified Note</u>
M	G09G	2. This subclass does not cover the structural details of the indicating devices, such as panels or tubes per se, or assemblies of individual light sources, which are covered by the relevant subclasses, e.g. H01J, H01K, H01L, H10K, G02F, G09F, H05B.	2. This subclass does not cover the structural details of the indicating devices, such as panels or tubes per se, or assemblies of individual light sources, which are covered by the relevant subclasses, e.g. G02F, G09F, H01J, H01K, H05B, H10H, H10K.

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SUBCLASS H02M – APPARATUS FOR CONVERSION BETWEEN AC AND AC, BETWEEN AC AND DC, OR BETWEEN DC AND DC, AND FOR USE WITH MAINS OR SIMILAR POWER SUPPLY SYSTEMS; CONVERSION OF DC OR AC INPUT POWER INTO SURGE OUTPUT POWER; CONTROL OR REGULATION THEREOF

<u>Type*</u>	<u>Location</u>	<u>Old Note</u>	<u>New/Modified Note</u>
M	H02M	1. This subclass covers only circuits or apparatus for the conversion of electric power, or arrangements for control or regulation of such circuits or apparatus. The electrotechnical elements employed are dealt within the appropriate subclasses, e.g. inductors, transformers H01F, capacitors, electrolytic rectifiers H01G, mercury rectifying or other discharge tubes H01J, semiconductor devices H01L, H10 impedance networks or resonant circuit not primarily concerned with the transfer of electric power H03H.	1. This subclass covers only circuits or apparatus for the conversion of electric power, or arrangements for control or regulation of such circuits or apparatus. The electrotechnical elements employed are dealt within the appropriate subclasses, e.g. inductors, transformers H01F, capacitors, electrolytic rectifiers H01G, mercury rectifying or other discharge tubes H01J, semiconductor devices H10, impedance networks or resonant circuit not primarily concerned with the transfer of electric power H03H.

SUBCLASS H02N – ELECTRIC MACHINES NOT OTHERWISE PROVIDED FOR

<u>Type*</u>	<u>Location</u>	<u>Old Note</u>	<u>New/Modified Note</u>
M	H02N	2. Specific provision for generators, motors, or other means for converting between electric and other forms of energy also exists in other subclasses, e.g. in class H10 and subclasses H01L, H01M, H02K, H04R.	2. Specific provision for generators, motors or other means for converting between electric and other forms of energy also exists in other subclasses, e.g. in class H10 and subclasses H01M, H02K, H04R.

SUBCLASS H01L – SEMICONDUCTOR DEVICES NOT COVERED BY CLASS H10

<u>Type*</u>	<u>Location</u>	<u>Old Note</u>	<u>New/Modified Note</u>
D	H01L	1. This subclass is residual to class H10.	<u>Delete</u> entire note

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<u>Type*</u>	<u>Location</u>	<u>Old Note</u>	<u>New/Modified Note</u>
		<p>2. This subclass covers :</p> <p>a. semiconductor devices for rectifying, amplifying, oscillating or switching; their constructional details or arrangements; their assemblies or integrated devices; their manufacture or treatment;</p> <p>b. semiconductor devices sensitive to radiation; their constructional details or arrangements; their assemblies or integrated devices; their manufacture or treatment;</p> <p>c. semiconductor devices for light emission; their constructional details or arrangements; their assemblies or integrated devices; their manufacture or treatment;</p> <p>d. processes or apparatus for the manufacture or treatment of semiconductor or solid-state devices where the type of device is not listed under bullets a to c, above, or not essential;</p> <p>e. constructional details or arrangements of semiconductor or solid-state devices not covered by class H10 and not specific to types of devices listed under bullets a to c, above;</p> <p>f. packaging or assembling of semiconductor or solid-state devices covered by this subclass or by class H10.</p> <p>3. In this subclass, the following terms or expressions are used with the meaning indicated:</p> <ul style="list-style-type: none"> • "wafer" means a slice of semiconductor or crystalline substrate material, which can be modified by impurity diffusion (doping), ion implantation or epitaxy, and whose active surface can be processed into arrays of discrete components or 	

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<u>Type*</u>	<u>Location</u>	<u>Old Note</u>	<u>New/Modified Note</u>
		<p>integrated circuits;</p> <ul style="list-style-type: none"> • "solid state body" means the body of material within which, or at the surface of which, the physical effects characteristic of the device occur; • "electrode" is a region in or on the body of the device (other than the solid state body itself), which exerts an electrical influence on the solid state body, irrespective of whether or not an external electrical connection is made thereto. An electrode may include several portions and the term includes metallic regions which exert influence on the solid state body through an insulating region (e.g. capacitive coupling) and inductive coupling arrangements to the body. The dielectric region in a capacitive arrangement is regarded as part of the electrode. In arrangements including several portions, only those portions which exert an influence on the solid state body by virtue of their shape, size, or disposition or the material of which they are formed are considered to be part of the electrode. The other portions are considered to be "arrangements for conducting electric current to or from the solid state body" or "interconnections between solid state components formed in or on a common substrate", i.e. leads; • "device" means an electric circuit element; where an electric circuit element is one of a plurality of elements formed in or on a common substrate it is referred to as a "component"; • "complete device" is a device in its fully assembled 	

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<u>Type*</u>	<u>Location</u>	<u>Old Note</u>	<u>New/Modified Note</u>
		<p>state which may or may not require further treatment, e.g. electroforming, before it is ready for use but which does not require the addition of further structural units;</p> <ul style="list-style-type: none"> • "parts" includes all structural units which are included in a complete device; • "container" is an enclosure forming part of the complete device and is essentially a solid construction in which the body of the device is placed, or which is formed around the body without forming an intimate layer thereon. An enclosure which consists of one or more layers formed on the body and in intimate contact therewith is referred to as an "encapsulation"; • "integrated circuit" is a device where all components, e.g. diodes or resistors, are built up on a common substrate and form the device including interconnections between the components; • "assembly" of a device is the building up of the device from its constructional units; the term covers the provision of fillings in containers. <p>4. In this subclass, both the process or apparatus for the manufacture or treatment of a device and the device itself are classified, whenever both of these are described sufficiently to be of interest.</p> <p>5. Attention is drawn to Note (3) after the title of section C, which Note indicates to which version of the Periodic Table of chemical elements the IPC refers. In this subclass, the system used is the 8 group system indicated by Roman numerals in the Periodic Table</p>	

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<u>Type*</u>	<u>Location</u>	<u>Old Note</u>	<u>New/Modified Note</u>
		thereunder.	

SUBCLASS H10D – INORGANIC ELECTRIC SEMICONDUCTOR DEVICES

<u>Type*</u>	<u>Location</u>	<u>Old Note</u>	<u>New/Modified Note</u>
N	H10D 64/01		{Processes or apparatus specially adapted for the manufacture or treatment of devices, or parts thereof, covered by class H10, which are generically applicable to these devices are covered by subclass H10P}

SUBCLASS H10P - GENERIC PROCESSES OR APPARATUS FOR THE MANUFACTURE OR TREATMENT OF DEVICES COVERED BY CLASS H10

<u>Type*</u>	<u>Location</u>	<u>Old Note</u>	<u>New/Modified Note</u>
N	H10P		<p>1. This subclass <u>covers</u> processes or apparatus specially adapted for the manufacture or treatment of devices, or parts thereof, covered by class H10, which are generically applicable to these devices.</p> <p>2. Attention is drawn to the following:</p> <p>a. processes or apparatus specially adapted for the manufacture or treatment of devices, or parts thereof, which are covered by a single subclass of H10B - H10N, are classified in the subclass in question. For example, the manufacture of a transistor is classified in subclass H10D;</p> <p>b. processes or apparatus specially adapted for the manufacture or treatment of generic packages, interconnections, connectors or other constructional details of devices, which are covered by subclass H10W, are classified in the subclass in question. For example, the formation of a copper pillar bump connector is classified in subclass H10W.</p>
N	H10P 10/00		1. This group <u>covers</u> bonding of wafers or substrates either

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<u>Type*</u>	<u>Location</u>	<u>Old Note</u>	<u>New/Modified Note</u>
			(i) before the step of making of any interconnections or (ii) before the step of packaging of devices, whichever step comes first. 2. Attention is drawn to the following: • aspects of bonding involving chips, package parts or interconnections, e.g. chip-on-chip bonding or chip-on-wafer bonding, are classified in subclass H10W, e.g. in group H10W 80/00.
N	H10P 30/20		{ When classifying in this group, the classification both in process and material subgroups is mandatory }
N	H10P 32/1408		{ In the range H10P 32/1408 - 32/1414 the main compositional part of the applied layer just before the diffusion step has to be considered for classification }
N	H10P 54/00		This group <u>covers</u> cutting or separating of wafers or substrates having semiconductor or solid-state devices formed, or to be formed, therein or thereon. The cutting may be partial, e.g. for making a groove.
N	H10P 56/00		{ debonding means separation at the bonding interface following a previous bonding step }
N	H10P 58/00		When classifying in this group, any process step involving cutting or separating, which is considered to represent information of interest for search, may also be classified in group H10P 54/00.
N	H10P 70/00		This group <u>does not cover</u> the cleaning of package elements, package parts or other constructional details, e.g. cleaning of packages after moulding, which are covered by the related groups of subclass H10W.
N	H10P 90/00		1. This group <u>covers</u> multistep processes for the preparation of wafers before the subsequent manufacture of semiconductor devices or solid-state devices therein or thereon.

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<u>Type*</u>	<u>Location</u>	<u>Old Note</u>	<u>New/Modified Note</u>
			2. This group <u>does not cover</u> the single-crystal growth of semiconductor ingots, which is covered by subclass C30B.

*N = new note, M = modified note, D = deleted note

NOTE: The "Location" column only requires the symbol PRIOR to the location of the note. No further directions such as "before" or "after" are required.

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D. New, Modified or Deleted Guidance Heading(s)**SUBCLASS H10P - GENERIC PROCESSES OR APPARATUS FOR THE MANUFACTURE OR TREATMENT OF DEVICES COVERED BY CLASS H10**

<u>Type*</u>	<u>Location</u>	<u>Old Guidance Heading</u>	<u>New/Modified Guidance Heading</u>
N	H10P 10/00 – H10P 14/00		Building up of layers, structures or materials
N	H10P 30/00 – H10P 36/00		Modification of layers, structures or materials
N	H10P 50/00 – H10P 58/00		Removal of layers, structures or materials
N	H10P 70/00 – H10P 95/00		Other manufacture or treatment

*N = new guidance heading, M = modified guidance heading, D = deleted guidance heading

NOTES:

- The “Location” column requires the symbol AFTER the guidance heading location. No further directions such as “before” or “after” are required.
- In cases where there may be confusion as to whether a new group falls within the scope of a guidance heading, indicate the guidance heading and whether the group does or does not go with the guidance heading. This can be included in the “Location” column. For example, the guidance heading “Compounds containing carbon together with sulfur, selenium or tellurium with or without hydrogen, halogens, oxygen or nitrogen” encompasses groups C07C 301/00-395/00 only. If a new group C07C 398/00 is proposed and is included in the guidance heading scope, indicate this in the “Location” column as follows: 398/00 to be included under the guidance heading: “Compounds containing carbon together with sulfur, selenium or tellurium with or without hydrogen, halogens, oxygen or nitrogen.”

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2. B. DEFINITIONS QUICK FIX

Symbol	Location of change (e.g., section title)	Existing reference symbol or text	Action; New symbol; New text
H01L	Definition		<u>Delete</u> entire definition
H01L 21/00	Definition		<u>Delete</u> entire definition
H01L21/02002	Definition		<u>Delete</u> entire definition
H01L21/02005	Definition		<u>Delete</u> entire definition
H01L21/0201	Definition		<u>Delete</u> entire definition
H01L21/02013	Definition		<u>Delete</u> entire definition
H01L21/02016	Definition		<u>Delete</u> entire definition
H01L21/02019	Definition		<u>Delete</u> entire definition
H01L21/02021	Definition		<u>Delete</u> entire definition
H01L21/02024	Definition		<u>Delete</u> entire definition
H01L21/02027	Definition		<u>Delete</u> entire definition
H01L21/0203	Definition		<u>Delete</u> entire definition
H01L21/02032	Definition		<u>Delete</u> entire definition
H01L21/02035	Definition		<u>Delete</u> entire definition
H01L21/02041	Definition		<u>Delete</u> entire definition
H01L21/02043	Definition		<u>Delete</u> entire definition
H01L21/02046	Definition		<u>Delete</u> entire definition
H01L21/02052	Definition		<u>Delete</u> entire definition
H01L21/02054	Definition		<u>Delete</u> entire definition
H01L21/02057	Definition		<u>Delete</u> entire definition
H01L21/0206	Definition		<u>Delete</u> entire definition
H01L21/02079	Definition		<u>Delete</u> entire definition
H01L21/02082	Definition		<u>Delete</u> entire definition
H01L21/02087	Definition		<u>Delete</u> entire definition
H01L21/0209	Definition		<u>Delete</u> entire definition
H01L21/02096	Definition		<u>Delete</u> entire definition
H01L21/02098	Definition		<u>Delete</u> entire definition
H01L21/02101	Definition		<u>Delete</u> entire definition
H01L21/02104	Definition		<u>Delete</u> entire definition
H01L21/02107	Definition		<u>Delete</u> entire definition
H01L21/02112	Definition		<u>Delete</u> entire definition
H01L21/02115	Definition		<u>Delete</u> entire definition
H01L21/02118	Definition		<u>Delete</u> entire definition
H01L21/02129	Definition		<u>Delete</u> entire definition
H01L21/02164	Definition		<u>Delete</u> entire definition
H01L21/02167	Definition		<u>Delete</u> entire definition
H01L21/0217	Definition		<u>Delete</u> entire definition
H01L21/02172	Definition		<u>Delete</u> entire definition
H01L21/02175	Definition		<u>Delete</u> entire definition
H01L21/02197	Definition		<u>Delete</u> entire definition
H01L21/022	Definition		<u>Delete</u> entire definition
H01L21/02214	Definition		<u>Delete</u> entire definition
H01L21/02219	Definition		<u>Delete</u> entire definition
H01L21/02227	Definition		<u>Delete</u> entire definition
H01L21/02252	Definition		<u>Delete</u> entire definition

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Symbol	Location of change (e.g., section title)	Existing reference symbol or text	Action; New symbol; New text
H01L21/02255	Definition		Delete entire definition
H01L21/02263	Definition		Delete entire definition
H01L21/02266	Definition		Delete entire definition
H01L21/02269	Definition		Delete entire definition
H01L21/02271	Definition		Delete entire definition
H01L21/0228	Definition		Delete entire definition
H01L21/02288	Definition		Delete entire definition
H01L21/02293	Definition		Delete entire definition
H01L21/02296	Definition		Delete entire definition
H01L21/02299	Definition		Delete entire definition
H01L21/02301	Definition		Delete entire definition
H01L21/02318	Definition		Delete entire definition
H01L21/02321	Definition		Delete entire definition
H01L21/02326	Definition		Delete entire definition
H01L21/02332	Definition		Delete entire definition
H01L21/02334	Definition		Delete entire definition
H01L21/02365	Definition		Delete entire definition
H01L21/02606	Definition		Delete entire definition
H01L21/02658	Definition		Delete entire definition
H01L21/02664	Definition		Delete entire definition
H01L21/02697	Definition		Delete entire definition
H01L21/027	Definition		Delete entire definition
H01L21/0271	Definition		Delete entire definition
H01L21/0273	Definition		Delete entire definition
H01L21/0276	Definition		Delete entire definition
H01L21/0277	Definition		Delete entire definition
H01L21/0278	Definition		Delete entire definition
H01L21/033	Definition		Delete entire definition
H01L21/0331	Definition		Delete entire definition
H01L21/0335	Definition		Delete entire definition
H01L21/0337	Definition		Delete entire definition
H01L21/0338	Definition		Delete entire definition
H01L21/04	Definition		Delete entire definition
H01L21/0405	Definition		Delete entire definition
H01L21/0445	Definition		Delete entire definition
H01L21/046	Definition		Delete entire definition
H01L21/18	Definition		Delete entire definition
H01L21/185	Definition		Delete entire definition
H01L21/187	Definition		Delete entire definition
H01L21/22	Definition		Delete entire definition
H01L21/223	Definition		Delete entire definition
H01L21/225	Definition		Delete entire definition
H01L21/2254	Definition		Delete entire definition
H01L21/228	Definition		Delete entire definition
H01L21/24	Definition		Delete entire definition
H01L21/26	Definition		Delete entire definition
H01L21/263	Definition		Delete entire definition

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Symbol	Location of change (e.g., section title)	Existing reference symbol or text	Action; New symbol; New text
H01L21/265	Definition		Delete entire definition
H01L21/266	Definition		Delete entire definition
H01L21/28	Definition		Delete entire definition
H01L21/28008	Definition		Delete entire definition
H01L21/28017	Definition		Delete entire definition
H01L21/28026	Definition		Delete entire definition
H01L21/28035	Definition		Delete entire definition
H01L21/28052	Definition		Delete entire definition
H01L21/28061	Definition		Delete entire definition
H01L21/28114	Definition		Delete entire definition
H01L21/28123	Definition		Delete entire definition
H01L21/28158	Definition		Delete entire definition
H01L21/28185	Definition		Delete entire definition
H01L21/28211	Definition		Delete entire definition
H01L21/28229	Definition		Delete entire definition
H01L21/283	Definition		Delete entire definition
H01L21/285	Definition		Delete entire definition
H01L21/28525	Definition		Delete entire definition
H01L21/28531	Definition		Delete entire definition
H01L21/288	Definition		Delete entire definition
H01L21/30	Definition		Delete entire definition
H01L21/304	Definition		Delete entire definition
H01L21/3043	Definition		Delete entire definition
H01L21/306	Definition		Delete entire definition
H01L21/30608	Definition		Delete entire definition
H01L21/30621	Definition		Delete entire definition
H01L21/30625	Definition		Delete entire definition
H01L21/3063	Definition		Delete entire definition
H01L21/3065	Definition		Delete entire definition
H01L21/308	Definition		Delete entire definition
H01L21/3085	Definition		Delete entire definition
H01L21/3086	Definition		Delete entire definition
H01L21/3088	Definition		Delete entire definition
H01L21/31	Definition		Delete entire definition
H01L21/3105	Definition		Delete entire definition
H01L21/31051	Definition		Delete entire definition
H01L21/31053	Definition		Delete entire definition
H01L21/31055	Definition		Delete entire definition
H01L21/31056	Definition		Delete entire definition
H01L21/31105	Definition		Delete entire definition
H01L21/31111	Definition		Delete entire definition
H01L21/31116	Definition		Delete entire definition
H01L21/31127	Definition		Delete entire definition
H01L21/31133	Definition		Delete entire definition
H01L21/31144	Definition		Delete entire definition
H01L21/3115	Definition		Delete entire definition
H01L21/3205	Definition		Delete entire definition

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Symbol	Location of change (e.g., section title)	Existing reference symbol or text	Action; New symbol; New text
H01L21/321	Definition		Delete entire definition
H01L21/32105	Definition		Delete entire definition
H01L21/3211	Definition		Delete entire definition
H01L21/32115	Definition		Delete entire definition
H01L21/3212	Definition		Delete entire definition
H01L21/3213	Definition		Delete entire definition
H01L21/32131	Definition		Delete entire definition
H01L21/32132	Definition		Delete entire definition
H01L21/32133	Definition		Delete entire definition
H01L21/32134	Definition		Delete entire definition
H01L21/32136	Definition		Delete entire definition
H01L21/32137	Definition		Delete entire definition
H01L21/32138	Definition		Delete entire definition
H01L21/32139	Definition		Delete entire definition
H01L21/3215	Definition		Delete entire definition
H01L21/322	Definition		Delete entire definition
H01L21/3221	Definition		Delete entire definition
H01L21/3225	Definition		Delete entire definition
H01L21/34	Definition		Delete entire definition
H01L21/38	Definition		Delete entire definition
H01L21/42	Definition		Delete entire definition
H01L21/425	Definition		Delete entire definition
H01L21/426	Definition		Delete entire definition
H01L21/44	Definition		Delete entire definition
H01L21/441	Definition		Delete entire definition
H01L21/445	Definition		Delete entire definition
H01L21/447	Definition		Delete entire definition
H01L21/449	Definition		Delete entire definition
H01L21/46	Definition		Delete entire definition
H01L21/465	Definition		Delete entire definition
H01L21/467	Definition		Delete entire definition
H01L21/469	Definition		Delete entire definition
H01L21/47	Definition		Delete entire definition
H01L21/4763	Definition		Delete entire definition
H01L21/67	Definition		Delete entire definition
H01L21/67017	Definition		Delete entire definition
H01L21/67028	Definition		Delete entire definition
H01L21/67092	Definition		Delete entire definition
H01L21/67103	Definition		Delete entire definition
H01L21/67109	Definition		Delete entire definition
H01L21/67115	Definition		Delete entire definition
H01L21/67121	Definition		Delete entire definition
H01L21/67126	Definition		Delete entire definition
H01L21/67132	Definition		Delete entire definition
H01L21/67138	Definition		Delete entire definition
H01L21/67144	Definition		Delete entire definition
H01L21/6715	Definition		Delete entire definition

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Symbol	Location of change (e.g., section title)	Existing reference symbol or text	Action; New symbol; New text
H01L21/67213	Definition		Delete entire definition
H01L21/67219	Definition		Delete entire definition
H01L21/67225	Definition		Delete entire definition
H01L21/6723	Definition		Delete entire definition
H01L21/67242	Definition		Delete entire definition
H01L21/67276	Definition		Delete entire definition
H01L21/673	Definition		Delete entire definition
H01L21/67333	Definition		Delete entire definition
H01L21/6734	Definition		Delete entire definition
H01L21/67363	Definition		Delete entire definition
H01L21/67366	Definition		Delete entire definition
H01L21/67706	Definition		Delete entire definition
H01L21/67721	Definition		Delete entire definition
H01L21/67742	Definition		Delete entire definition
H01L21/67763	Definition		Delete entire definition
H01L21/67766	Definition		Delete entire definition
H01L21/67784	Definition		Delete entire definition
H01L21/67796	Definition		Delete entire definition
H01L21/68	Definition		Delete entire definition
H01L21/682	Definition		Delete entire definition
H01L21/683	Definition		Delete entire definition
H01L21/6835	Definition		Delete entire definition
H01L21/6836	Definition		Delete entire definition
H01L21/687	Definition		Delete entire definition
H01L21/70	Definition		Delete entire definition
H01L21/7624	Definition		Delete entire definition
H01L21/78	Definition		Delete entire definition
H01L21/7806	Definition		Delete entire definition
H01L21/7813	Definition		Delete entire definition
H01L 22/00	Definition		Delete entire definition
H01L22/10	Definition		Delete entire definition
H01L22/12	Definition		Delete entire definition
H01L22/20	Definition		Delete entire definition
H01L22/24	Definition		Delete entire definition
H01L22/26	Definition		Delete entire definition
H01L22/34	Definition		Delete entire definition
H01L2221/68372	Definition		Delete entire definition

Notes:

Use this Definitions Quick Fix (DQF) table to:

- Delete an entire definition
- Delete an entire section
- Change a reference symbol
- Delete a reference symbol
- Delete text in a References section
- Correct one error in spelling, article use, or verb tense

Otherwise, use the standard template.

Reminder: Never delete F symbol definitions.

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3. REVISION CONCORDANCE LIST (RCL)

Type*	From CPC Symbol (existing)	To CPC Symbol(s)
D	H01L 21/00	<administrative transfer to H10P 95/00>
D	H01L 21/02	<administrative transfer to H10P 95/00>
D	H01L 21/02002	<administrative transfer to H10P 90/00>
D	H01L 21/02005	<administrative transfer to H10P 90/12>
D	H01L 21/02008	<administrative transfer to H10P 90/12>
D	H01L 21/0201	<administrative transfer to H10P 90/12>
D	H01L 21/02013	<administrative transfer to H10P 90/123>
D	H01L 21/02016	<administrative transfer to H10P 90/124>
D	H01L 21/02019	<administrative transfer to H10P 90/126>
D	H01L 21/02021	<administrative transfer to H10P 90/128>
D	H01L 21/02024	<administrative transfer to H10P 90/129>
D	H01L 21/02027	<administrative transfer to H10P 90/14>
D	H01L 21/0203	<administrative transfer to H10P 90/15>
D	H01L 21/02032	<administrative transfer to H10P 90/16>
D	H01L 21/02035	<administrative transfer to H10P 90/18>
D	H01L 21/02041	<administrative transfer to H10P 70/00>
D	H01L 21/02043	<administrative transfer to H10P 70/10>
D	H01L 21/02046	<administrative transfer to H10P 70/12>
D	H01L 21/02049	<administrative transfer to H10P 70/125>
D	H01L 21/02052	<administrative transfer to H10P 70/15>
D	H01L 21/02054	<administrative transfer to H10P 70/18>
D	H01L 21/02057	<administrative transfer to H10P 70/20>
D	H01L 21/0206	<administrative transfer to H10P 70/23>
D	H01L 21/02063	<administrative transfer to H10P 70/234>
D	H01L 21/02065	<administrative transfer to H10P 70/237>
D	H01L 21/02068	<administrative transfer to H10P 70/27>
D	H01L 21/02071	<administrative transfer to H10P 70/273>
D	H01L 21/02074	<administrative transfer to H10P 70/277>
D	H01L 21/02076	<administrative transfer to H10P 70/30>
D	H01L 21/02079	<administrative transfer to H10P 70/40>
D	H01L 21/02082	<administrative transfer to H10P 70/50>
D	H01L 21/02085	<administrative transfer to H10P 70/52>
D	H01L 21/02087	<administrative transfer to H10P 70/54>
D	H01L 21/0209	<administrative transfer to H10P 70/56>
D	H01L 21/02093	<administrative transfer to H10P 70/58>
D	H01L 21/02096	<administrative transfer to H10P 70/60>
D	H01L 21/02098	<administrative transfer to H10P 70/70>
D	H01L 21/02101	<administrative transfer to H10P 70/80>
D	H01L 21/02104	<administrative transfer to H10P 14/00>
D	H01L 21/02107	<administrative transfer to H10P 14/60>
D	H01L 21/02109	<administrative transfer to H10P 14/66>
D	H01L 21/02112	<administrative transfer to H10P 14/68>
D	H01L 21/02115	<administrative transfer to H10P 14/6902>
D	H01L 21/02118	<administrative transfer to H10P 14/683 >
D	H01L 21/0212	<administrative transfer to H10P 14/687 >
D	H01L 21/02123	<administrative transfer to H10P 14/6903>
D	H01L 21/02126	<administrative transfer to H10P 14/6922>

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Type*	<u>From CPC Symbol (existing)</u>	<u>To CPC Symbol(s)</u>
D	H01L 21/02129	<administrative transfer to H10P 14/6923>
D	H01L 21/02131	<administrative transfer to H10P 14/6924>
D	H01L 21/02134	<administrative transfer to H10P 14/6925>
D	H01L 21/02137	<administrative transfer to H10P 14/6926>
D	H01L 21/0214	<administrative transfer to H10P 14/6927>
D	H01L 21/02142	<administrative transfer to H10P 14/6928>
D	H01L 21/02145	<administrative transfer to H10P 14/6929>
D	H01L 21/02148	<administrative transfer to H10P 14/693>
D	H01L 21/0215	<administrative transfer to H10P 14/6931>
D	H01L 21/02153	<administrative transfer to H10P 14/6932>
D	H01L 21/02156	<administrative transfer to H10P 14/6933>
D	H01L 21/02159	<administrative transfer to H10P 14/6934>
D	H01L 21/02161	<administrative transfer to H10P 14/6936>
D	H01L 21/02164	<administrative transfer to H10P 14/69215>
D	H01L 21/02167	<administrative transfer to H10P 14/6905>
D	H01L 21/0217	<administrative transfer to H10P 14/69433>
D	H01L 21/02172	<administrative transfer to H10P 14/6938>
D	H01L 21/02175	<administrative transfer to H10P 14/6939>
D	H01L 21/02178	<administrative transfer to H10P 14/69391>
D	H01L 21/02181	<administrative transfer to H10P 14/69392>
D	H01L 21/02183	<administrative transfer to H10P 14/69393>
D	H01L 21/02186	<administrative transfer to H10P 14/69394>
D	H01L 21/02189	<administrative transfer to H10P 14/69395>
D	H01L 21/02192	<administrative transfer to H10P 14/69396>
D	H01L 21/02194	<administrative transfer to H10P 14/69397>
D	H01L 21/02197	<administrative transfer to H10P 14/69398>
D	H01L 21/022	<administrative transfer to H10P 14/662>
D	H01L 21/02203	<administrative transfer to H10P 14/665>
D	H01L 21/02205	<administrative transfer to H10P 14/668>
D	H01L 21/02208	<administrative transfer to H10P 14/6681>
D	H01L 21/02211	<administrative transfer to H10P 14/6682>
D	H01L 21/02214	<administrative transfer to H10P 14/6684>
D	H01L 21/02216	<administrative transfer to H10P 14/6686>
D	H01L 21/02219	<administrative transfer to H10P 14/6687>
D	H01L 21/02222	<administrative transfer to H10P 14/6689>
D	H01L 21/02225	<administrative transfer to H10P 14/63>
D	H01L 21/02227	<administrative transfer to H10P 14/6302>
D	H01L 21/0223	<administrative transfer to H10P 14/6304>
D	H01L 21/02233	<administrative transfer to H10P 14/6306>
D	H01L 21/02236	<administrative transfer to H10P 14/6308>
D	H01L 21/02238	<administrative transfer to H10P 14/6309>
D	H01L 21/02241	<administrative transfer to H10P 14/6312>
D	H01L 21/02244	<administrative transfer to H10P 14/6314>
D	H01L 21/02247	<administrative transfer to H10P 14/6316>
D	H01L 21/02249	<administrative transfer to H10P 14/6318>
D	H01L 21/02252	<administrative transfer to H10P 14/6319>
D	H01L 21/02255	<administrative transfer to H10P 14/6322>
D	H01L 21/02258	<administrative transfer to H10P 14/6324>
D	H01L 21/0226	<administrative transfer to H10P 14/6326>

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Type*	<u>From CPC Symbol (existing)</u>	<u>To CPC Symbol(s)</u>
D	H01L 21/02263	<administrative transfer to H10P 14/6328>
D	H01L 21/02266	<administrative transfer to H10P 14/6329>
D	H01L 21/02269	<administrative transfer to H10P 14/6332>
D	H01L 21/02271	<administrative transfer to H10P 14/6334>
D	H01L 21/02274	<administrative transfer to H10P 14/6336>
D	H01L 21/02277	<administrative transfer to H10P 14/6338>
D	H01L 21/0228	<administrative transfer to H10P 14/6339>
D	H01L 21/02282	<administrative transfer to H10P 14/6342>
D	H01L 21/02285	<administrative transfer to H10P 14/6344>
D	H01L 21/02288	<administrative transfer to H10P 14/6346>
D	H01L 21/0229	<administrative transfer to H10P 14/6348>
D	H01L 21/02293	<administrative transfer to H10P 14/6349>
D	H01L 21/02296	<administrative transfer to H10P 14/65>
D	H01L 21/02299	<administrative transfer to H10P 14/6502>
D	H01L 21/02301	<administrative transfer to H10P 14/6504>
D	H01L 21/02304	<administrative transfer to H10P 14/6506>
D	H01L 21/02307	<administrative transfer to H10P 14/6508>
D	H01L 21/0231	<administrative transfer to H10P 14/6509>
D	H01L 21/02312	<administrative transfer to H10P 14/6512>
D	H01L 21/02315	<administrative transfer to H10P 14/6514>
D	H01L 21/02318	<administrative transfer to H10P 14/6516>
D	H01L 21/02321	<administrative transfer to H10P 14/6518>
D	H01L 21/02323	<administrative transfer to H10P 14/6519>
D	H01L 21/02326	<administrative transfer to H10P 14/6522>
D	H01L 21/02329	<administrative transfer to H10P 14/6524>
D	H01L 21/02332	<administrative transfer to H10P 14/6526>
D	H01L 21/02334	<administrative transfer to H10P 14/6528>
D	H01L 21/02337	<administrative transfer to H10P 14/6529>
D	H01L 21/0234	<administrative transfer to H10P 14/6532>
D	H01L 21/02343	<administrative transfer to H10P 14/6534>
D	H01L 21/02345	<administrative transfer to H10P 14/6536>
D	H01L 21/02348	<administrative transfer to H10P 14/6538>
D	H01L 21/02351	<administrative transfer to H10P 14/6539>
D	H01L 21/02354	<administrative transfer to H10P 14/6542>
D	H01L 21/02356	<administrative transfer to H10P 14/6544>
D	H01L 21/02359	<administrative transfer to H10P 14/6546>
D	H01L 21/02362	<administrative transfer to H10P 14/6548>
D	H01L 21/02365	<administrative transfer to H10P 14/20>
D	H01L 21/02367	<administrative transfer to H10P 14/29>
D	H01L 21/0237	<administrative transfer to H10P 14/2901>
D	H01L 21/02373	<administrative transfer to H10P 14/2902>
D	H01L 21/02376	<administrative transfer to H10P 14/2903>
D	H01L 21/02378	<administrative transfer to H10P 14/2904>
D	H01L 21/02381	<administrative transfer to H10P 14/2905>
D	H01L 21/02384	<administrative transfer to H10P 14/2906>
D	H01L 21/02387	<administrative transfer to H10P 14/2907>
D	H01L 21/02389	<administrative transfer to H10P 14/2908>
D	H01L 21/02392	<administrative transfer to H10P 14/2909>
D	H01L 21/02395	<administrative transfer to H10P 14/2911>

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Type*	From CPC Symbol (existing)	To CPC Symbol(s)
D	H01L 21/02398	<administrative transfer to H10P 14/2912>
D	H01L 21/024	<administrative transfer to H10P 14/2913>
D	H01L 21/02403	<administrative transfer to H10P 14/2914>
D	H01L 21/02406	<administrative transfer to H10P 14/2915>
D	H01L 21/02409	<administrative transfer to H10P 14/2916>
D	H01L 21/02411	<administrative transfer to H10P 14/2917>
D	H01L 21/02414	<administrative transfer to H10P 14/2918>
D	H01L 21/02417	<administrative transfer to H10P 14/2919>
D	H01L 21/0242	<administrative transfer to H10P 14/2921>
D	H01L 21/02422	<administrative transfer to H10P 14/2922>
D	H01L 21/02425	<administrative transfer to H10P 14/2923>
D	H01L 21/02428	<administrative transfer to H10P 14/2924>
D	H01L 21/0243	<administrative transfer to H10P 14/2925>
D	H01L 21/02433	<administrative transfer to H10P 14/2926>
D	H01L 21/02436	<administrative transfer to H10P 14/32>
D	H01L 21/02439	<administrative transfer to H10P 14/3202>
D	H01L 21/02441	<administrative transfer to H10P 14/3204>
D	H01L 21/02444	<administrative transfer to H10P 14/3206>
D	H01L 21/02447	<administrative transfer to H10P 14/3208>
D	H01L 21/0245	<administrative transfer to H10P 14/3211>
D	H01L 21/02452	<administrative transfer to H10P 14/3212>
D	H01L 21/02455	<administrative transfer to H10P 14/3214>
D	H01L 21/02458	<administrative transfer to H10P 14/3216>
D	H01L 21/02461	<administrative transfer to H10P 14/3218>
D	H01L 21/02463	<administrative transfer to H10P 14/3221>
D	H01L 21/02466	<administrative transfer to H10P 14/3222>
D	H01L 21/02469	<administrative transfer to H10P 14/3224>
D	H01L 21/02472	<administrative transfer to H10P 14/3226>
D	H01L 21/02474	<administrative transfer to H10P 14/3228>
D	H01L 21/02477	<administrative transfer to H10P 14/3231>
D	H01L 21/0248	<administrative transfer to H10P 14/3232>
D	H01L 21/02483	<administrative transfer to H10P 14/3234>
D	H01L 21/02485	<administrative transfer to H10P 14/3236>
D	H01L 21/02488	<administrative transfer to H10P 14/3238>
D	H01L 21/02491	<administrative transfer to H10P 14/3241>
D	H01L 21/02494	<administrative transfer to H10P 14/3242>
D	H01L 21/02496	<administrative transfer to H10P 14/3244>
D	H01L 21/02499	<administrative transfer to H10P 14/3246>
D	H01L 21/02502	<administrative transfer to H10P 14/3248>
D	H01L 21/02505	<administrative transfer to H10P 14/3251>
D	H01L 21/02507	<administrative transfer to H10P 14/3252>
D	H01L 21/0251	<administrative transfer to H10P 14/3254>
D	H01L 21/02513	<administrative transfer to H10P 14/3256>
D	H01L 21/02516	<administrative transfer to H10P 14/3258>
D	H01L 21/02518	<administrative transfer to H10P 14/34>
D	H01L 21/02521	<administrative transfer to H10P 14/3402>
D	H01L 21/02524	<administrative transfer to H10P 14/3404>
D	H01L 21/02527	<administrative transfer to H10P 14/3406>
D	H01L 21/02529	<administrative transfer to H10P 14/3408>

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Type*	<u>From CPC Symbol (existing)</u>	<u>To CPC Symbol(s)</u>
D	H01L 21/02532	<administrative transfer to H10P 14/3411>
D	H01L 21/02535	<administrative transfer to H10P 14/3412>
D	H01L 21/02538	<administrative transfer to H10P 14/3414>
D	H01L 21/0254	<administrative transfer to H10P 14/3416>
D	H01L 21/02543	<administrative transfer to H10P 14/3418>
D	H01L 21/02546	<administrative transfer to H10P 14/3421>
D	H01L 21/02549	<administrative transfer to H10P 14/3422>
D	H01L 21/02551	<administrative transfer to H10P 14/3424>
D	H01L 21/02554	<administrative transfer to H10P 14/3426>
D	H01L 21/02557	<administrative transfer to H10P 14/3428>
D	H01L 21/0256	<administrative transfer to H10P 14/3431>
D	H01L 21/02562	<administrative transfer to H10P 14/3432>
D	H01L 21/02565	<administrative transfer to H10P 14/3434>
D	H01L 21/02568	<administrative transfer to H10P 14/3436>
D	H01L 21/0257	<administrative transfer to H10P 14/3438>
D	H01L 21/02573	<administrative transfer to H10P 14/3441>
D	H01L 21/02576	<administrative transfer to H10P 14/3442>
D	H01L 21/02579	<administrative transfer to H10P 14/3444>
D	H01L 21/02581	<administrative transfer to H10P 14/3446>
D	H01L 21/02584	<administrative transfer to H10P 14/3448>
D	H01L 21/02587	<administrative transfer to H10P 14/3451>
D	H01L 21/0259	<administrative transfer to H10P 14/3452>
D	H01L 21/02592	<administrative transfer to H10P 14/3454>
D	H01L 21/02595	<administrative transfer to H10P 14/3456>
D	H01L 21/02598	<administrative transfer to H10P 14/3458>
D	H01L 21/02601	<administrative transfer to H10P 14/3461>
D	H01L 21/02603	<administrative transfer to H10P 14/3462>
D	H01L 21/02606	<administrative transfer to H10P 14/3464>
D	H01L 21/02609	<administrative transfer to H10P 14/3466>
D	H01L 21/02612	<administrative transfer to H10P 14/20>
D	H01L 21/02614	<administrative transfer to H10P 14/203>
D	H01L 21/02617	<administrative transfer to H10P 14/20>
D	H01L 21/0262	<administrative transfer to H10P 14/24>
D	H01L 21/02623	<administrative transfer to H10P 14/26>
D	H01L 21/02625	<administrative transfer to H10P 14/263>
D	H01L 21/02628	<administrative transfer to H10P 14/265>
D	H01L 21/02631	<administrative transfer to H10P 14/22>
D	H01L 21/02634	<administrative transfer to H10P 14/20>
D	H01L 21/02636	<administrative transfer to H10P 14/27>
D	H01L 21/02639	<administrative transfer to H10P 14/271>
D	H01L 21/02642	<administrative transfer to H10P 14/272>
D	H01L 21/02645	<administrative transfer to H10P 14/274>
D	H01L 21/02647	<administrative transfer to H10P 14/276>
D	H01L 21/0265	<administrative transfer to H10P 14/278>
D	H01L 21/02653	<administrative transfer to H10P 14/279>
D	H01L 21/02656	<administrative transfer to H10P 14/20>
D	H01L 21/02658	<administrative transfer to H10P 14/36>
D	H01L 21/02661	<administrative transfer to H10P 14/3602>
D	H01L 21/02664	<administrative transfer to H10P 14/38>

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Type*	From CPC Symbol (existing)	To CPC Symbol(s)
D	H01L 21/02667	<administrative transfer to H10P 14/3802>
D	H01L 21/02669	<administrative transfer to H10P 14/3804>
D	H01L 21/02672	<administrative transfer to H10P 14/3806>
D	H01L 21/02675	<administrative transfer to H10P 14/3808>
D	H01L 21/02678	<administrative transfer to H10P 14/381>
D	H01L 21/0268	<administrative transfer to H10P 14/3812>
D	H01L 21/02683	<administrative transfer to H10P 14/3814>
D	H01L 21/02686	<administrative transfer to H10P 14/3816>
D	H01L 21/02689	<administrative transfer to H10P 14/3818>
D	H01L 21/02691	<administrative transfer to H10P 14/382>
D	H01L 21/02694	<administrative transfer to H10P 14/3822>
D	H01L 21/02697	<administrative transfer to H10P 14/40>
D	H01L 21/027	<administrative transfer to H10P 76/00>
D	H01L 21/0271	<administrative transfer to H10P 76/20>
D	H01L 21/0272	<administrative transfer to H10P 76/202>
D	H01L 21/0273	<administrative transfer to H10P 76/204>
D	H01L 21/0274	<administrative transfer to H10P 76/2041>
D	H01L 21/0275	<administrative transfer to H10P 76/2042>
D	H01L 21/0276	<administrative transfer to H10P 76/2043>
D	H01L 21/0277	<administrative transfer to H10P 76/2045>
D	H01L 21/0278	<administrative transfer to H10P 76/2047>
D	H01L 21/0279	<administrative transfer to H10P 76/2049>
D	H01L 21/033	<administrative transfer to H10P 76/40>
D	H01L 21/0331	<administrative transfer to H10P 76/403>
D	H01L 21/0332	<administrative transfer to H10P 76/405>
D	H01L 21/0334	<administrative transfer to H10P 76/408>
D	H01L 21/0335	<administrative transfer to H10P 76/4083>
D	H01L 21/0337	<administrative transfer to H10P 76/4085>
D	H01L 21/0338	<administrative transfer to H10P 76/4088>
D	H01L 21/04	<administrative transfer to H10P 95/00>
D	H01L 21/0405	<administrative transfer to H10D 62/8303>
D	H01L 21/041	<administrative transfer to H10P 95/92>
D	H01L 21/0415	<administrative transfer to H10P 30/2044>
D	H01L 21/042	<administrative transfer to H10P 50/00>
D	H01L 21/0425	<administrative transfer to H10D 64/0114>
D	H01L 21/043	<administrative transfer to H10D 64/0114>
D	H01L 21/0435	<administrative transfer to H10D 64/0122>
D	H01L 21/044	<administrative transfer to H10D 64/01364>
D	H01L 21/0445	<administrative transfer to H10D 62/8325>
D	H01L 21/045	<administrative transfer to H10D 62/8325>
D	H01L 21/0455	<administrative transfer to H10P 32/172>
D	H01L 21/046	<administrative transfer to H10P 30/2042 and H10P 30/21 simultaneously>
D	H01L 21/0465	<administrative transfer to H10P 30/22>
D	H01L 21/047	<administrative transfer to H10P 30/2042 and H10P 30/222 simultaneously>
D	H01L 21/0475	<administrative transfer to H10P 50/00>
D	H01L 21/048	<administrative transfer to H10D 64/0115>
D	H01L 21/0485	<administrative transfer to H10D 64/0115>

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Type*	From CPC Symbol (existing)	To CPC Symbol(s)
D	H01L 21/049	<administrative transfer to H10D 64/01366>
D	H01L 21/0495	<administrative transfer to H10D 64/0123>
D	H01L 21/18	<administrative transfer to H10P 10/00>
D	H01L 21/182	<administrative transfer to H10P 14/3824>
D	H01L 21/185	<administrative transfer to H10P 10/12>
D	H01L 21/187	<administrative transfer to H10P 10/128>
D	H01L 21/20	<administrative transfer to H10P 14/20>
D	H01L 21/2003	<administrative transfer to H10P 14/29>
D	H01L 21/2007	<administrative transfer to H10P 90/1914>
D	H01L 21/2011	<administrative transfer to H10P 10/14>
D	H01L 21/2015	<administrative transfer to H10P 14/29>
D	H01L 21/22	<administrative transfer to H10P 32/00>
D	H01L 21/2205	<administrative transfer to H10P 32/15>
D	H01L 21/221	<administrative transfer to H10P 32/18 and H10P 32/171 simultaneously>
D	H01L 21/2215	<administrative transfer to H10P 32/18 and H10P 32/174 simultaneously>
D	H01L 21/222	<administrative transfer to H10P 32/185>
D	H01L 21/2225	<administrative transfer to H10P 32/19>
D	H01L 21/223	<administrative transfer to H10P 32/12 and H10P 32/171 simultaneously >
D	H01L 21/2233	<administrative transfer to H10P 32/12 and H10P 32/174 simultaneously>
D	H01L 21/2236	<administrative transfer to H10P 32/1204>
D	H01L 21/225	<administrative transfer to H10P 32/14>
D	H01L 21/2251	<administrative transfer to H10P 32/14 and H10P 32/171 simultaneously>
D	H01L 21/2252	<administrative transfer to H10P 32/1404 and H10P 32/171 simultaneously>
D	H01L 21/2253	<administrative transfer to H10P 32/1406 and H10P 32/171 simultaneously >
D	H01L 21/2254	<administrative transfer to H10P 32/1408 and H10P 32/171 simultaneously >
D	H01L 21/2255	<administrative transfer to H10P 32/141 and H10P 32/171 simultaneously >
D	H01L 21/2256	<administrative transfer to H10P 32/1412 and H10P 32/171 simultaneously >
D	H01L 21/2257	<administrative transfer to H10P 32/1414 and H10P 32/171 simultaneously >
D	H01L 21/2258	<administrative transfer to H10P 32/14 and H10P 32/174 simultaneously>
D	H01L 21/228	<administrative transfer to H10P 32/16>
D	H01L 21/24	<administrative transfer to H10P 95/50>
D	H01L 21/242	<administrative transfer to H10P 95/50>
D	H01L 21/244	<administrative transfer to H10P 95/50>
D	H01L 21/246	<administrative transfer to H10P 95/50>
D	H01L 21/248	<administrative transfer to H10P 95/50>
D	H01L 21/26	<administrative transfer to H10P 34/00>
D	H01L 21/2605	<administrative transfer to H10P 34/10>

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Type*	From CPC Symbol (existing)	To CPC Symbol(s)
D	H01L 21/261	<administrative transfer to H10P 34/20>
D	H01L 21/263	<administrative transfer to H10P 34/40>
D	H01L 21/2633	<administrative transfer to H10P 50/20>
D	H01L 21/2636	<administrative transfer to H10P 95/90>
D	H01L 21/265	<administrative transfer to H10P 30/20>
D	H01L 21/26506	<administrative transfer to H10P 30/204 and H10P 30/208 simultaneously>
D	H01L 21/26513	<administrative transfer to H10P 30/204 and H10P 30/21 simultaneously>
D	H01L 21/2652	<administrative transfer to H10P 30/204 and H10P 30/212 simultaneously>
D	H01L 21/26526	<administrative transfer to H10P 30/204 and H10P 30/214 simultaneously>
D	H01L 21/26533	<administrative transfer to H10P 30/209>
D	H01L 21/2654	<administrative transfer to H10P 30/206 and H10P 30/208 simultaneously>
D	H01L 21/26546	<administrative transfer to H10P 30/206 and H10P 30/21 simultaneously>
D	H01L 21/26553	<administrative transfer to H10P 30/206 and H10P 30/212 simultaneously>
D	H01L 21/2656	<administrative transfer to H10P 30/206 and H10P 30/218 simultaneously>
D	H01L 21/26566	<administrative transfer to H10P 30/224>
D	H01L 2021/26573	<administrative transfer to H10P 30/2044>
D	H01L 21/2658	<administrative transfer to H10P 30/225>
D	H01L 21/26586	<administrative transfer to H10P 30/222>
D	H01L 21/26593	<administrative transfer to H10P 30/226>
D	H01L 21/266	<administrative transfer to H10P 30/22>
D	H01L 21/268	<administrative transfer to H10P 34/42>
D	H01L 21/2683	<administrative transfer to H10P 34/42>
D	H01L 21/2686	<administrative transfer to H10P 34/422>
D	H01L 21/28	<administrative transfer to H10D 64/011>
D	H01L 21/28008	<administrative transfer to H10D 64/013>
D	H01L 21/28017	<administrative transfer to H10D 64/01302>
D	H01L 21/28026	<administrative transfer to H10D 64/01304>
D	H01L 21/28035	<administrative transfer to H10D 64/01306>
D	H01L 21/28044	<administrative transfer to H10D 64/01308>
D	H01L 21/28052	<administrative transfer to H10D 64/0131>
D	H01L 21/28061	<administrative transfer to H10D 64/01312>
D	H01L 21/2807	<administrative transfer to H10D 64/01314>
D	H01L 21/28079	<administrative transfer to H10D 64/01316>
D	H01L 21/28088	<administrative transfer to H10D 64/01318>
D	H01L 21/28097	<administrative transfer to H10D 64/0132>
D	H01L 21/28105	<administrative transfer to H10D 64/01322>
D	H01L 21/28114	<administrative transfer to H10D 64/01324>
D	H01L 21/28123	<administrative transfer to H10D 64/01326>
D	H01L 21/28132	<administrative transfer to H10D 64/01328>
D	H01L 21/28141	<administrative transfer to H10D 64/01334>
D	H01L 21/2815	<administrative transfer to H10D 64/0133>

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Type*	From CPC Symbol (existing)	To CPC Symbol(s)
D	H01L 21/28158	<administrative transfer to H10D 64/01332>
D	H01L 21/28167	<administrative transfer to H10D 64/01336>
D	H01L 21/28176	<administrative transfer to H10D 64/01338>
D	H01L 21/28185	<administrative transfer to H10D 64/0134>
D	H01L 21/28194	<administrative transfer to H10D 64/01342>
D	H01L 21/28202	<administrative transfer to H10D 64/01344>
D	H01L 21/28211	<administrative transfer to H10D 64/01346>
D	H01L 21/2822	<administrative transfer to H10D 64/01348>
D	H01L 21/28229	<administrative transfer to H10D 64/0135>
D	H01L 21/28238	<administrative transfer to H10D 64/01352>
D	H01L 21/28247	<administrative transfer to H10D 64/01354>
D	H01L 21/28255	<administrative transfer to H10D 64/01356>
D	H01L 21/28264	<administrative transfer to H10D 64/01358>
D	H01L 21/283	<administrative transfer to H10P 14/40>
D	H01L 21/285	<administrative transfer to H10P 14/42>
D	H01L 21/28506	<administrative transfer to H10P 14/40>
D	H01L 21/28512	<administrative transfer to H10D 64/0111>
D	H01L 21/28518	<administrative transfer to H10D 64/0112>
D	H01L 21/28525	<administrative transfer to H10D 64/0113>
D	H01L 21/28531	<administrative transfer to H10D 64/0113>
D	H01L 21/28537	<administrative transfer to H10D 64/0121>
D	H01L 21/2855	<administrative transfer to H10P 14/44>
D	H01L 21/28556	<administrative transfer to H10P 14/43>
D	H01L 21/28562	<administrative transfer to H10P 14/432>
D	H01L 21/28568	<administrative transfer to H10P 14/418>
D	H01L 21/28575	<administrative transfer to H10D 64/0116>
D	H01L 21/28581	<administrative transfer to H10D 64/0124>
D	H01L 21/28587	<administrative transfer to H10D 64/0125>
D	H01L 21/28593	<administrative transfer to H10D 64/0126>
D	H01L 21/288	<administrative transfer to H10P 14/46>
D	H01L 21/2885	<administrative transfer to H10P 14/47>
D	H01L 21/30	<administrative transfer to H10P 95/00>
D	H01L 21/3003	<administrative transfer to H10P 95/94>
D	H01L 21/3006	<administrative transfer to H10P 95/94>
D	H01L 21/302	<administrative transfer to H10P 50/00>
D	H01L 21/304	<administrative transfer to H10P 52/00>
D	H01L 21/3043	<administrative transfer to H10P 52/00>
D	H01L 21/3046	<administrative transfer to H10P 52/00>
D	H01L 21/306	<administrative transfer to H10P 50/00>
D	H01L 21/30604	<administrative transfer to H10P 50/642>
D	H01L 21/30608	<administrative transfer to H10P 50/644>
D	H01L 21/30612	<administrative transfer to H10P 50/646>
D	H01L 21/30617	<administrative transfer to H10P 50/648>
D	H01L 21/30621	<administrative transfer to H10P 50/246>
D	H01L 21/30625	<administrative transfer to H10P 52/402>
D	H01L 21/3063	<administrative transfer to H10P 50/613>
D	H01L 21/30635	<administrative transfer to H10P 50/617>
D	H01L 21/3065	<administrative transfer to H10P 50/242>
D	H01L 21/30655	<administrative transfer to H10P 50/244>

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Type*	From CPC Symbol (existing)	To CPC Symbol(s)
D	H01L 21/308	<administrative transfer to H10P 50/691>
D	H01L 21/3081	<administrative transfer to H10P 50/692>
D	H01L 21/3083	<administrative transfer to H10P 50/693>
D	H01L 21/3085	<administrative transfer to H10P 50/694>
D	H01L 21/3086	<administrative transfer to H10P 50/695>
D	H01L 21/3088	<administrative transfer to H10P 50/696>
D	H01L 21/31	<administrative transfer to H10P 14/60>
D	H01L 21/3105	<administrative transfer to H10P 95/00>
D	H01L 21/31051	<administrative transfer to H10P 95/06>
D	H01L 21/31053	<administrative transfer to H10P 95/062>
D	H01L 21/31055	<administrative transfer to H10P 95/064>
D	H01L 21/31056	<administrative transfer to H10P 95/066>
D	H01L 21/31058	<administrative transfer to H10P 95/08>
D	H01L 21/311	<administrative transfer to H10P 50/28>
D	H01L 21/31105	<administrative transfer to H10P 50/282>
D	H01L 21/31111	<administrative transfer to H10P 50/283>
D	H01L 21/31116	<administrative transfer to H10P 50/283>
D	H01L 21/31122	<administrative transfer to H10P 50/285>
D	H01L 21/31127	<administrative transfer to H10P 50/286>
D	H01L 21/31133	<administrative transfer to H10P 50/287>
D	H01L 21/31138	<administrative transfer to H10P 50/287>
D	H01L 21/31144	<administrative transfer to H10P 50/73>
D	H01L 21/3115	<administrative transfer to H10P 32/20>
D	H01L 21/31155	<administrative transfer to H10P 30/40>
D	H01L 21/32	<administrative transfer to H10P 14/61>
D	H01L 21/3205	<administrative transfer to H10P 14/40>
D	H01L 21/32051	<administrative transfer to H10P 14/412>
D	H01L 21/32053	<administrative transfer to H10P 14/414>
D	H01L 21/32055	<administrative transfer to H10P 14/416>
D	H01L 21/32056	<administrative transfer to H10P 14/40>
D	H01L 21/32058	<administrative transfer to H10P 14/40>
D	H01L 21/321	<administrative transfer to H10P 95/00>
D	H01L 21/32105	<administrative transfer to H10P 14/6308>
D	H01L 21/3211	<administrative transfer to H10P 14/6316>
D	H01L 21/32115	<administrative transfer to H10P 95/04>
D	H01L 21/3212	<administrative transfer to H10P 52/403>
D	H01L 21/32125	<administrative transfer to H10P 52/203>
D	H01L 21/3213	<administrative transfer to H10P 50/00>
D	H01L 21/32131	<administrative transfer to H10P 50/262>
D	H01L 21/32132	<administrative transfer to H10P 50/263>
D	H01L 21/32133	<administrative transfer to H10P 50/264>
D	H01L 21/32134	<administrative transfer to H10P 50/667>
D	H01L 21/32135	<administrative transfer to H10P 50/266>
D	H01L 21/32136	<administrative transfer to H10P 50/267>
D	H01L 21/32137	<administrative transfer to H10P 50/268>
D	H01L 21/32138	<administrative transfer to H10P 50/269>
D	H01L 21/32139	<administrative transfer to H10P 50/71>
D	H01L 21/3215	<administrative transfer to H10P 32/30>
D	H01L 21/32155	<administrative transfer to H10P 32/302>

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Type*	<u>From CPC Symbol (existing)</u>	<u>To CPC Symbol(s)</u>
D	H01L 21/322	<administrative transfer to H10P 36/00>
D	H01L 21/3221	<administrative transfer to H10P 36/03>
D	H01L 21/3223	<administrative transfer to H10P 95/405>
D	H01L 21/3225	<administrative transfer to H10P 36/20>
D	H01L 21/3226	<administrative transfer to H10P 36/07>
D	H01L 21/3228	<administrative transfer to H10P 95/408>
D	H01L 21/324	<administrative transfer to H10P 95/90>
D	H01L 21/3242	<administrative transfer to H10P 95/902>
D	H01L 21/3245	<administrative transfer to H10P 95/904>
D	H01L 21/3247	<administrative transfer to H10P 95/906>
D	H01L 21/326	<administrative transfer to H10P 95/80>
D	H01L 21/34	<administrative transfer to H10P 10/00>
D	H01L 21/38	<administrative transfer to H10P 32/00>
D	H01L 21/383	<administrative transfer to H10P 32/12 and H10P 32/17 simultaneously>
D	H01L 21/385	<administrative transfer to H10P 32/14 and H10P 32/17 simultaneously >
D	H01L 21/388	<administrative transfer to H10P 32/16 and H10P 32/17 simultaneously >
D	H01L 21/40	<administrative transfer to H10P 95/50>
D	H01L 21/42	<administrative transfer to H10P 34/00>
D	H01L 21/423	<administrative transfer to H10P 34/40>
D	H01L 21/425	<administrative transfer to H10P 30/202>
D	H01L 21/426	<administrative transfer to H10P 30/22>
D	H01L 21/428	<administrative transfer to H10P 34/42>
D	H01L 21/44	<administrative transfer to H10D 64/011>
D	H01L 21/441	<administrative transfer to H10D 64/011>
D	H01L 21/443	<administrative transfer to H10D 64/011>
D	H01L 21/445	<administrative transfer to H10P 14/47>
D	H01L 21/447	<administrative transfer to H10P 14/40 >
D	H01L 21/449	<administrative transfer to H10P 14/40>
D	H01L 21/46	<administrative transfer to H10P 95/00>
D	H01L 21/461	<administrative transfer to H10P 50/00>
D	H01L 21/463	<administrative transfer to H10P 52/00, H10P 54/00 and H10P 95/60 simultaneously>
D	H01L 21/465	<administrative transfer to H10P 50/20, H10P 52/00 and H10P 95/70 simultaneously>
D	H01L 21/467	<administrative transfer to H10P 50/69>
D	H01L 21/469	<administrative transfer to H10P 14/60>
D	H01L 21/47	<administrative transfer to H10P 14/68>
D	H01L 21/471	<administrative transfer to H10P 14/69>
D	H01L 21/473	<administrative transfer to H10P 14/692 >
D	H01L 21/475	<administrative transfer to H10P 14/61>
D	H01L 21/4757	<administrative transfer to H10P 50/28>
D	H01L 21/47573	<administrative transfer to H10P 50/282>
D	H01L 21/47576	<administrative transfer to H10P 30/40>
D	H01L 21/4763	<administrative transfer to H10P 14/40>
D	H01L 21/47635	<administrative transfer to H10P 95/00>
D	H01L 21/477	<administrative transfer to H10P 95/90>

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Type*	From CPC Symbol (existing)	To CPC Symbol(s)
D	H01L 21/479	<administrative transfer to H10P 95/80>
D	H01L 21/62	<administrative transfer to H10P 95/00>
D	H01L 21/64	<administrative transfer to H10P 95/00>
D	H01L 21/67	<administrative transfer to H10P 72/00>
D	H01L 21/67005	<administrative transfer to H10P 72/00>
D	H01L 21/67011	<administrative transfer to H10P 72/04>
D	H01L 21/67017	<administrative transfer to H10P 72/0402>
D	H01L 21/67023	<administrative transfer to H10P 72/0404>
D	H01L 21/67028	<administrative transfer to H10P 72/0406>
D	H01L 21/67034	<administrative transfer to H10P 72/0408>
D	H01L 21/6704	<administrative transfer to H10P 72/0411>
D	H01L 21/67046	<administrative transfer to H10P 72/0412>
D	H01L 21/67051	<administrative transfer to H10P 72/0414>
D	H01L 21/67057	<administrative transfer to H10P 72/0416>
D	H01L 21/67063	<administrative transfer to H10P 72/0418>
D	H01L 21/67069	<administrative transfer to H10P 72/0421>
D	H01L 21/67075	<administrative transfer to H10P 72/0422>
D	H01L 21/6708	<administrative transfer to H10P 72/0424>
D	H01L 21/67086	<administrative transfer to H10P 72/0426>
D	H01L 21/67092	<administrative transfer to H10P 72/0428>
D	H01L 21/67098	<administrative transfer to H10P 72/0431>
D	H01L 21/67103	<administrative transfer to H10P 72/0432>
D	H01L 21/67109	<administrative transfer to H10P 72/0434>
D	H01L 21/67115	<administrative transfer to H10P 72/0436>
D	H01L 21/67121	<administrative transfer to H10P 72/0438>
D	H01L 21/67126	<administrative transfer to H10P 72/0441>
D	H01L 21/67132	<administrative transfer to H10P 72/0442>
D	H01L 21/67138	<administrative transfer to H10P 72/0444>
D	H01L 21/67144	<administrative transfer to H10P 72/0446>
D	H01L 21/6715	<administrative transfer to H10P 72/0448>
D	H01L 21/67155	<administrative transfer to H10P 72/0451>
D	H01L 21/67161	<administrative transfer to H10P 72/0452>
D	H01L 21/67167	<administrative transfer to H10P 72/0454>
D	H01L 21/67173	<administrative transfer to H10P 72/0456>
D	H01L 21/67178	<administrative transfer to H10P 72/0458>
D	H01L 21/67184	<administrative transfer to H10P 72/0461>
D	H01L 21/6719	<administrative transfer to H10P 72/0462>
D	H01L 21/67196	<administrative transfer to H10P 72/0464>
D	H01L 21/67201	<administrative transfer to H10P 72/0466>
D	H01L 21/67207	<administrative transfer to H10P 72/0468>
D	H01L 21/67213	<administrative transfer to H10P 72/0471>
D	H01L 21/67219	<administrative transfer to H10P 72/0472>
D	H01L 21/67225	<administrative transfer to H10P 72/0474>
D	H01L 21/6723	<administrative transfer to H10P 72/0476>
D	H01L 21/67236	<administrative transfer to H10P 72/0478>
D	H01L 21/67242	<administrative transfer to H10P 72/06>
D	H01L 21/67248	<administrative transfer to H10P 72/0602>
D	H01L 21/67253	<administrative transfer to H10P 72/0604>
D	H01L 21/67259	<administrative transfer to H10P 72/0606>

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Type*	<u>From CPC Symbol (existing)</u>	<u>To CPC Symbol(s)</u>
D	H01L 21/67265	<administrative transfer to H10P 72/0608>
D	H01L 21/67271	<administrative transfer to H10P 72/0611>
D	H01L 21/67276	<administrative transfer to H10P 72/0612>
D	H01L 21/67282	<administrative transfer to H10P 72/0614>
D	H01L 21/67288	<administrative transfer to H10P 72/0616>
D	H01L 21/67294	<administrative transfer to H10P 72/0618>
D	H01L 21/673	<administrative transfer to H10P 72/10>
D	H01L 21/67303	<administrative transfer to H10P 72/12 >
D	H01L 21/67306	<administrative transfer to H10P 72/123>
D	H01L 21/67309	<administrative transfer to H10P 72/127>
D	H01L 21/67313	<administrative transfer to H10P 72/13>
D	H01L 21/67316	<administrative transfer to H10P 72/135>
D	H01L 21/6732	<administrative transfer to H10P 72/14>
D	H01L 21/67323	<administrative transfer to H10P 72/145>
D	H01L 21/67326	<administrative transfer to H10P 72/15>
D	H01L 21/6733	<administrative transfer to H10P 72/155>
D	H01L 21/67333	<administrative transfer to H10P 72/16>
D	H01L 21/67336	<administrative transfer to H10P 72/165>
D	H01L 21/6734	<administrative transfer to H10P 72/17>
D	H01L 21/67343	<administrative transfer to H10P 72/175>
D	H01L 21/67346	<administrative transfer to H10P 72/18>
D	H01L 21/6735	<administrative transfer to H10P 72/19>
D	H01L 21/67353	<administrative transfer to H10P 72/1902>
D	H01L 21/67356	<administrative transfer to H10P 72/1904>
D	H01L 21/67359	<administrative transfer to H10P 72/1906>
D	H01L 21/67363	<administrative transfer to H10P 72/1908>
D	H01L 21/67366	<administrative transfer to H10P 72/1911>
D	H01L 21/67369	<administrative transfer to H10P 72/1912>
D	H01L 21/67373	<administrative transfer to H10P 72/1914>
D	H01L 21/67376	<administrative transfer to H10P 72/1916>
D	H01L 21/67379	<administrative transfer to H10P 72/1918>
D	H01L 21/67383	<administrative transfer to H10P 72/1921>
D	H01L 21/67386	<administrative transfer to H10P 72/1922>
D	H01L 21/67389	<administrative transfer to H10P 72/1924>
D	H01L 21/67393	<administrative transfer to H10P 72/1926>
D	H01L 21/67396	<administrative transfer to H10P 72/1928>
D	H01L 21/677	<administrative transfer to H10P 72/30>
D	H01L 21/67703	<administrative transfer to H10P 72/32>
D	H01L 21/67706	<administrative transfer to H10P 72/3202>
D	H01L 21/67709	<administrative transfer to H10P 72/3204>
D	H01L 21/67712	<administrative transfer to H10P 72/3206>
D	H01L 21/67715	<administrative transfer to H10P 72/3208>
D	H01L 21/67718	<administrative transfer to H10P 72/3211>
D	H01L 21/67721	<administrative transfer to H10P 72/3212>
D	H01L 21/67724	<administrative transfer to H10P 72/3214>
D	H01L 21/67727	<administrative transfer to H10P 72/3216>
D	H01L 21/6773	<administrative transfer to H10P 72/3218>
D	H01L 21/67733	<administrative transfer to H10P 72/3221>
D	H01L 21/67736	<administrative transfer to H10P 72/3222>

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Type*	From CPC Symbol (existing)	To CPC Symbol(s)
D	H01L 21/67739	<administrative transfer to H10P 72/33>
D	H01L 21/67742	<administrative transfer to H10P 72/3302>
D	H01L 21/67745	<administrative transfer to H10P 72/3304>
D	H01L 21/67748	<administrative transfer to H10P 72/3306>
D	H01L 21/67751	<administrative transfer to H10P 72/3308>
D	H01L 21/67754	<administrative transfer to H10P 72/3311>
D	H01L 21/67757	<administrative transfer to H10P 72/3312>
D	H01L 21/6776	<administrative transfer to H10P 72/3314>
D	H01L 21/67763	<administrative transfer to H10P 72/34>
D	H01L 21/67766	<administrative transfer to H10P 72/3402>
D	H01L 21/67769	<administrative transfer to H10P 72/3404>
D	H01L 21/67772	<administrative transfer to H10P 72/3406>
D	H01L 21/67775	<administrative transfer to H10P 72/3408>
D	H01L 21/67778	<administrative transfer to H10P 72/3411>
D	H01L 21/67781	<administrative transfer to H10P 72/3412>
D	H01L 21/67784	<administrative transfer to H10P 72/36>
D	H01L 21/67787	<administrative transfer to H10P 72/3602>
D	H01L 21/6779	<administrative transfer to H10P 72/3604>
D	H01L 21/67793	<administrative transfer to H10P 72/37>
D	H01L 21/67796	<administrative transfer to H10P 72/38>
D	H01L 21/68	<administrative transfer to H10P 72/50>
D	H01L 21/681	<administrative transfer to H10P 72/53>
D	H01L 21/682	<administrative transfer to H10P 72/57>
D	H01L 21/683	<administrative transfer to H10P 72/70>
D	H01L 21/6831	<administrative transfer to H10P 72/72>
D	H01L 21/6833	<administrative transfer to H10P 72/722>
D	H01L 21/6835	<administrative transfer to H10P 72/74>
D	H01L 21/6836	<administrative transfer to H10P 72/7402>
D	H01L 21/6838	<administrative transfer to H10P 72/78>
D	H01L 21/687	<administrative transfer to H10P 72/76 >
D	H01L 21/68707	<administrative transfer to H10P 72/7602>
D	H01L 21/68714	<administrative transfer to H10P 72/7604>
D	H01L 21/68721	<administrative transfer to H10P 72/7606>
D	H01L 21/68728	<administrative transfer to H10P 72/7608>
D	H01L 21/68735	<administrative transfer to H10P 72/7611>
D	H01L 21/68742	<administrative transfer to H10P 72/7612>
D	H01L 21/6875	<administrative transfer to H10P 72/7614>
D	H01L 21/68757	<administrative transfer to H10P 72/7616>
D	H01L 21/68764	<administrative transfer to H10P 72/7618>
D	H01L 21/68771	<administrative transfer to H10P 72/7621>
D	H01L 21/68778	<administrative transfer to H10P 72/7622>
D	H01L 21/68785	<administrative transfer to H10P 72/7624>
D	H01L 21/68792	<administrative transfer to H10P 72/7626>
D	H01L 21/70	<administrative transfer to H10D 84/01>
D	H01L 21/702	<administrative transfer to H10D 84/01>
D	H01L 21/705	<administrative transfer to H10D 84/01>
D	H01L 21/707	<administrative transfer to H10D 84/01>
D	H01L 21/7624	<administrative transfer to H10P 90/1906 and H10W 10/181 simultaneously>

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Type*	From CPC Symbol (existing)	To CPC Symbol(s)
D	H01L 21/76243	<administrative transfer to H10P 90/1908 and H10W 10/181 simultaneously >
D	H01L 21/76245	<administrative transfer to H10P 90/191 and H10W 10/181 simultaneously >
D	H01L 21/76248	<administrative transfer to H10P 90/1912 and H10W 10/181 simultaneously >
D	H01L 21/76251	<administrative transfer to H10P 90/1914 and H10W 10/181 simultaneously >
D	H01L 21/76254	<administrative transfer to H10P 90/1916 and H10W 10/181 simultaneously >
D	H01L 21/76256	<administrative transfer to H10P 90/1922 and H10W 10/181 simultaneously >
D	H01L 21/76259	<administrative transfer to H10P 90/1924 and H10W 10/181 simultaneously >
D	H01L 21/76262	<administrative transfer to H10P 90/1912 and H10W 10/181 simultaneously >
D	H01L 21/77	<administrative transfer to H10D 84/01>
D	H01L 21/78	<administrative transfer to H10P 54/00>
D	H01L 21/7806	<administrative transfer to H10P 95/11>
D	H01L 21/7813	<administrative transfer to H10P 95/112>
D	H01L 22/00	<administrative transfer to H10P 74/00>
D	H01L 22/10	<administrative transfer to H10P 74/20>
D	H01L 22/12	<administrative transfer to H10P 74/203>
D	H01L 22/14	<administrative transfer to H10P 74/207>
D	H01L 22/20	<administrative transfer to H10P 74/23>
D	H01L 22/22	<administrative transfer to H10P 74/232>
D	H01L 22/24	<administrative transfer to H10P 74/235>
D	H01L 22/26	<administrative transfer to H10P 74/238>
D	H01L 22/30	<administrative transfer to H10P 74/27>
D	H01L 22/32	<administrative transfer to H10P 74/273>
D	H01L 22/34	<administrative transfer to H10P 74/277>
D	H01L 2221/00	<No transfer>
D	H01L 2221/67	<administrative transfer to H10P 72/00>
D	H01L 2221/683	<administrative transfer to H10P 72/70>
D	H01L 2221/68304	<administrative transfer to H10P 72/74>
D	H01L 2221/68309	<administrative transfer to H10P 72/7408>
D	H01L 2221/68313	<administrative transfer to H10P 72/741>
D	H01L 2221/68318	<administrative transfer to H10P 72/7412>
D	H01L 2221/68322	<administrative transfer to H10P 72/7414>
D	H01L 2221/68327	<administrative transfer to H10P 72/7416>
D	H01L 2221/68331	<administrative transfer to H10P 72/7418>
D	H01L 2221/68336	<administrative transfer to H10P 72/742>
D	H01L 2221/6834	<administrative transfer to H10P 72/7422>
D	H01L 2221/68345	<administrative transfer to H10P 72/7424>
D	H01L 2221/6835	<administrative transfer to H10P 72/7426>
D	H01L 2221/68354	<administrative transfer to H10P 72/7428>
D	H01L 2221/68359	<administrative transfer to H10P 72/743>
D	H01L 2221/68363	<administrative transfer to H10P 72/7432>
D	H01L 2221/68368	<administrative transfer to H10P 72/7434>

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Type*	From CPC Symbol (existing)	To CPC Symbol(s)
D	H01L 2221/68372	<administrative transfer to H10P 72/7436>
D	H01L 2221/68377	<administrative transfer to H10P 72/7438>
D	H01L 2221/68381	<administrative transfer to H10P 72/744>
D	H01L 2221/68386	<administrative transfer to H10P 72/7442>
D	H01L 2221/6839	<administrative transfer to H10P 72/7444>
D	H01L 2221/68395	<administrative transfer to H10P 72/7446>
Q	H10D 64/011	H10D 64/011, H10D 64/0111, H10D 64/0112, H10D 64/01125, H10D 64/0113, H10D 64/0114, H10D 64/0115, H10D 64/0116, H10D 64/0117, H10D 64/0118, H10D 64/012, H10D 64/0121, H10D 64/0122, H10D 64/0123, H10D 64/0124, H10D 64/0125, H10D 64/0126, H10D 64/013, H10D 64/01302, H10D 64/01304, H10D 64/01306, H10D 64/01308, H10D 64/0131, H10D 64/01312, H10D 64/01314, H10D 64/01316, H10D 64/01318, H10D 64/0132, H10D 64/01322, H10D 64/01324, H10D 64/01326, H10D 64/01328, H10D 64/0133, H10D 64/01332, H10D 64/01334, H10D 64/01336, H10D 64/01338, H10D 64/0134, H10D 64/01342, H10D 64/01344, H10D 64/01346, H10D 64/01348, H10D 64/0135, H10D 64/01352, H10D 64/01354, H10D 64/01356, H10D 64/01358, H10D 64/0136, H10D 64/01362, H10D 64/01364, H10D 64/01366
Q	H10D 64/0112	H10D 64/0112, H10D 64/01125
Q	H10D 64/0114	H10D 64/0114, H10D 64/0122, H10D 64/01364
Q	H10D 64/0115	H10D 64/0115, H10D 64/0123, H10D 64/01366
Q	H10D 64/0125	H10D 64/0125, H10D 64/0117, H10D 64/0136
Q	H10D 64/0126	H10D 64/0126, H10D 64/0118, H10D 64/01362
C	H10D 84/01	H10D 84/01, H10D 84/0102, H10D 84/0105, H10D 84/0107, H10D 84/0109, H10D 84/0112, H10D 84/0114, H10D 84/0116, H10D 84/0119, H10D 84/0121, H10D 84/0123, H10D 84/0126, H10D 84/0128, H10D 84/013, H10D 84/0133, H10D 84/0135, H10D 84/0137, H10D 84/014, H10D 84/0142, H10D 84/0144, H10D 84/0147, H10D 84/0149, H10D 84/0151, H10D 84/0153, H10D 84/0156, H10D 84/0158, H10D 84/016, H10D 84/0163, H10D 84/0165, H10D 84/0167, H10D 84/017, H10D 84/0172, H10D 84/0174, H10D 84/0177, H10D 84/0179, H10D 84/0181, H10D 84/0184, H10D 84/0186, H10D 84/0188, H10D 84/0191, H10D 84/0193, H10D 84/0195, H10D 84/0198, H10D 84/02, H10D 84/03, H10D 84/032, H10D 84/035, H10D 84/038, H10D 84/05, H10D 84/07, H10D 84/08, H10D 86/01, H10D 86/011, H10D 86/021, H10D 86/0212, H10D 86/0214, H10D 86/0221, H10D 86/0223, H10D 86/0225, H10D 86/0227, H10D 86/0229, H10D 86/0231, H10D 86/0241, H10D 86/0251, H10D 86/03, H10D 87/00, H10D 88/01, H10D 88/101, H10D 89/60, H10D 89/601, H10D 89/611, H10D 89/711, H10D 89/713, H10D 89/811, H10D 89/813, H10D 89/814, H10D 89/815, H10D 89/817, H10D 89/819, H10D 89/911, H10D 89/921, H10D 89/931
D	H10D 89/011	<administrative transfer to H10P 58/00>
D	H10D 89/013	<administrative transfer to H10P 58/00>
D	H10D 89/015	<administrative transfer to H10P 58/00>
Q	H10P 10/00	H10P 10/00, H10P 14/00, H10P 95/00
Q	H10P 10/12	H10P 10/12, H10P 10/126, H10P 10/128, H10P 10/1285, H10P 54/52, H10P 56/00, H10P 90/1914, H10P 90/1916

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Type*	<u>From CPC Symbol (existing)</u>	<u>To CPC Symbol(s)</u>
Q	H10P 14/29	H10P 14/29, H10P 14/2924, H10P 14/2925, H10P 14/2926
Q	H10P 14/42	H10P 14/42, H10P 14/43
Q	H10P 14/44	H10P 14/44, H10P 14/45
Q	H10P 14/46	H10P 14/46, H10P 14/48
Q	H10P 14/47	H10P 14/46, H10P 14/47, H10P 14/48, H10D 64/011, H10D 64/012, H10D 64/013,
Q	H10P 14/60	H10P 14/60, H10P 95/70, H10P 95/80
Q	H10P 14/6308	H10P 14/6308, H10P 14/6309, H10P 14/6318, H10P 14/6319, H10P 14/6322, H10P 14/6324
Q	H10P 14/6316	H10P 14/6316, H10P 14/6318, H10P 14/6319, H10P 14/6322, H10P 14/6324
Q	H10P 14/68	H10P 14/68, H10P 14/69
Q	H10P 14/683	H10P 14/683, H10P 14/69
Q	H10P 14/687	H10P 14/687, H10P 14/69
Q	H10P 14/69	H10P 14/69, H10P 14/694
Q	H10P 14/6903	H10P 14/6903, H10P 14/6921, H10P 14/6943
Q	H10P 14/6938	H10P 14/6938, H10P 14/6906, H10P 14/6947
Q	H10P 14/6939	H10P 14/6939, H10P 14/6907, H10P 14/69471
Q	H10P 14/69391	H10P 14/69391, H10P 14/6908, H10P 14/69472
Q	H10P 14/69392	H10P 14/69392, H10P 14/6909, H10P 14/69473
Q	H10P 14/69393	H10P 14/69393, H10P 14/691, H10P 14/69474
Q	H10P 14/69394	H10P 14/69394, H10P 14/6911, H10P 14/69475
Q	H10P 14/69395	H10P 14/69395, H10P 14/6912, H10P 14/69476
Q	H10P 14/69396	H10P 14/69396, H10P 14/6913, H10P 14/69477
Q	H10P 14/69397	H10P 14/69397, H10P 14/6914, H10P 14/69478
Q	H10P 30/20	H10P 30/20, H10P 30/00
Q	H10P 30/202	H10P 30/202, H10P 30/208, H10P 30/21, H10P 30/212, H10P 30/22, H10P 30/221, H10P 30/222, H10P 30/28
Q	H10P 30/2042	H10P 30/2042, H10P 30/21, H10P 30/218, H10P 30/28
Q	H10P 30/2044	H10P 30/2044, H10P 30/208, H10P 30/21, H10P 30/212, H10P 30/22, H10P 30/221, H10P 30/222, H10P 30/28
Q	H10P 30/21	H10P 30/21, H10P 30/214, H10P 30/28
Q	H10P 30/212	H10P 30/212, H10P 30/214, H10P 30/28
Q	H10P 30/222	H10P 30/222, H10P 30/221
Q	H10P 30/40	H10P 30/40, H10P 32/20
Q	H10P 32/00	H10P 32/00, H10P 32/10
Q	H10P 34/00	H10P 34/00, H10P 34/10, H10P 34/20, H10P 34/40
Q	H10P 36/00	H10P 36/00, H10P 36/20, H10P 95/40
Q	H10P 36/03	H10P 36/03, H10P 95/402
Q	H10P 50/00	H10P 50/00, H10P 50/20, H10P 50/24, H10P 50/26, H10P 50/60, H10P 50/61, H10P 50/64, H10P 50/66, H10P 52/00, H10P 95/00, H10P 95/02, H10P 95/70
Q	H10P 50/20	H10P 50/20, H10P 50/24, H10P 50/26, H10P 50/60, H10P 50/61, H10P 50/64, H10P 50/66
Q	H10P 50/264	H10P 50/264, H10P 50/663
Q	H10P 50/28	H10P 50/28, H10P 50/68
Q	H10P 50/282	H10P 50/282, H10P 50/683
Q	H10P 50/283	H10P 50/283, H10P 50/683
Q	H10P 50/286	H10P 50/286, H10P 50/68

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Type*	From CPC Symbol (existing)	To CPC Symbol(s)
Q	H10P 50/287	H10P 50/287, H10P 50/68
Q	H10P 52/00	H10P 52/00, H10P 52/20, H10P 52/40, H10P 54/00, H10P 54/20, H10P 54/30, H10P 54/40, H10P 54/50, H10P 54/52, H10P 54/90, H10P 54/92, H10P 54/922, H10P 54/924, H10P 54/94, H10P 95/60
Q	H10P 52/402	H10P 52/402, H10P 52/202
Q	H10P 58/00	H10P 58/00, H10P 58/20, H10P 58/22, H10P 54/00, H10P 54/20, H10P 54/30, H10P 54/40, H10P 54/50, H10P 54/52, H10P 54/90; H10P 54/922, H10P 54/924, H10P 54/94
Q	H10P 72/70	H10P 72/70, H10P 72/72, H10P 72/74, H10P 72/7448, H10P 72/745
Q	H10P 72/7402	H10P 72/7402, H10P 72/7404, H10P 72/7406
Q	H10P 90/00	H10P 90/00, H10P 90/19, H10P 90/1902, H10P 90/1904, H10P 90/1906, H10P 90/21, H10P 90/212, H10P 90/22, H10P 90/24, H10P 56/00, H10P 10/12
Q	H10P 90/1914	H10P 90/1914, H10P 10/126, H10P 10/128, H10P 10/1285, H10P 10/14, H10P 54/52, H10P 90/1918, H10P 90/192
Q	H10P 90/1916	H10P 90/1916, H10P 10/126, H10P 10/128, H10P 10/1285, H10P 10/14, H10P 54/52, H10P 90/1918, H10P 90/192
Q	H10P 95/00	H10P 95/00, H10P 95/02, H10P 95/04, H10P 95/06, H10P 95/062, H10P 95/064, H10P 95/066, H10P 95/08, H10P 95/11, H10P 95/112, H10P 95/40, H10P 95/402, H10P 95/405, H10P 95/408, H10P 95/50, H10P 95/60, H10P 95/70, H10P 95/80, H10P 95/90
Q	H10P 95/062	H10P 52/407, H10P 52/207, H10P 95/062
Q	H10P 95/08	H10P 52/209, H10P 52/409, H10P 95/08
Q	H10P 95/60	H10P 95/60, H10P 95/02
Q	H10P 95/70	H10P 95/70, H10P 95/80, H10P 95/02
Q	H10P 95/90	H10P 95/90, H10P 30/28
Q	H10P 95/904	H10P 95/904, H10P 30/28
Q	H10P 95/92	H10P 95/92, H10P 32/173

* C = entries with modified file scope where reclassification of documents from the entries is involved; Q = new entries which are firstly populated with documents via administrative transfers from deleted (D) entries. Afterwards, the transferred documents into the Q entry will either stay or be moved to more appropriate entries, as determined by intellectual reclassification; D = deleted entries; F = frozen entries will be deleted once reclassification of documents from the entries is completed.

NOTES:

- Only C, D, F, and Q type entries are included in the table above.
- When multiple symbols are included in the “To” column, do not use ranges of symbols.
- For administrative transfer of documents, the following text should be used: “< administrative transfer to XX>”, “<administrative transfer to XX and YY simultaneously>”, or “<administrative transfer to XX, YY, ...and ZZ simultaneously>” when administrative transfer of the same documents is to more than one place.
- Administrative transfer to main trunk groups is assumed to be the source allocation type, unless otherwise indicated.
- Administrative transfer to 2000/Y series groups is assumed to be “additional information”.
- If needed, instructions for allocation type should be indicated within the angle brackets using the abbreviations “ADD” or “INV”: <administrative transfer to XX ADD>, <administrative transfer to XX INV>, or < administrative transfer to XX ADD, YY INV, ... and ZZ ADD simultaneously>.
- In certain situations, the “D” entries of 2000-series or Y-series groups may not require a destination (“To”) symbol, however it is required to specify “<no transfer>” in the “To” column for such cases.
- RCL is not needed for finalisation projects.

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4. CHANGES TO THE CPC-TO-IPC CONCORDANCE LIST (CICL)

<u>CPC</u>	<u>IPC</u>	<u>Action*</u>
H01L 21/00		DELETE
H01L 21/02		DELETE
H01L 21/02002		DELETE
H01L 21/02005		DELETE
H01L 21/02008		DELETE
H01L 21/0201		DELETE
H01L 21/02013		DELETE
H01L 21/02016		DELETE
H01L 21/02019		DELETE
H01L 21/02021		DELETE
H01L 21/02024		DELETE
H01L 21/02027		DELETE
H01L 21/0203		DELETE
H01L 21/02032		DELETE
H01L 21/02035		DELETE
H01L 21/02041		DELETE
H01L 21/02043		DELETE
H01L 21/02046		DELETE
H01L 21/02049		DELETE
H01L 21/02052		DELETE
H01L 21/02054		DELETE
H01L 21/02057		DELETE
H01L 21/0206		DELETE
H01L 21/02063		DELETE
H01L 21/02065		DELETE
H01L 21/02068		DELETE
H01L 21/02071		DELETE
H01L 21/02074		DELETE
H01L 21/02076		DELETE
H01L 21/02079		DELETE
H01L 21/02082		DELETE
H01L 21/02085		DELETE
H01L 21/02087		DELETE
H01L 21/0209		DELETE
H01L 21/02093		DELETE
H01L 21/02096		DELETE
H01L 21/02098		DELETE
H01L 21/02101		DELETE
H01L 21/02104		DELETE
H01L 21/02107		DELETE
H01L 21/02109		DELETE

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<u>CPC</u>	<u>IPC</u>	<u>Action*</u>
H01L 21/02112		DELETE
H01L 21/02115		DELETE
H01L 21/02118		DELETE
H01L 21/0212		DELETE
H01L 21/02123		DELETE
H01L 21/02126		DELETE
H01L 21/02129		DELETE
H01L 21/02131		DELETE
H01L 21/02134		DELETE
H01L 21/02137		DELETE
H01L 21/0214		DELETE
H01L 21/02142		DELETE
H01L 21/02145		DELETE
H01L 21/02148		DELETE
H01L 21/0215		DELETE
H01L 21/02153		DELETE
H01L 21/02156		DELETE
H01L 21/02159		DELETE
H01L 21/02161		DELETE
H01L 21/02164		DELETE
H01L 21/02167		DELETE
H01L 21/0217		DELETE
H01L 21/02172		DELETE
H01L 21/02175		DELETE
H01L 21/02178		DELETE
H01L 21/02181		DELETE
H01L 21/02183		DELETE
H01L 21/02186		DELETE
H01L 21/02189		DELETE
H01L 21/02192		DELETE
H01L 21/02194		DELETE
H01L 21/02197		DELETE
H01L 21/022		DELETE
H01L 21/02203		DELETE
H01L 21/02205		DELETE
H01L 21/02208		DELETE
H01L 21/02211		DELETE
H01L 21/02214		DELETE
H01L 21/02216		DELETE
H01L 21/02219		DELETE
H01L 21/02222		DELETE
H01L 21/02225		DELETE
H01L 21/02227		DELETE
H01L 21/0223		DELETE

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<u>CPC</u>	<u>IPC</u>	<u>Action*</u>
H01L 21/02233		DELETE
H01L 21/02236		DELETE
H01L 21/02238		DELETE
H01L 21/02241		DELETE
H01L 21/02244		DELETE
H01L 21/02247		DELETE
H01L 21/02249		DELETE
H01L 21/02252		DELETE
H01L 21/02255		DELETE
H01L 21/02258		DELETE
H01L 21/0226		DELETE
H01L 21/02263		DELETE
H01L 21/02266		DELETE
H01L 21/02269		DELETE
H01L 21/02271		DELETE
H01L 21/02274		DELETE
H01L 21/02277		DELETE
H01L 21/0228		DELETE
H01L 21/02282		DELETE
H01L 21/02285		DELETE
H01L 21/02288		DELETE
H01L 21/0229		DELETE
H01L 21/02293		DELETE
H01L 21/02296		DELETE
H01L 21/02299		DELETE
H01L 21/02301		DELETE
H01L 21/02304		DELETE
H01L 21/02307		DELETE
H01L 21/0231		DELETE
H01L 21/02312		DELETE
H01L 21/02315		DELETE
H01L 21/02318		DELETE
H01L 21/02321		DELETE
H01L 21/02323		DELETE
H01L 21/02326		DELETE
H01L 21/02329		DELETE
H01L 21/02332		DELETE
H01L 21/02334		DELETE
H01L 21/02337		DELETE
H01L 21/0234		DELETE
H01L 21/02343		DELETE
H01L 21/02345		DELETE
H01L 21/02348		DELETE
H01L 21/02351		DELETE

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<u>CPC</u>	<u>IPC</u>	<u>Action*</u>
H01L 21/02354		DELETE
H01L 21/02356		DELETE
H01L 21/02359		DELETE
H01L 21/02362		DELETE
H01L 21/02365		DELETE
H01L 21/02367		DELETE
H01L 21/0237		DELETE
H01L 21/02373		DELETE
H01L 21/02376		DELETE
H01L 21/02378		DELETE
H01L 21/02381		DELETE
H01L 21/02384		DELETE
H01L 21/02387		DELETE
H01L 21/02389		DELETE
H01L 21/02392		DELETE
H01L 21/02395		DELETE
H01L 21/02398		DELETE
H01L 21/024		DELETE
H01L 21/02403		DELETE
H01L 21/02406		DELETE
H01L 21/02409		DELETE
H01L 21/02411		DELETE
H01L 21/02414		DELETE
H01L 21/02417		DELETE
H01L 21/0242		DELETE
H01L 21/02422		DELETE
H01L 21/02425		DELETE
H01L 21/02428		DELETE
H01L 21/0243		DELETE
H01L 21/02433		DELETE
H01L 21/02436		DELETE
H01L 21/02439		DELETE
H01L 21/02441		DELETE
H01L 21/02444		DELETE
H01L 21/02447		DELETE
H01L 21/0245		DELETE
H01L 21/02452		DELETE
H01L 21/02455		DELETE
H01L 21/02458		DELETE
H01L 21/02461		DELETE
H01L 21/02463		DELETE
H01L 21/02466		DELETE
H01L 21/02469		DELETE
H01L 21/02472		DELETE

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<u>CPC</u>	<u>IPC</u>	<u>Action*</u>
H01L 21/02474		DELETE
H01L 21/02477		DELETE
H01L 21/0248		DELETE
H01L 21/02483		DELETE
H01L 21/02485		DELETE
H01L 21/02488		DELETE
H01L 21/02491		DELETE
H01L 21/02494		DELETE
H01L 21/02496		DELETE
H01L 21/02499		DELETE
H01L 21/02502		DELETE
H01L 21/02505		DELETE
H01L 21/02507		DELETE
H01L 21/0251		DELETE
H01L 21/02513		DELETE
H01L 21/02516		DELETE
H01L 21/02518		DELETE
H01L 21/02521		DELETE
H01L 21/02524		DELETE
H01L 21/02527		DELETE
H01L 21/02529		DELETE
H01L 21/02532		DELETE
H01L 21/02535		DELETE
H01L 21/02538		DELETE
H01L 21/0254		DELETE
H01L 21/02543		DELETE
H01L 21/02546		DELETE
H01L 21/02549		DELETE
H01L 21/02551		DELETE
H01L 21/02554		DELETE
H01L 21/02557		DELETE
H01L 21/0256		DELETE
H01L 21/02562		DELETE
H01L 21/02565		DELETE
H01L 21/02568		DELETE
H01L 21/0257		DELETE
H01L 21/02573		DELETE
H01L 21/02576		DELETE
H01L 21/02579		DELETE
H01L 21/02581		DELETE
H01L 21/02584		DELETE
H01L 21/02587		DELETE
H01L 21/0259		DELETE
H01L 21/02592		DELETE

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<u>CPC</u>	<u>IPC</u>	<u>Action*</u>
H01L 21/02595		DELETE
H01L 21/02598		DELETE
H01L 21/02601		DELETE
H01L 21/02603		DELETE
H01L 21/02606		DELETE
H01L 21/02609		DELETE
H01L 21/02612		DELETE
H01L 21/02614		DELETE
H01L 21/02617		DELETE
H01L 21/0262		DELETE
H01L 21/02623		DELETE
H01L 21/02625		DELETE
H01L 21/02628		DELETE
H01L 21/02631		DELETE
H01L 21/02634		DELETE
H01L 21/02636		DELETE
H01L 21/02639		DELETE
H01L 21/02642		DELETE
H01L 21/02645		DELETE
H01L 21/02647		DELETE
H01L 21/0265		DELETE
H01L 21/02653		DELETE
H01L 21/02656		DELETE
H01L 21/02658		DELETE
H01L 21/02661		DELETE
H01L 21/02664		DELETE
H01L 21/02667		DELETE
H01L 21/02669		DELETE
H01L 21/02672		DELETE
H01L 21/02675		DELETE
H01L 21/02678		DELETE
H01L 21/0268		DELETE
H01L 21/02683		DELETE
H01L 21/02686		DELETE
H01L 21/02689		DELETE
H01L 21/02691		DELETE
H01L 21/02694		DELETE
H01L 21/02697		DELETE
H01L 21/027		DELETE
H01L 21/0271		DELETE
H01L 21/0272		DELETE
H01L 21/0273		DELETE
H01L 21/0274		DELETE
H01L 21/0275		DELETE

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<u>CPC</u>	<u>IPC</u>	<u>Action*</u>
H01L 21/0276		DELETE
H01L 21/0277		DELETE
H01L 21/0278		DELETE
H01L 21/0279		DELETE
H01L 21/033		DELETE
H01L 21/0331		DELETE
H01L 21/0332		DELETE
H01L 21/0334		DELETE
H01L 21/0335		DELETE
H01L 21/0337		DELETE
H01L 21/0338		DELETE
H01L 21/04		DELETE
H01L 21/0405		DELETE
H01L 21/041		DELETE
H01L 21/0415		DELETE
H01L 21/042		DELETE
H01L 21/0425		DELETE
H01L 21/043		DELETE
H01L 21/0435		DELETE
H01L 21/044		DELETE
H01L 21/0445		DELETE
H01L 21/045		DELETE
H01L 21/0455		DELETE
H01L 21/046		DELETE
H01L 21/0465		DELETE
H01L 21/047		DELETE
H01L 21/0475		DELETE
H01L 21/048		DELETE
H01L 21/0485		DELETE
H01L 21/049		DELETE
H01L 21/0495		DELETE
H01L 21/18		DELETE
H01L 21/182		DELETE
H01L 21/185		DELETE
H01L 21/187		DELETE
H01L 21/20		DELETE
H01L 21/2003		DELETE
H01L 21/2007		DELETE
H01L 21/2011		DELETE
H01L 21/2015		DELETE
H01L 21/22		DELETE
H01L 21/2205		DELETE
H01L 21/221		DELETE
H01L 21/2215		DELETE

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<u>CPC</u>	<u>IPC</u>	<u>Action*</u>
H01L 21/222		DELETE
H01L 21/2225		DELETE
H01L 21/223		DELETE
H01L 21/2233		DELETE
H01L 21/2236		DELETE
H01L 21/225		DELETE
H01L 21/2251		DELETE
H01L 21/2252		DELETE
H01L 21/2253		DELETE
H01L 21/2254		DELETE
H01L 21/2255		DELETE
H01L 21/2256		DELETE
H01L 21/2257		DELETE
H01L 21/2258		DELETE
H01L 21/228		DELETE
H01L 21/24		DELETE
H01L 21/242		DELETE
H01L 21/244		DELETE
H01L 21/246		DELETE
H01L 21/248		DELETE
H01L 21/26		DELETE
H01L 21/2605		DELETE
H01L 21/261		DELETE
H01L 21/263		DELETE
H01L 21/2633		DELETE
H01L 21/2636		DELETE
H01L 21/265		DELETE
H01L 21/26506		DELETE
H01L 21/26513		DELETE
H01L 21/2652		DELETE
H01L 21/26526		DELETE
H01L 21/26533		DELETE
H01L 21/2654		DELETE
H01L 21/26546		DELETE
H01L 21/26553		DELETE
H01L 21/2656		DELETE
H01L 21/26566		DELETE
H01L 2021/26573		DELETE
H01L 21/2658		DELETE
H01L 21/26586		DELETE
H01L 21/26593		DELETE
H01L 21/266		DELETE
H01L 21/268		DELETE
H01L 21/2683		DELETE

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<u>CPC</u>	<u>IPC</u>	<u>Action*</u>
H01L 21/2686		DELETE
H01L 21/28		DELETE
H01L 21/28008		DELETE
H01L 21/28017		DELETE
H01L 21/28026		DELETE
H01L 21/28035		DELETE
H01L 21/28044		DELETE
H01L 21/28052		DELETE
H01L 21/28061		DELETE
H01L 21/2807		DELETE
H01L 21/28079		DELETE
H01L 21/28088		DELETE
H01L 21/28097		DELETE
H01L 21/28105		DELETE
H01L 21/28114		DELETE
H01L 21/28123		DELETE
H01L 21/28132		DELETE
H01L 21/28141		DELETE
H01L 21/2815		DELETE
H01L 21/28158		DELETE
H01L 21/28167		DELETE
H01L 21/28176		DELETE
H01L 21/28185		DELETE
H01L 21/28194		DELETE
H01L 21/28202		DELETE
H01L 21/28211		DELETE
H01L 21/2822		DELETE
H01L 21/28229		DELETE
H01L 21/28238		DELETE
H01L 21/28247		DELETE
H01L 21/28255		DELETE
H01L 21/28264		DELETE
H01L 21/283		DELETE
H01L 21/285		DELETE
H01L 21/28506		DELETE
H01L 21/28512		DELETE
H01L 21/28518		DELETE
H01L 21/28525		DELETE
H01L 21/28531		DELETE
H01L 21/28537		DELETE
H01L 21/2855		DELETE
H01L 21/28556		DELETE
H01L 21/28562		DELETE
H01L 21/28568		DELETE

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<u>CPC</u>	<u>IPC</u>	<u>Action*</u>
H01L 21/28575		DELETE
H01L 21/28581		DELETE
H01L 21/28587		DELETE
H01L 21/28593		DELETE
H01L 21/288		DELETE
H01L 21/2885		DELETE
H01L 21/30		DELETE
H01L 21/3003		DELETE
H01L 21/3006		DELETE
H01L 21/302		DELETE
H01L 21/304		DELETE
H01L 21/3043		DELETE
H01L 21/3046		DELETE
H01L 21/306		DELETE
H01L 21/30604		DELETE
H01L 21/30608		DELETE
H01L 21/30612		DELETE
H01L 21/30617		DELETE
H01L 21/30621		DELETE
H01L 21/30625		DELETE
H01L 21/3063		DELETE
H01L 21/30635		DELETE
H01L 21/3065		DELETE
H01L 21/30655		DELETE
H01L 21/308		DELETE
H01L 21/3081		DELETE
H01L 21/3083		DELETE
H01L 21/3085		DELETE
H01L 21/3086		DELETE
H01L 21/3088		DELETE
H01L 21/31		DELETE
H01L 21/3105		DELETE
H01L 21/31051		DELETE
H01L 21/31053		DELETE
H01L 21/31055		DELETE
H01L 21/31056		DELETE
H01L 21/31058		DELETE
H01L 21/311		DELETE
H01L 21/31105		DELETE
H01L 21/31111		DELETE
H01L 21/31116		DELETE
H01L 21/31122		DELETE
H01L 21/31127		DELETE
H01L 21/31133		DELETE

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<u>CPC</u>	<u>IPC</u>	<u>Action*</u>
H01L 21/31138		DELETE
H01L 21/31144		DELETE
H01L 21/3115		DELETE
H01L 21/31155		DELETE
H01L 21/32		DELETE
H01L 21/3205		DELETE
H01L 21/32051		DELETE
H01L 21/32053		DELETE
H01L 21/32055		DELETE
H01L 21/32056		DELETE
H01L 21/32058		DELETE
H01L 21/321		DELETE
H01L 21/32105		DELETE
H01L 21/3211		DELETE
H01L 21/32115		DELETE
H01L 21/3212		DELETE
H01L 21/32125		DELETE
H01L 21/3213		DELETE
H01L 21/32131		DELETE
H01L 21/32132		DELETE
H01L 21/32133		DELETE
H01L 21/32134		DELETE
H01L 21/32135		DELETE
H01L 21/32136		DELETE
H01L 21/32137		DELETE
H01L 21/32138		DELETE
H01L 21/32139		DELETE
H01L 21/3215		DELETE
H01L 21/32155		DELETE
H01L 21/322		DELETE
H01L 21/3221		DELETE
H01L 21/3223		DELETE
H01L 21/3225		DELETE
H01L 21/3226		DELETE
H01L 21/3228		DELETE
H01L 21/324		DELETE
H01L 21/3242		DELETE
H01L 21/3245		DELETE
H01L 21/3247		DELETE
H01L 21/326		DELETE
H01L 21/34		DELETE
H01L 21/38		DELETE
H01L 21/383		DELETE
H01L 21/385		DELETE

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<u>CPC</u>	<u>IPC</u>	<u>Action*</u>
H01L 21/388		DELETE
H01L 21/40		DELETE
H01L 21/42		DELETE
H01L 21/423		DELETE
H01L 21/425		DELETE
H01L 21/426		DELETE
H01L 21/428		DELETE
H01L 21/44		DELETE
H01L 21/441		DELETE
H01L 21/443		DELETE
H01L 21/445		DELETE
H01L 21/447		DELETE
H01L 21/449		DELETE
H01L 21/46		DELETE
H01L 21/461		DELETE
H01L 21/463		DELETE
H01L 21/465		DELETE
H01L 21/467		DELETE
H01L 21/469		DELETE
H01L 21/47		DELETE
H01L 21/471		DELETE
H01L 21/473		DELETE
H01L 21/475		DELETE
H01L 21/4757		DELETE
H01L 21/47573		DELETE
H01L 21/47576		DELETE
H01L 21/4763		DELETE
H01L 21/47635		DELETE
H01L 21/477		DELETE
H01L 21/479		DELETE
H01L 21/62		DELETE
H01L 21/64		DELETE
H01L 21/67		DELETE
H01L 21/67005		DELETE
H01L 21/67011		DELETE
H01L 21/67017		DELETE
H01L 21/67023		DELETE
H01L 21/67028		DELETE
H01L 21/67034		DELETE
H01L 21/6704		DELETE
H01L 21/67046		DELETE
H01L 21/67051		DELETE
H01L 21/67057		DELETE
H01L 21/67063		DELETE

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<u>CPC</u>	<u>IPC</u>	<u>Action*</u>
H01L 21/67069		DELETE
H01L 21/67075		DELETE
H01L 21/6708		DELETE
H01L 21/67086		DELETE
H01L 21/67092		DELETE
H01L 21/67098		DELETE
H01L 21/67103		DELETE
H01L 21/67109		DELETE
H01L 21/67115		DELETE
H01L 21/67121		DELETE
H01L 21/67126		DELETE
H01L 21/67132		DELETE
H01L 21/67138		DELETE
H01L 21/67144		DELETE
H01L 21/6715		DELETE
H01L 21/67155		DELETE
H01L 21/67161		DELETE
H01L 21/67167		DELETE
H01L 21/67173		DELETE
H01L 21/67178		DELETE
H01L 21/67184		DELETE
H01L 21/6719		DELETE
H01L 21/67196		DELETE
H01L 21/67201		DELETE
H01L 21/67207		DELETE
H01L 21/67213		DELETE
H01L 21/67219		DELETE
H01L 21/67225		DELETE
H01L 21/6723		DELETE
H01L 21/67236		DELETE
H01L 21/67242		DELETE
H01L 21/67248		DELETE
H01L 21/67253		DELETE
H01L 21/67259		DELETE
H01L 21/67265		DELETE
H01L 21/67271		DELETE
H01L 21/67276		DELETE
H01L 21/67282		DELETE
H01L 21/67288		DELETE
H01L 21/67294		DELETE
H01L 21/673		DELETE
H01L 21/67303		DELETE
H01L 21/67306		DELETE
H01L 21/67309		DELETE

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<u>CPC</u>	<u>IPC</u>	<u>Action*</u>
H01L 21/67313		DELETE
H01L 21/67316		DELETE
H01L 21/6732		DELETE
H01L 21/67323		DELETE
H01L 21/67326		DELETE
H01L 21/6733		DELETE
H01L 21/67333		DELETE
H01L 21/67336		DELETE
H01L 21/6734		DELETE
H01L 21/67343		DELETE
H01L 21/67346		DELETE
H01L 21/6735		DELETE
H01L 21/67353		DELETE
H01L 21/67356		DELETE
H01L 21/67359		DELETE
H01L 21/67363		DELETE
H01L 21/67366		DELETE
H01L 21/67369		DELETE
H01L 21/67373		DELETE
H01L 21/67376		DELETE
H01L 21/67379		DELETE
H01L 21/67383		DELETE
H01L 21/67386		DELETE
H01L 21/67389		DELETE
H01L 21/67393		DELETE
H01L 21/67396		DELETE
H01L 21/677		DELETE
H01L 21/67703		DELETE
H01L 21/67706		DELETE
H01L 21/67709		DELETE
H01L 21/67712		DELETE
H01L 21/67715		DELETE
H01L 21/67718		DELETE
H01L 21/67721		DELETE
H01L 21/67724		DELETE
H01L 21/67727		DELETE
H01L 21/6773		DELETE
H01L 21/67733		DELETE
H01L 21/67736		DELETE
H01L 21/67739		DELETE
H01L 21/67742		DELETE
H01L 21/67745		DELETE
H01L 21/67748		DELETE
H01L 21/67751		DELETE

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<u>CPC</u>	<u>IPC</u>	<u>Action*</u>
H01L 21/67754		DELETE
H01L 21/67757		DELETE
H01L 21/6776		DELETE
H01L 21/67763		DELETE
H01L 21/67766		DELETE
H01L 21/67769		DELETE
H01L 21/67772		DELETE
H01L 21/67775		DELETE
H01L 21/67778		DELETE
H01L 21/67781		DELETE
H01L 21/67784		DELETE
H01L 21/67787		DELETE
H01L 21/6779		DELETE
H01L 21/67793		DELETE
H01L 21/67796		DELETE
H01L 21/68		DELETE
H01L 21/681		DELETE
H01L 21/682		DELETE
H01L 21/683		DELETE
H01L 21/6831		DELETE
H01L 21/6833		DELETE
H01L 21/6835		DELETE
H01L 21/6836		DELETE
H01L 21/6838		DELETE
H01L 21/687		DELETE
H01L 21/68707		DELETE
H01L 21/68714		DELETE
H01L 21/68721		DELETE
H01L 21/68728		DELETE
H01L 21/68735		DELETE
H01L 21/68742		DELETE
H01L 21/6875		DELETE
H01L 21/68757		DELETE
H01L 21/68764		DELETE
H01L 21/68771		DELETE
H01L 21/68778		DELETE
H01L 21/68785		DELETE
H01L 21/68792		DELETE
H01L 21/70		DELETE
H01L 21/702		DELETE
H01L 21/705		DELETE
H01L 21/707		DELETE
H01L 21/7624		DELETE
H01L 21/76243		DELETE

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<u>CPC</u>	<u>IPC</u>	<u>Action*</u>
H01L 21/76245		DELETE
H01L 21/76248		DELETE
H01L 21/76251		DELETE
H01L 21/76254		DELETE
H01L 21/76256		DELETE
H01L 21/76259		DELETE
H01L 21/76262		DELETE
H01L 21/77		DELETE
H01L 21/78		DELETE
H01L 21/7806		DELETE
H01L 21/7813		DELETE
H01L 22/00		DELETE
H01L 22/10		DELETE
H01L 22/12		DELETE
H01L 22/14		DELETE
H01L 22/20		DELETE
H01L 22/22		DELETE
H01L 22/24		DELETE
H01L 22/26		DELETE
H01L 22/30		DELETE
H01L 22/32		DELETE
H01L 22/34		DELETE
H01L 2221/00		DELETE
H01L 2221/10		DELETE
H01L 2221/1005		DELETE
H01L 2221/101		DELETE
H01L 2221/1015		DELETE
H01L 2221/1021		DELETE
H01L 2221/1026		DELETE
H01L 2221/1031		DELETE
H01L 2221/1036		DELETE
H01L 2221/1042		DELETE
H01L 2221/1047		DELETE
H01L 2221/1052		DELETE
H01L 2221/1057		DELETE
H01L 2221/1063		DELETE
H01L 2221/1068		DELETE
H01L 2221/1073		DELETE
H01L 2221/1078		DELETE
H01L 2221/1084		DELETE
H01L 2221/1089		DELETE
H01L 2221/1094		DELETE
H01L 2221/67		DELETE
H01L 2221/683		DELETE

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<u>CPC</u>	<u>IPC</u>	<u>Action*</u>
H01L 2221/68304		DELETE
H01L 2221/68309		DELETE
H01L 2221/68313		DELETE
H01L 2221/68318		DELETE
H01L 2221/68322		DELETE
H01L 2221/68327		DELETE
H01L 2221/68331		DELETE
H01L 2221/68336		DELETE
H01L 2221/6834		DELETE
H01L 2221/68345		DELETE
H01L 2221/6835		DELETE
H01L 2221/68354		DELETE
H01L 2221/68359		DELETE
H01L 2221/68363		DELETE
H01L 2221/68368		DELETE
H01L 2221/68372		DELETE
H01L 2221/68377		DELETE
H01L 2221/68381		DELETE
H01L 2221/68386		DELETE
H01L 2221/6839		DELETE
H01L 2221/68395		DELETE
H10D 64/011	H10D 64/01	NEW
H10D 64/0111	H10D 64/01	NEW
H10D 64/0112	H10D 64/01	NEW
H10D 64/01125	H10D 64/01	NEW
H10D 64/0113	H10D 64/01	NEW
H10D 64/0114	H10D 64/01	NEW
H10D 64/0115	H10D 64/01	NEW
H10D 64/0116	H10D 64/01	NEW
H10D 64/0117	H10D 64/01	NEW
H10D 64/0118	H10D 64/01	NEW
H10D 64/012	H10D 64/01	NEW
H10D 64/0121	H10D 64/01	NEW
H10D 64/0122	H10D 64/01	NEW
H10D 64/0123	H10D 64/01	NEW
H10D 64/0124	H10D 64/01	NEW
H10D 64/0125	H10D 64/01	NEW
H10D 64/0126	H10D 64/01	NEW
H10D 64/013	H10D 64/01	NEW
H10D 64/01302	H10D 64/01	NEW
H10D 64/01304	H10D 64/01	NEW
H10D 64/01306	H10D 64/01	NEW
H10D 64/01308	H10D 64/01	NEW
H10D 64/0131	H10D 64/01	NEW

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<u>CPC</u>	<u>IPC</u>	<u>Action*</u>
H10D 64/01312	H10D 64/01	NEW
H10D 64/01314	H10D 64/01	NEW
H10D 64/01316	H10D 64/01	NEW
H10D 64/01318	H10D 64/01	NEW
H10D 64/0132	H10D 64/01	NEW
H10D 64/01322	H10D 64/01	NEW
H10D 64/01324	H10D 64/01	NEW
H10D 64/01326	H10D 64/01	NEW
H10D 64/01328	H10D 64/01	NEW
H10D 64/0133	H10D 64/01	NEW
H10D 64/01332	H10D 64/01	NEW
H10D 64/01334	H10D 64/01	NEW
H10D 64/01336	H10D 64/01	NEW
H10D 64/01338	H10D 64/01	NEW
H10D 64/0134	H10D 64/01	NEW
H10D 64/01342	H10D 64/01	NEW
H10D 64/01344	H10D 64/01	NEW
H10D 64/01346	H10D 64/01	NEW
H10D 64/01348	H10D 64/01	NEW
H10D 64/0135	H10D 64/01	NEW
H10D 64/01352	H10D 64/01	NEW
H10D 64/01354	H10D 64/01	NEW
H10D 64/01356	H10D 64/01	NEW
H10D 64/01358	H10D 64/01	NEW
H10D 64/0136	H10D 64/01	NEW
H10D 64/01362	H10D 64/01	NEW
H10D 64/01364	H10D 64/01	NEW
H10D 64/01366	H10D 64/01	NEW
H10D 89/011		DELETE
H10D 89/013		DELETE
H10D 89/015		DELETE
H10P 10/00	H10P 10/00	NEW
H10P 10/12	H10P 10/00	NEW
H10P 10/126	H10P 10/00	NEW
H10P 10/128	H10P 10/00	NEW
H10P 10/1285	H10P 10/00	NEW
H10P 10/14	H10P 10/00	NEW
H10P 14/00	H10P 14/00	NEW
H10P 14/20	H10P 14/20	NEW
H10P 14/203	H10P 14/20	NEW
H10P 14/22	H10P 14/22	NEW
H10P 14/24	H10P 14/24	NEW
H10P 14/26	H10P 14/26	NEW
H10P 14/263	H10P 14/26	NEW

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<u>CPC</u>	<u>IPC</u>	<u>Action*</u>
H10P 14/265	H10P 14/26	NEW
H10P 14/27	H10P 14/20	NEW
H10P 14/271	H10P 14/20	NEW
H10P 14/272	H10P 14/20	NEW
H10P 14/274	H10P 14/20	NEW
H10P 14/276	H10P 14/20	NEW
H10P 14/278	H10P 14/20	NEW
H10P 14/279	H10P 14/20	NEW
H10P 14/29	H10P 14/20	NEW
H10P 14/2901	H10P 14/20	NEW
H10P 14/2902	H10P 14/20	NEW
H10P 14/2903	H10P 14/20	NEW
H10P 14/2904	H10P 14/20	NEW
H10P 14/2905	H10P 14/20	NEW
H10P 14/2906	H10P 14/20	NEW
H10P 14/2907	H10P 14/20	NEW
H10P 14/2908	H10P 14/20	NEW
H10P 14/2909	H10P 14/20	NEW
H10P 14/2911	H10P 14/20	NEW
H10P 14/2912	H10P 14/20	NEW
H10P 14/2913	H10P 14/20	NEW
H10P 14/2914	H10P 14/20	NEW
H10P 14/2915	H10P 14/20	NEW
H10P 14/2916	H10P 14/20	NEW
H10P 14/2917	H10P 14/20	NEW
H10P 14/2918	H10P 14/20	NEW
H10P 14/2919	H10P 14/20	NEW
H10P 14/2921	H10P 14/20	NEW
H10P 14/2922	H10P 14/20	NEW
H10P 14/2923	H10P 14/20	NEW
H10P 14/2924	H10P 14/20	NEW
H10P 14/2925	H10P 14/20	NEW
H10P 14/2926	H10P 14/20	NEW
H10P 14/32	H10P 14/20	NEW
H10P 14/3202	H10P 14/20	NEW
H10P 14/3204	H10P 14/20	NEW
H10P 14/3206	H10P 14/20	NEW
H10P 14/3208	H10P 14/20	NEW
H10P 14/3211	H10P 14/20	NEW
H10P 14/3212	H10P 14/20	NEW
H10P 14/3214	H10P 14/20	NEW
H10P 14/3216	H10P 14/20	NEW
H10P 14/3218	H10P 14/20	NEW
H10P 14/3221	H10P 14/20	NEW

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<u>CPC</u>	<u>IPC</u>	<u>Action*</u>
H10P 14/3222	H10P 14/20	NEW
H10P 14/3224	H10P 14/20	NEW
H10P 14/3226	H10P 14/20	NEW
H10P 14/3228	H10P 14/20	NEW
H10P 14/3231	H10P 14/20	NEW
H10P 14/3232	H10P 14/20	NEW
H10P 14/3234	H10P 14/20	NEW
H10P 14/3236	H10P 14/20	NEW
H10P 14/3238	H10P 14/20	NEW
H10P 14/3241	H10P 14/20	NEW
H10P 14/3242	H10P 14/20	NEW
H10P 14/3244	H10P 14/20	NEW
H10P 14/3246	H10P 14/20	NEW
H10P 14/3248	H10P 14/20	NEW
H10P 14/3251	H10P 14/20	NEW
H10P 14/3252	H10P 14/20	NEW
H10P 14/3254	H10P 14/20	NEW
H10P 14/3256	H10P 14/20	NEW
H10P 14/3258	H10P 14/20	NEW
H10P 14/34	H10P 14/20	NEW
H10P 14/3402	H10P 14/20	NEW
H10P 14/3404	H10P 14/20	NEW
H10P 14/3406	H10P 14/20	NEW
H10P 14/3408	H10P 14/20	NEW
H10P 14/3411	H10P 14/20	NEW
H10P 14/3412	H10P 14/20	NEW
H10P 14/3414	H10P 14/20	NEW
H10P 14/3416	H10P 14/20	NEW
H10P 14/3418	H10P 14/20	NEW
H10P 14/3421	H10P 14/20	NEW
H10P 14/3422	H10P 14/20	NEW
H10P 14/3424	H10P 14/20	NEW
H10P 14/3426	H10P 14/20	NEW
H10P 14/3428	H10P 14/20	NEW
H10P 14/3431	H10P 14/20	NEW
H10P 14/3432	H10P 14/20	NEW
H10P 14/3434	H10P 14/20	NEW
H10P 14/3436	H10P 14/20	NEW
H10P 14/3438	H10P 14/20	NEW
H10P 14/3441	H10P 14/20	NEW
H10P 14/3442	H10P 14/20	NEW
H10P 14/3444	H10P 14/20	NEW
H10P 14/3446	H10P 14/20	NEW
H10P 14/3448	H10P 14/20	NEW

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<u>CPC</u>	<u>IPC</u>	<u>Action*</u>
H10P 14/3451	H10P 14/20	NEW
H10P 14/3452	H10P 14/20	NEW
H10P 14/3454	H10P 14/20	NEW
H10P 14/3456	H10P 14/20	NEW
H10P 14/3458	H10P 14/20	NEW
H10P 14/3461	H10P 14/20	NEW
H10P 14/3462	H10P 14/20	NEW
H10P 14/3464	H10P 14/20	NEW
H10P 14/3466	H10P 14/20	NEW
H10P 14/36	H10P 14/20	NEW
H10P 14/3602	H10P 14/20	NEW
H10P 14/38	H10P 14/20	NEW
H10P 14/3802	H10P 14/20	NEW
H10P 14/3804	H10P 14/20	NEW
H10P 14/3806	H10P 14/20	NEW
H10P 14/3808	H10P 14/20	NEW
H10P 14/381	H10P 14/20	NEW
H10P 14/3812	H10P 14/20	NEW
H10P 14/3814	H10P 14/20	NEW
H10P 14/3816	H10P 14/20	NEW
H10P 14/3818	H10P 14/20	NEW
H10P 14/382	H10P 14/20	NEW
H10P 14/3822	H10P 14/20	NEW
H10P 14/3824	H10P 14/20	NEW
H10P 14/40	H10P 14/40	NEW
H10P 14/412	H10P 14/40	NEW
H10P 14/414	H10P 14/40	NEW
H10P 14/416	H10P 14/40	NEW
H10P 14/418	H10P 14/40	NEW
H10P 14/42	H10P 14/42	NEW
H10P 14/43	H10P 14/43	NEW
H10P 14/432	H10P 14/43	NEW
H10P 14/44	H10P 14/44	NEW
H10P 14/45	H10P 14/45	NEW
H10P 14/46	H10P 14/46	NEW
H10P 14/47	H10P 14/47	NEW
H10P 14/48	H10P 14/47	NEW
H10P 14/60	H10P 14/60	NEW
H10P 14/61	H10P 14/61	NEW
H10P 14/63	H10P 14/60	NEW
H10P 14/6302	H10P 14/60	NEW
H10P 14/6304	H10P 14/60	NEW
H10P 14/6306	H10P 14/60	NEW
H10P 14/6308	H10P 14/60	NEW

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<u>CPC</u>	<u>IPC</u>	<u>Action*</u>
H10P 14/6309	H10P 14/60	NEW
H10P 14/6312	H10P 14/60	NEW
H10P 14/6314	H10P 14/60	NEW
H10P 14/6316	H10P 14/60	NEW
H10P 14/6318	H10P 14/60	NEW
H10P 14/6319	H10P 14/60	NEW
H10P 14/6322	H10P 14/60	NEW
H10P 14/6324	H10P 14/60	NEW
H10P 14/6326	H10P 14/60	NEW
H10P 14/6328	H10P 14/60	NEW
H10P 14/6329	H10P 14/60	NEW
H10P 14/6332	H10P 14/60	NEW
H10P 14/6334	H10P 14/60	NEW
H10P 14/6336	H10P 14/60	NEW
H10P 14/6338	H10P 14/60	NEW
H10P 14/6339	H10P 14/60	NEW
H10P 14/6342	H10P 14/60	NEW
H10P 14/6344	H10P 14/60	NEW
H10P 14/6346	H10P 14/60	NEW
H10P 14/6348	H10P 14/60	NEW
H10P 14/6349	H10P 14/60	NEW
H10P 14/65	H10P 14/60	NEW
H10P 14/6502	H10P 14/60	NEW
H10P 14/6504	H10P 14/60	NEW
H10P 14/6506	H10P 14/60	NEW
H10P 14/6508	H10P 14/60	NEW
H10P 14/6509	H10P 14/60	NEW
H10P 14/6512	H10P 14/60	NEW
H10P 14/6514	H10P 14/60	NEW
H10P 14/6516	H10P 14/60	NEW
H10P 14/6518	H10P 14/60	NEW
H10P 14/6519	H10P 14/60	NEW
H10P 14/6522	H10P 14/60	NEW
H10P 14/6524	H10P 14/60	NEW
H10P 14/6526	H10P 14/60	NEW
H10P 14/6528	H10P 14/60	NEW
H10P 14/6529	H10P 14/60	NEW
H10P 14/6532	H10P 14/60	NEW
H10P 14/6534	H10P 14/60	NEW
H10P 14/6536	H10P 14/60	NEW
H10P 14/6538	H10P 14/60	NEW
H10P 14/6539	H10P 14/60	NEW
H10P 14/6542	H10P 14/60	NEW
H10P 14/6544	H10P 14/60	NEW

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<u>CPC</u>	<u>IPC</u>	<u>Action*</u>
H10P 14/6546	H10P 14/60	NEW
H10P 14/6548	H10P 14/60	NEW
H10P 14/66	H10P 14/60	NEW
H10P 14/662	H10P 14/60	NEW
H10P 14/665	H10P 14/60	NEW
H10P 14/668	H10P 14/60	NEW
H10P 14/6681	H10P 14/60	NEW
H10P 14/6682	H10P 14/60	NEW
H10P 14/6684	H10P 14/60	NEW
H10P 14/6686	H10P 14/60	NEW
H10P 14/6687	H10P 14/60	NEW
H10P 14/6689	H10P 14/60	NEW
H10P 14/68	H10P 14/68	NEW
H10P 14/683	H10P 14/68	NEW
H10P 14/687	H10P 14/68	NEW
H10P 14/69	H10P 14/69	NEW
H10P 14/6902	H10P 14/69	NEW
H10P 14/6903	H10P 14/69	NEW
H10P 14/6905	H10P 14/69	NEW
H10P 14/6906	H10P 14/69	NEW
H10P 14/6907	H10P 14/69	NEW
H10P 14/6908	H10P 14/69	NEW
H10P 14/6909	H10P 14/69	NEW
H10P 14/691	H10P 14/69	NEW
H10P 14/6911	H10P 14/69	NEW
H10P 14/6912	H10P 14/69	NEW
H10P 14/6913	H10P 14/69	NEW
H10P 14/6914	H10P 14/69	NEW
H10P 14/692	H10P 14/692	NEW
H10P 14/6921	H10P 14/692	NEW
H10P 14/69215	H10P 14/692	NEW
H10P 14/6922	H10P 14/692	NEW
H10P 14/6923	H10P 14/692	NEW
H10P 14/6924	H10P 14/692	NEW
H10P 14/6925	H10P 14/692	NEW
H10P 14/6926	H10P 14/692	NEW
H10P 14/6927	H10P 14/692	NEW
H10P 14/6928	H10P 14/692	NEW
H10P 14/6929	H10P 14/692	NEW
H10P 14/693	H10P 14/692	NEW
H10P 14/6931	H10P 14/692	NEW
H10P 14/6932	H10P 14/692	NEW
H10P 14/6933	H10P 14/692	NEW
H10P 14/6934	H10P 14/692	NEW

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<u>CPC</u>	<u>IPC</u>	<u>Action*</u>
H10P 14/6936	H10P 14/692	NEW
H10P 14/6938	H10P 14/692	NEW
H10P 14/6939	H10P 14/692	NEW
H10P 14/69391	H10P 14/692	NEW
H10P 14/69392	H10P 14/692	NEW
H10P 14/69393	H10P 14/692	NEW
H10P 14/69394	H10P 14/692	NEW
H10P 14/69395	H10P 14/692	NEW
H10P 14/69396	H10P 14/692	NEW
H10P 14/69397	H10P 14/692	NEW
H10P 14/69398	H10P 14/692	NEW
H10P 14/694	H10P 14/694	NEW
H10P 14/6943	H10P 14/694	NEW
H10P 14/69433	H10P 14/694	NEW
H10P 14/6947	H10P 14/694	NEW
H10P 14/69471	H10P 14/694	NEW
H10P 14/69472	H10P 14/694	NEW
H10P 14/69473	H10P 14/694	NEW
H10P 14/69474	H10P 14/694	NEW
H10P 14/69475	H10P 14/694	NEW
H10P 14/69476	H10P 14/694	NEW
H10P 14/69477	H10P 14/694	NEW
H10P 14/69478	H10P 14/694	NEW
H10P 30/00	H10P 30/00	NEW
H10P 30/20	H10P 30/20	NEW
H10P 30/202	H10P 30/20	NEW
H10P 30/204	H10P 30/20	NEW
H10P 30/2042	H10P 30/20	NEW
H10P 30/2044	H10P 30/20	NEW
H10P 30/206	H10P 30/20	NEW
H10P 30/208	H10P 30/20	NEW
H10P 30/209	H10P 30/20	NEW
H10P 30/21	H10P 30/20	NEW
H10P 30/212	H10P 30/20	NEW
H10P 30/214	H10P 30/20	NEW
H10P 30/218	H10P 30/20	NEW
H10P 30/22	H10P 30/22	NEW
H10P 30/221	H10P 30/22	NEW
H10P 30/222	H10P 30/20	NEW
H10P 30/224	H10P 30/20	NEW
H10P 30/225	H10P 30/20	NEW
H10P 30/226	H10P 30/20	NEW
H10P 30/28	H10P 30/28	NEW
H10P 30/40	H10P 30/40	NEW

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<u>CPC</u>	<u>IPC</u>	<u>Action*</u>
H10P 32/00	H10P 32/00	NEW
H10P 32/10	H10P 32/10	NEW
H10P 32/12	H10P 32/12	NEW
H10P 32/1204	H10P 32/12	NEW
H10P 32/14	H10P 32/14	NEW
H10P 32/1404	H10P 32/14	NEW
H10P 32/1406	H10P 32/14	NEW
H10P 32/1408	H10P 32/14	NEW
H10P 32/141	H10P 32/14	NEW
H10P 32/1412	H10P 32/14	NEW
H10P 32/1414	H10P 32/14	NEW
H10P 32/15	H10P 32/10	NEW
H10P 32/16	H10P 32/16	NEW
H10P 32/17	H10P 32/10	NEW
H10P 32/171	H10P 32/10	NEW
H10P 32/172	H10P 32/10	NEW
H10P 32/173	H10P 32/10	NEW
H10P 32/174	H10P 32/10	NEW
H10P 32/18	H10P 32/10	NEW
H10P 32/185	H10P 32/10	NEW
H10P 32/19	H10P 32/10	NEW
H10P 32/20	H10P 32/20	NEW
H10P 32/30	H10P 32/30	NEW
H10P 32/302	H10P 32/30	NEW
H10P 34/00	H10P 34/00	NEW
H10P 34/10	H10P 34/00	NEW
H10P 34/20	H10P 34/20	NEW
H10P 34/40	H10P 34/40	NEW
H10P 34/42	H10P 34/42	NEW
H10P 34/422	H10P 34/42	NEW
H10P 36/00	H10P 36/00	NEW
H10P 36/03	H10P 36/00	NEW
H10P 36/07	H10P 36/00	NEW
H10P 36/20	H10P 36/20	NEW
H10P 50/00	H10P 50/00	NEW
H10P 50/20	H10P 50/20	NEW
H10P 50/24	H10P 50/24	NEW
H10P 50/242	H10P 50/24	NEW
H10P 50/244	H10P 50/24	NEW
H10P 50/246	H10P 50/24	NEW
H10P 50/26	H10P 50/26	NEW
H10P 50/262	H10P 50/26	NEW
H10P 50/263	H10P 50/26	NEW
H10P 50/264	H10P 50/26	NEW

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<u>CPC</u>	<u>IPC</u>	<u>Action*</u>
H10P 50/266	H10P 50/26	NEW
H10P 50/267	H10P 50/26	NEW
H10P 50/268	H10P 50/26	NEW
H10P 50/269	H10P 50/26	NEW
H10P 50/28	H10P 50/28	NEW
H10P 50/282	H10P 50/28	NEW
H10P 50/283	H10P 50/28	NEW
H10P 50/285	H10P 50/28	NEW
H10P 50/286	H10P 50/28	NEW
H10P 50/287	H10P 50/28	NEW
H10P 50/60	H10P 50/60	NEW
H10P 50/61	H10P 50/61	NEW
H10P 50/613	H10P 50/61	NEW
H10P 50/617	H10P 50/61	NEW
H10P 50/64	H10P 50/64	NEW
H10P 50/642	H10P 50/64	NEW
H10P 50/644	H10P 50/64	NEW
H10P 50/646	H10P 50/64	NEW
H10P 50/648	H10P 50/64	NEW
H10P 50/66	H10P 50/66	NEW
H10P 50/663	H10P 50/66	NEW
H10P 50/667	H10P 50/66	NEW
H10P 50/68	H10P 50/68	NEW
H10P 50/683	H10P 50/68	NEW
H10P 50/69	H10P 50/00	NEW
H10P 50/691	H10P 50/00	NEW
H10P 50/692	H10P 50/00	NEW
H10P 50/693	H10P 50/00	NEW
H10P 50/694	H10P 50/00	NEW
H10P 50/695	H10P 50/00	NEW
H10P 50/696	H10P 50/00	NEW
H10P 50/71	H10P 50/00	NEW
H10P 50/73	H10P 50/00	NEW
H10P 52/00	H10P 52/00	NEW
H10P 52/20	H10P 52/20	NEW
H10P 52/202	H10P 52/20	NEW
H10P 52/203	H10P 52/20	NEW
H10P 52/207	H10P 52/20	NEW
H10P 52/209	H10P 52/20	NEW
H10P 52/40	H10P 52/40	NEW
H10P 52/402	H10P 52/40	NEW
H10P 52/403	H10P 52/40	NEW
H10P 52/407	H10P 52/40	NEW
H10P 52/409	H10P 52/40	NEW

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<u>CPC</u>	<u>IPC</u>	<u>Action*</u>
H10P 54/00	H10P 54/00	NEW
H10P 54/20	H10P 54/20	NEW
H10P 54/30	H10P 54/30	NEW
H10P 54/40	H10P 54/40	NEW
H10P 54/50	H10P 54/50	NEW
H10P 54/52	H10P 54/50	NEW
H10P 54/90	H10P 54/90	NEW
H10P 54/92	H10P 54/92	NEW
H10P 54/922	H10P 54/92	NEW
H10P 54/924	H10P 54/92	NEW
H10P 54/94	H10P 54/94	NEW
H10P 56/00	H10P 56/00	NEW
H10P 58/00	H10P 58/00	NEW
H10P 58/20	H10P 58/00	NEW
H10P 58/22	H10P 58/00	NEW
H10P 70/00	H10P 70/00	NEW
H10P 70/10	H10P 70/00	NEW
H10P 70/12	H10P 70/00	NEW
H10P 70/125	H10P 70/00	NEW
H10P 70/15	H10P 70/00	NEW
H10P 70/18	H10P 70/00	NEW
H10P 70/20	H10P 70/00	NEW
H10P 70/23	H10P 70/00	NEW
H10P 70/234	H10P 70/00	NEW
H10P 70/237	H10P 70/00	NEW
H10P 70/27	H10P 70/00	NEW
H10P 70/273	H10P 70/00	NEW
H10P 70/277	H10P 70/00	NEW
H10P 70/30	H10P 70/00	NEW
H10P 70/40	H10P 70/00	NEW
H10P 70/50	H10P 70/00	NEW
H10P 70/52	H10P 70/00	NEW
H10P 70/54	H10P 70/00	NEW
H10P 70/56	H10P 70/00	NEW
H10P 70/58	H10P 70/00	NEW
H10P 70/60	H10P 70/00	NEW
H10P 70/70	H10P 70/00	NEW
H10P 70/80	H10P 70/00	NEW
H10P 72/00	H10P 72/00	NEW
H10P 72/04	H10P 72/00	NEW
H10P 72/0402	H10P 72/00	NEW
H10P 72/0404	H10P 72/00	NEW
H10P 72/0406	H10P 72/00	NEW
H10P 72/0408	H10P 72/00	NEW

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H10P 72/0411	H10P 72/00	NEW
H10P 72/0412	H10P 72/00	NEW
H10P 72/0414	H10P 72/00	NEW
H10P 72/0416	H10P 72/00	NEW
H10P 72/0418	H10P 72/00	NEW
H10P 72/0421	H10P 72/00	NEW
H10P 72/0422	H10P 72/00	NEW
H10P 72/0424	H10P 72/00	NEW
H10P 72/0426	H10P 72/00	NEW
H10P 72/0428	H10P 72/00	NEW
H10P 72/0431	H10P 72/00	NEW
H10P 72/0432	H10P 72/00	NEW
H10P 72/0434	H10P 72/00	NEW
H10P 72/0436	H10P 72/00	NEW
H10P 72/0438	H10P 72/00	NEW
H10P 72/0441	H10P 72/00	NEW
H10P 72/0442	H10P 72/00	NEW
H10P 72/0444	H10P 72/00	NEW
H10P 72/0446	H10P 72/00	NEW
H10P 72/0448	H10P 72/00	NEW
H10P 72/0451	H10P 72/00	NEW
H10P 72/0452	H10P 72/00	NEW
H10P 72/0454	H10P 72/00	NEW
H10P 72/0456	H10P 72/00	NEW
H10P 72/0458	H10P 72/00	NEW
H10P 72/0461	H10P 72/00	NEW
H10P 72/0462	H10P 72/00	NEW
H10P 72/0464	H10P 72/00	NEW
H10P 72/0466	H10P 72/00	NEW
H10P 72/0468	H10P 72/00	NEW
H10P 72/0471	H10P 72/00	NEW
H10P 72/0472	H10P 72/00	NEW
H10P 72/0474	H10P 72/00	NEW
H10P 72/0476	H10P 72/00	NEW
H10P 72/0478	H10P 72/00	NEW
H10P 72/06	H10P 72/00	NEW
H10P 72/0602	H10P 72/00	NEW
H10P 72/0604	H10P 72/00	NEW
H10P 72/0606	H10P 72/00	NEW
H10P 72/0608	H10P 72/00	NEW
H10P 72/0611	H10P 72/00	NEW
H10P 72/0612	H10P 72/00	NEW
H10P 72/0614	H10P 72/00	NEW
H10P 72/0616	H10P 72/00	NEW

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<u>CPC</u>	<u>IPC</u>	<u>Action*</u>
H10P 72/0618	H10P 72/00	NEW
H10P 72/10	H10P 72/10	NEW
H10P 72/12	H10P 72/10	NEW
H10P 72/123	H10P 72/10	NEW
H10P 72/127	H10P 72/10	NEW
H10P 72/13	H10P 72/10	NEW
H10P 72/135	H10P 72/10	NEW
H10P 72/14	H10P 72/10	NEW
H10P 72/145	H10P 72/10	NEW
H10P 72/15	H10P 72/10	NEW
H10P 72/155	H10P 72/10	NEW
H10P 72/16	H10P 72/10	NEW
H10P 72/165	H10P 72/10	NEW
H10P 72/17	H10P 72/10	NEW
H10P 72/175	H10P 72/10	NEW
H10P 72/18	H10P 72/10	NEW
H10P 72/19	H10P 72/10	NEW
H10P 72/1902	H10P 72/10	NEW
H10P 72/1904	H10P 72/10	NEW
H10P 72/1906	H10P 72/10	NEW
H10P 72/1908	H10P 72/10	NEW
H10P 72/1911	H10P 72/10	NEW
H10P 72/1912	H10P 72/10	NEW
H10P 72/1914	H10P 72/10	NEW
H10P 72/1916	H10P 72/10	NEW
H10P 72/1918	H10P 72/10	NEW
H10P 72/1921	H10P 72/10	NEW
H10P 72/1922	H10P 72/10	NEW
H10P 72/1924	H10P 72/10	NEW
H10P 72/1926	H10P 72/10	NEW
H10P 72/1928	H10P 72/10	NEW
H10P 72/30	H10P 72/30	NEW
H10P 72/32	H10P 72/30	NEW
H10P 72/3202	H10P 72/30	NEW
H10P 72/3204	H10P 72/30	NEW
H10P 72/3206	H10P 72/30	NEW
H10P 72/3208	H10P 72/30	NEW
H10P 72/3211	H10P 72/30	NEW
H10P 72/3212	H10P 72/30	NEW
H10P 72/3214	H10P 72/30	NEW
H10P 72/3216	H10P 72/30	NEW
H10P 72/3218	H10P 72/30	NEW
H10P 72/3221	H10P 72/30	NEW
H10P 72/3222	H10P 72/30	NEW

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H10P 72/33	H10P 72/30	NEW
H10P 72/3302	H10P 72/30	NEW
H10P 72/3304	H10P 72/30	NEW
H10P 72/3306	H10P 72/30	NEW
H10P 72/3308	H10P 72/30	NEW
H10P 72/3311	H10P 72/30	NEW
H10P 72/3312	H10P 72/30	NEW
H10P 72/3314	H10P 72/30	NEW
H10P 72/34	H10P 72/30	NEW
H10P 72/3402	H10P 72/30	NEW
H10P 72/3404	H10P 72/30	NEW
H10P 72/3406	H10P 72/30	NEW
H10P 72/3408	H10P 72/30	NEW
H10P 72/3411	H10P 72/30	NEW
H10P 72/3412	H10P 72/30	NEW
H10P 72/36	H10P 72/30	NEW
H10P 72/3602	H10P 72/30	NEW
H10P 72/3604	H10P 72/30	NEW
H10P 72/37	H10P 72/30	NEW
H10P 72/38	H10P 72/30	NEW
H10P 72/50	H10P 72/50	NEW
H10P 72/53	H10P 72/50	NEW
H10P 72/57	H10P 72/50	NEW
H10P 72/70	H10P 72/70	NEW
H10P 72/72	H10P 72/72	NEW
H10P 72/722	H10P 72/72	NEW
H10P 72/74	H10P 72/70	NEW
H10P 72/7402	H10P 72/70	NEW
H10P 72/7404	H10P 72/70	NEW
H10P 72/7406	H10P 72/70	NEW
H10P 72/7408	H10P 72/70	NEW
H10P 72/741	H10P 72/70	NEW
H10P 72/7412	H10P 72/70	NEW
H10P 72/7414	H10P 72/70	NEW
H10P 72/7416	H10P 72/70	NEW
H10P 72/7418	H10P 72/70	NEW
H10P 72/742	H10P 72/70	NEW
H10P 72/7422	H10P 72/70	NEW
H10P 72/7424	H10P 72/70	NEW
H10P 72/7426	H10P 72/70	NEW
H10P 72/7428	H10P 72/70	NEW
H10P 72/743	H10P 72/70	NEW
H10P 72/7432	H10P 72/70	NEW
H10P 72/7434	H10P 72/70	NEW

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<u>CPC</u>	<u>IPC</u>	<u>Action*</u>
H10P 72/7436	H10P 72/70	NEW
H10P 72/7438	H10P 72/70	NEW
H10P 72/744	H10P 72/70	NEW
H10P 72/7442	H10P 72/70	NEW
H10P 72/7444	H10P 72/70	NEW
H10P 72/7446	H10P 72/70	NEW
H10P 72/7448	H10P 72/70	NEW
H10P 72/745	H10P 72/70	NEW
H10P 72/76	H10P 72/76	NEW
H10P 72/7602	H10P 72/76	NEW
H10P 72/7604	H10P 72/76	NEW
H10P 72/7606	H10P 72/76	NEW
H10P 72/7608	H10P 72/76	NEW
H10P 72/7611	H10P 72/76	NEW
H10P 72/7612	H10P 72/76	NEW
H10P 72/7614	H10P 72/76	NEW
H10P 72/7616	H10P 72/76	NEW
H10P 72/7618	H10P 72/76	NEW
H10P 72/7621	H10P 72/76	NEW
H10P 72/7622	H10P 72/76	NEW
H10P 72/7624	H10P 72/76	NEW
H10P 72/7626	H10P 72/76	NEW
H10P 72/78	H10P 72/78	NEW
H10P 74/00	H10P 74/00	NEW
H10P 74/20	H10P 74/20	NEW
H10P 74/203	H10P 74/20	NEW
H10P 74/207	H10P 74/20	NEW
H10P 74/23	H10P 74/00	NEW
H10P 74/232	H10P 74/00	NEW
H10P 74/235	H10P 74/00	NEW
H10P 74/238	H10P 74/00	NEW
H10P 74/27	H10P 74/00	NEW
H10P 74/273	H10P 74/00	NEW
H10P 74/277	H10P 74/00	NEW
H10P 76/00	H10P 76/00	NEW
H10P 76/20	H10P 76/20	NEW
H10P 76/202	H10P 76/20	NEW
H10P 76/204	H10P 76/20	NEW
H10P 76/2041	H10P 76/20	NEW
H10P 76/2042	H10P 76/20	NEW
H10P 76/2043	H10P 76/20	NEW
H10P 76/2045	H10P 76/20	NEW
H10P 76/2047	H10P 76/20	NEW
H10P 76/2049	H10P 76/20	NEW

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<u>CPC</u>	<u>IPC</u>	<u>Action*</u>
H10P 76/40	H10P 76/40	NEW
H10P 76/403	H10P 76/40	NEW
H10P 76/405	H10P 76/40	NEW
H10P 76/408	H10P 76/40	NEW
H10P 76/4083	H10P 76/40	NEW
H10P 76/4085	H10P 76/40	NEW
H10P 76/4088	H10P 76/40	NEW
H10P 90/00	H10P 90/00	NEW
H10P 90/12	H10P 90/00	NEW
H10P 90/123	H10P 90/00	NEW
H10P 90/124	H10P 90/00	NEW
H10P 90/126	H10P 90/00	NEW
H10P 90/128	H10P 90/00	NEW
H10P 90/129	H10P 90/00	NEW
H10P 90/14	H10P 90/00	NEW
H10P 90/15	H10P 90/00	NEW
H10P 90/16	H10P 90/00	NEW
H10P 90/18	H10P 90/00	NEW
H10P 90/19	H10P 90/00	NEW
H10P 90/1902	H10P 90/00	NEW
H10P 90/1904	H10P 90/00	NEW
H10P 90/1906	H10P 90/00	NEW
H10P 90/1908	H10P 90/00	NEW
H10P 90/191	H10P 90/00	NEW
H10P 90/1912	H10P 90/00	NEW
H10P 90/1914	H10P 90/00	NEW
H10P 90/1916	H10P 90/00	NEW
H10P 90/1918	H10P 90/00	NEW
H10P 90/192	H10P 90/00	NEW
H10P 90/1922	H10P 90/00	NEW
H10P 90/1924	H10P 90/00	NEW
H10P 90/21	H10P 90/00	NEW
H10P 90/212	H10P 90/00	NEW
H10P 90/22	H10P 90/00	NEW
H10P 90/24	H10P 90/00	NEW
H10P 95/00	H10P 95/00	NEW
H10P 95/02	H10P 95/00	NEW
H10P 95/04	H10P 95/00	NEW
H10P 95/06	H10P 95/00	NEW
H10P 95/062	H10P 95/00	NEW
H10P 95/064	H10P 95/00	NEW
H10P 95/066	H10P 95/00	NEW
H10P 95/08	H10P 95/00	NEW
H10P 95/11	H10P 95/00	NEW

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<u>CPC</u>	<u>IPC</u>	<u>Action*</u>
H10P 95/112	H10P 95/00	NEW
H10P 95/40	H10P 95/40	NEW
H10P 95/402	H10P 95/40	NEW
H10P 95/405	H10P 95/40	NEW
H10P 95/408	H10P 95/40	NEW
H10P 95/50	H10P 95/00	NEW
H10P 95/60	H10P 95/60	NEW
H10P 95/70	H10P 95/70	NEW
H10P 95/80	H10P 95/80	NEW
H10P 95/90	H10P 95/90	NEW
H10P 95/902	H10P 95/90	NEW
H10P 95/904	H10P 95/90	NEW
H10P 95/906	H10P 95/90	NEW
H10P 95/92	H10P 95/00	NEW
H10P 95/94	H10P 95/00	NEW

* Action column:

- For an (N) or (Q) entry, provide an IPC symbol and complete the Action column with “NEW.”
- For an existing CPC main trunk entry or indexing entry where the existing IPC symbol needs to be changed, provide an updated IPC symbol and complete the Action column with “UPDATED.”
- For a (D) CPC entry or indexing entry complete the Action column with “DELETE.” IPC symbol does not need to be included in the IPC column.
- For an (N) 2000 series CPC entry which is positioned within the main trunk scheme (breakdown code) provide an IPC symbol and complete the action column with “NEW”.
- For an (N) 2000 series CPC entry positioned at the end of the CPC scheme (orthogonal code), with no IPC equivalent, complete the IPC column with “CPCONLY” and complete the action column with “NEW”.

NOTES:

- F symbols are not included in the CICL table above.
- T and M symbols are not included in the CICL table above unless a change to the existing IPC is desired.

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5. CROSS-REFERENCE LIST (CRL)

Scheme references impacted by this revision project

<u>Location of reference to be changed</u>	<u>Referenced subclass or group to be changed</u>	<u>Action; New reference symbol; New text</u>
B65D	H01L 21/00	In the Warning, replace “H01L21/00” with “H10W”
B81C 1/00611	H01L	H10
B81C 1/00841	H01L 21/306	H10P 50/00
C04B 35/62222	H01L	H10W
C04B 41/5338	H01L 21/306	H10P 50/00
C09G 1/02	H01L	H10P 52/40
C09K 3/14	H01L	H10P 52/40
C09K 13/00	H01L	H10P 52/40
C23F	H01L 21/00	In the Warning, replace “H01L21/00” with “H10P50/00”
C30B	H01L	Delete H01L
G01K 7/16	H01L	Delete both references H01C and H01L, and associated text “resistive elements per se”
G01T 5/08	H01L	Delete “semiconductor devices H01L” and preceding semicolon
G03F 7/00	H01L	Delete H01L
G03F 7/00	H01L 21/00	Replace “e.g. H01L21/00” with H10P 76/00
G06K 7/10841	H01L	H10
G09G	H01L	H10H
H03B 9/00	H01L	H10
H04R 23/006	H01L	H10
G02B 6/131	H01L 21/02365	H10P 14/20
C23C 18/1642	H01L 21/288	H10P 14/48
B23Q 3/00	H01L 21/67	H10P 72/00
G01R 31/00	H01L 22/00	H10P 74/00
G01R 31/26	H01L 22/00	H10P 74/00
G01R 31/2648	H01L 22/00	H10P 74/00
G01R 31/2831	H01L 22/00	H10P 74/00
G01R 31/2893	H01L 21/67	H10P 72/00
B65G 49/07	H01L 21/677	H10P 72/30
B25J	H01L 21/68	H10P 72/50
B25J 15/00	H01L 21/68707	H10P 72/7602
H02S 50/10	H01L 22/00	H10P 74/00
G01N 21/9501	H01L 22/10	H10P 74/20
G01N 21/956	H01L 22/10	H10P 74/20

Definitions references impacted by this revision project

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A47G 19/08	H01L 21/00	Informative references	H10P 95/00
A61B 8/00	H01L	Informative references	Delete reference
A61N 5/00	H01L 21/26	Limiting references	H10P 34/00
B01B	H01L 21/00	Relationships with other classification places	H10P
B01J	H01L 21/00	Informative references	H10P
B05B	H01L 21/00	Informative references	H10P
B05D	H01L	Limiting references	H10
B05D 1/005	H01L 21/00	Limiting references	H10P 14/6342
B05D 5/12	H01L	Special rules of classification	H10
B08B	H01L 21/02	Application-oriented references	H10P 95/00
B08B	H01L 21/67	Application-oriented references	H10P 72/00
B21F	H01L	Informative references	H10
B23K 26/12	H01L 21/3065	Informative references	H10P 50/20
B23K 26/18	H01L 21/3065	Informative references	H10P 50/20
B23K 26/20	H01L 21/185	Informative references	H10P 10/12
B23K 26/352	H01L 21/00	Informative references	H10P
B23K 35/00	H01L	Informative references	H10
B23Q	H01L 21/67	Relationships with other classification places	H10P 72/00
B23Q	H01L	Relationships with other classification places	Delete “and H01L” and preceding comma
B23Q 3/00	H01L 21/67	Limiting references	H10P 72/00

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B24B 9/065	H01L 21/02021	Informative references	H10P 90/128
B24B 37/00	H01L 21/00	Informative references	H10P
B24B 37/04	H01L 21/304	Informative references	H10P 52/00
B24B 37/27	H01L 21/673	Informative references	H10P 72/00
B24B 37/345	H01L 21/677	Informative references	H10P 72/30
B24B 37/345	H01L 21/68	Informative references	H10P 72/50
B24B 37/345	H01L 21/683	Informative references	H10P 72/70
B24C	H01L 21/3046	Limiting references	H10P 52/00
B24C 3/322	H01L 21/3046	Limiting references	H10P 52/00
B25B 11/00	H01L 21/6838	Application- oriented references	H10P 72/78
B25J	H01L 21/67742	Application- oriented references	H10P 72/3302
B25J	H01L 21/67766	Application- oriented references	H10P 72/3402
B25J	H01L 21/68707	Application- oriented references	H10P 72/7602
B25J 9/042	H01L 21/67742	Limiting references	H10P 72/3302
B25J 9/042	H01L 21/68707	Limiting references	H10P 72/7602
B25J 9/107	H01L 21/67739	Informative references	H10P 72/33
B25J 9/107	H01L 21/68707	Informative references	H10P 72/7602
B26D	H01L 21/304	Application- oriented references	H10P 14/38
B28D	H01L 21/00	Informative references	H10P
B28D 5/00	H01L 21/00	Limiting references	Delete reference
B28D 5/00	H01L 21/00	Informative references	H10P

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B29C 43/021	H01L 21/027	Informative references	H10P 76/00
B29C 43/021	H01L 21/67092	Informative references	H10P 72/0428
B29C 64/00	H01L 21/00	Informative references	H10P
B32B 18/00	H01L	Relationships with other classification places	H10W
B33Y	H01L 21/00	Informative references	H10P
B41M	H01L	Limiting references	H10
B65B 9/00	H01L 21/673	Informative references	H10P 72/10
B65B 23/00	H01L 21/673	Informative references	H10P 72/10
B65D 85/48	H01L 21/673	Informative references	H10P 72/10
B65G	H01L 21/67	Application- oriented references	H10P 72/00
B65G 47/911	H01L 21/6838	Informative references	H10P 72/78
B65G 49/06	H01L 21/677	Informative references	H10P 72/30
B65G 51/03	H01L 21/67784	Informative references	H10P 72/36
B65H	H01L 21/67	Relationships with other classification places	H10P 72/00
B65H 35/00	H01L 21/67132	Informative references	H10P 72/0442
C04B 35/01	H01L 21/02403	Informative references	H10P 14/2914 H10P 14/2918
C04B 35/01	H01L 21/02414	Informative references	H10P 14/2918
C04B 35/10	H01L 21/02178	Informative references	H10P 14/69391
C04B 35/14	H01L 21/31608	Informative references	H10P 14/6328
C04B 35/46	H01L 21/02186	Informative references	H10P 14/69394
C04B 35/465	H01L 21/31691	Informative references	H10P 14/69398

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C04B 35/48	H01L 21/02181	Informative references	H10P 14/69392, H10P 14/6909, H10P 14/69473
C04B 35/48	H01L 21/31645	Informative references	Delete
C04B 35/48	H01L 21/02189	Informative references	H10P 14/69395, H10P 14/6912, H10P 14/69476
C04B 35/48	H01L 21/31641	Informative references	Delete
C04B 35/491	H01L 21/31691	Informative references	H10P 14/69398
C04B 35/495	H01L 21/02183	Informative references	H10P 14/69393, H10P 14/691, H10P 14/69474
C04B 35/495	H01L 21/31645	Informative references	Delete
C04B 35/50	H01L 21/02192	Informative references	H10P 14/69396
C04B 35/5154	H01L 21/02392	Informative references	H10P 14/2909
C04B 35/52	H01L 21/02376	Informative references	H10P 14/2903
C04B 35/547	H01L 21/02406	Informative references	H10P 14/2915
C04B 35/547	H01L 21/02409	Informative references	H10P 14/2916
C04B 35/547	H01L 21/02411	Informative references	H10P 14/2917
C04B 35/5603	H01L 21/02126	Informative references	H10P 14/6922
C04B 35/5603	H01L 21/31633	Informative references	H10P 14/6922
C04B 35/565	H01L 21/02167	Informative references	H10P 14/6905
C04B 35/565	H01L 21/02447	Informative references	H10P 14/3208
C04B 35/565	H01L 21/02529	Informative references	H10P 14/3408
C04B 35/565	H01L 21/3148	Informative references	H10P 14/2904
C04B 35/565	H01L 21/02378	Informative references	H10P 14/2904
C04B 35/565	H01L 21/0445	Informative references	H10D 62/8325
C04B 35/58014	H01L 21/28088	Informative references	H10D 64/01318
C04B 35/584	H01L 21/0217	Informative references	H10P 14/69433

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C04B 35/584	H01L 21/3185	Informative references	H10P 14/60
C04B 35/591	H01L 21/3211	Informative references	H10P 14/6316
C04B 35/597	H01L 21/0214	Informative references	H10P 14/6927
C04B 35/597	H01L 21/02326	Informative references	H10P 14/6522
C04B 35/597	H01L 21/02332	Informative references	H10P 14/6526
C04B 35/62222	H01L	Relationships with other classification places	H10W
C04B 35/624	H01L 21/02282	Informative references	H10P 14/6342
C04B 41/00	H01L 21/00	Informative references	H10P
C04B 41/00	H01L	Limiting references	Delete H01L and preceding comma
C04B 41/00	H01L 21/306	Limiting references	H10P 50/00
C07F	H01L	Informative references	H10
C09D 123/00	H01L	Informative references	H10F
C09D 135/00	H01L	Informative references	H10F
C09D 137/00	H01L	Informative references	H10F
C09D 139/00	H01L	Informative references	H10F
C09D 141/00	H01L	Informative references	H10F
C09D 143/00	H01L	Informative references	H10F
C09D 145/00	H01L	Informative references	H10F
C09D 149/00	H01L	Informative references	H10F
C09K 3/14	H01L	Informative references	H10P and preceding semicolon
C09K 3/14	H01L	Limiting references	H10P, and also replace “friction” with “Friction”
C09K 3/1454	H01L	Informative references	H10P
C09K 3/1454	H01L 21/00	Informative references	H10P

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C09K 13/00	H01L	Limiting references	H10P, H10W
C22C	H01L	Informative references	H10
C22F	H01L	Informative references	H10
C23C	H01L	Informative references	Delete H01L
C23C 8/00	H01L 21/00	Limiting references	H10P
C23C 10/00	H01L 21/00	Limiting references	H10P
C23C 12/00	H01L 21/00	Limiting references	H10P
C23C 14/00	H01L	Informative references	H10
C23C 16/00	H01L	Informative references	H10
C23C 16/00	H01L	Special rules of classification	H10
C23C 18/00	H01L 21/00	Informative references	H10P
C23C 26/00	H01L	Limiting references	H10
C23C 28/00	H01L	Relationships with other classification places	H10
C23F	H01L 21/306	Informative references	H10P 50/00
C23F	H01L 21/32115	Informative references	H10P 95/04
C23F	H01L 21/3213	Informative references	H10P 50/00
C23F	H01L 21/67005	Informative references	H10P 72/00
C23F 1/00	H01L 21/30604	Informative references	H10P 50/642
C23F 1/00	H01L 21/308	Informative references	H10P 50/691
C23F 1/00	H01L 21/32134	Informative references	H10P 50/667
C23F 1/00	H01L 21/67075	Informative references	H10P 72/0422
C23F 1/00	H01L 21/00	Limiting references	H10P

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C23F 1/00	H01L 21/00	Relationships with other classification places	H10P
C23F 1/00	Old text: The C23F1/24 IPC group is not used in the internal ECLA classification scheme. Subject-matter covered by this group is classified in the following groups: C09K13/00 - C09K13/08.	Special rules of classification	Replace existing text with: Acidic compositions for etching silicon or germanium are classified in the following groups: C09K 13/00 - C09K 13/08.
C23F 3/00	H01L 21/3212	Informative references	H10P 52/403
C23F 4/00	H01L 21/32136	Informative references	H10P 50/267
C23F 4/00	H01L 21/00	Limiting references	H10P
C23G	H01L 21/02041	Informative references	H10P 70/00
C23G 1/00	H01L 21/02041	Informative references	H10P 70/00
C23G 5/00	H01L 21/02041	Informative references	H10P 70/00
C25D	H01L 21/00	Informative references	H10P
C25D 7/00	H01L 21/00	Informative references	Delete H01L from second table row
C25D 7/00	H01L 21/00	Informative references	H10P
C25D 7/12	H01L 21/2885	Application- oriented references	H10P 14/47
C25D 11/00	H01L 21/00	Informative references	H10P
C25F	H01L 21/00	Limiting references	H10P
C25F	H01L 21/306	Limiting references	H10P 50/00
C25F	H01L 21/465	Limiting references	H10P 50/20, H10P 52/00, H10P 95/70
C30B	H01L 21/02	Informative references	H10P 95/02
C30B	H01L	Limiting references	Delete reference

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C30B	H01L	Relationships with other classification places	Replace “subclass H01L” with “class H10”
F04C 25/02	H01L 21/67	Informative references	H10P 72/00
F16B 47/00	H01L 21/6838	Application- oriented references	H10P 72/78
F16C 29/00	H01L 21/68	Application- oriented references	H10P 72/50
F24F 3/00	H01L 21/67017	Informative references	H10P 72/0402
F25B 21/02	H01L	Informative references	H10
F27B 17/00	H01L 21/67	Informative references	H10P 72/00
G01K 13/00	H01L 21/67248	Application- oriented references	H10P 72/0602
G01L 9/00	H01L 21/00	Special rules of classification	H10P
G01M 99/00	H01L 22/00	Informative references	H10P 74/00
G01N 15/00	H01L 21/00	Informative references	H10P
G01R	H01L 22/00	References out of a residual place	H10P 74/00
G01R 21/08	H01L	Informative references	H10N 50/00
G01R 31/00	H01L 22/00	Limiting references	H10P 74/00
G01R 31/26	H01L 22/00	Limiting references	H10P 74/00
G01S	H01L	Informative references	H10
G02F 1/00	H01L	Relationships with other classification places	H10
G03F 1/00	H01L 21/027	Limiting references	H10P 76/00
G03F 1/00	G02N	Informative references	G01N
G03F 7/00	H01L	Definition statement	Delete H01L and the second e.g.

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DATE: JANUARY 1, 2026

PROJECT RP12800

<u>Location of reference to be changed</u>	<u>Referenced subclass or group to be changed</u>	<u>Section of definition</u>	<u>Action; New reference symbol; New text</u>
G03F 7/00	H01L 21/00	Definition statement	H10P 76/00
G03F 7/00	H01L 21/00	Limiting references	Insert new text: Manufacture or treatment of masks on semiconductor bodies H10P 76/00
G03F 7/36	H01L 21/00	Limiting references	H10P
G03F 9/00	H01L	Limiting references	H10
G05B	H01L 21/00	Application- oriented references	H10P
G06F 3/0412	H01L	Special rules of classification	H10K
G06T 7/70	H01L 21/681	Informative references	H10P 72/53
G06V	H01L	Informative references	H10
G11B 5/00	H01L	Special rules of classification	H10
G11B 5/00	H01L	Special rules of classification	H10
G11B 7/261	H01L 21/027	Informative references	H10P 76/00
G11C	H01L 21/00	Informative references	H10P
G11C 5/005	H01L 21/26	Informative references	H10P 34/00
G11C 11/34	H01L 21/00	Informative references	H10P
G11C 13/00	H01L	Relationships with other classification places	H10
G11C 29/00	H01L	Relationships with other classification places	H10
G11C 29/006	H01L 22/00	Informative references	H10P 74/00
H01B	H01L	Relationships with other classification places	H10
H01J 37/20	H01L 21/67	Informative references	H10P 72/00

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DATE: JANUARY 1, 2026

PROJECT RP12800

<u>Location of reference to be changed</u>	<u>Referenced subclass or group to be changed</u>	<u>Section of definition</u>	<u>Action; New reference symbol; New text</u>
H01J 37/32	H01L 21/2236	Informative references	H10P 32/1204
H01J 37/32	H01L 21/30	Informative references	H10P 95/00
H01J 37/32	H01L 21/46	Informative references	Delete reference symbol and preceding comma
H01J 37/32	H01L 21/67	Informative references	H10P 72/00
H01J 37/32	H01L 21/67005	Informative references	H10P 72/00
H01J 37/32	H01L 21/67063	Informative references	H10P 72/0418
H01J 37/32	H01L 21/67155	Informative references	H10P 72/0451
H01J 37/32	H01L 21/67201	Informative references	H10P 74/00
H01J 37/32	H01L 22/00	Informative references	H10P 74/00
H01M 10/00	H01L	Informative references	H10
H01R	H01L	Informative references	H10
H01S	H01L 21/027	Application- oriented references	H10P 76/00
H02M	H01L	Relationships with other classification places	Delete H01L and comma
H02M 7/00	H01L	Informative references	H10
H02N 13/00	H01L 21/6831	Informative references	H10P 72/72
H02N 15/00	H01L 21/6831	Informative references	H10P 72/72
H02N 15/00	H01L 21/6833	Informative references	H10P 72/722
H02S 50/10	H01L 22/00	Limiting references	H10P 74/00
H03B 9/00	H01L	Informative references	Delete H01L
H03F	H01L	Informative references	H10
H03H	H01L	Informative references	H10W 44/00
H03H 3/00	H01L	Informative references	H10

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<u>Location of reference to be changed</u>	<u>Referenced subclass or group to be changed</u>	<u>Section of definition</u>	<u>Action; New reference symbol; New text</u>
H03H 9/00	H01L	Informative references	H10
H03K 17/10	H01L	Limiting references	H10
H03K 17/12	H01L	Limiting references	H10
H04N 5/30	H01L	Informative references	H10
H04R 23/006	H01L	Informative references	H10
H05B 1/00	H01L	Informative references	H10
H05B 3/00	H01L 21/67	Application- oriented references	H10P 72/00
H05B 3/00	H01L	Informative references	H10
H05B 3/143	H01L 21/67098	Application- oriented references	H10P 72/0431
H05B 11/00	H01L	Informative references	H10
H05F 1/00	H01L 21/67396	Limiting references	H10P 72/1928
H05K 13/00	H01L 21/00	Informative references	H10P
H05K 13/0061	H01L 21/67	Informative references	H10P 72/00
H10F 10/00	H01L 22/00	Informative references	H10P 74/00
H10F 71/00	H01L 21/00	Informative references	H10P
H10F 71/00	H01L 22/00	Informative references	H10P 74/00
H10K 71/00	H01L 21/00	Informative references	H10P
H10N	H01L	Informative references	Delete reference
H10N 10/01	H01L 21/00	Informative references	H10P
H10N 30/00	H01L 21/00	Informative references	H10P
H10N 30/01	H01L 21/00	Informative references	H10P
H10N 30/06	H01L 21/00	Informative references	H10P
H10N 30/07	H01L 21/70	Informative references	H10D 84/01

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<u>Location of reference to be changed</u>	<u>Referenced subclass or group to be changed</u>	<u>Section of definition</u>	<u>Action; New reference symbol; New text</u>
H10N 35/00	H01L 21/00	Informative references	H10P
H10N 35/01	H01L 21/00	Informative references	H10P
H10N 50/01	H01L 21/00	Informative references	H10P
H10N 52/01	H01L 21/00	Informative references	H10P
H10N 60/01	H01L 21/00	Informative references	H10P

NOTES:

- The CRL tables above are used for changes to locations **outside** of the project scope. Changes to references in scheme titles or definitions **inside** the project scope will be reflected in the “scheme change” template or one of the “definition” templates.
- In addition to other changes proposed in the tables above, in the column titled “Referenced subclass or group to be changed,” **referenced** D symbols should indicate an action of “delete” or should indicate a replacement symbol and **referenced** F symbols should indicate a replacement symbol.
- When a reference is deleted, text related to that reference will also be deleted unless other references or a range of references associated with the same text remain.